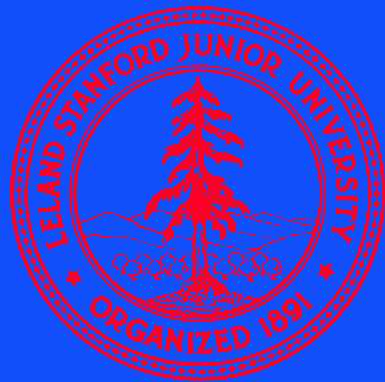
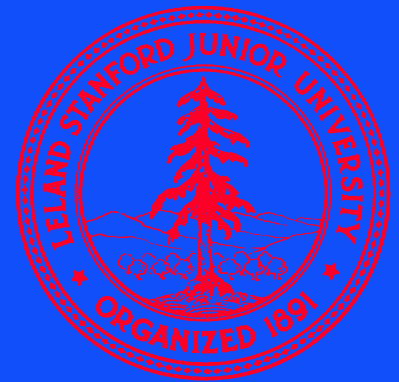


# MECHANICAL TRANSDUCERS

EE312, Prof. Greg Kovacs



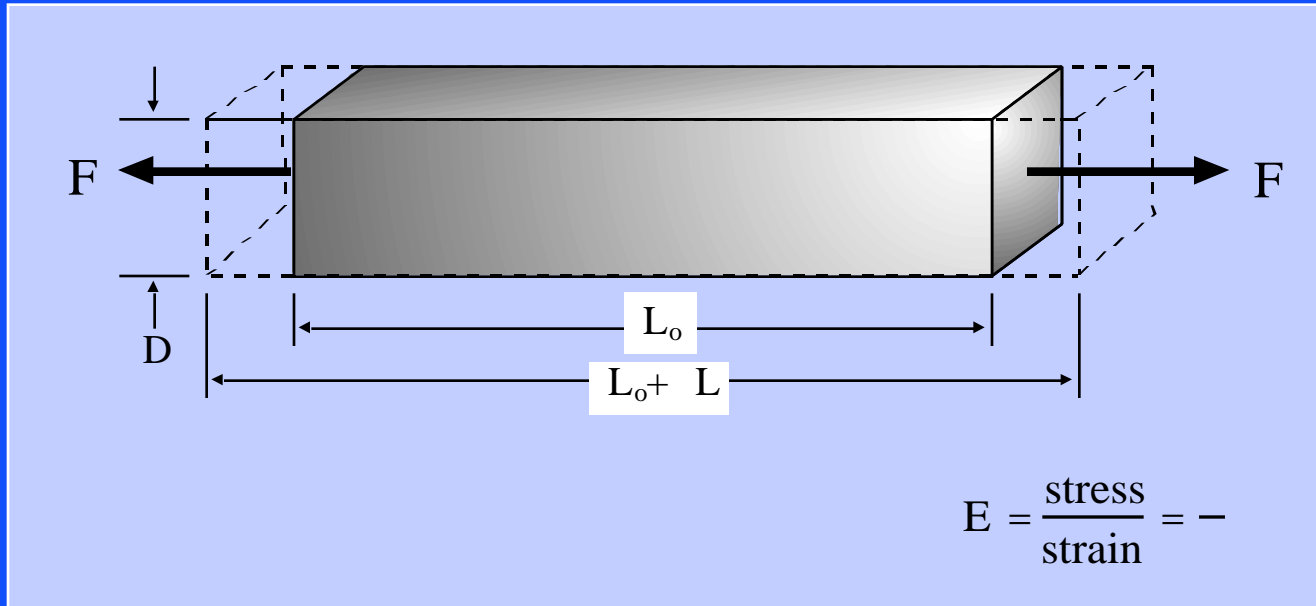
Stanford University



# MECHANICAL TRANSDUCER EXAMPLES

- Strain gauges
- Accelerometers
- Gyroscopes
- Pressure sensors
- Actuators
- Others... (optical, fluidic, etc., covered in their respective sections)

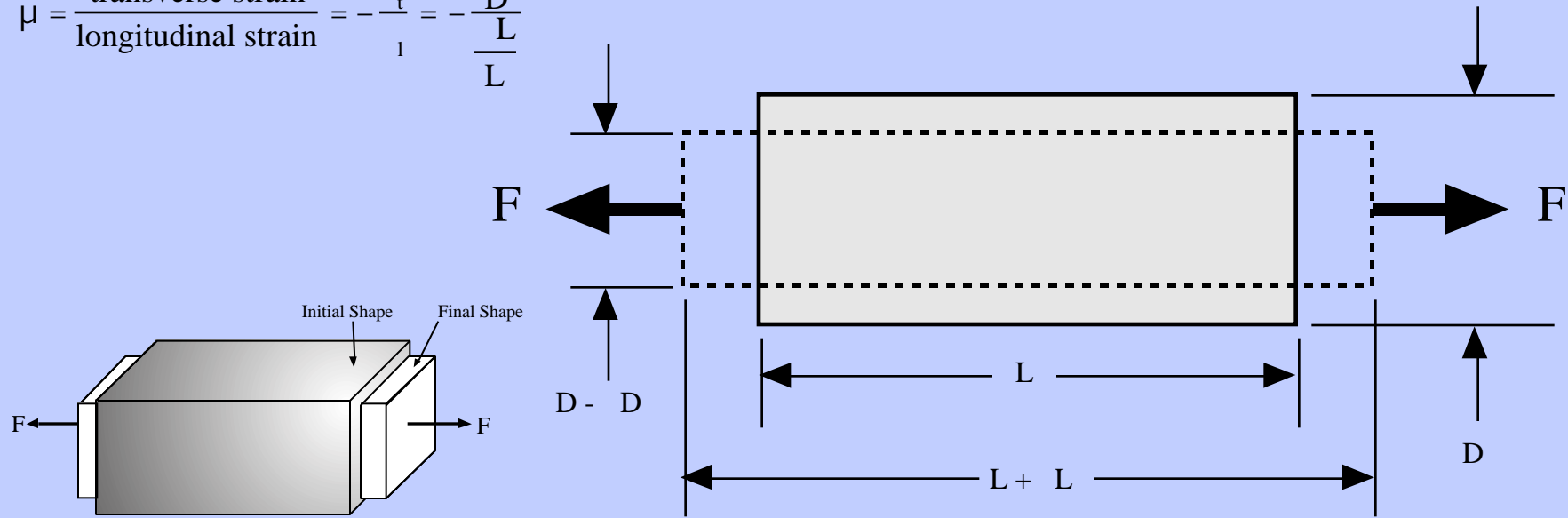
# STRESS AND STRAIN



- Strain,  $\epsilon$ , is the deformation of a solid ( $\Delta L/L$ ) due to stress.
- Stress,  $\sigma$ , is the force acting on a unit area of a solid ( $F/A$ ).
- The Young's Modulus,  $E$ , is the ratio of stress over strain, and describes the “firmness” of a material (hard,  $E$  large, soft,  $E$  small).

# POISSON STRAIN

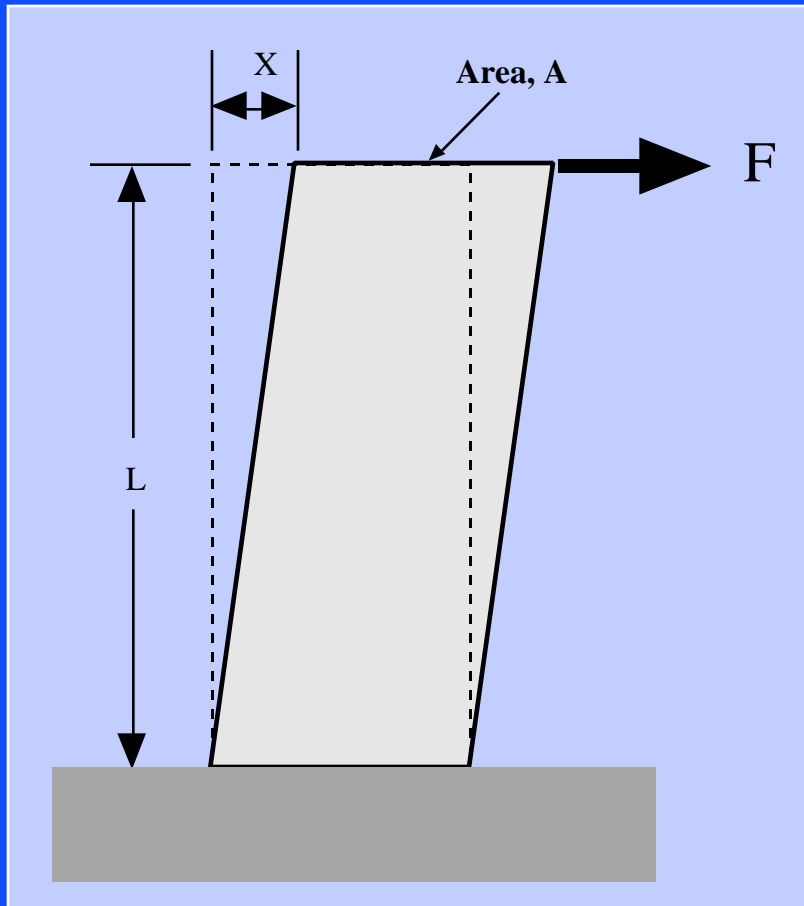
$$\mu = \frac{\text{transverse strain}}{\text{longitudinal strain}} = -\frac{\frac{t}{l}}{\frac{L}{L}} = -\frac{\frac{D}{D}}{\frac{L}{L}}$$



- For most materials, as they lengthen in one direction, they contract in another (Poisson strain).
- The Poisson ratio,  $\mu$ , is the ratio of dimensional change in girth to length for a bar.



# SHEAR



- Shear is force applied to an object in the plane of an opposing force, such as an anchor point.
- The shear modulus,  $G$ , represents the degree of displacement an object will allow under shear stress.

$$G = \frac{\text{shear stress}}{\text{shear displacement angle (rad)}} = \frac{\frac{F}{A}}{\frac{X}{L}} = \frac{FL}{AX}$$

# MECHANICAL PROPERTIES OF SILICON

Material	Yield Strength ( $10^9$ N/m <sup>2</sup> )	Knoop Hardness (kg/mm <sup>2</sup> )	Young's Modulus ( $10^{11}$ N/m <sup>2</sup> )	Density (g/cm <sup>3</sup> )	Thermal Conductivity (W/cm°C)	Thermal Expansion Coefficient ( $10^6$ /°C)
*Diamond	53	7000	10.35	3.5	20	1
*SiC	21	2480	7	3.2	3.5	3.3
*TiC	20	2470	4.97	4.9	3.3	6.4
*Al <sub>2</sub> O <sub>3</sub>	15.4	2100	5.3	4	0.5	5.4
*Si <sub>3</sub> N <sub>4</sub>	14	3486	3.85	3.1	0.19	0.8
*Iron	12.6	400	1.96	7.8	0.803	12
SiO <sub>2</sub> (fibers)	8.4	820	0.73	2.5	0.014	0.55
*Si	7	850	1.9	2.3	1.57	2.33
Steel (max strength)	4.2	1500	2.1	7.9	0.97	12
W	4	485	4.1	19.3	1.78	4.5
Stainless Steel	2.1	660	2	7.9	0.329	17.3
Mo	2.1	275	3.43	10.3	1.38	5
Al	0.17	130	0.7	2.7	2.36	25

Reference: Petersen, K. E., "Silicon as a Mechanical Material," Proceedings of the IEEE, vol. 70, no. 5, May 1982, pp. 420 - 457.

# SENSING IN MECHANICAL TRANSDUCERS

- Many mechanisms can be harnessed in microstructures to sense strain or displacement.
- *Piezoresistive* sensing makes use of the fact that majority carrier mobilities in certain materials (e.g. doped regions of single crystal or polysilicon) are modulated by stress (force/area), thus varying resistivity.
- Piezoresistive circuits can generate fairly high power signals but generally require temperature compensation.
- *Piezoelectric* materials generate potentials proportional to change in length(no DC response) and generate large voltages.
- *Capacitive* sensing relies on measuring changes in capacitors with moving plate(s), on a micro scale producing very low power signals but with no temperature effects.
- *Tunneling* and *optical* means may also be utilized.

# MECHANICAL SENSING MECHANISMS

Mechanism	Parameter Sensed	Needs Local Circuits?	DC Response?	Complex System?	Linearity	Issues
Metal Strain Sensor	strain	NO	YES	+	+++	<ul style="list-style-type: none"> <li>• low sensitivity</li> <li>• very simple</li> </ul>
Piezoresistive Strain Sensor	strain	NO	YES	+	+++	<ul style="list-style-type: none"> <li>• temperature effects can be significant</li> <li>• easy to integrate</li> </ul>
Piezoelectric	force	NO	NO	++	++	<ul style="list-style-type: none"> <li>• high sensitivity</li> <li>• fabrication can be complex</li> </ul>
Capacitive	displacement	YES	YES	++	poor	<ul style="list-style-type: none"> <li>• very simple</li> <li>• extremely low temperature coefficients</li> </ul>
Tunneling	displacement	YES	YES	+++	poor	<ul style="list-style-type: none"> <li>• sensitive to surface states</li> <li>• drift performance not yet proven</li> </ul>
Optical	displacement	NO	YES	+++	+++	<ul style="list-style-type: none"> <li>• rarely employed in mechanical microsensors</li> </ul>

# STRAIN GAUGES

- Gauge factor is used to express the sensitivity of strain gauges (relative change in R over strain).

$$GF = \frac{\text{relative resistance change}}{\text{strain}} = \frac{\frac{R}{L}}{\frac{R}{L}} = \frac{R}{L}$$

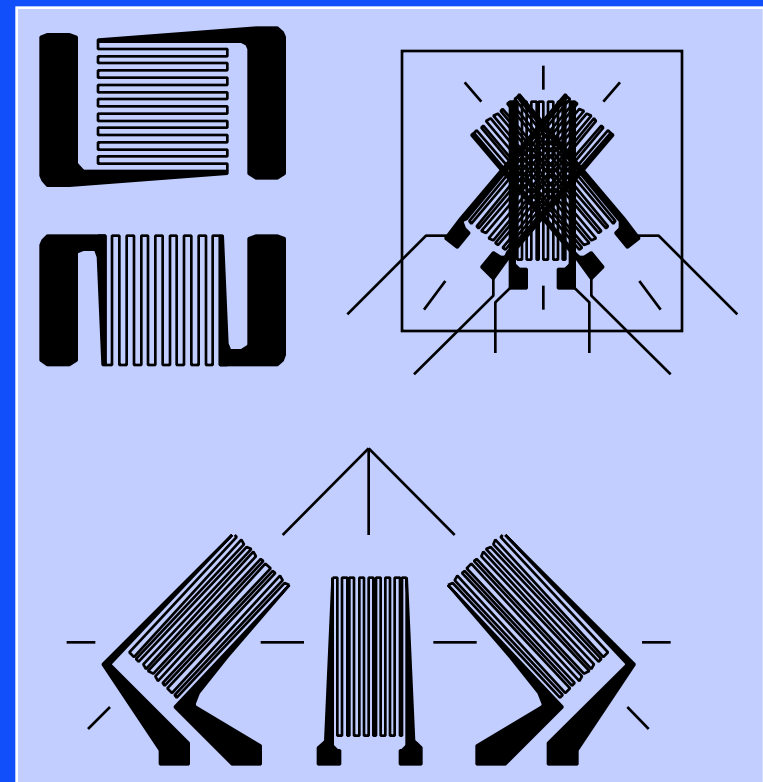
- The resistance can vary due to a dimensional effect or if the resistivity varies under strain.

$$GF = \frac{\frac{dR}{dL}}{\frac{R}{L}} = \frac{\frac{dR}{R}}{\frac{dL}{L}} = (1 + 2\mu) + \frac{d}{1}$$

- Thin-film metallic strain gauges have a GF of roughly 2 (resistivity does not vary much), but semiconductor strain gauges have GF of up to 200 due to strain-dependent modulation of majority carrier mobilities ( $\Delta R$  with strain up for p-type and down for n-type).

# STRAIN GAUGES

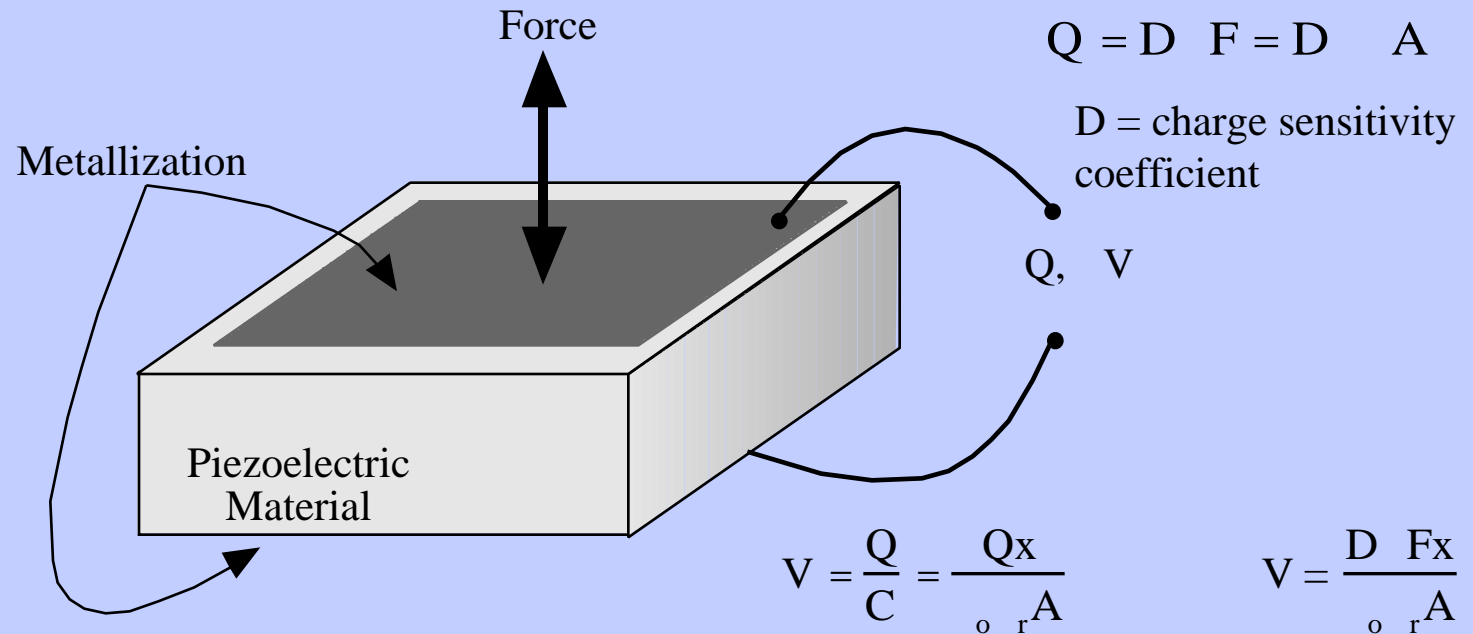
Type of Strain Gauge	Gauge Factor
Metal Foil	1 - 5
Thin-Film Metal	2
Bar Semiconductor	80 - 150
Diffused Semiconductor	80 - 200



**Metal foil strain gauges, after Norton (1989).**

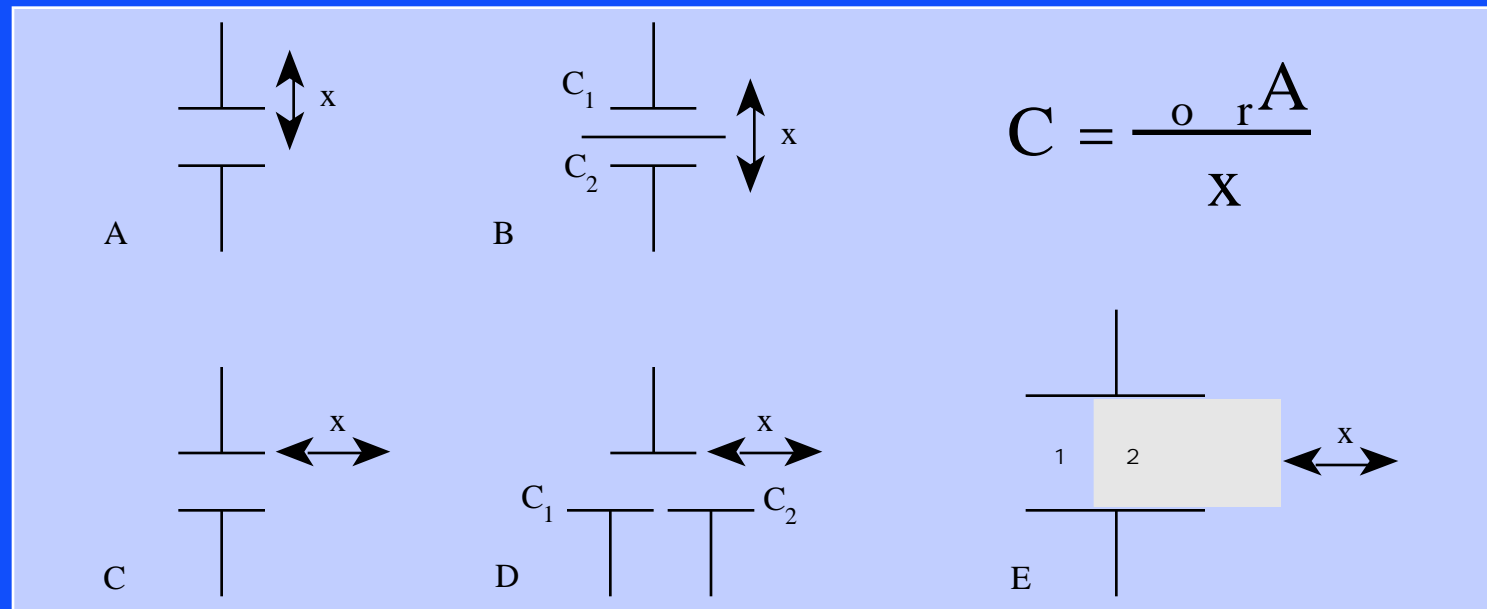
Reference: Norton, A. N., "Handbook of Transducers," Prentice-Hall, Inc., Englewood Cliffs, NJ, 1989.

# PIEZOELECTRIC SENSING



- Electrical potential develops on opposite faces of a slab under externally-applied stress, and has no DC response.
- Piezoelectric materials must have a built-in polarization (silicon is not piezoelectric, but GaAs is).
- Example materials: quartz, polyvinylidene fluoride (PVDF), lead zirconate-titanate (PZT), barium titanate, zinc oxide, etc.

# CAPACITIVE SENSING



**Modes of capacitive sensing, after Cobbold (1974).**

Reference: Cobbold, R. S. C., "Transducers for Biomedical Measurements," John Wiley and Sons, New York, NY, 1974.

G. Kovacs © 2000



# TUNNELING-BASED SENSING

- Tunneling current is extremely sensitive to position and, with external feedback, can be used to construct extremely sensitive mechanical transducers.

$$I = I_0 e^{(-\beta \sqrt{\phi} z)}$$

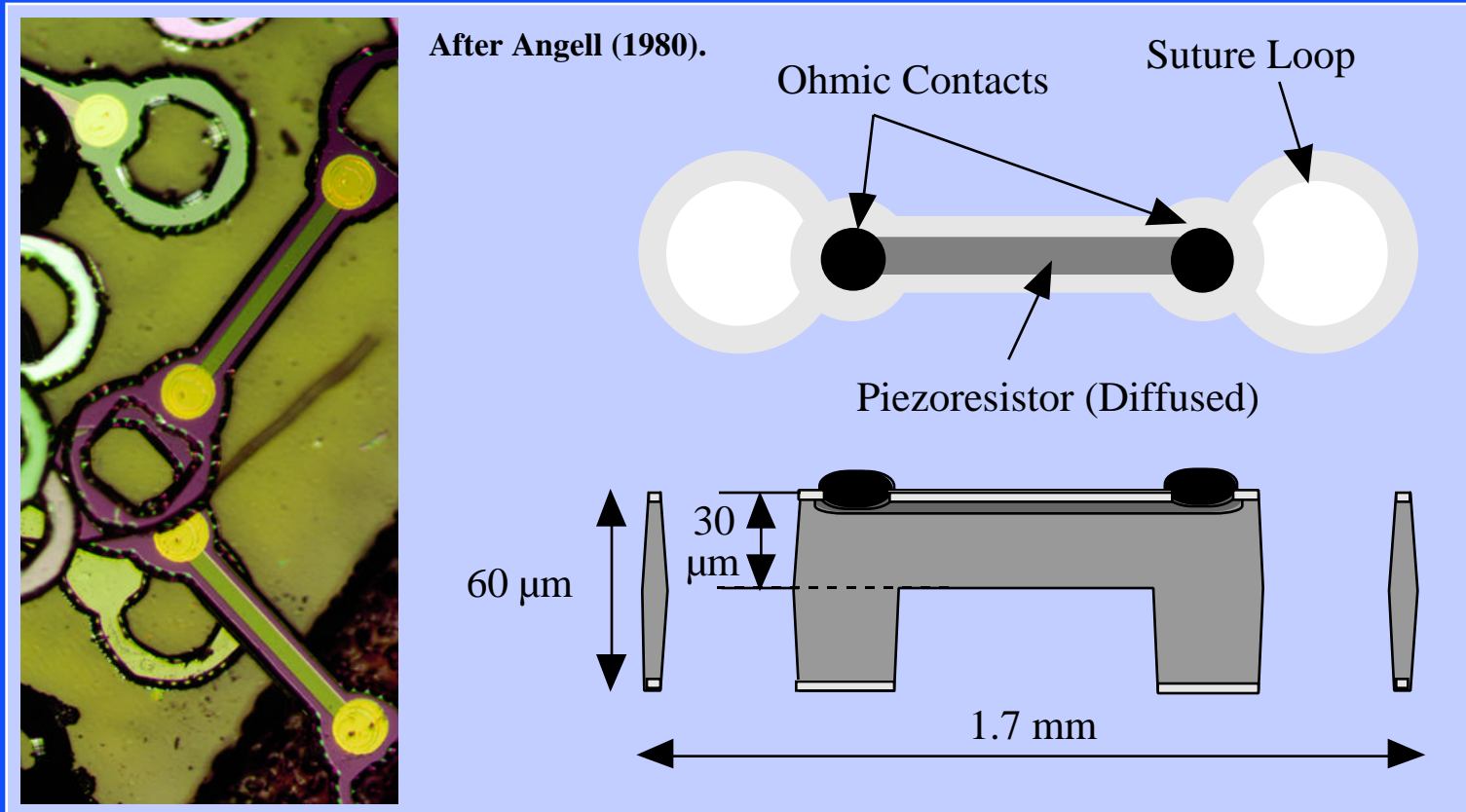
$I_0$  = scaling factor

$\beta$  = conversion factor = 1.025 eV<sup>-1/2</sup>/Å

$\phi$  = tunnel barrier height in eV = 0.5 eV

$z$  = tip/surface separation in Å = 10 Å

# MICROMACHINED STRAIN GAUGES



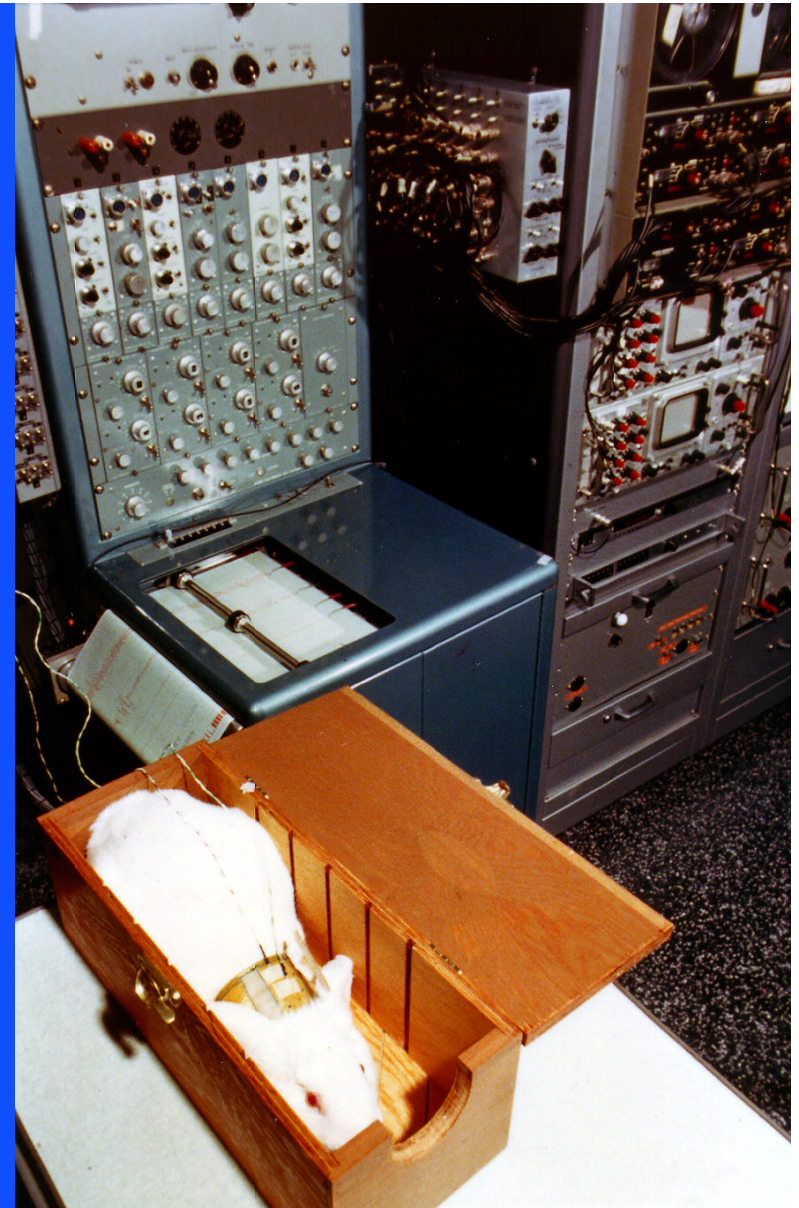
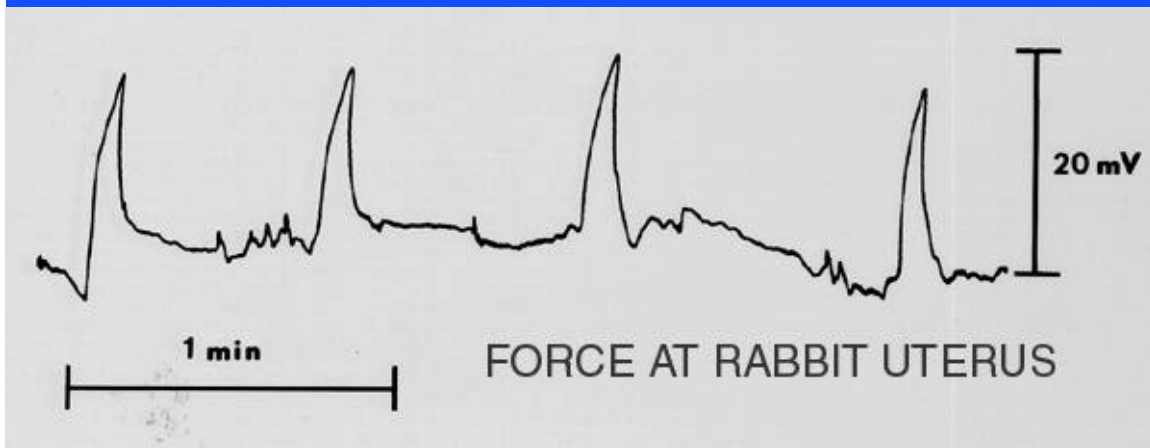
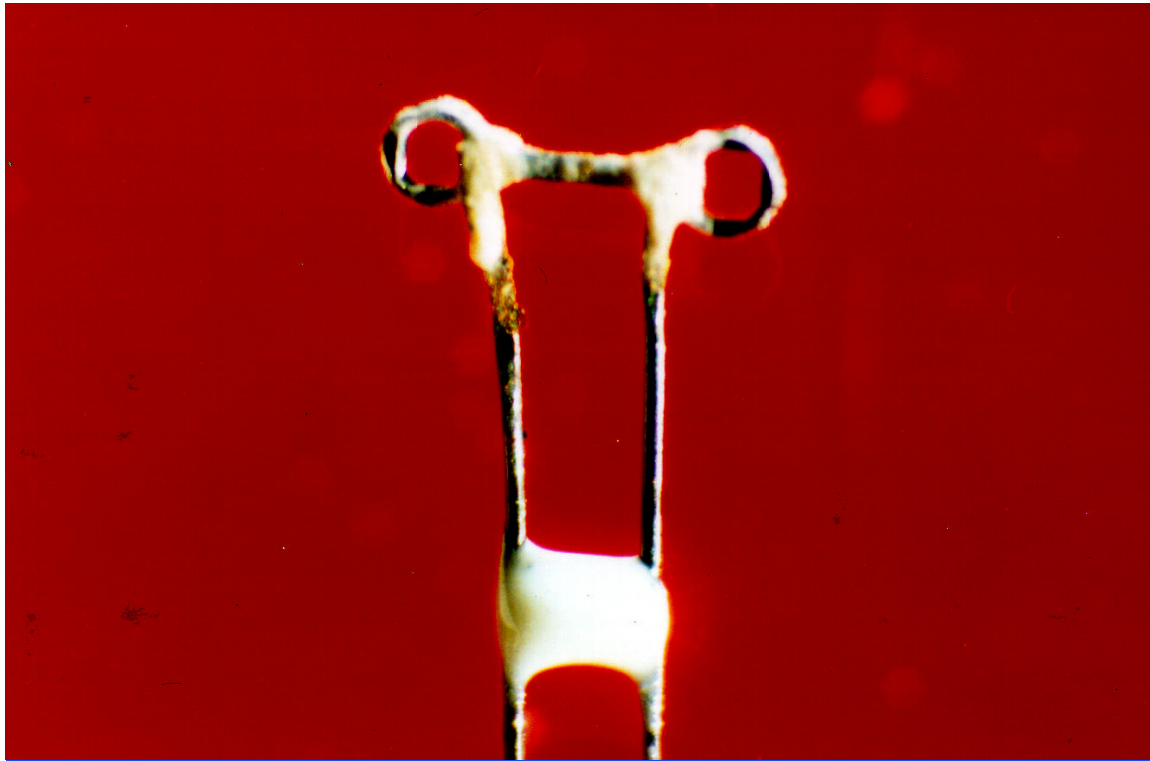
Reference: Angell, J. B., "Transducers for in vivo measurement of force, strain and motion," in "Physical Sensors for Biomedical Applications," Neuman, M. R., Fleming, D. G., Cheung, P. W., and Ko, W. H. [eds.], CRC Press, Boca Raton, FL, 1980, pp. 46 - 53.



**Implantable strain gauges on a penny.**

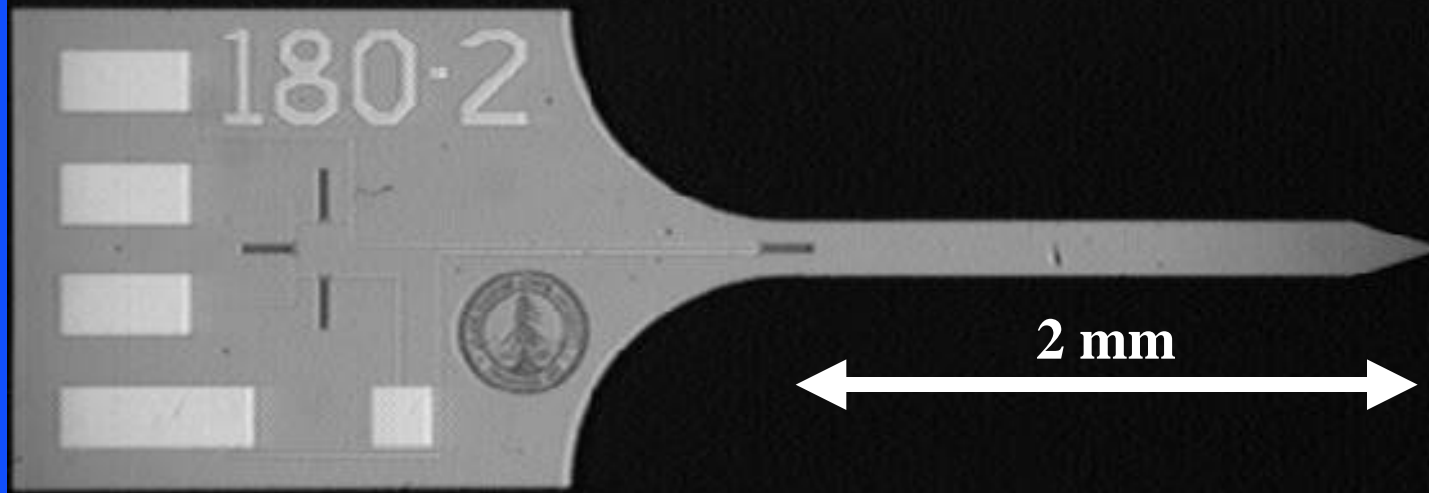
Reference: Angell, J. B., "Transducers for in vivo measurement of force, strain and motion," in Physical Sensors for Biomedical Applications, Neuman, M. R., Fleming, D. G., Cheung, P. W., and Ko, W. H., (Eds.), CRC Press, Boca Raton, FL, 1980, pp. 46 - 53.

G. Kovacs © 2000





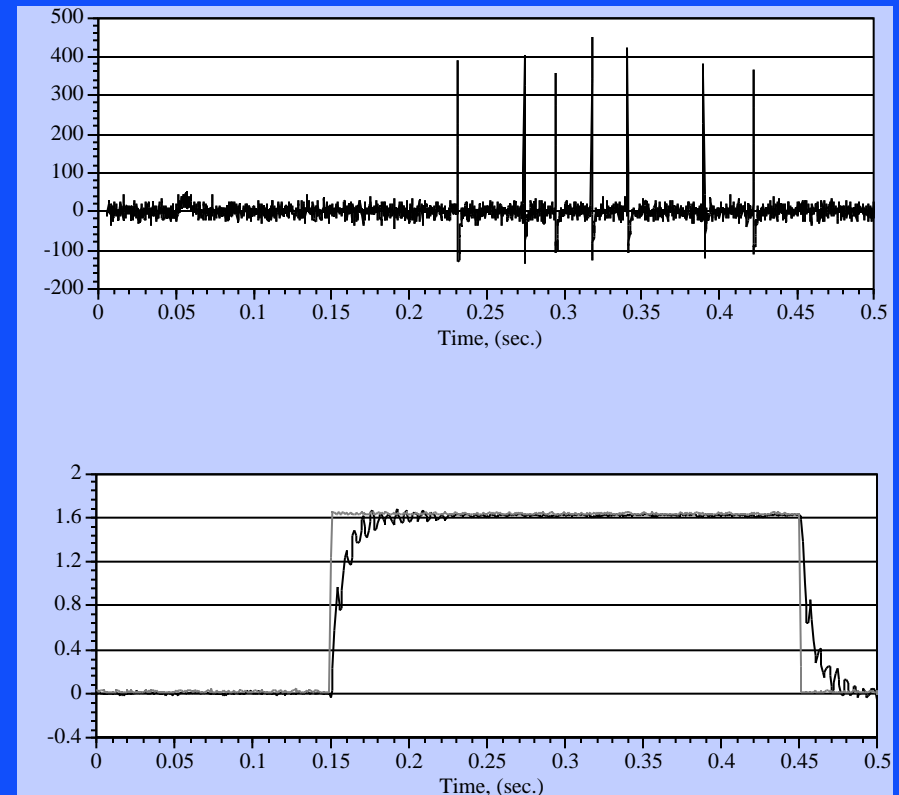
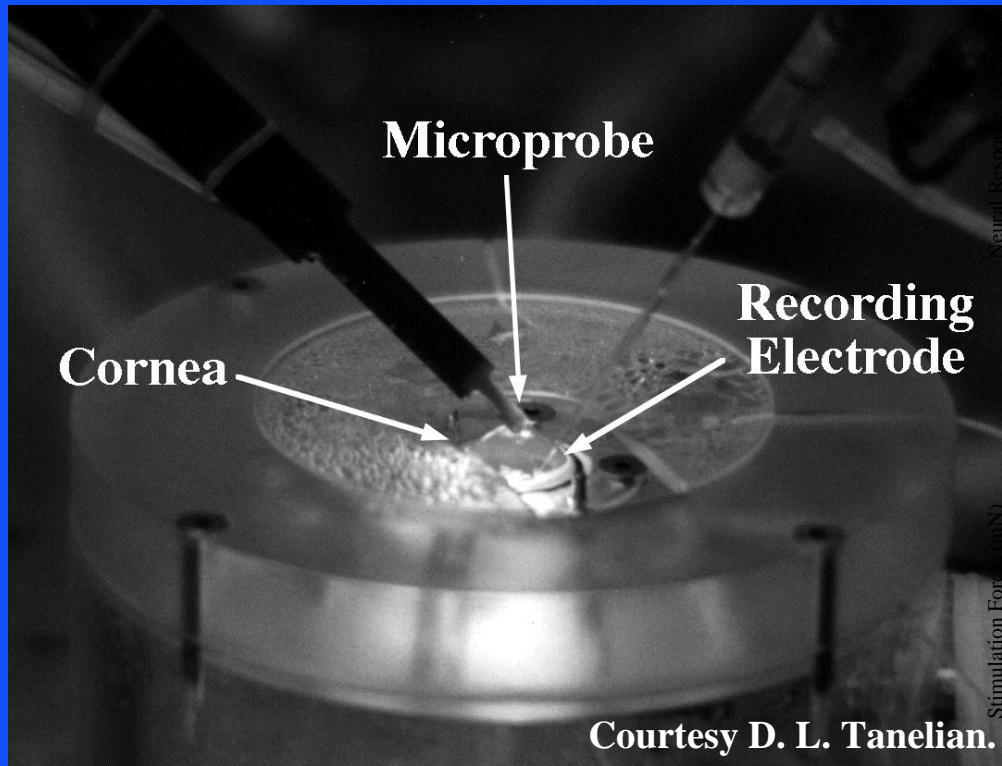
# SILICON STRAIN GAUGE PROBE



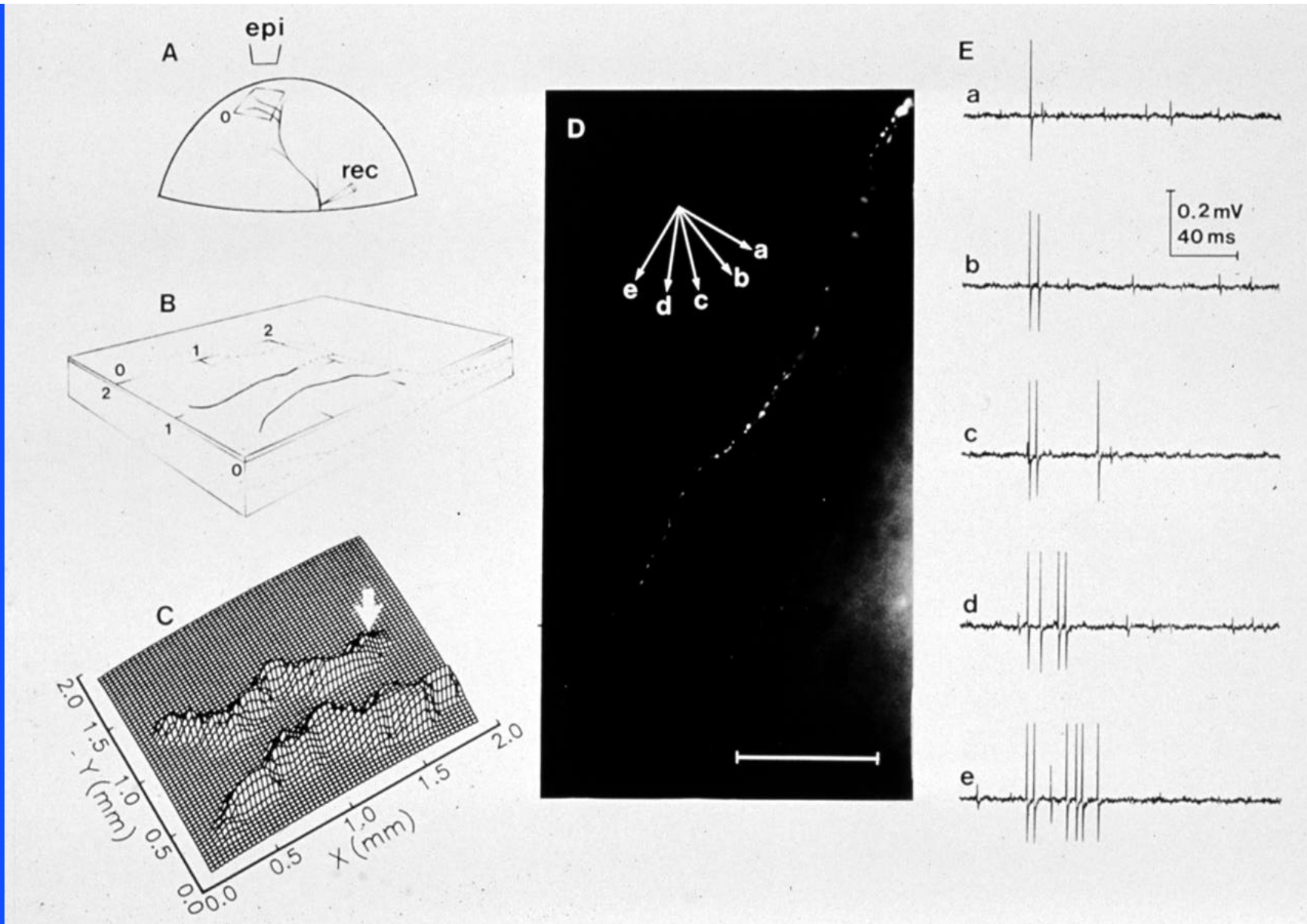
Courtesy B. J. Kane.

Reference: Kane, B. J., Stormont, C. W., Crowder, S. W., Tanelian, D. L., and Kovacs, G. T. A., "Force-Sensing Microprobe for Precise Stimulation Of Mechanosensitive Tissues," IEEE Transactions on Biomedical Engineering, vol. 42, no. 8, Aug. 1995, pp. 745 - 750.

# MICROPROBES USED IN MAPPING MECHANORECEPTORS OF THE CORNEA

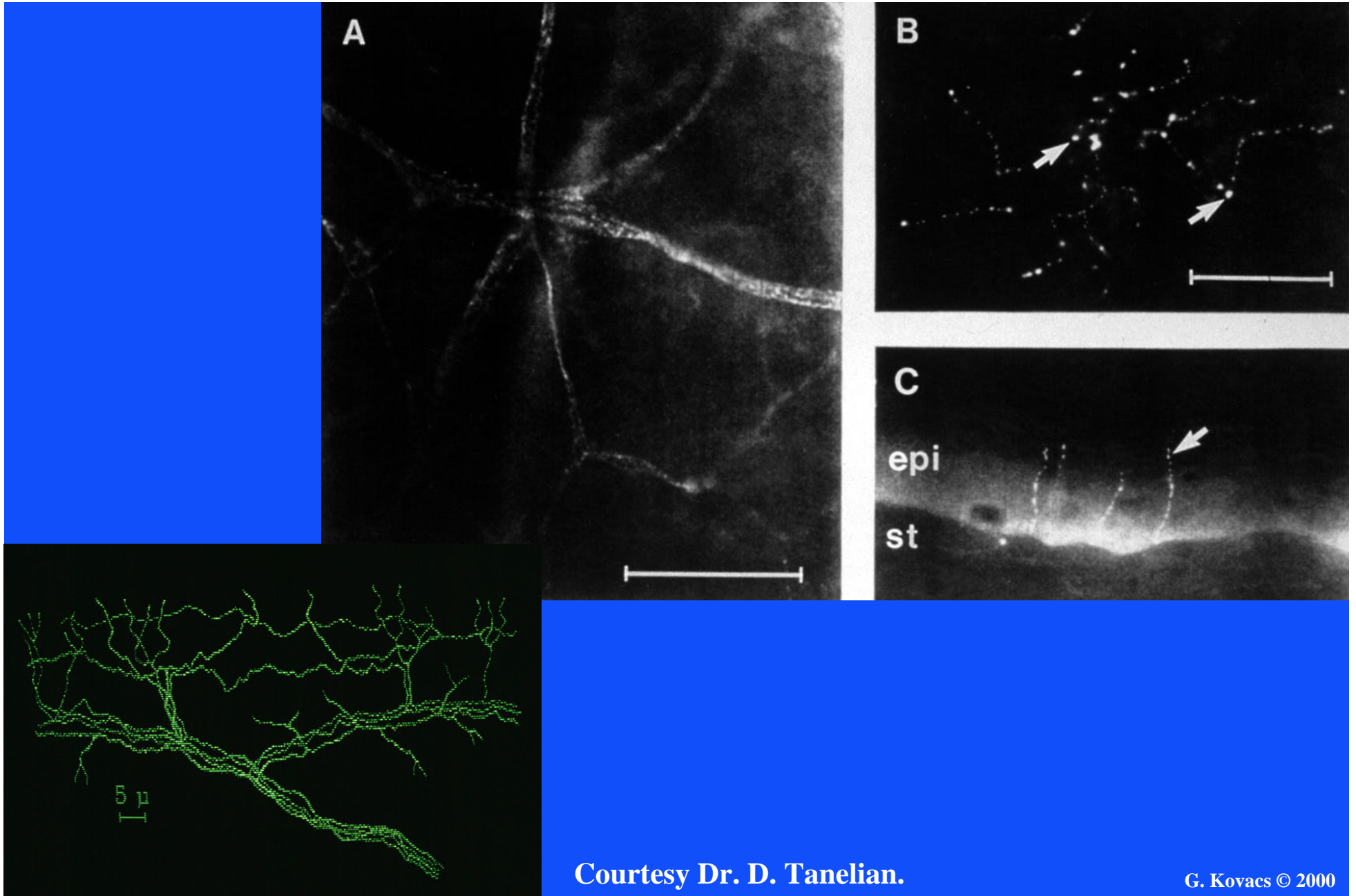


Reference: Kane, B. J., Storment, C. W., Crowder, S. W., Tanelian, D. L., and Kovacs, G. T. A., "Force-Sensing Microprobe for Precise Stimulation Of Mechanosensitive Tissues," IEEE Transactions on Biomedical Engineering, vol. 42, no. 8, Aug. 1995, pp. 745 - 750.



Courtesy Dr. D. Tanelian.

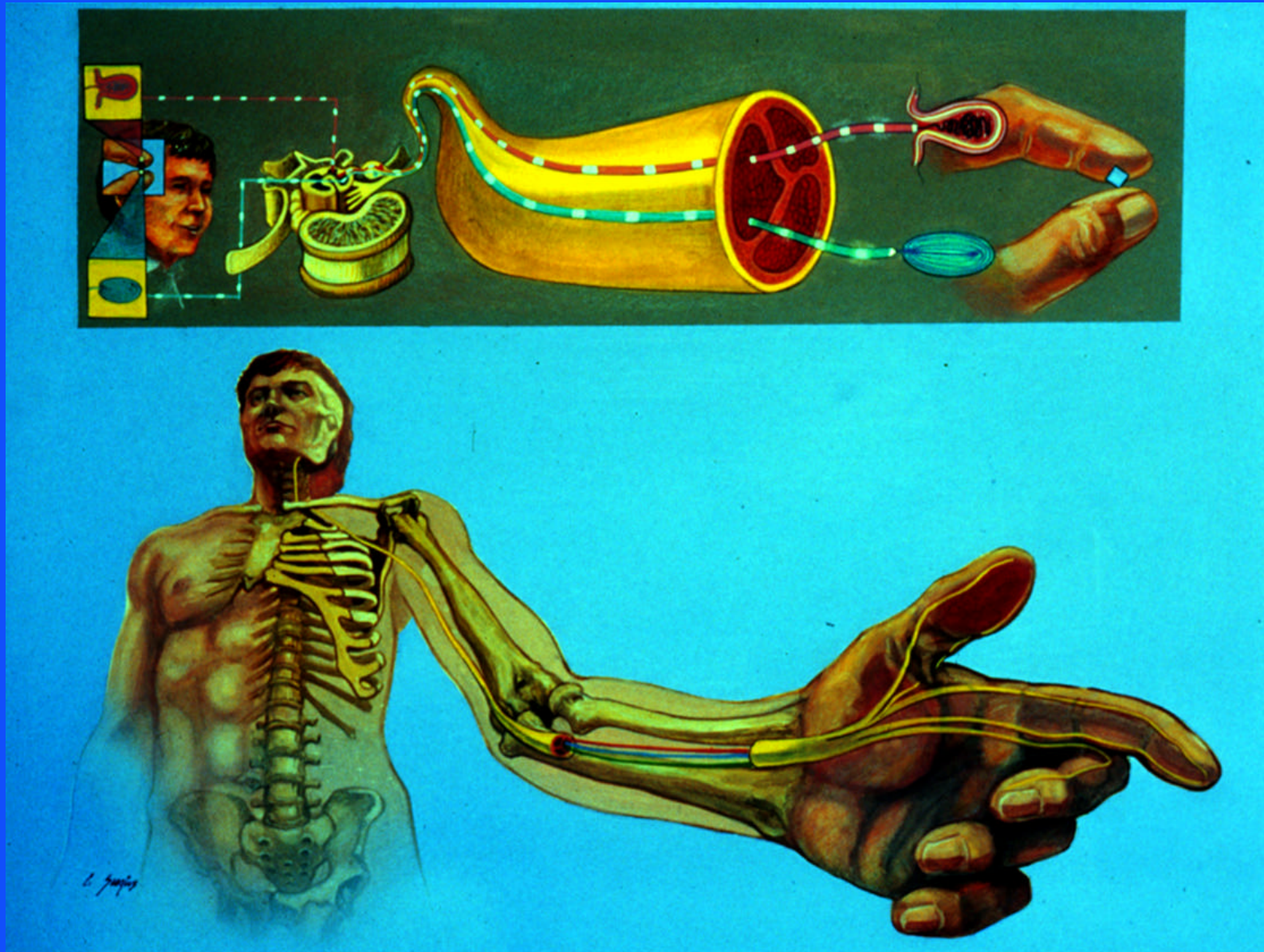
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Courtesy Dr. D. Tanelian.

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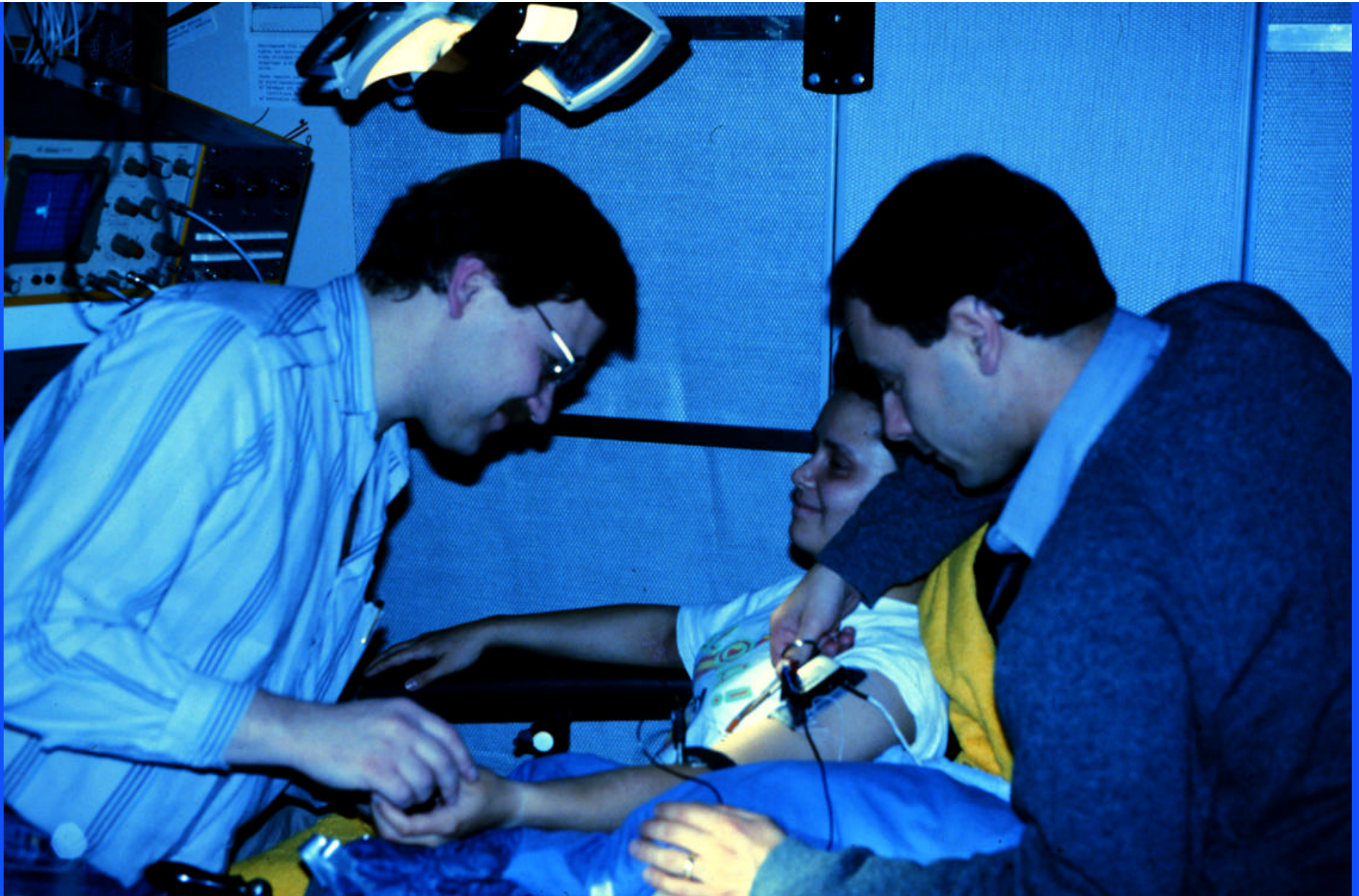




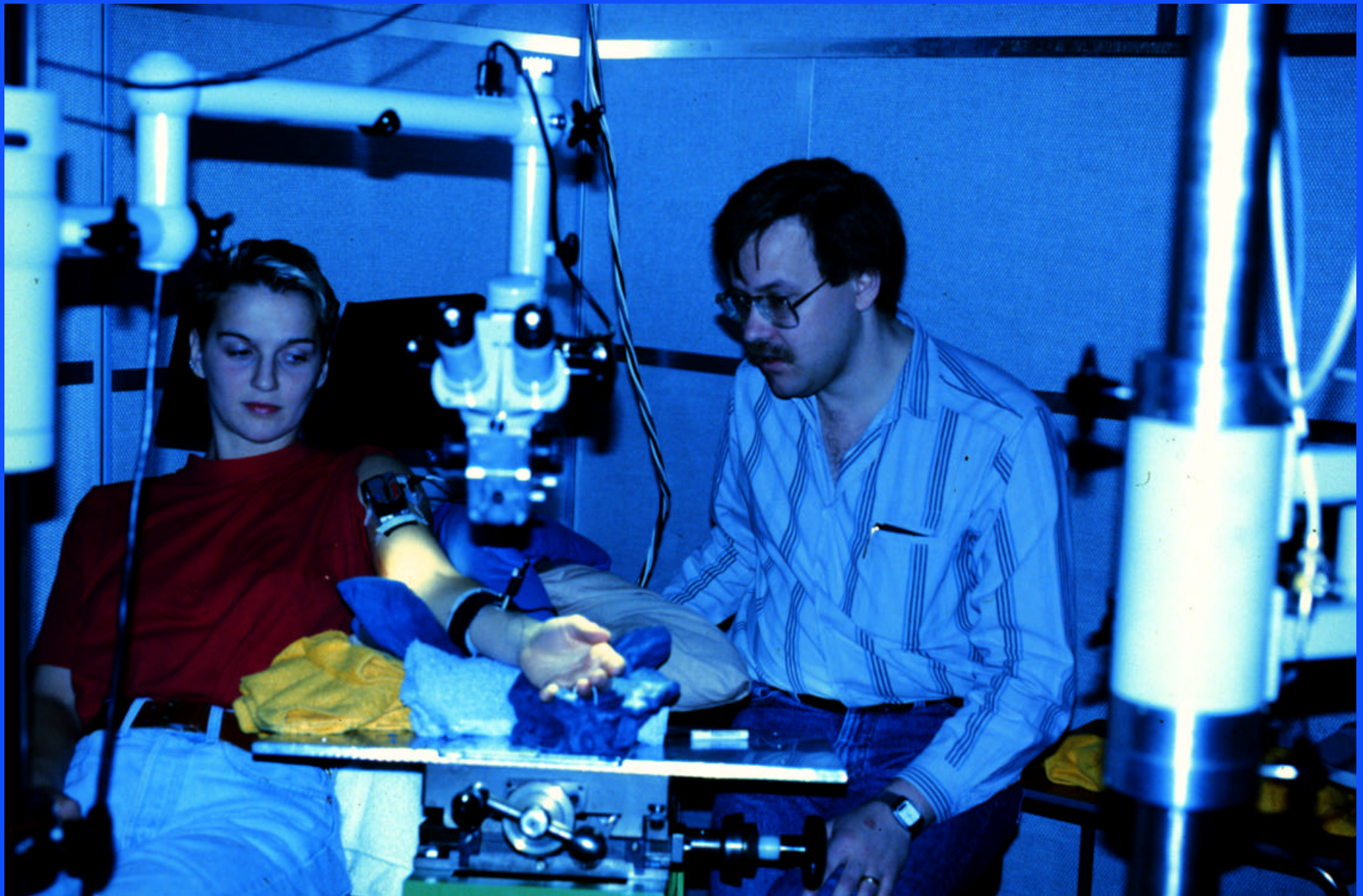
Courtesy Dr. J. Rosen.

G. Kovacs © 2000











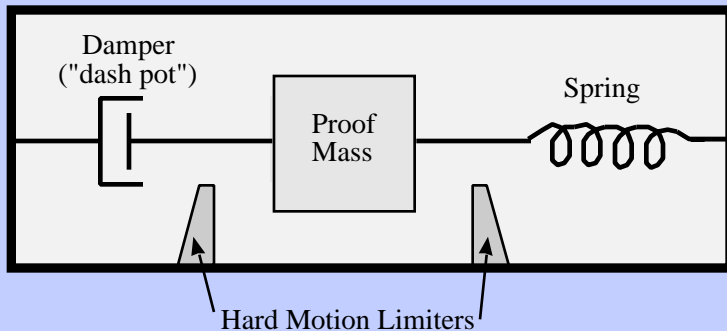




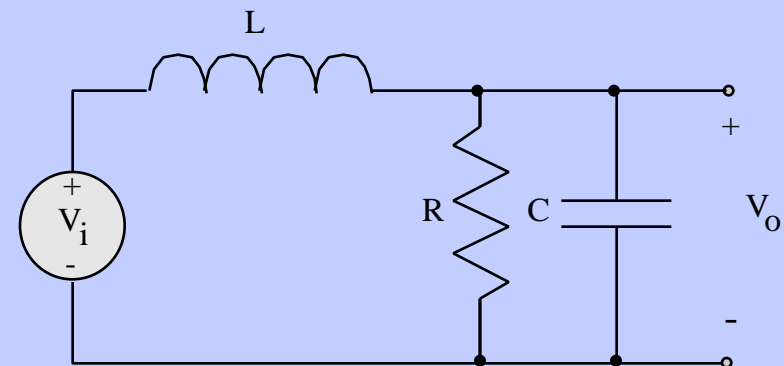
# BASIC ACCELEROMETER CONCEPTS

- Accelerometers use a proof mass to sense acceleration by measuring the force on the mass ( $F=ma$ ).
- The mass may be allowed to move against a restoring force (e.g. spring,  $F=kx$ ) and the displacement measured.
- The mass may be held in place by a closed loop force balancing system and the balancing force (error signal) measured.
- The basic accelerometer is a second-order system with a damping term.

$$H(S) = \frac{\frac{k}{m}}{S^2 + \frac{b}{m}S + \frac{k}{m}}$$

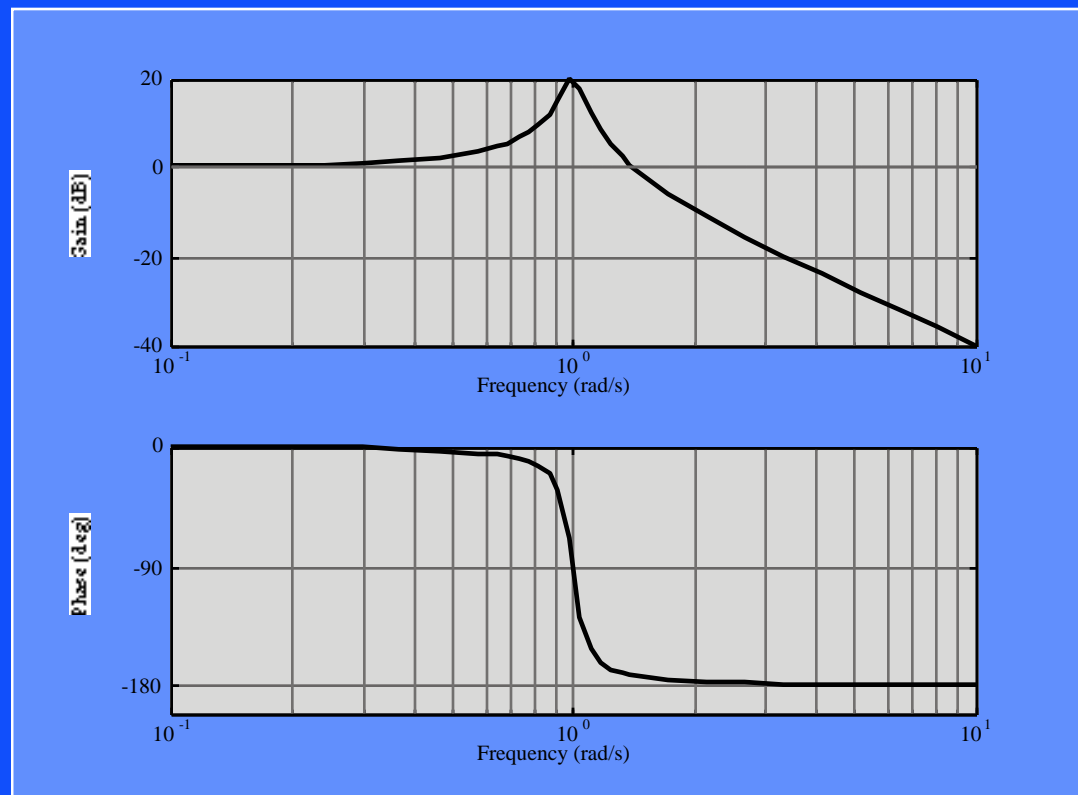


$$H(S) = \frac{\frac{1}{LC}}{S^2 + \frac{1}{RC}S + \frac{1}{LC}} = \frac{\frac{2}{\omega_o}}{S^2 + \frac{\omega_o}{Q}S + \frac{\omega_o^2}{\omega_o^2}}$$





# TYPICAL SECOND-ORDER RESPONSE



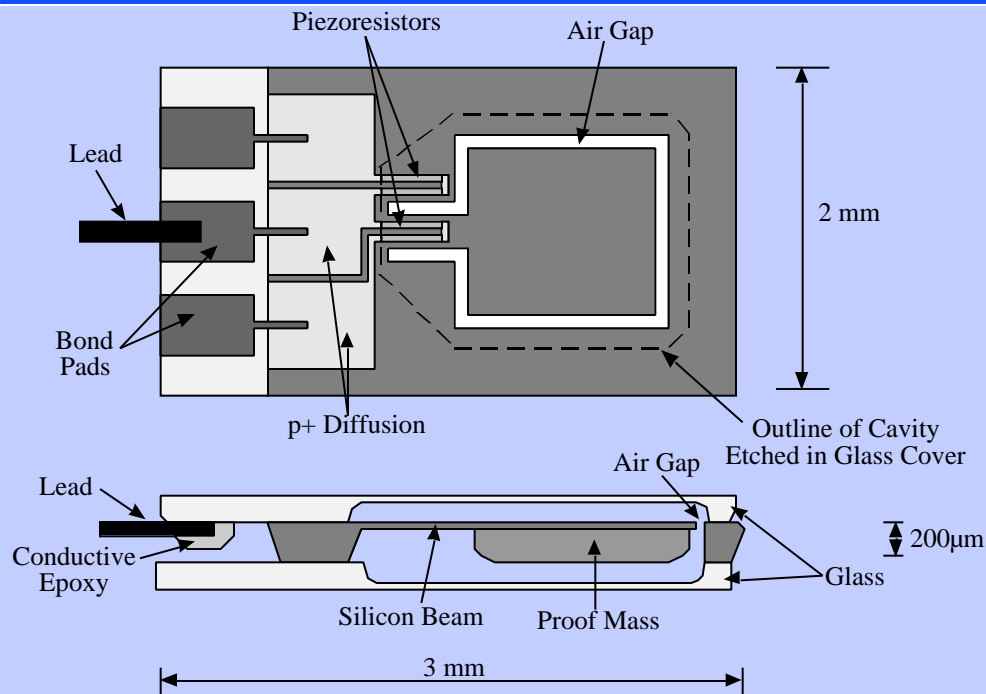
# ACCELEROMETERS FOR AUTOMOTIVE APPLICATIONS

Range	$\pm 1g$	antilock braking (ABS)/traction control system (TCS)
	$\pm 2g$	vertical body motion
	$\pm 40g$	wheel motion
	$\pm 50g$	airbag deployment
	$\pm 100^\circ/s$	steering feedback
Accuracy	$\pm 2 \%$	5% at temperature extremes
Cross-Axis Sensitivity	$< 1 - 3 \%$	all applications
Shock Survivability	$> 500g$	1 m drop onto concrete
Frequency Response	0 to 5 Hz	vertical motion
	0.5 to 50 Hz	horizontal motion (up to 1 kHz for airbags)
Temperature Range	-40 to 85 °C	most applications
	-40 to 125°C	under hood

Reference: MacDonald, G. A., "A Review of Low Cost Accelerometers for Vehicle Dynamics," Sensors and Actuators A, vol. A21 - A23, 1990, pp. 303 - 307.

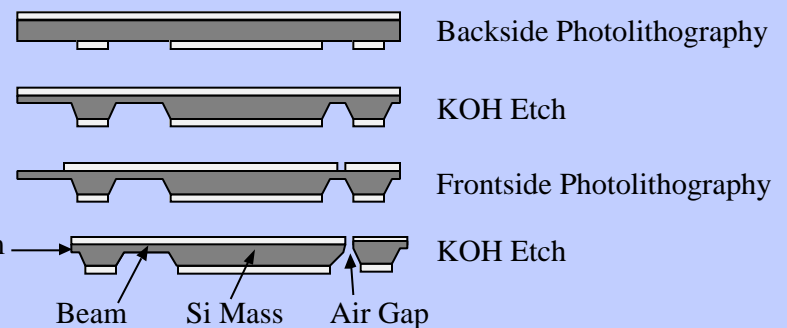
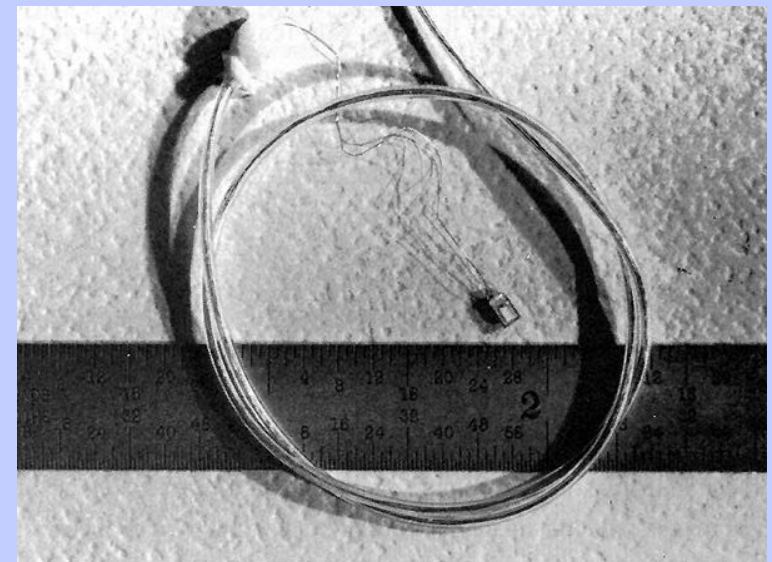


# EARLY MICROMACHINED ACCELEROMETER (ROYLANCE)



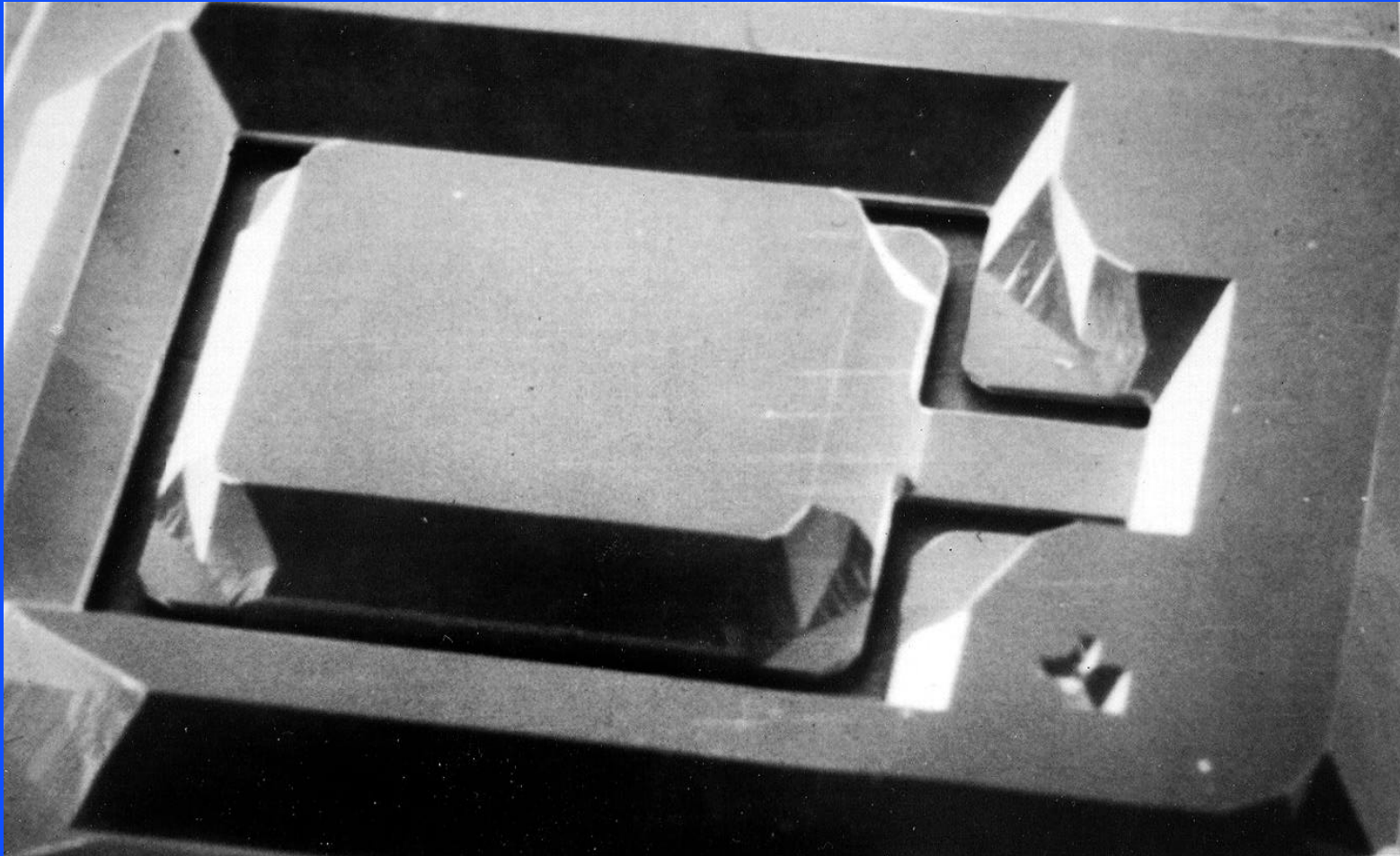
**Reference: Roylance, L. M. and Angell, J. B., "A Batch-Fabricated Silicon Accelerometer," IEEE Transactions on Electron Devices, vol. ED-26, no. 12, Dec. 1979, pp. 1911 - 1917.**

SiO<sub>2</sub>  
Silicon

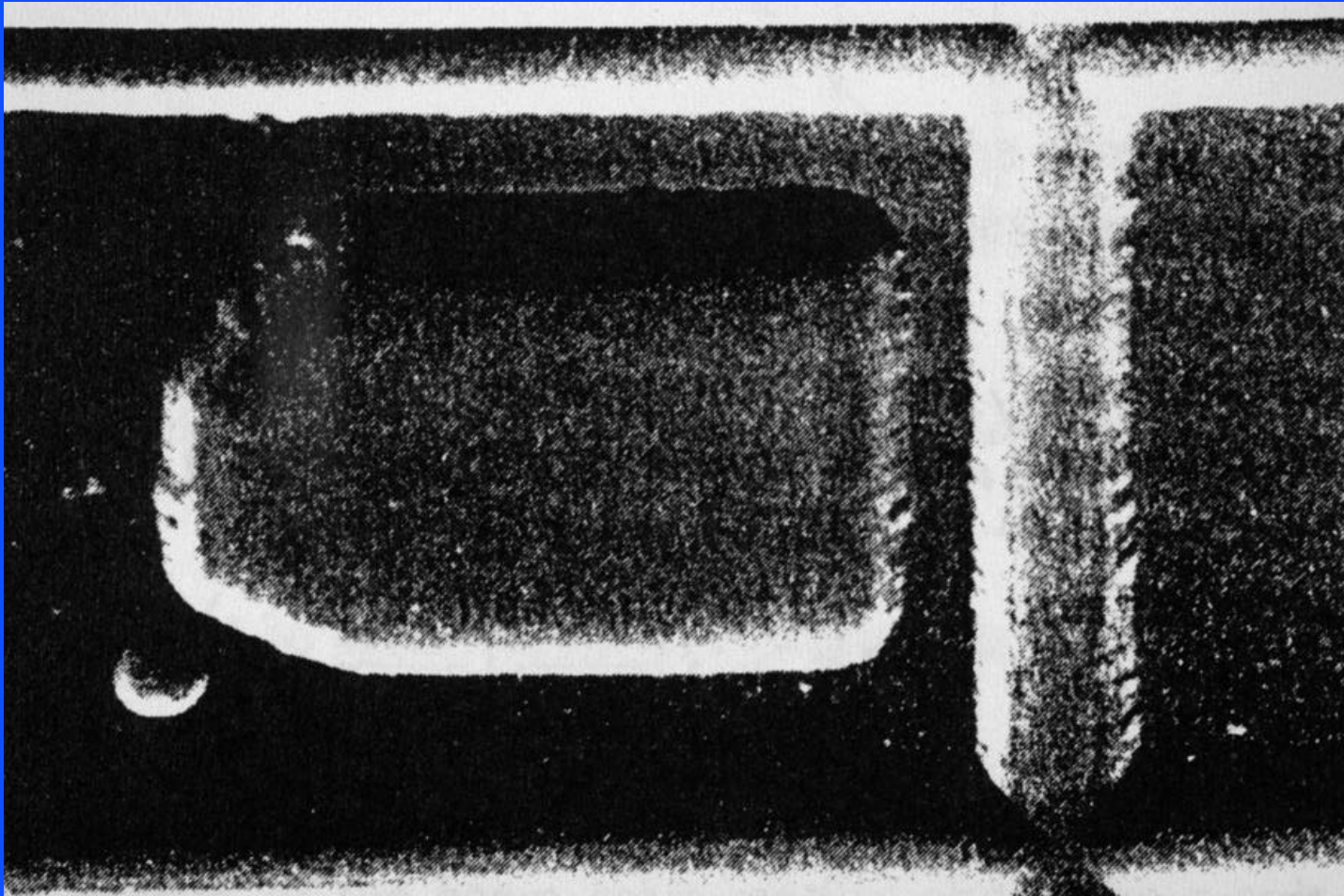


**After Roylance and Angell (1979).**

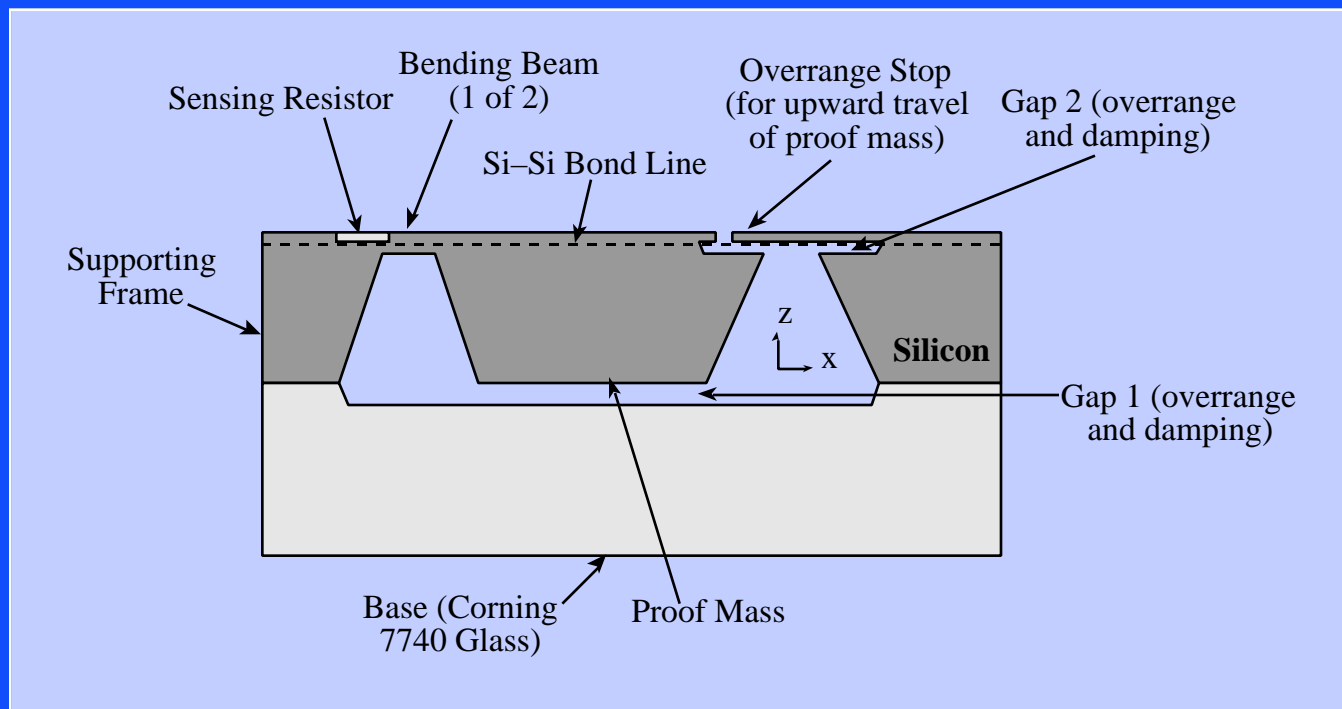
# Roylance - Micromachined Accelerometer - 1974



# GLASS CAVITY ETCH

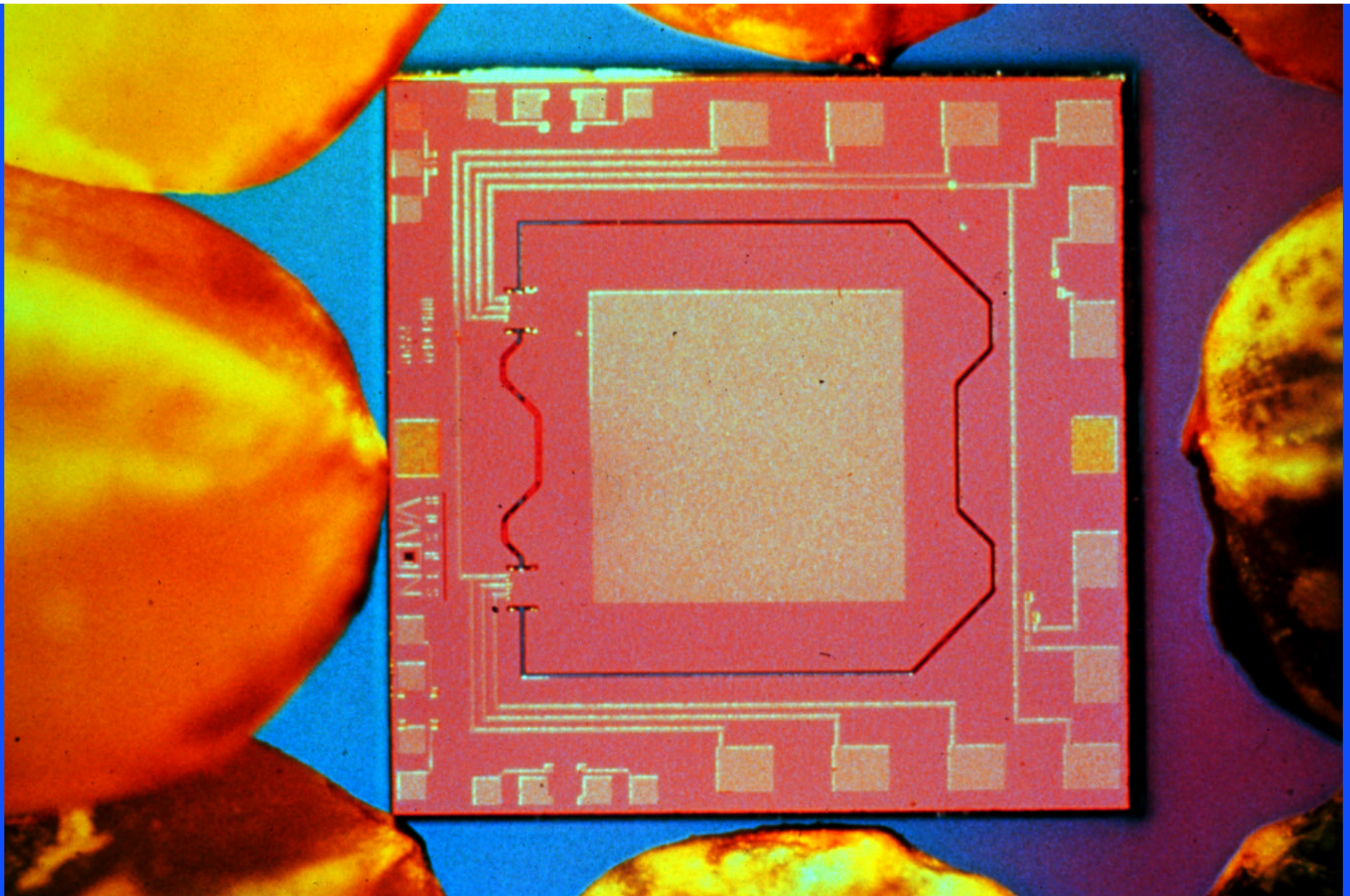


# MODERN MICROMACHINED ACCELEROMETER (STRAIN GAUGE TYPE)



Courtesy of K. Petersen.

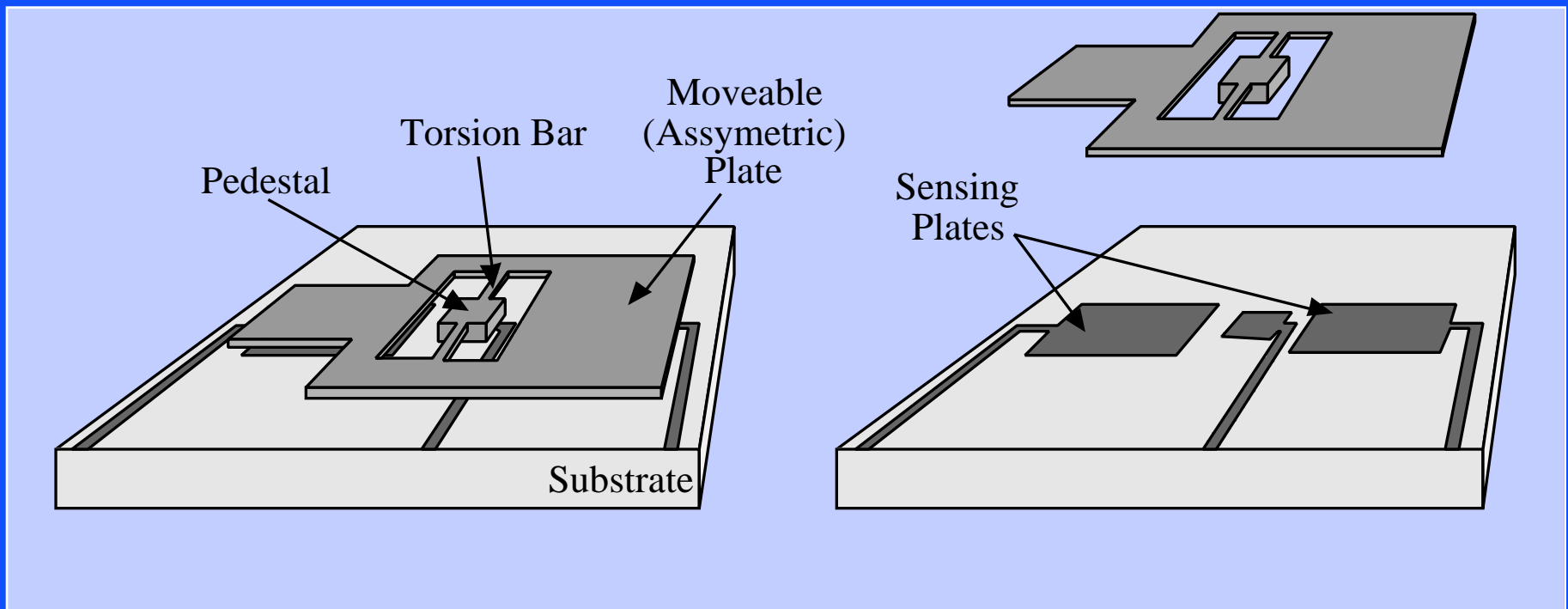




Courtesy of Lucas NovaSensor.

G. Kovacs © 2000

# OPEN-LOOP CAPACITIVE ACCELEROMETER



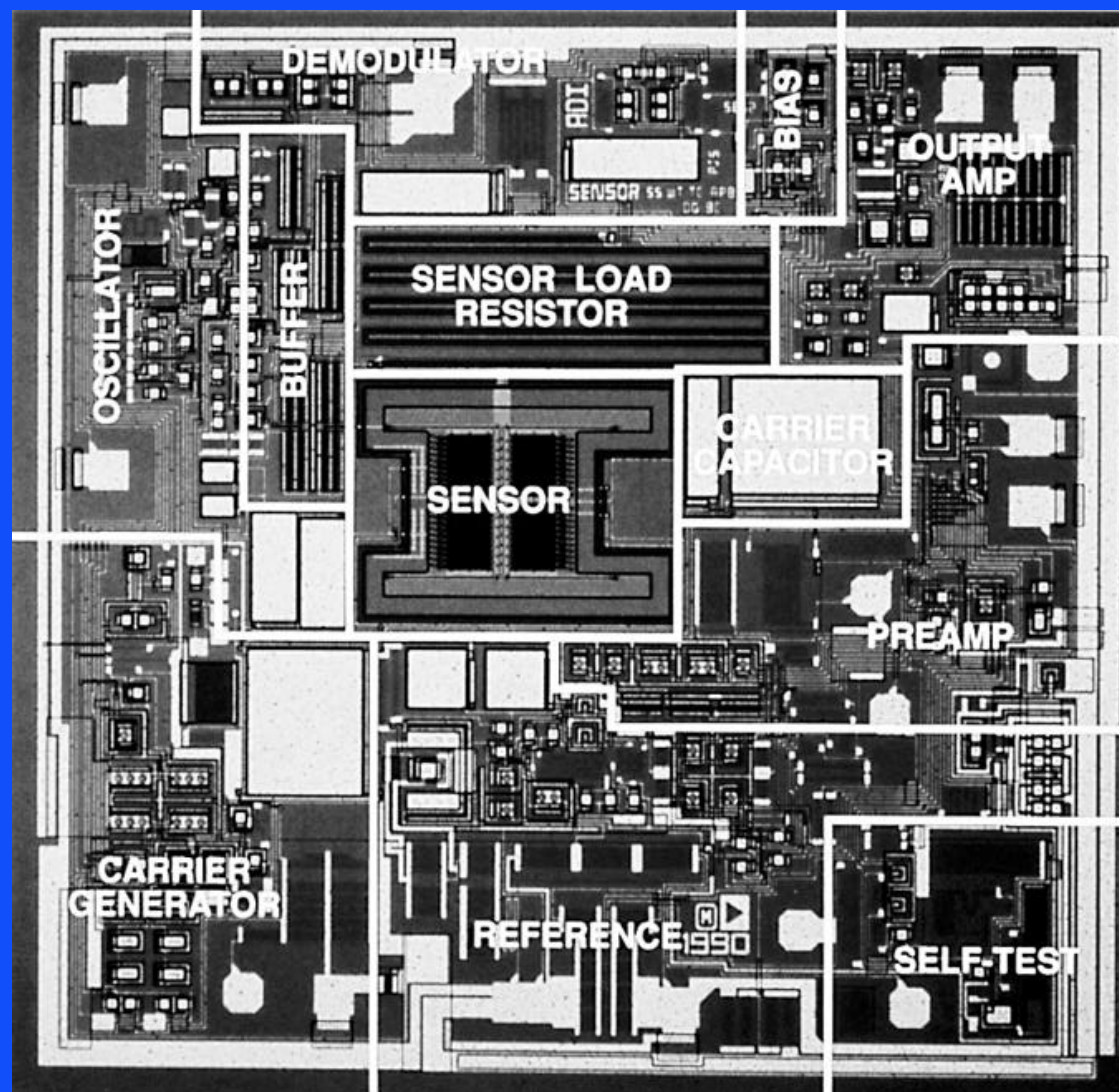
Adapted from Cole (1991).

Reference: Cole, J. C., "A New Sense Element Technology for Accelerometer Subsystems," Proceedings of the International Conference on Solid-State Sensors and Actuators, Transducers '91, San Francisco, CA, June 24 - 27, 1991, pp. 93 - 96.



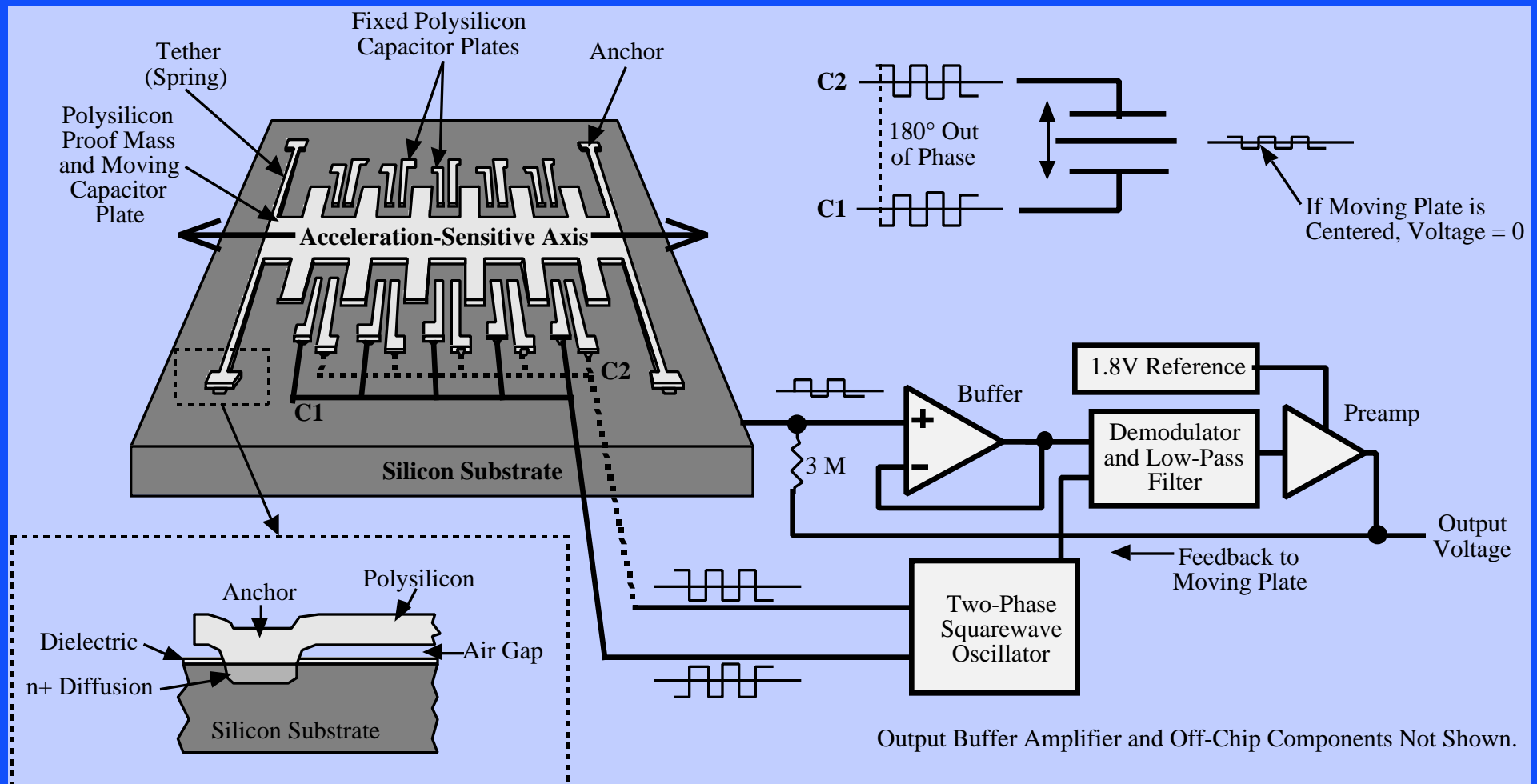
# CAPACITIVE ACCELEROMETER ANALOG DEVICES ADXL-50

- Micromachined polysilicon proof mass formed from 2  $\mu\text{m}$  thick polysilicon on BiMOS.
- Capacitive force-rebalance method keeps mass stationary.
- On-chip circuitry provides signal conditioning and self-test.



(3 X 3 mm chip)

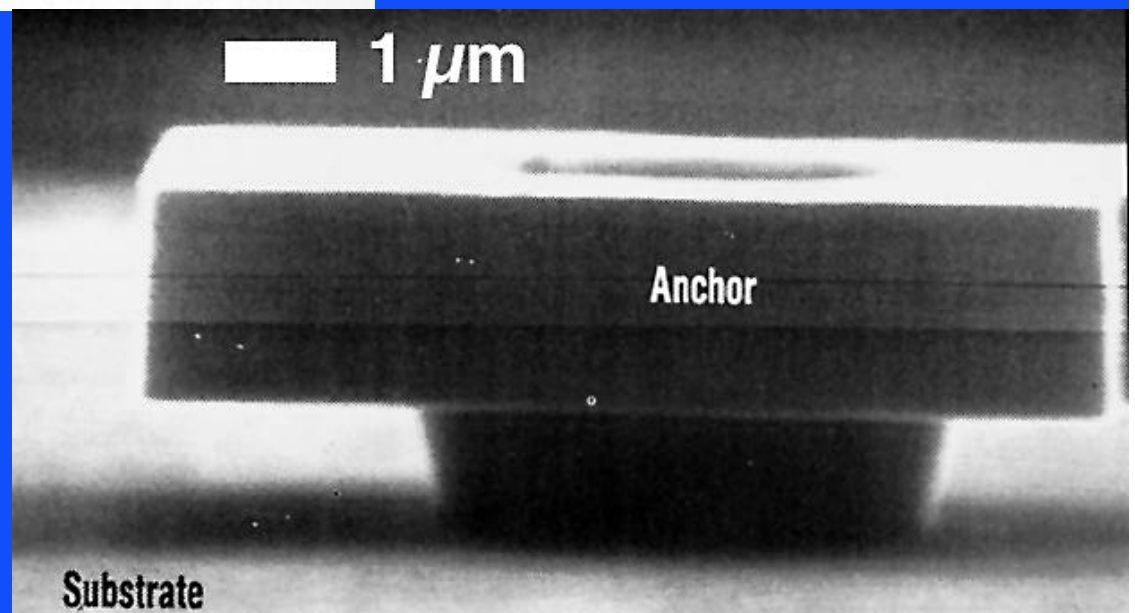
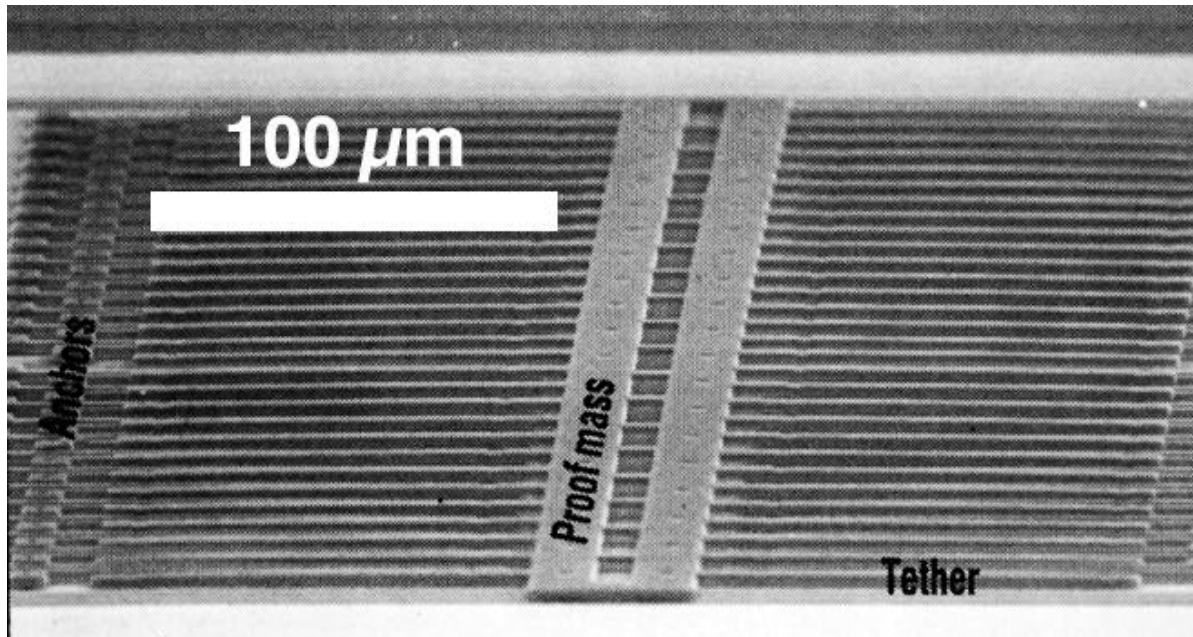
Image courtesy of Dr. R. Payne.



Adapted from Goodenough (1991) and Analog Devices data sheet.

Reference: Goodenough, F., "Airbags Boom When IC Accelerometer Sees 50g," Electronic Design, vol. 39, no. 15, Aug. 8, 1991.

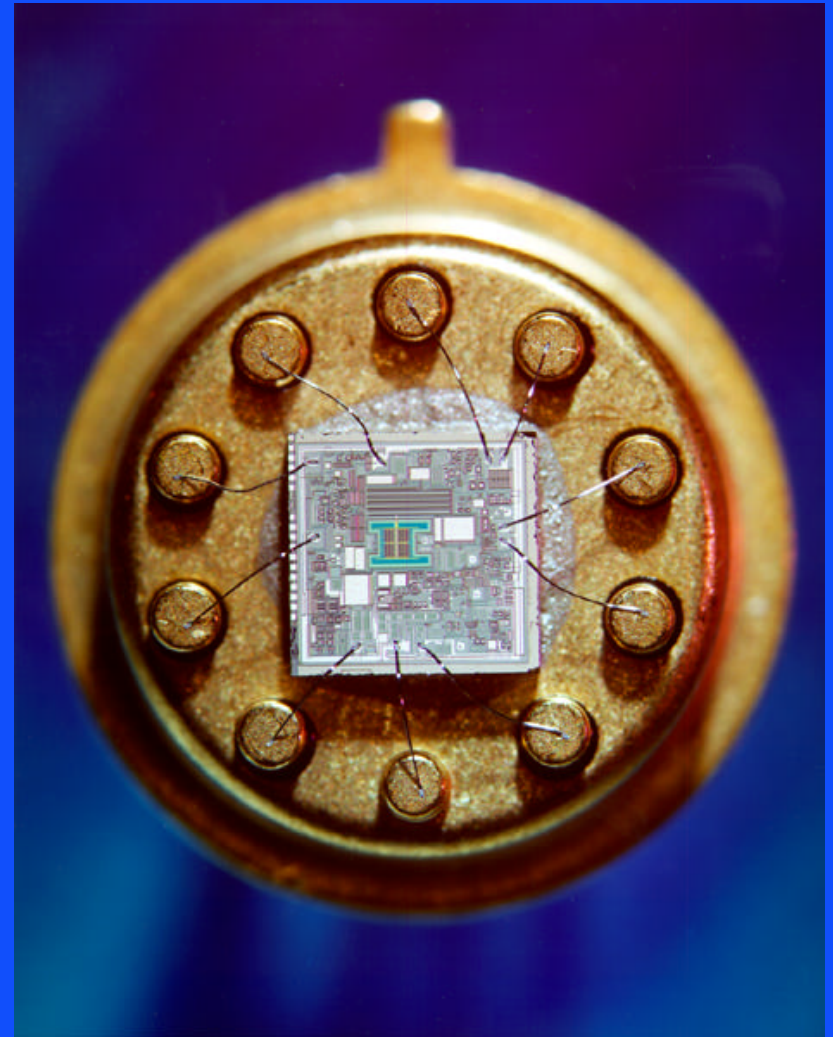
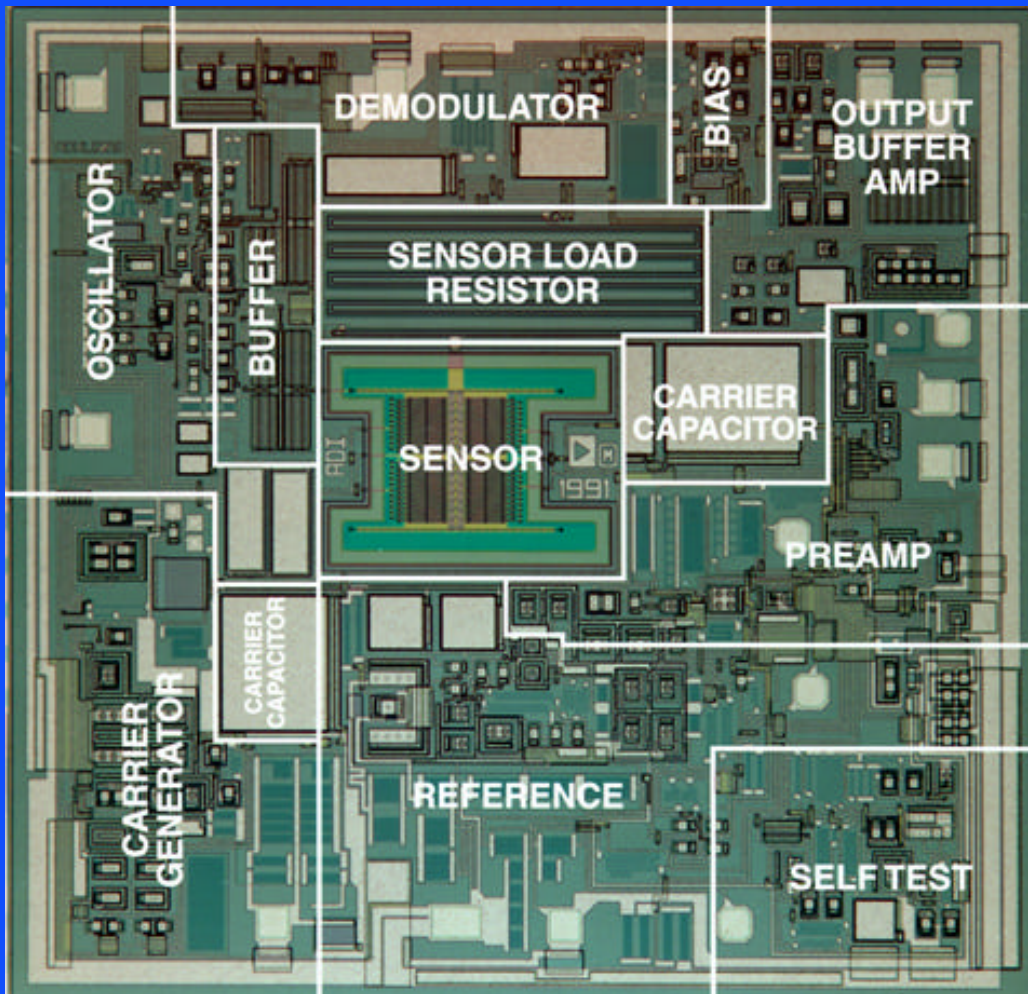




Images courtesy Dr. R. Payne, Analog Devices, Inc.

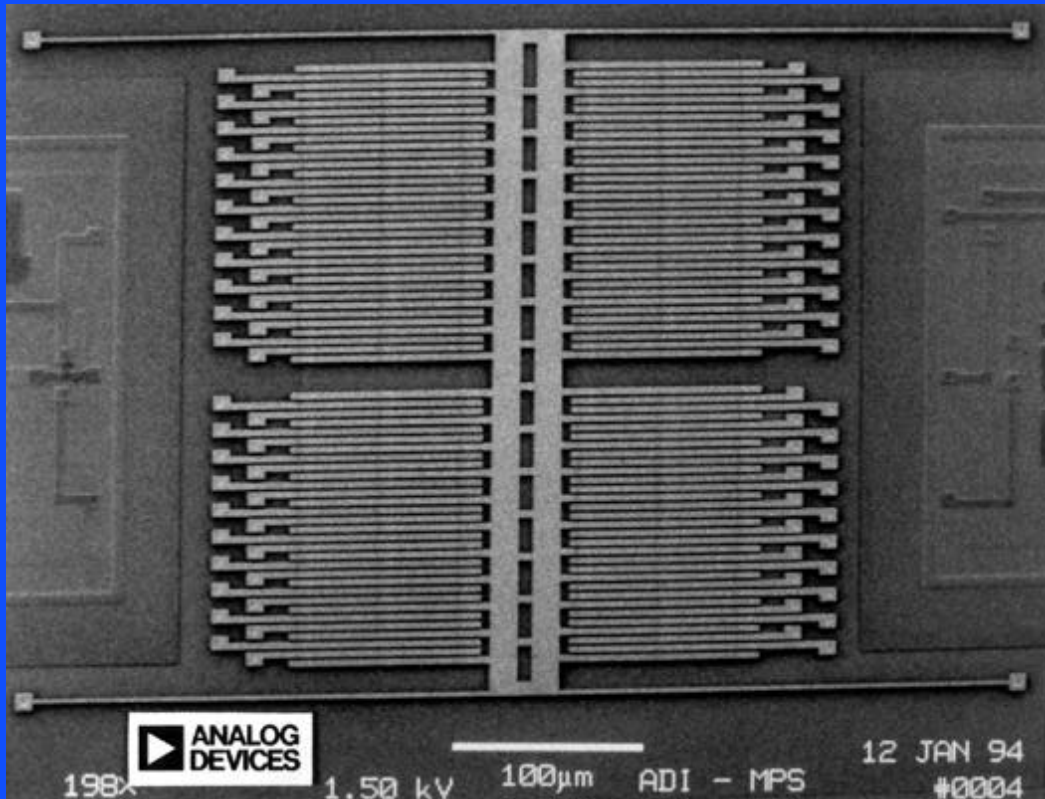
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# ANALOG DEVICES ADXL-50

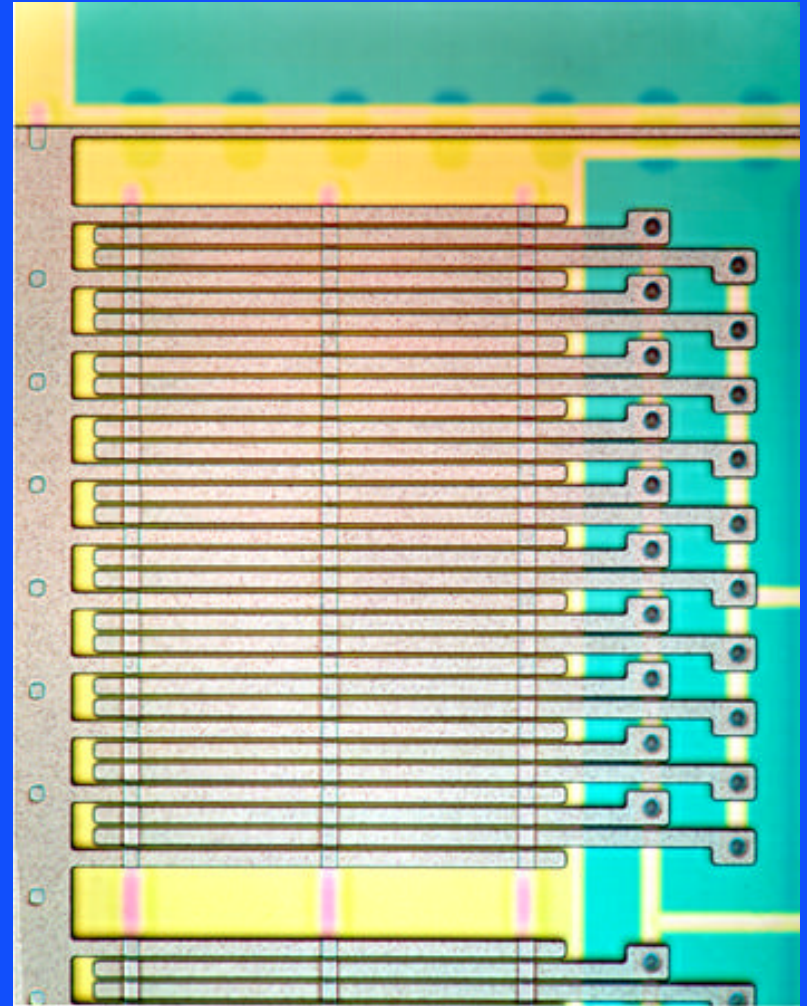


Images courtesy Dr. R. Payne, Analog Devices, Inc.





Images courtesy Dr. R. Payne, Analog Devices, Inc.



# ADXL-05 ACCELEROMETER

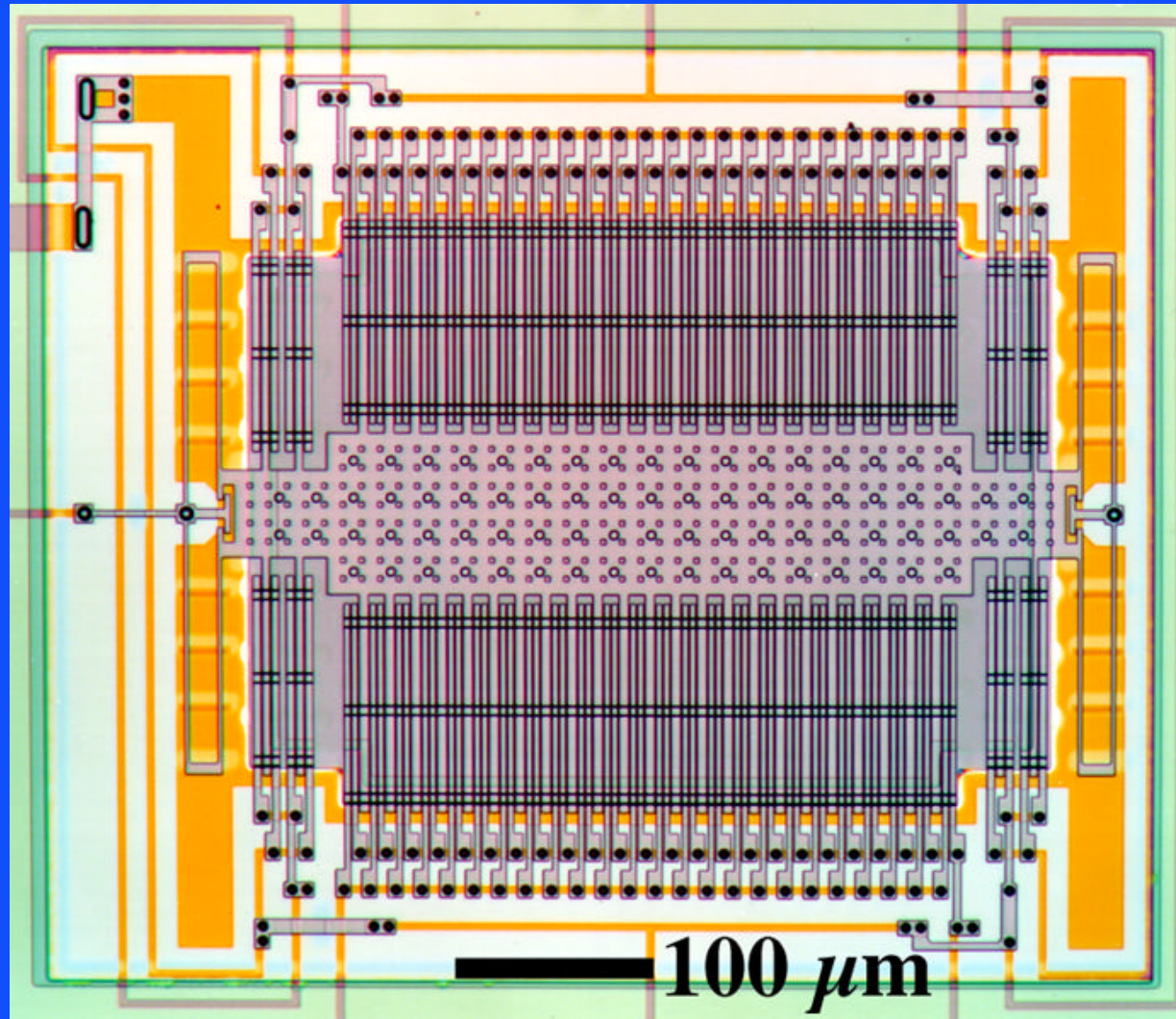
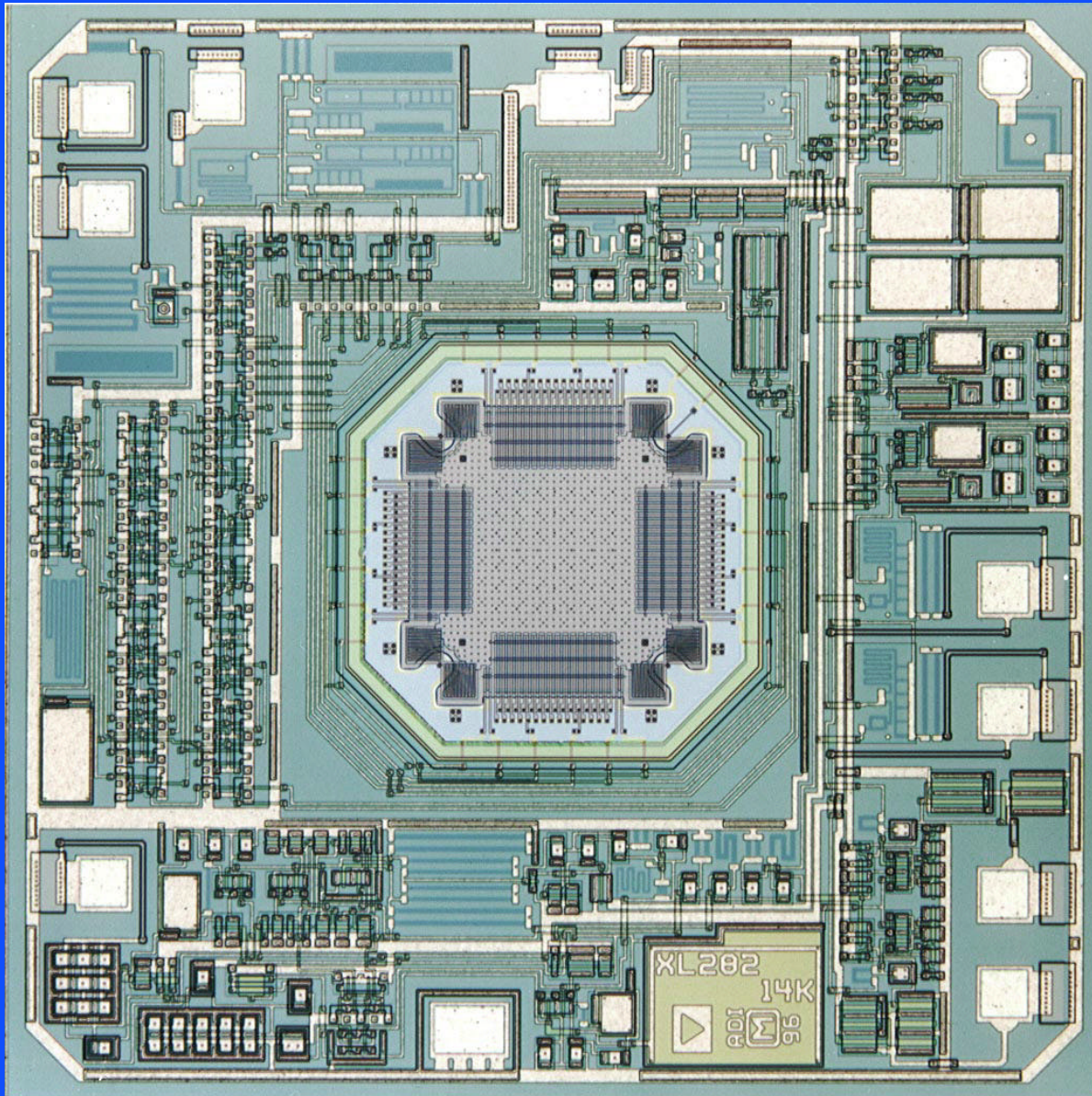


Image courtesy Dr. R. Payne, Analog Devices, Inc.



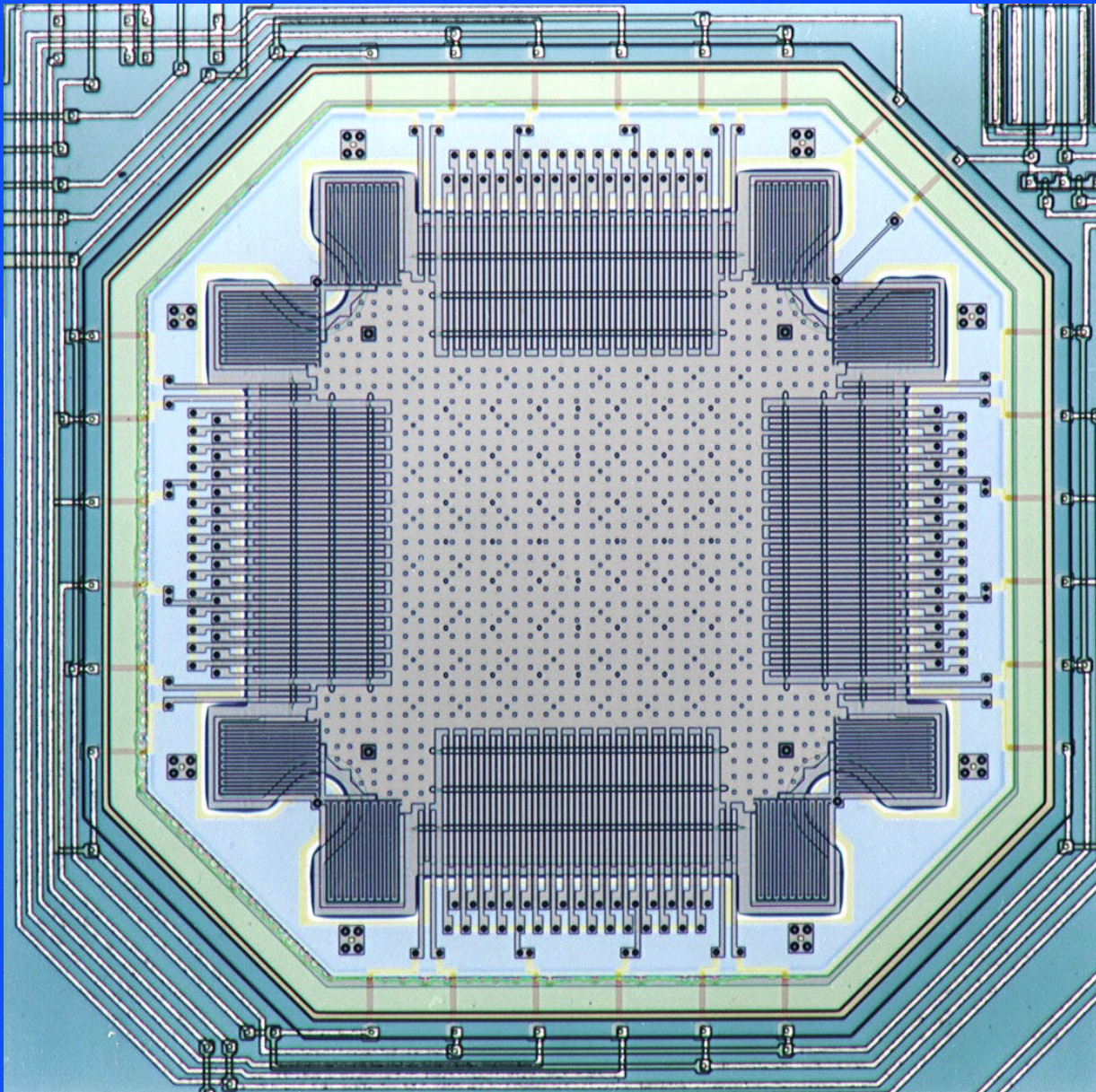
# ADXL-202



Courtesy Dr. M. Judy, Analog Devices, Inc.

G. Kovacs © 2000





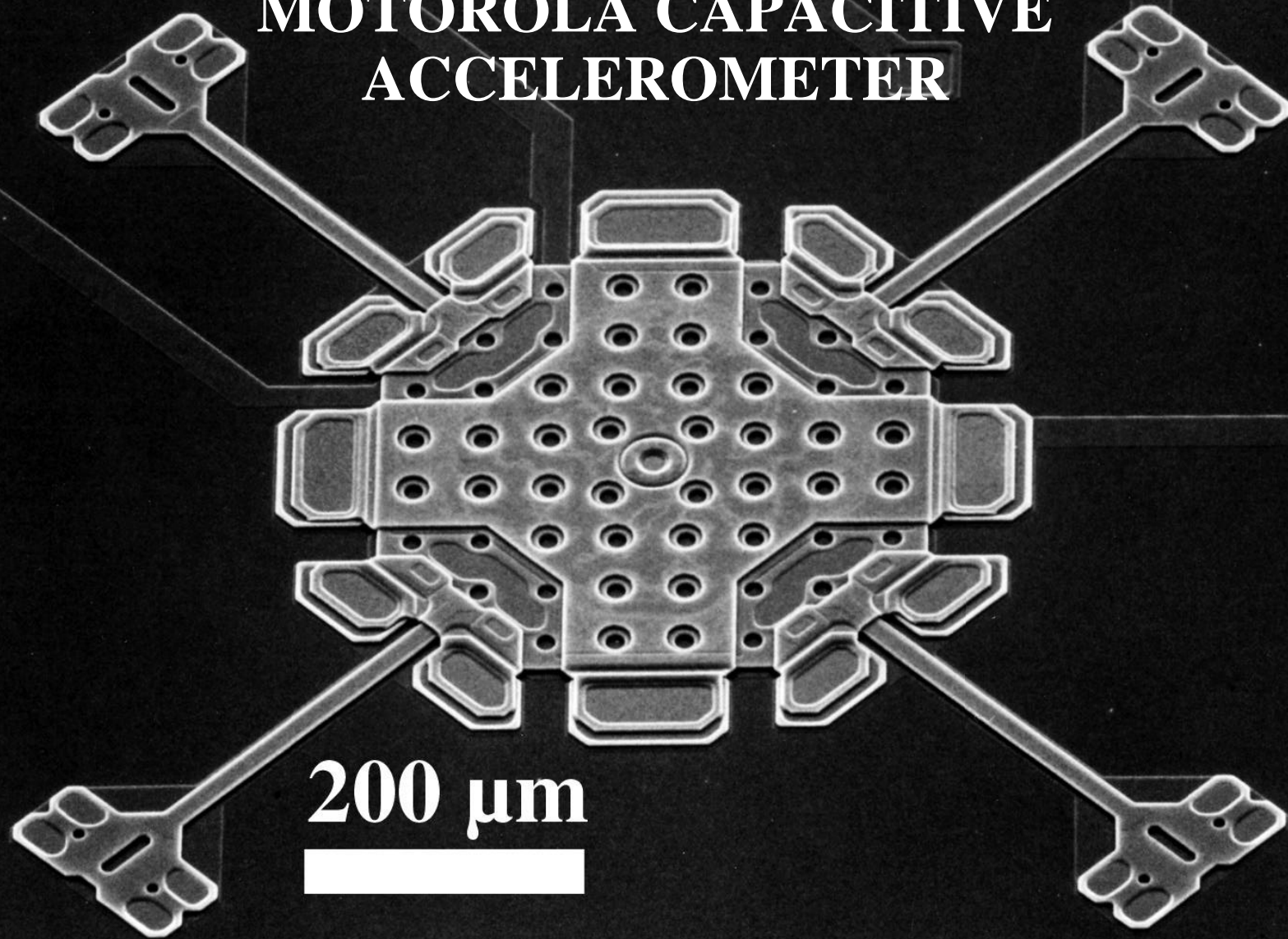
# ADXL-202 CORE

Courtesy Dr. M. Judy, Analog Devices, Inc.

G. Kovacs © 2000



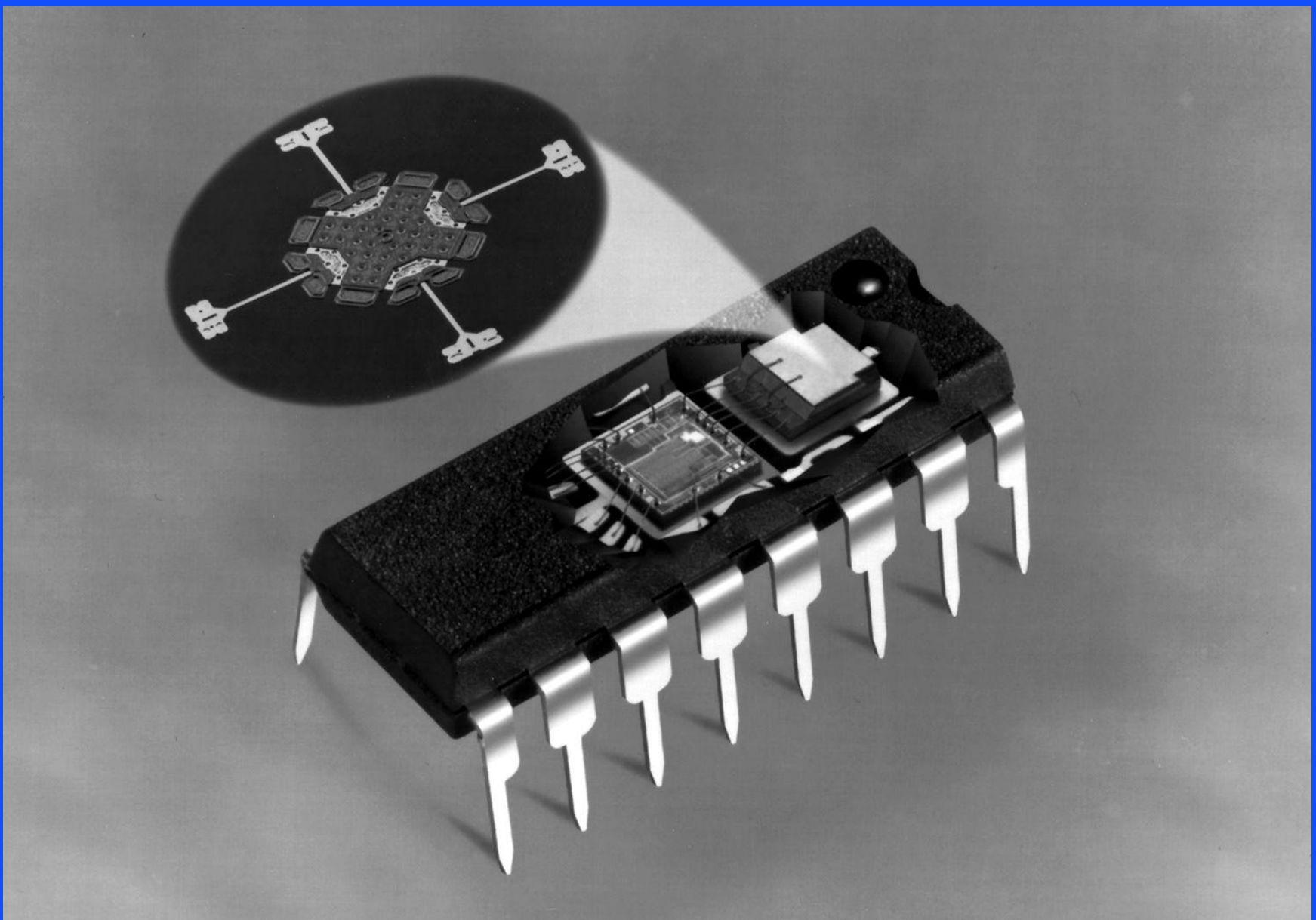
# MOTOROLA CAPACITIVE ACCELEROMETER



Courtesy Dr. Lj. Ristic, Motorola, Inc.

G. Kovacs © 2000

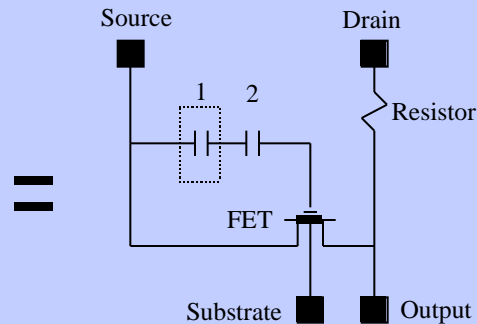
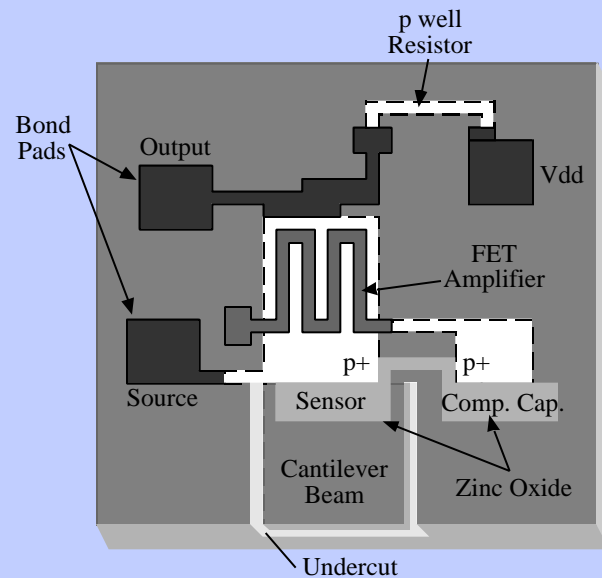




Courtesy Dr. Lj. Ristic, Motorola, Inc.

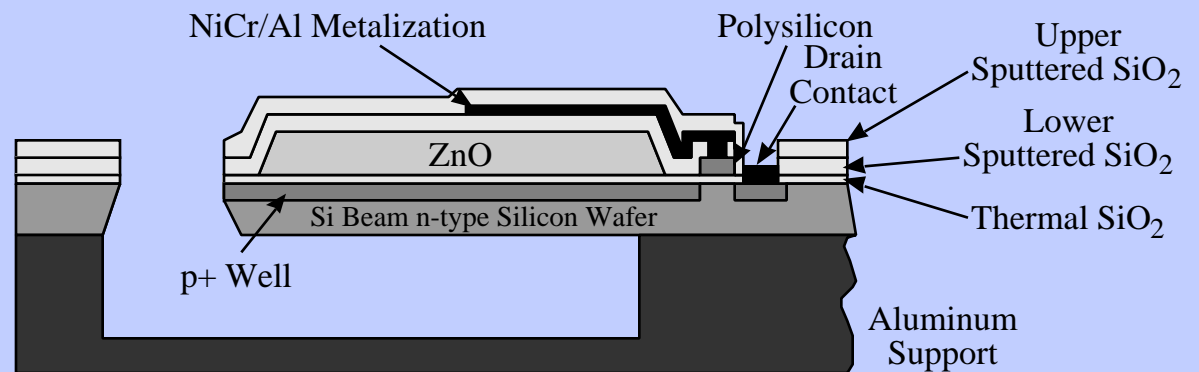
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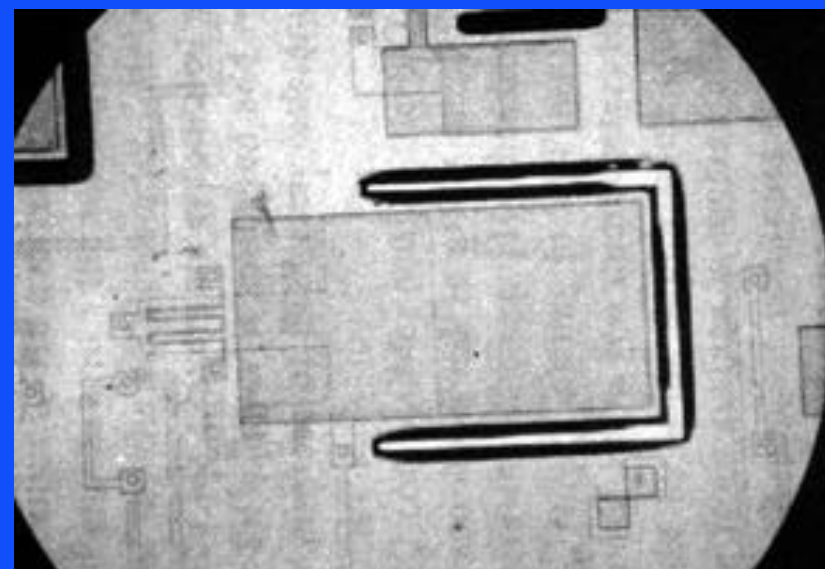
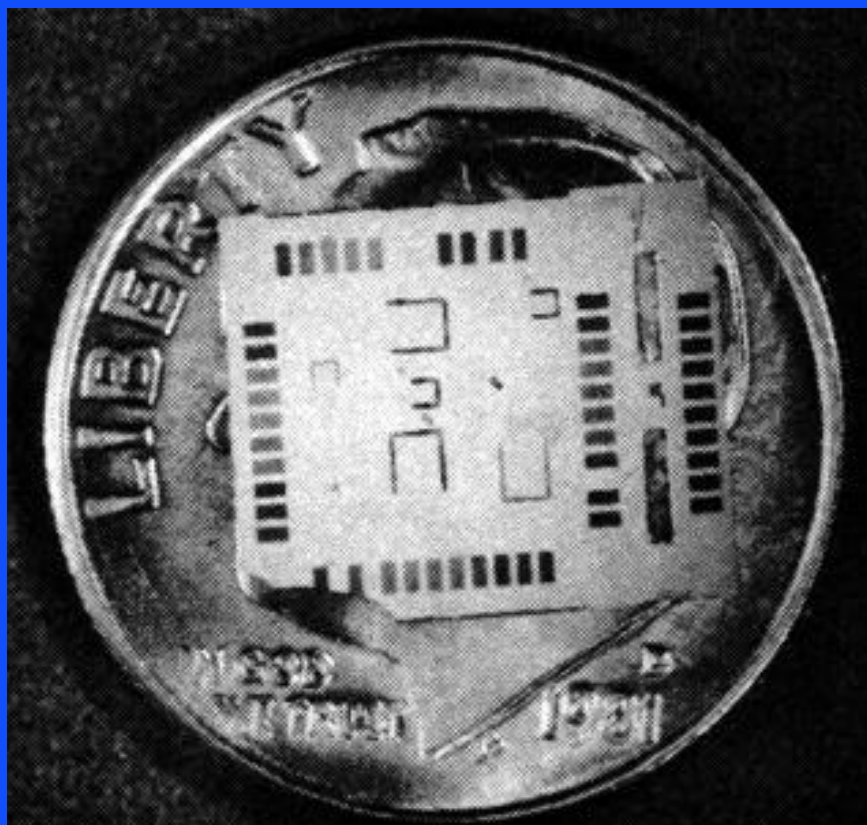
# PIEZOELECTRIC ACCELEROMETERS



Piezoelectric thin film capacitors:  
 1 - Strained capacitor on beam  
 2 - Unstrained compensation capacitor

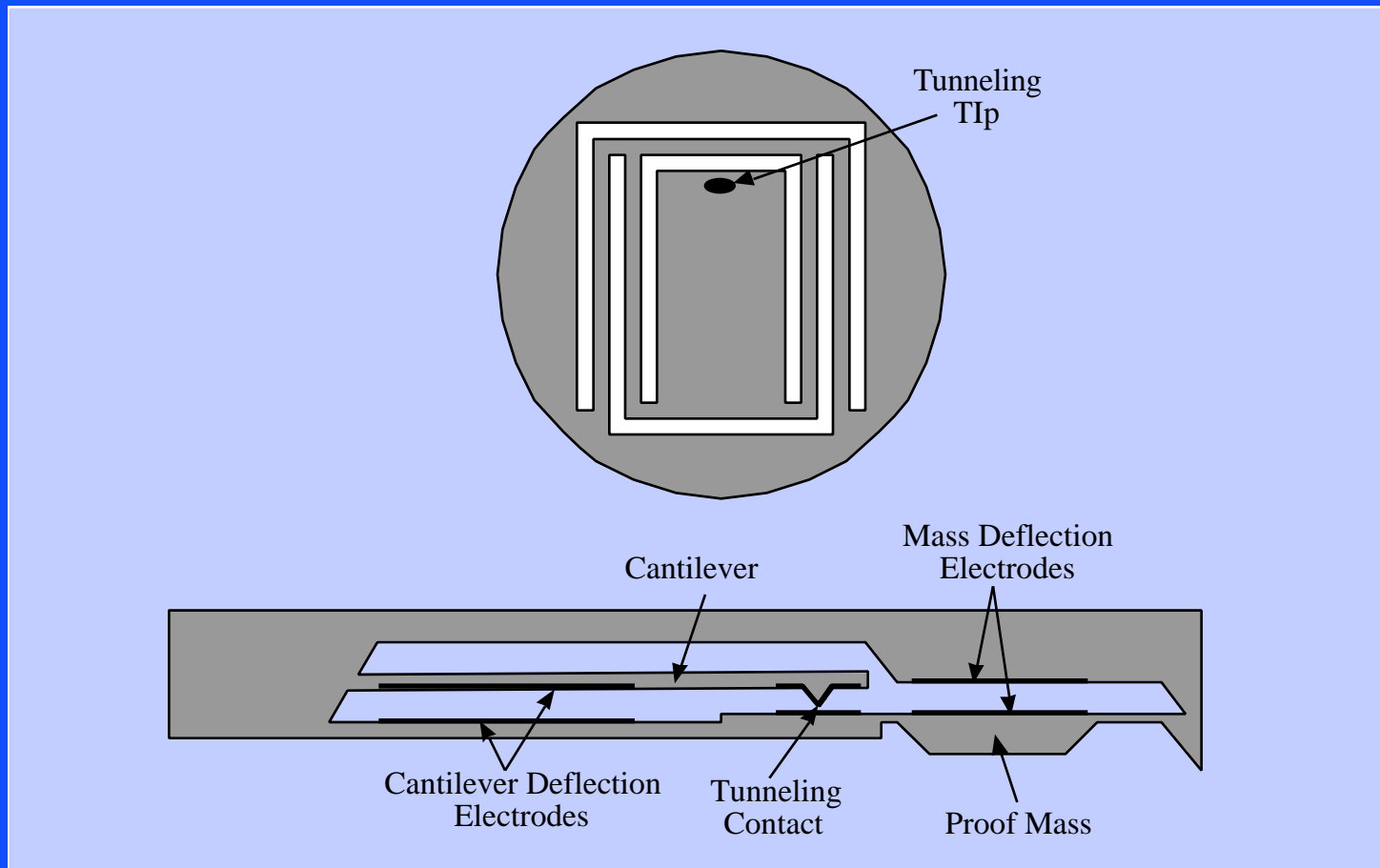
Reference: Chen, P.-L., Muller, R. S., Shiosaki, T., and White, R. M., "Silicon Cantilever Beam Accelerometer Utilizing a PI-FET Capacitive Transducer," IEEE Transactions on Electron Devices, vol. ED-26, 1979, p. 1857.





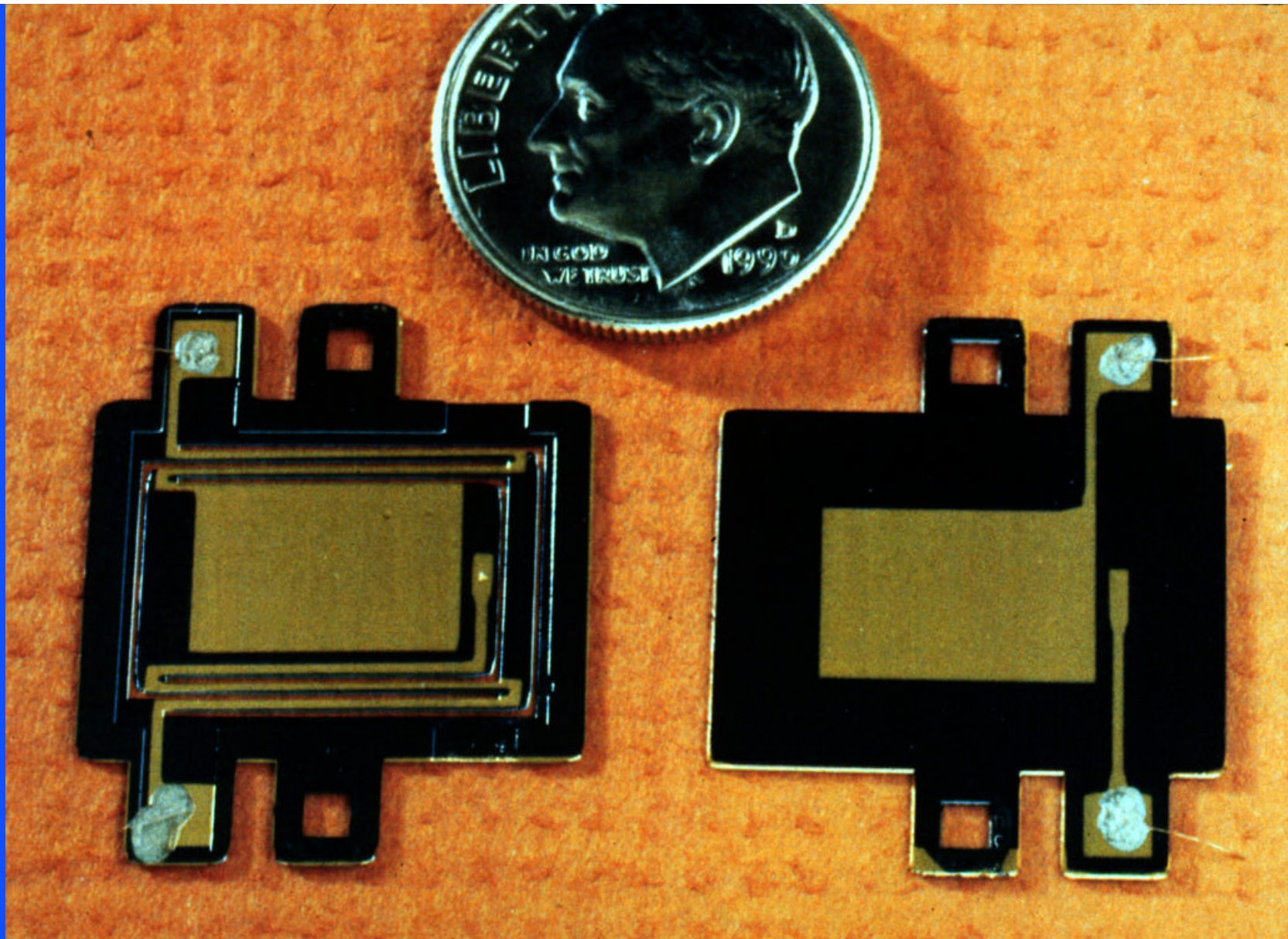
Source: Chen, P.-L., Muller, R. S., Shiosaki, T., and White, R. M., "Silicon Cantilever Beam Accelerometer Utilizing a PI-FET Capacitive Transducer," IEEE Transactions on Electron Devices, vol. ED-26, 1979, p. 1857.

# TUNNELING ACCELEROMETERS



Reference: Rockstad, H. K., Kenny, T. W., Reynolds, J. K., Kaiser, W. J., and Gabrielson, T. B., "A Miniature High-Sensitivity Broad-Band Accelerometer Based on Electron Tunneling Transducers," Proceedings of the 7th International Conference on Solid State Sensors and Actuators, Transducers '93, Yokohama, Japan, 7-10 June 1993, pp. 836 - 839 (also published in Sensors and Actuators A, vol. A43, no. 1 - 3, May 1994, 107 - 114).



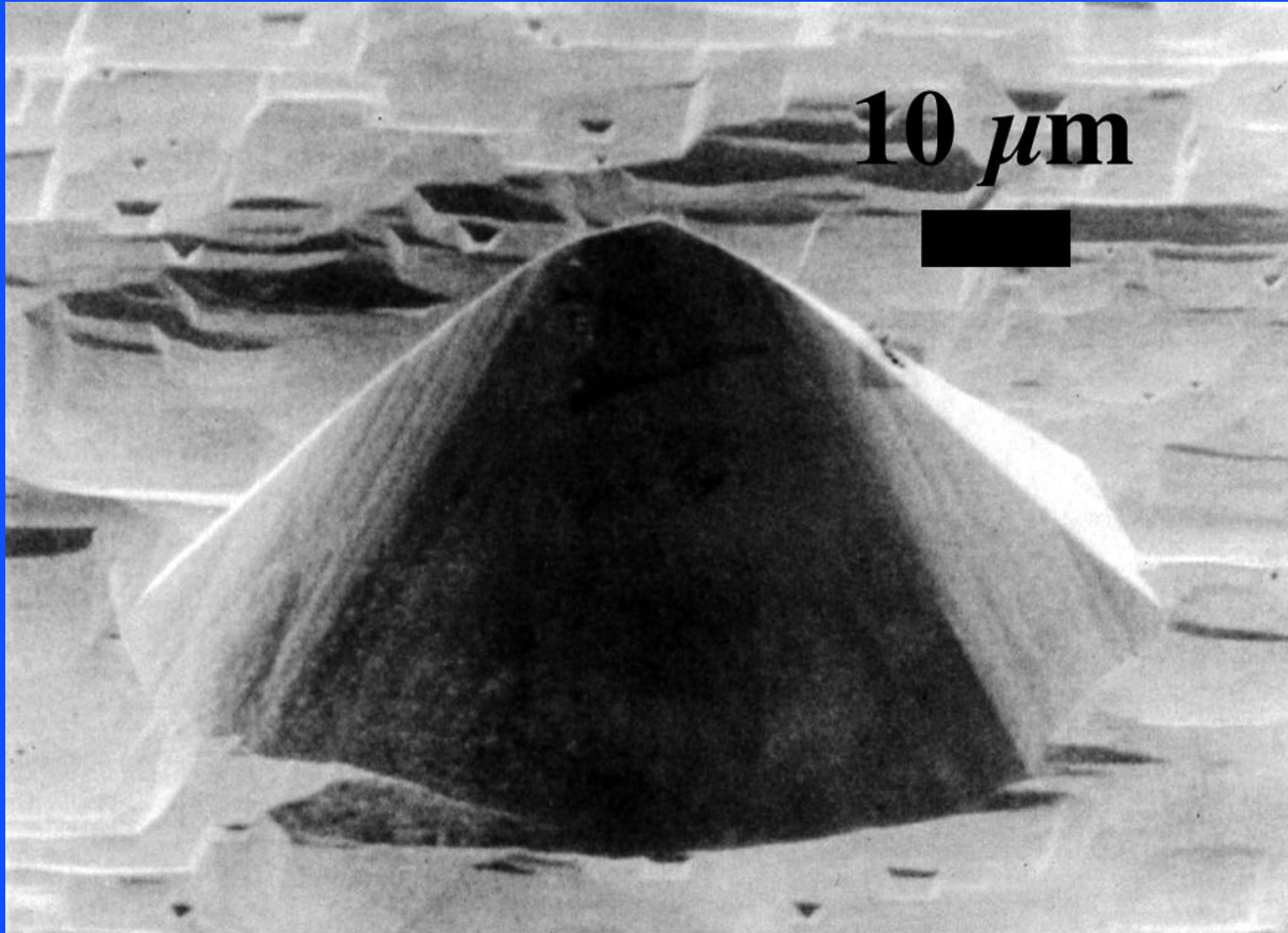


Courtesy Prof. T. Kenny, Stanford University.

G. Kovacs © 2000



# TUNNELING TIP



Courtesy Prof. T. Kenny, Stanford University.

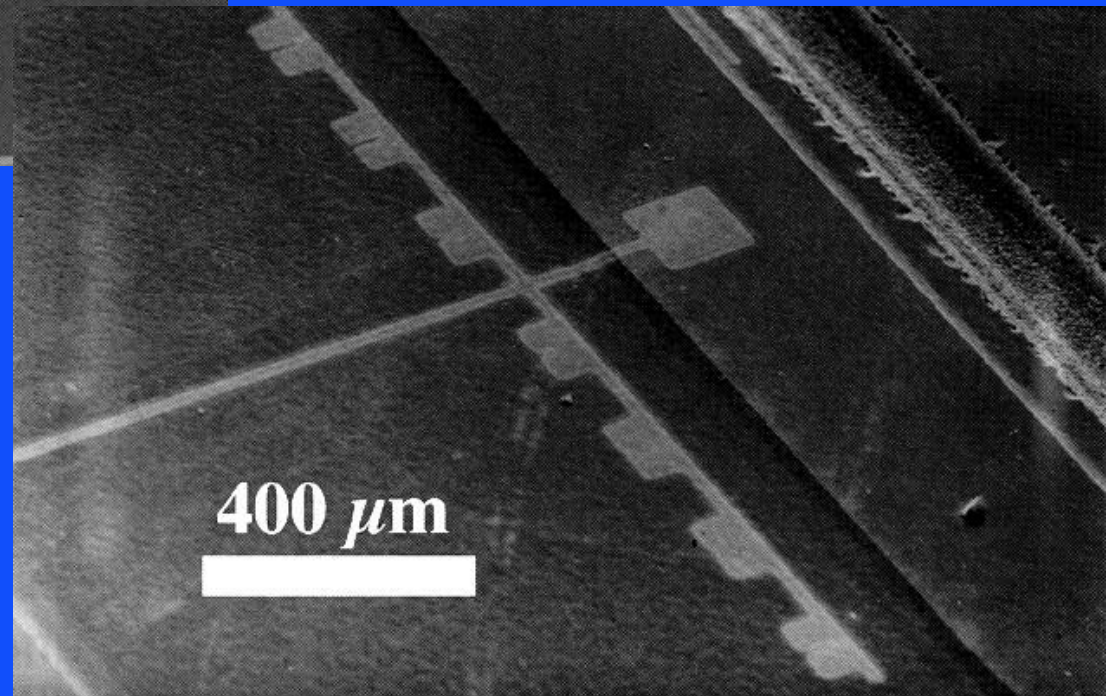
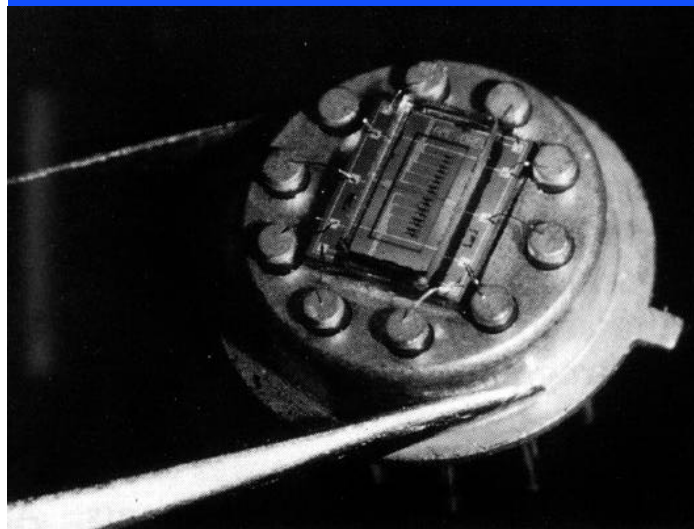
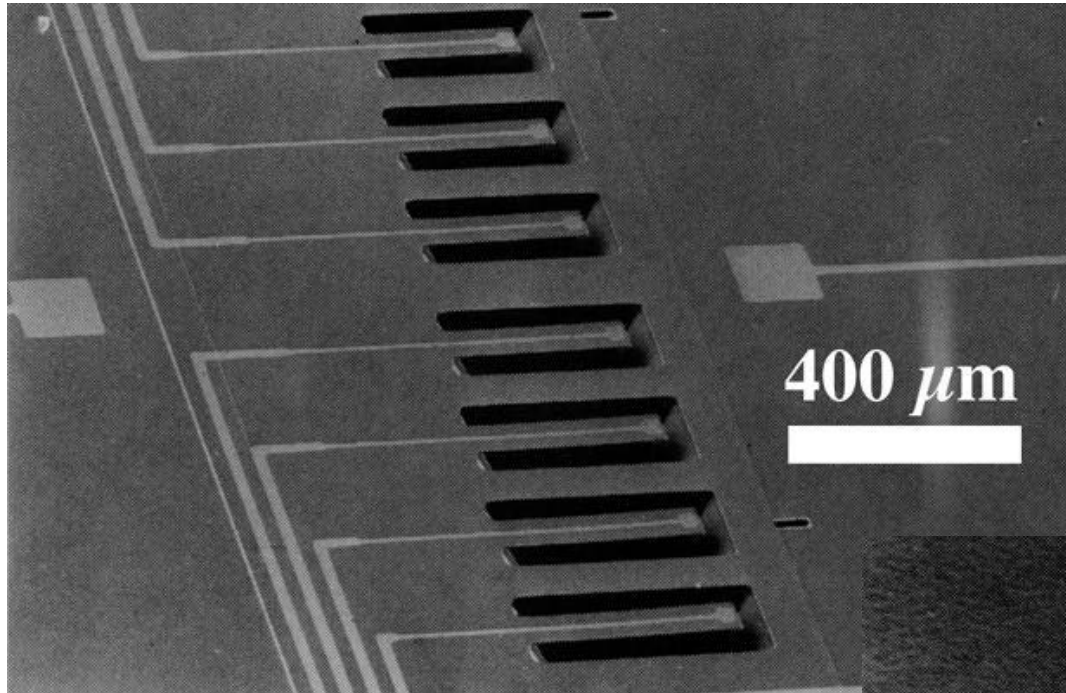
G. Kovacs © 2000

# ACCELEROMETER ARRAYS

- Can use scaled arrays of accelerometers to create a system with greatly extended dynamic range.
- In nature, this type of scaling of a particular type of transducer is often employed.
- Circuitry or other means must be able to detect which sensing element in the array is in its optimally linear range, and use its output.
- Overlapping sensor ranges ensure continuous coverage.
- Most sensitive sensors must be able to withstand “full-scale” signals.
- This concept can be applied to many other types of sensors and actuators.

# THRESHOLD ACCELEROMETER ARRAY

Source: Loke, Y., McKinnon, G. H., and Brett, M. J.,  
“Fabrication and Characterization of Silicon Micromachined  
Threshold Accelerometers,” *Sensors and Actuators*, vol. A29, no.  
3, Dec. 1991, pp. 235 - 240.

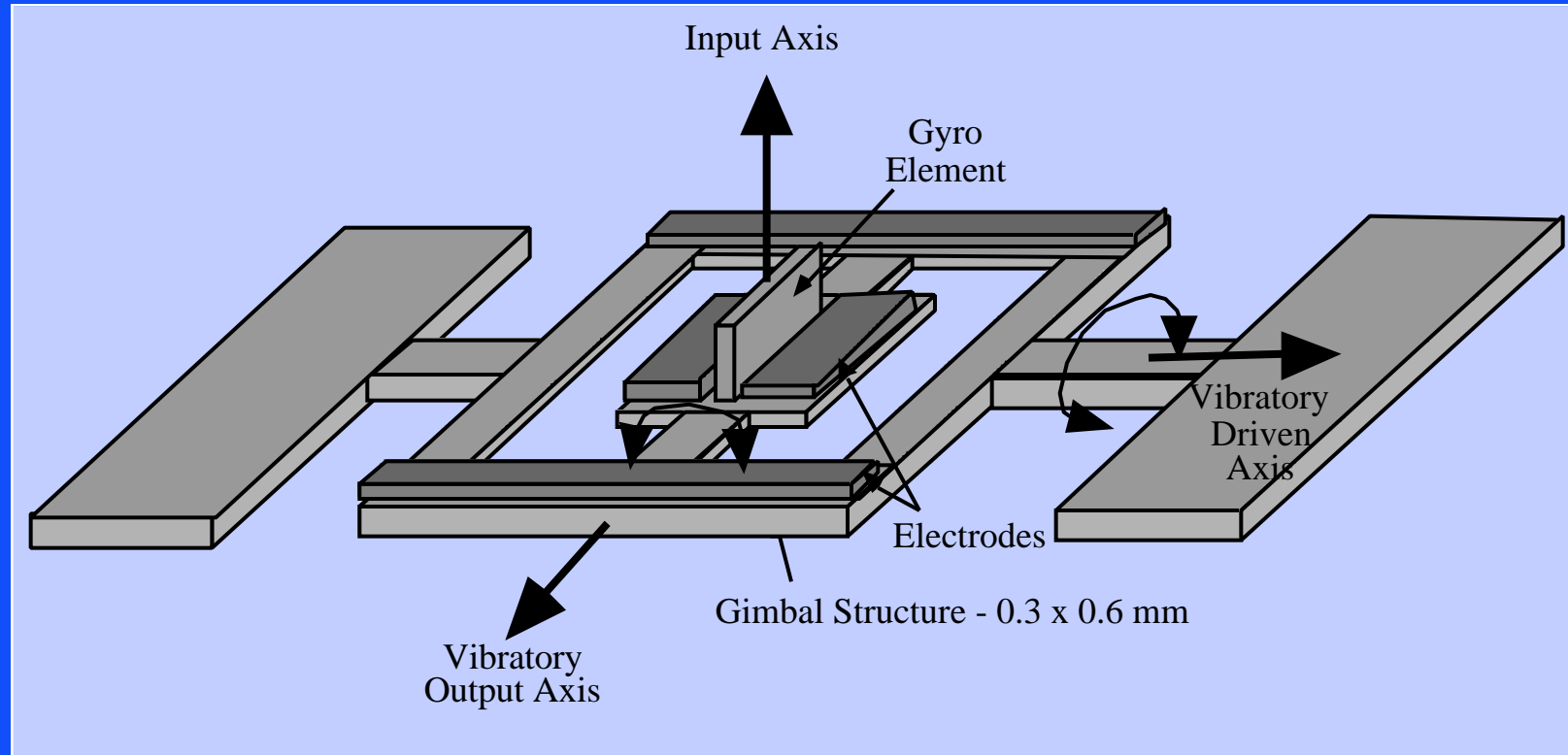


# MICROMACHINED GYROSCOPES

- It is believed that there is tremendous market potential for micromachined gyroscopes in automotive and other applications.
- There are three basic modes of gyroscope operation:
  - 1) Whole Angle Mode - allow free movement and measure angle of deflection.
  - 2) Open-Loop Vibration Mode - set up fixed vibration modes and measure the deviation (Coriolis acceleration) of these modes to determine rotation rate.
  - 3) Force-to-Rebalance Mode - set up fixed vibration modes, but operate closed loop. (as a deviation is measured it is continuously driven to zero by feedback circuitry)
- Micromachined gyroscopes are generally of the latter two types.



# MICROMACHINED FORCE-TO-REBALANCE GYRO

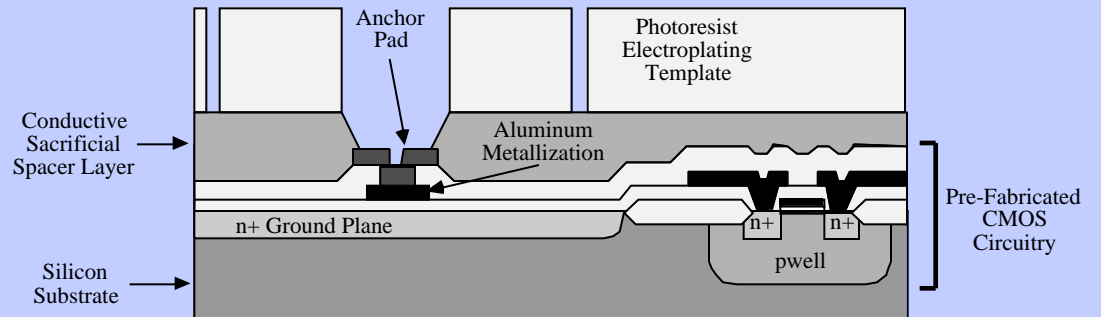
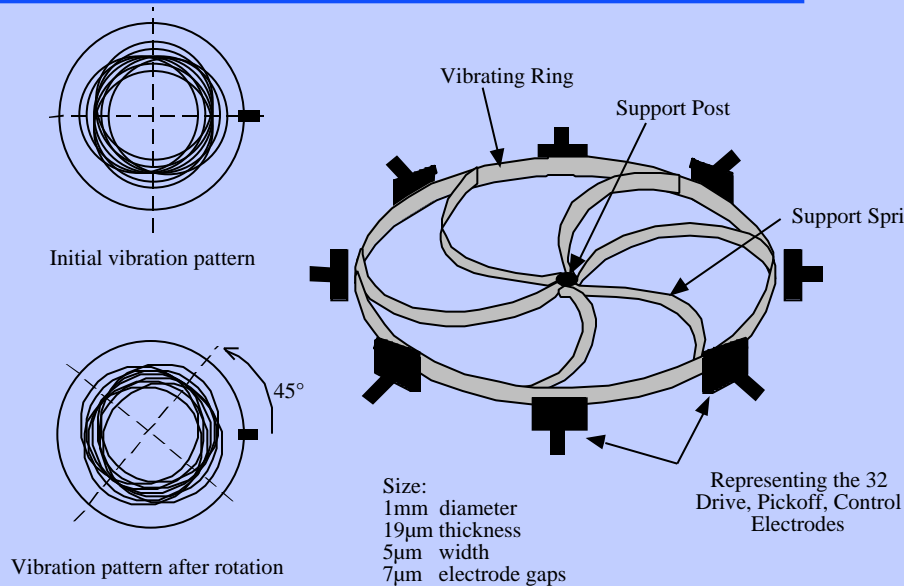


After Greiff, et al. (1991).

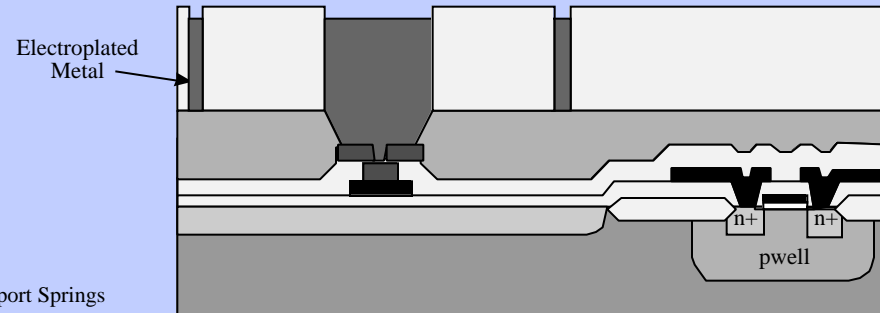
Reference: Greiff, P., Boxenhorn, B., King, T., and Niles, L., "Silicon Monolithic Micromechanical Gyroscope," Transducers '91, p. 966-968.

# MICROMACHINED RESONANT RING GYRO

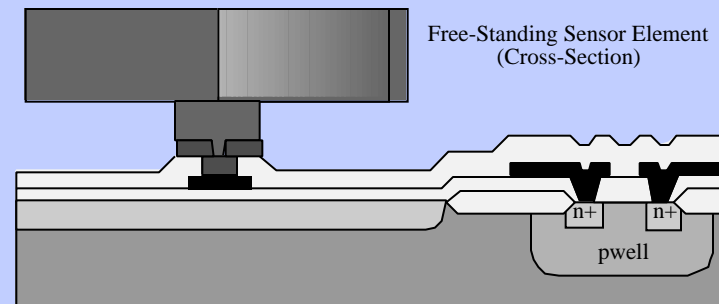
Reference: Putty, M. and Najafi, K., "A Micromachined Vibrating Ring Gyroscope," Solid State Sensor and Actuator Workshop, Hilton Head, South Carolina, June 13-16, 1994, p. 213-220.



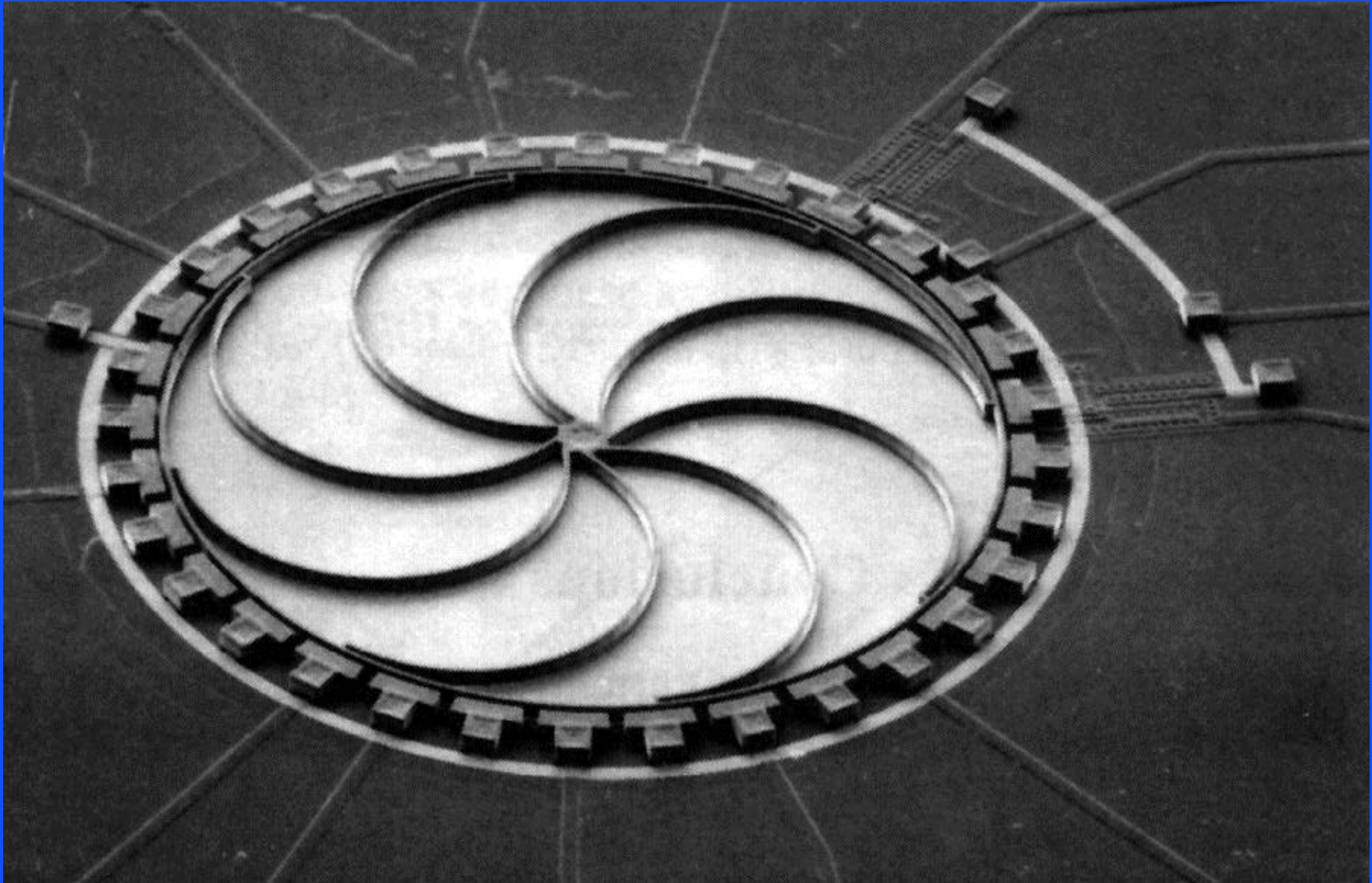
1. Electroplating template definition by UV exposure.



2. Electroplating of sensor element.



3. Template and sacrificial spacer layer removal.

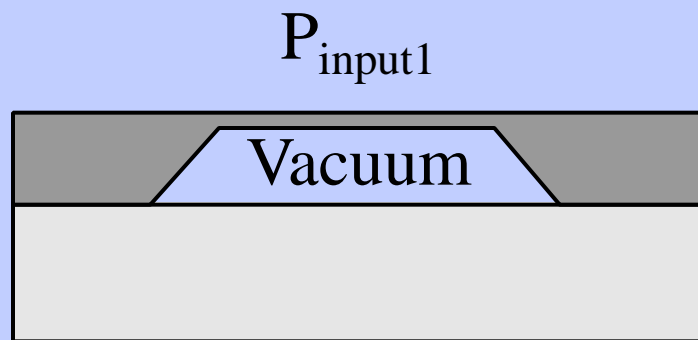


Source: Putty, M. and Najafi, K., "A Micromachined Vibrating Ring Gyroscope," Solid State Sensor and Actuator Workshop, Hilton Head, South Carolina, June 13-16, 1994, p. 213-220.

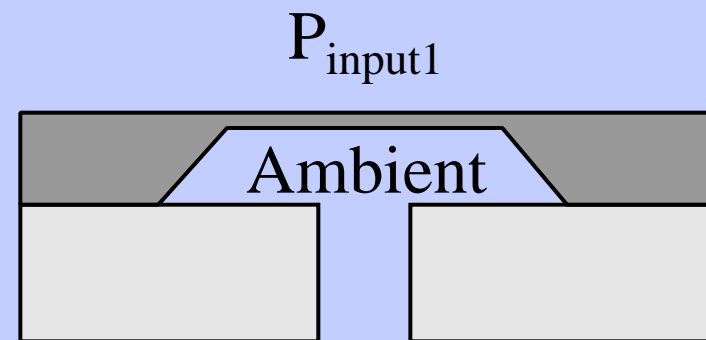
# BASIC PRESSURE SENSOR CONCEPTS

- Generally, the deflection of a membrane is used to measure pressure via displacement/strain measurements (generally piezoresistive or capacitive).
- Resonant frequency of a damped resonator can be used to measure membrane deflection (very accurately).
- Heat dissipation from a heated element can also be used (Pirani technique), generally only useful for moderate vacuum levels.
- Most shipping pressure sensors use membrane deflection methods.

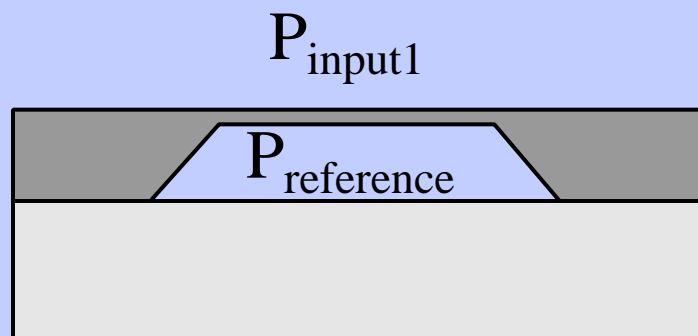




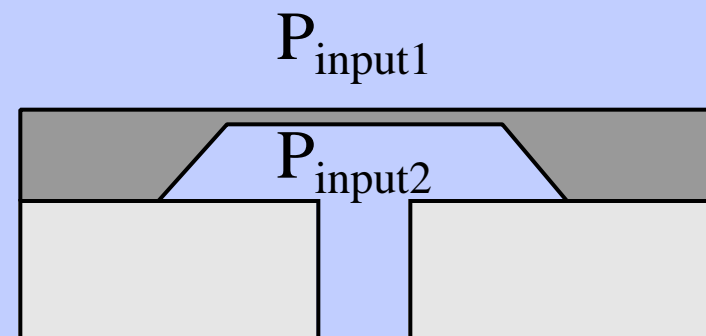
ABSOLUTE



GAGE



SEALED GAGE



DIFFERENTIAL

Reference: Bryzek, J., Petersen, K., Mallon, J. R., Christel, L., and Pourahmadi, F., "Silicon Sensors and Microstructures," Lucas NovaSensor, 1055 Mission Court, Fremont, CA, 1991.

# SAMAUN RELATIVE PRESSURE SENSOR - 1969

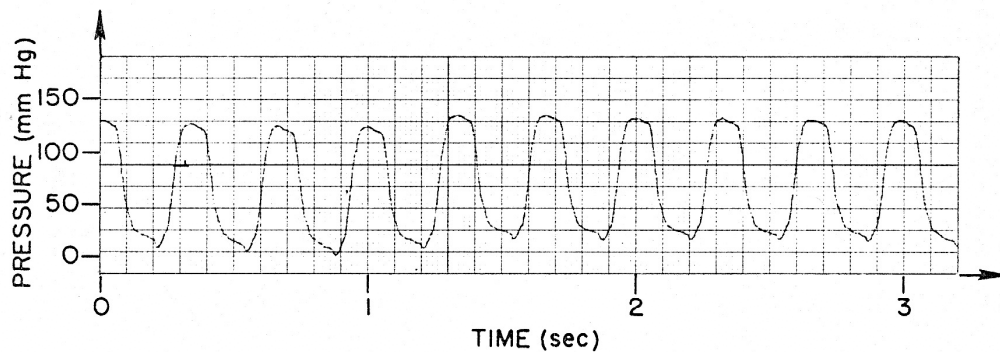
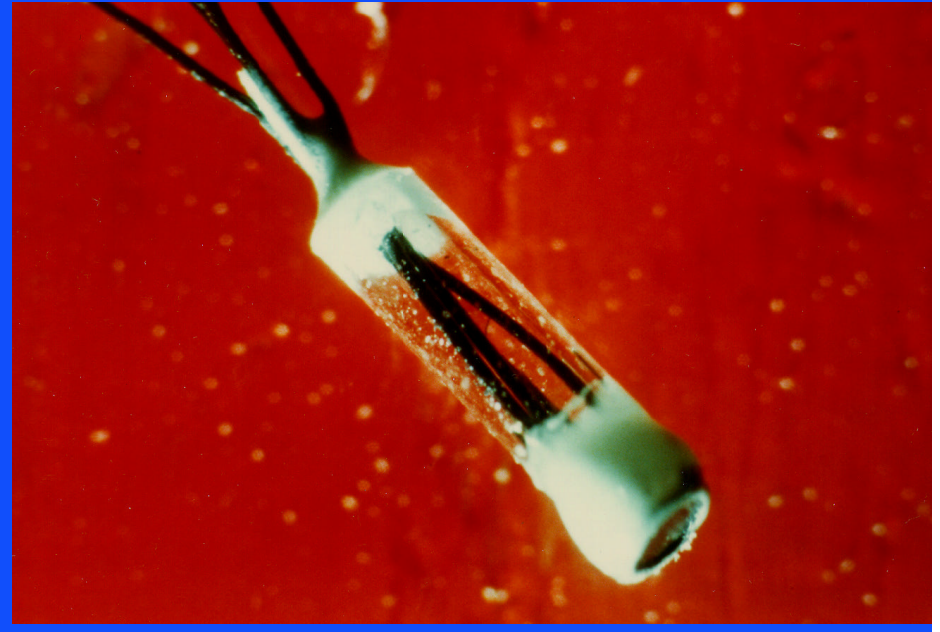
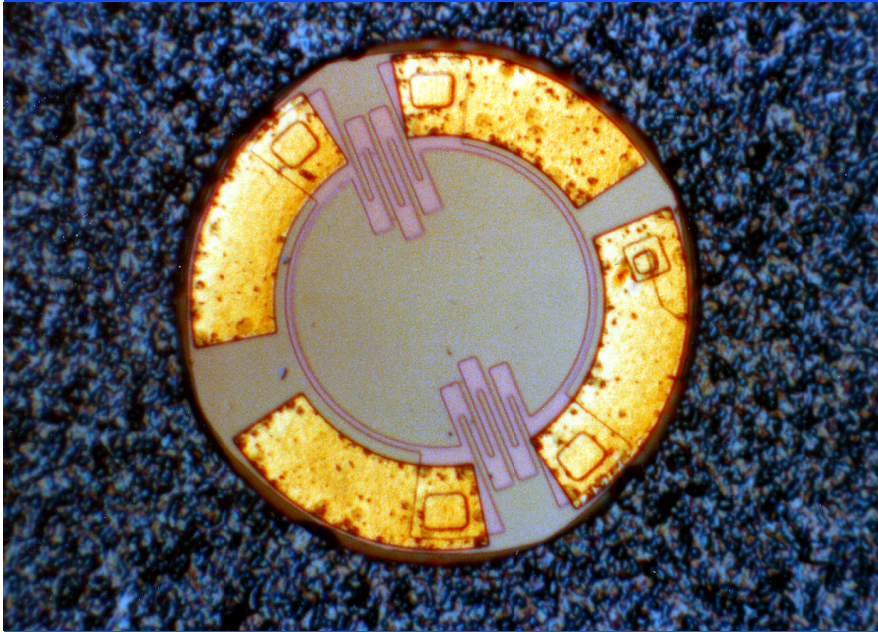
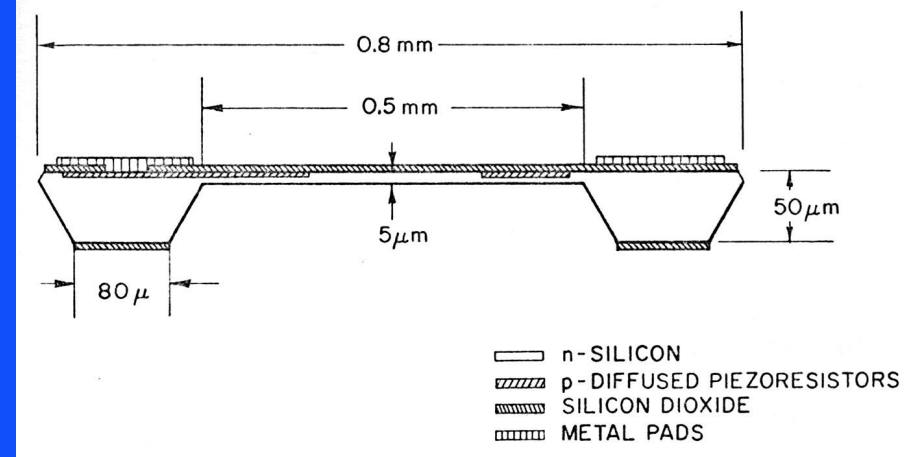


Fig. 5.2. Recording of the blood pressure in the left ventricle of a dog.

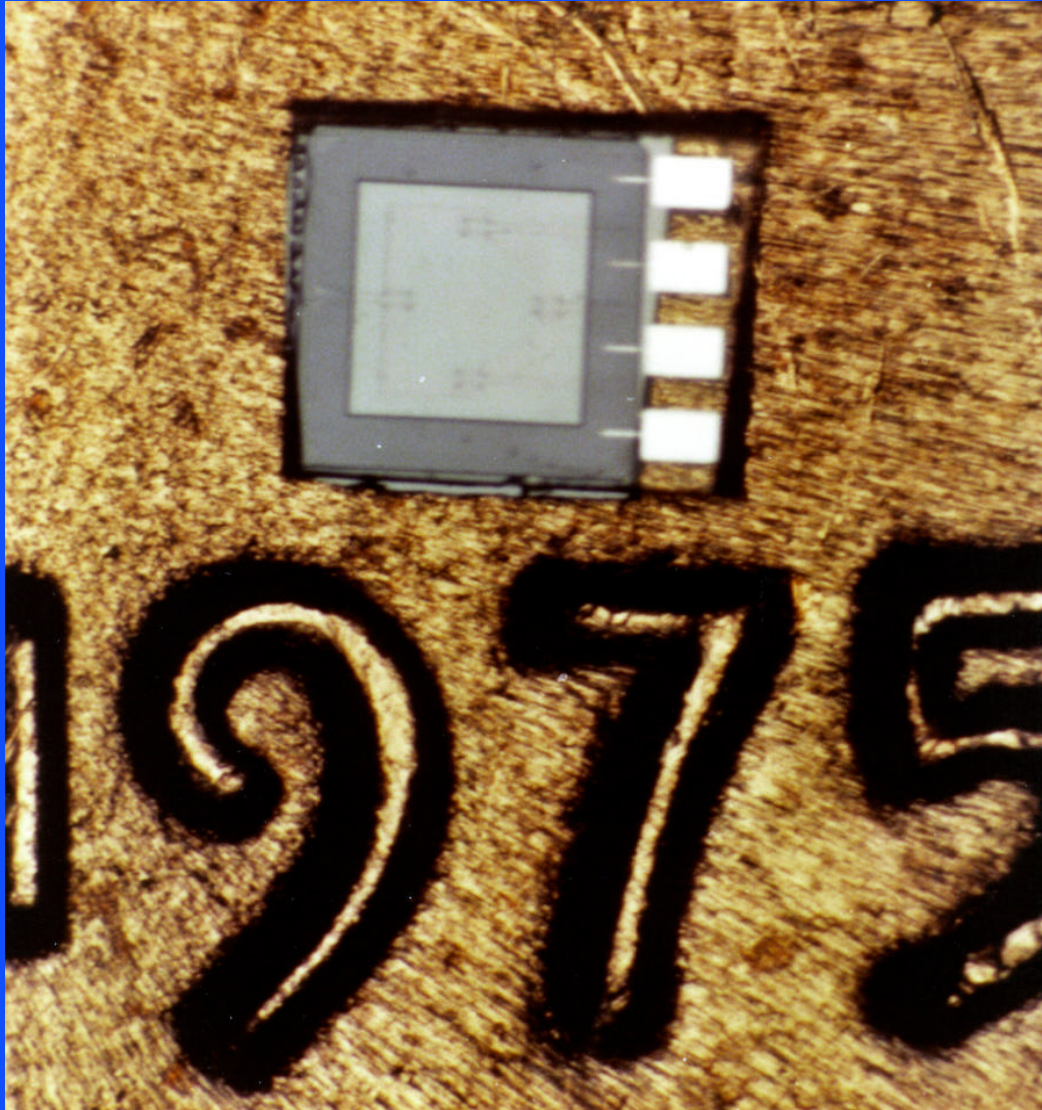


Courtesy Prof. J. Angell, Stanford University.

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# BARTH - ABSOLUTE PRESSURE SENSOR - 1974



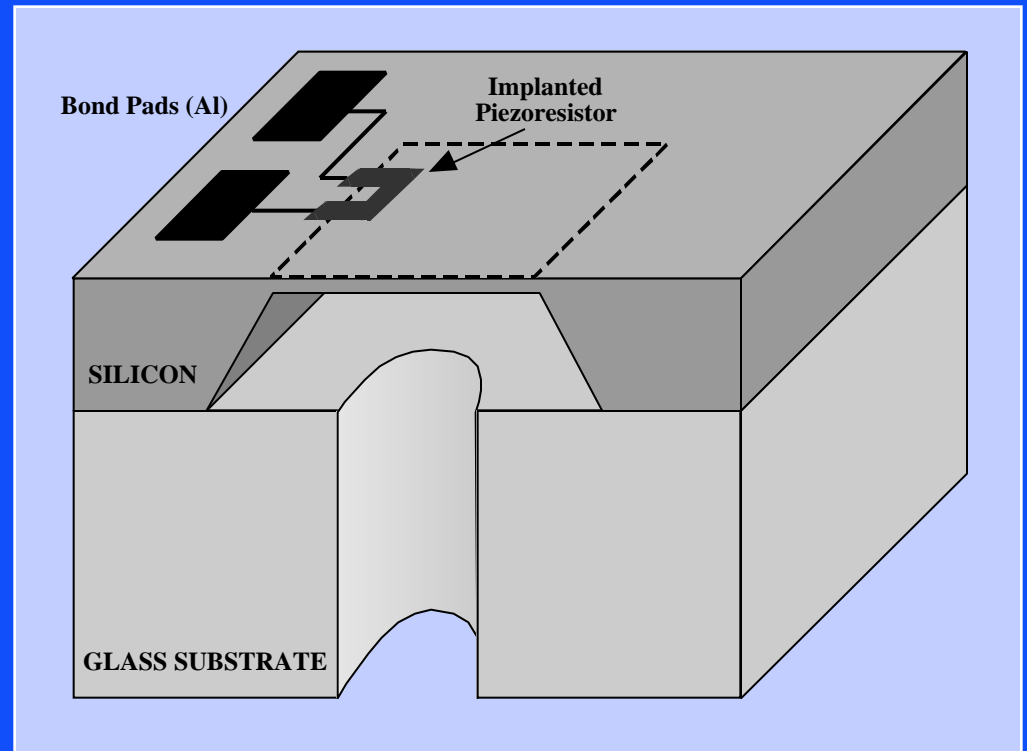
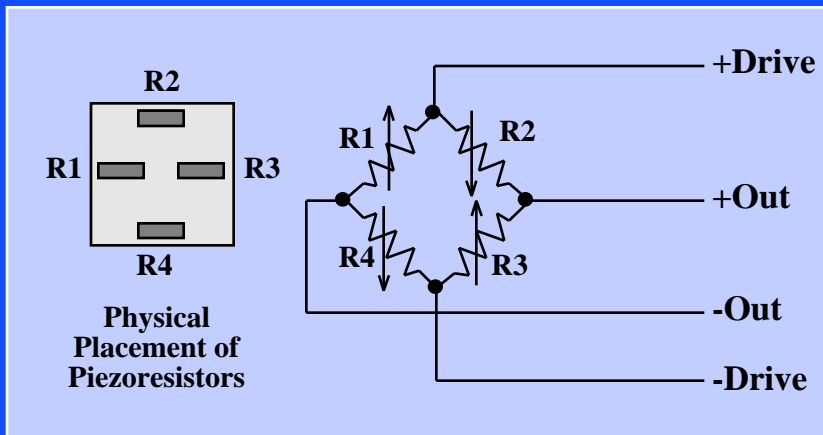
Courtesy Prof. J. Angell, Stanford University.



G. Kovacs © 2000

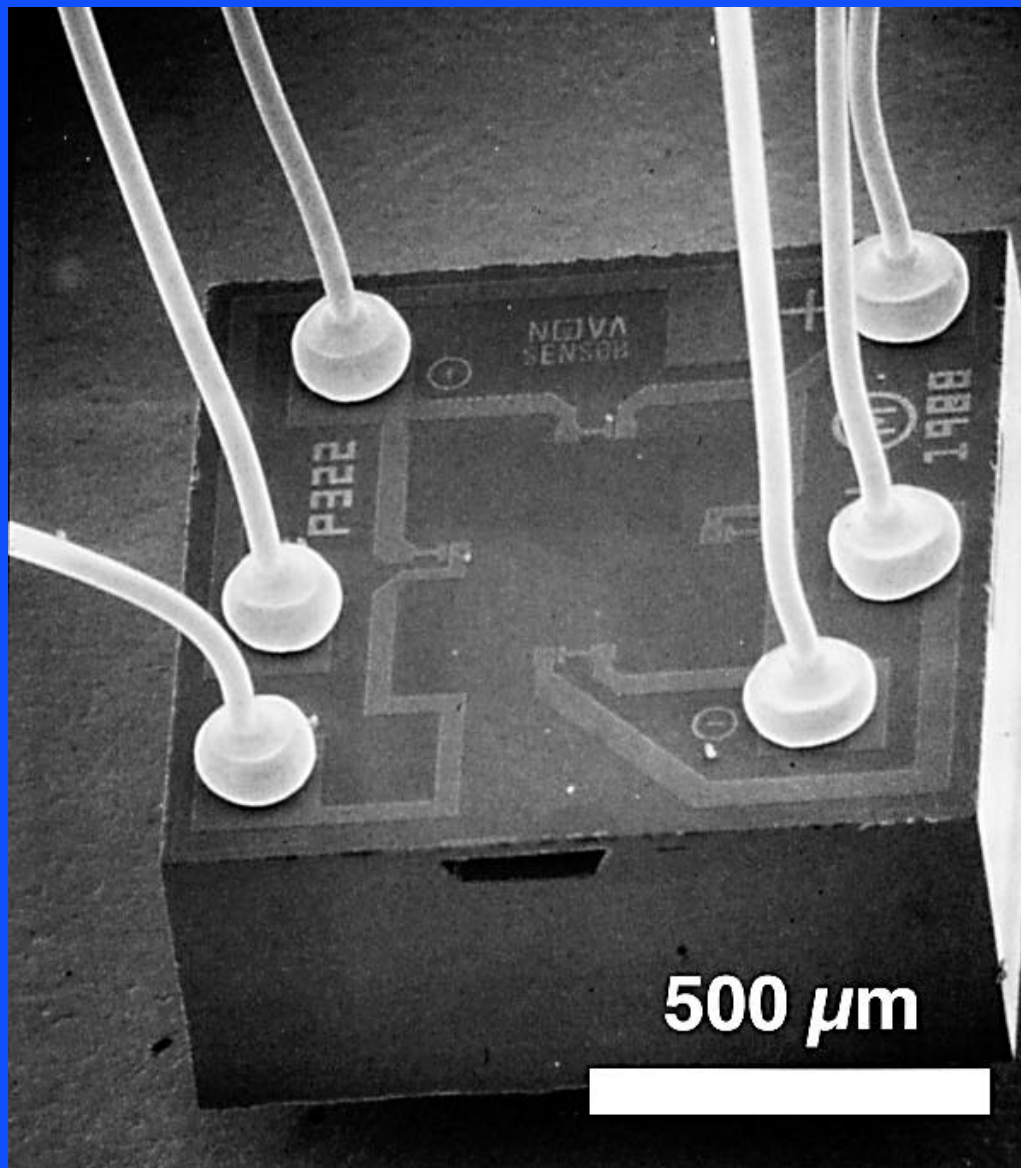
# EXAMPLE PRESSURE SENSOR (LUCAS NOVASENSOR)

- Piezoresistive strain sensors.
- Electrochemical etch stop membrane.
- Fusion bonded reference cavity or port.
- On-chip temperature compensation.

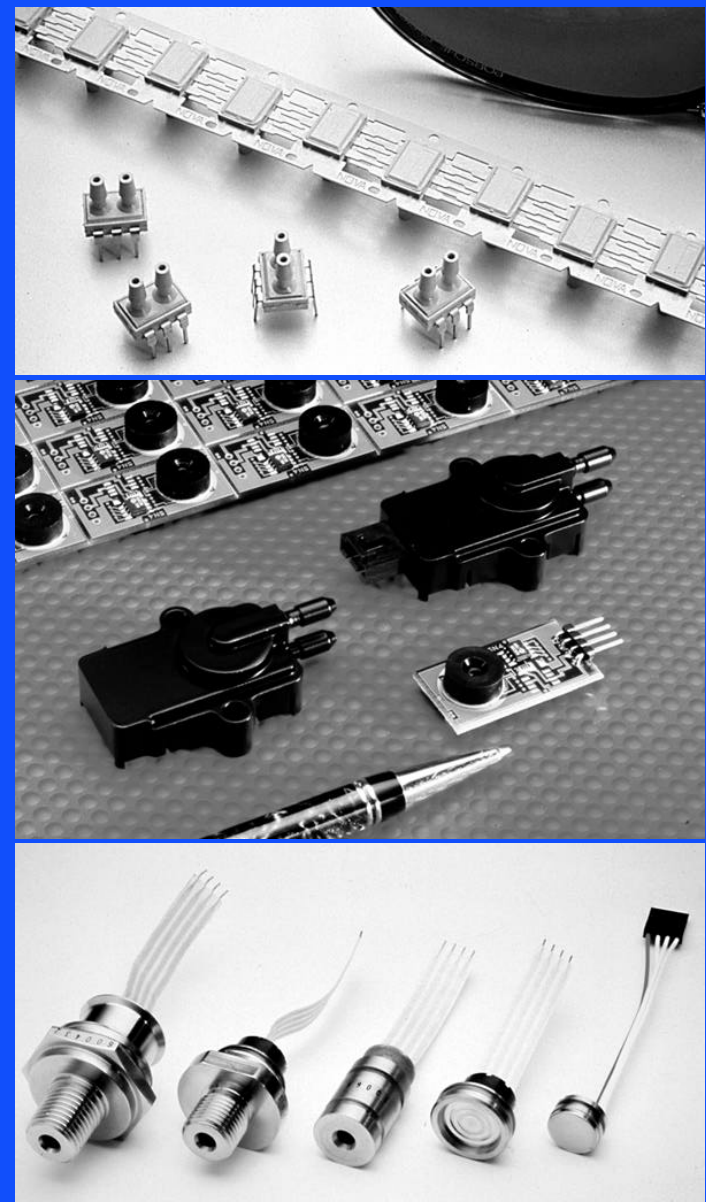


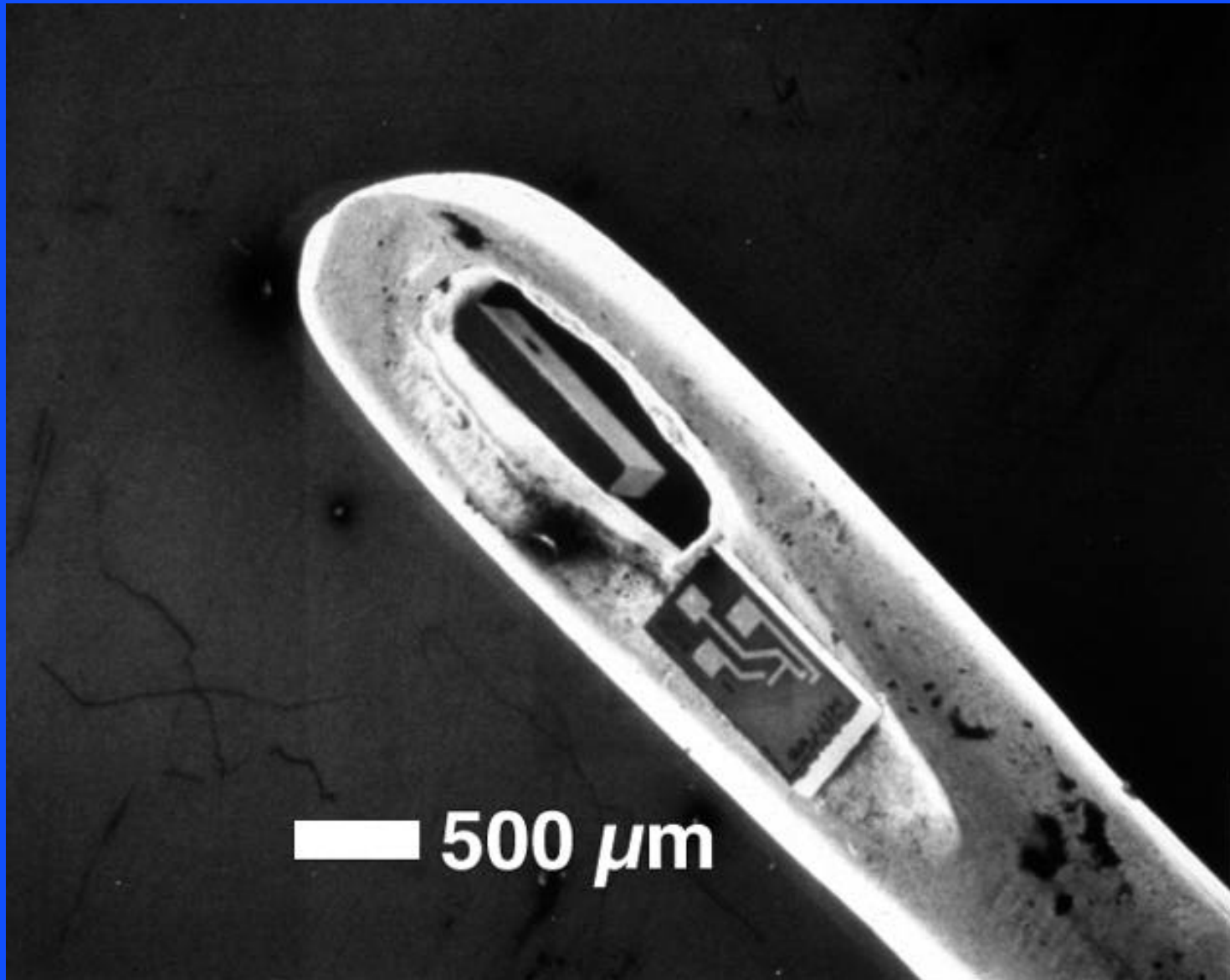
Reference: Bryzek, J., Petersen, K., Mallon, J. R., Christel, L., and Pourahmadi, F., "Silicon Sensors and Microstructures," Lucas NovaSensor, 1055 Mission Court, Fremont, CA, 1991.



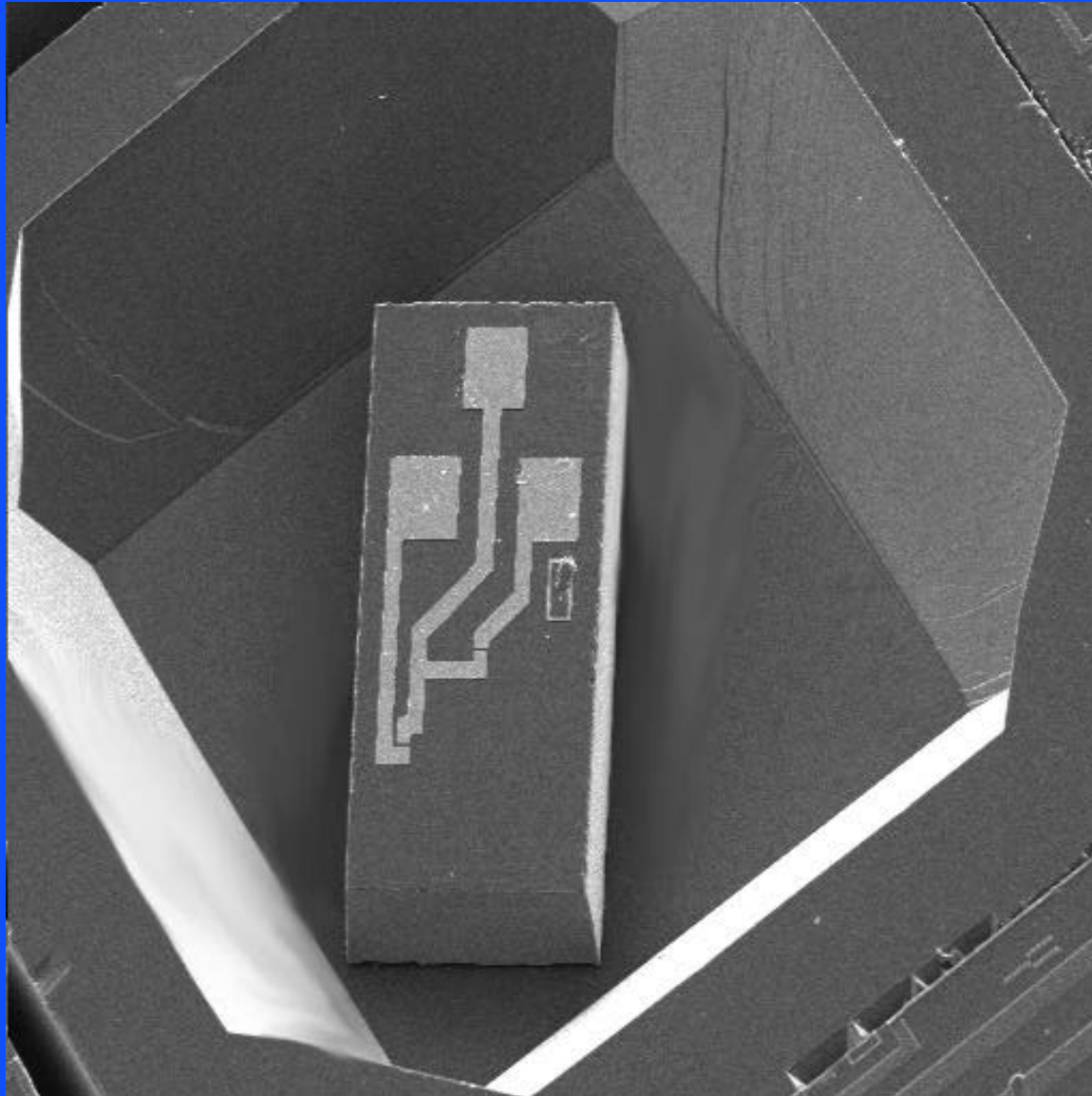


Images courtesy of Lucas NovaSensor.





Courtesy of Lucas NovaSensor.



Courtesy Prof. K. Petersen, Stanford University.

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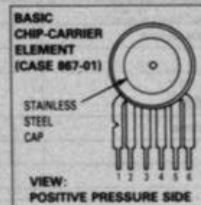
# MOTOROLA SEMICONDUCTOR TECHNICAL DATA

Order this document  
by MPX5100/D

## Advance Information

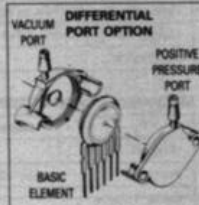
### On-Chip Signal Conditioned, 0.5 V to 4.5 V Output, Temperature Compensated & Calibrated, 0 to 15 PSI Silicon Pressure Sensors

- Ideally Suited for Microprocessor Based Systems
- Temperature Compensated Over 0°C to +85°C
- Patented Silicon Shear Stress Strain Gage
- 0 to 15 PSI (0 to 100 kPa) Differential Pressure Range
- Full Scale Output Calibrated: 0.5 V to 4.5 V
- Easy to use Chip Carrier Package
- Basic Element, Single and Dual Ported Devices Available
- Customized Output Available (Consult Factory)
- Available in Absolute, Differential & Gage Configurations



## MPX5100 SERIES

0-15 PSI  
X-ducer™  
SILICON  
PRESSURE SENSORS



Pin Number					
1	2	3	4	5	6
V <sub>out</sub>	Ground	V <sub>source</sub>	N/C	N/C	N/C

NOTE: Pins 4, 5 and 6 are internal device connections. Do not connect to external circuitry or ground.

#### MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Overpressure	P <sub>max</sub>	700	kPa
Burst Pressure	P <sub>BURST</sub>	1000	kPa
Supply Voltage (See Note 11, Page 2)	V <sub>S(max)</sub>	10	V <sub>dc</sub>
Storage Temperature	T <sub>stg</sub>	-50 to +150	°C
Operating Temperature	T <sub>A</sub>	0 to +85	°C

The MPX5100 Series piezoresistive transducer is a state-of-the-art, monolithic silicon pressure sensor designed for a wide range of applications, but particularly those employing a microcontroller or microprocessor with A/D inputs. This patented, single element X-ducer combines advanced micromachining techniques, thin film metallization and bipolar semiconductor processing to provide an accurate, high level analog output signal that is proportional to applied pressure.

Figure 1 shows a schematic of the internal circuitry integrated on-chip to provide temperature compensation, offset and span calibration and signal conditioning.

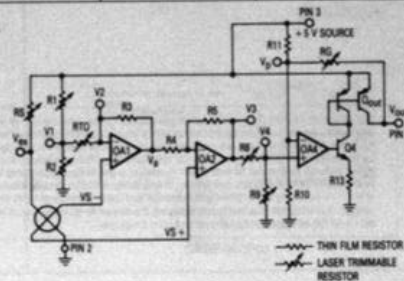


Figure 1. Fully Integrated Pressure Sensor Schematic

X-ducer is a trademark of Motorola Inc.

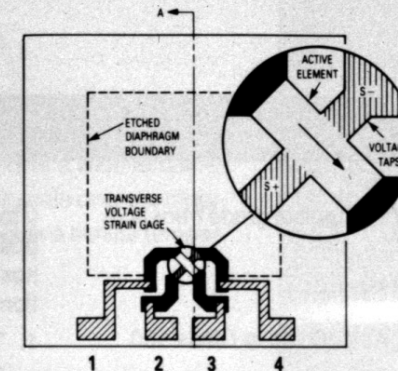
This document contains information on a new product. Specifications and information herein are subject to change without notice.



MOTOROLA

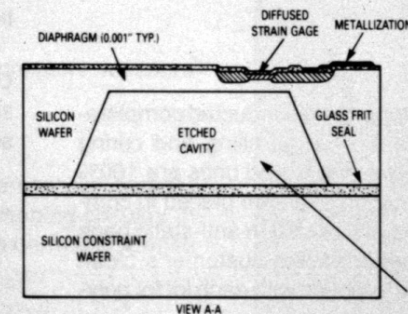
Rev. 1  
(Replaces AD1799)

©MOTOROLA INC., 1991

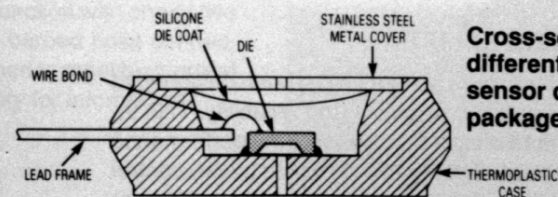


- PIN #
1. GROUND
  2. POSITIVE OUTPUT
  3. SUPPLY
  4. NEGATIVE OUTPUT

Figure 4.  
Basic Uncompensated  
Sensor Element —  
Top View



Cross-sectional  
diagram of  
an absolute  
sensor chip

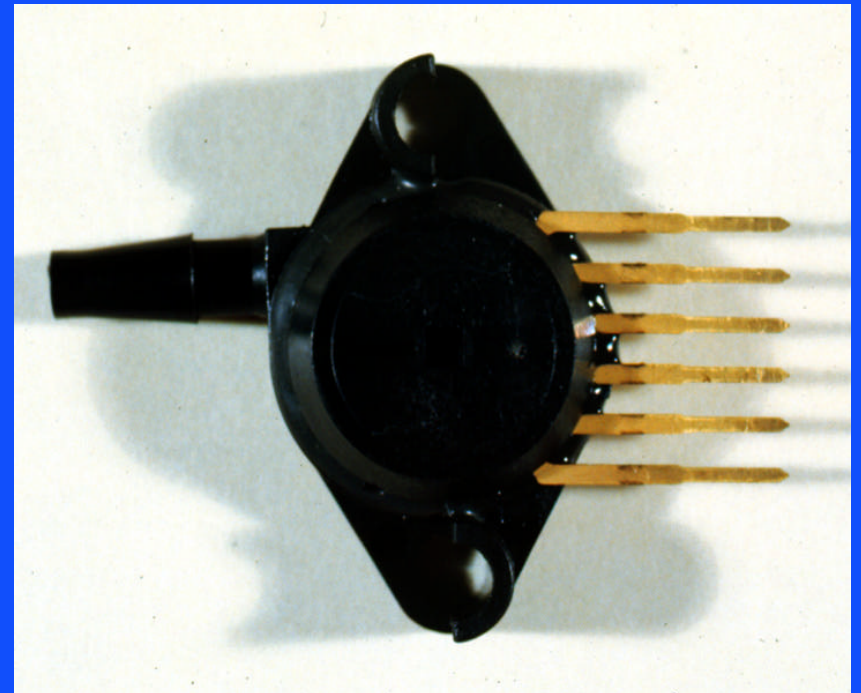
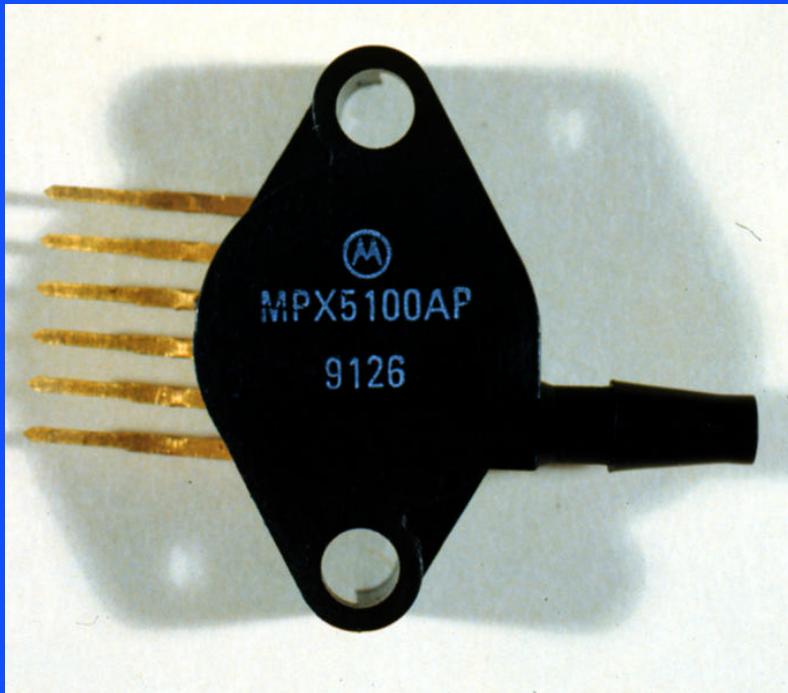


Cross-section of  
differential pressure  
sensor die in its basic  
package

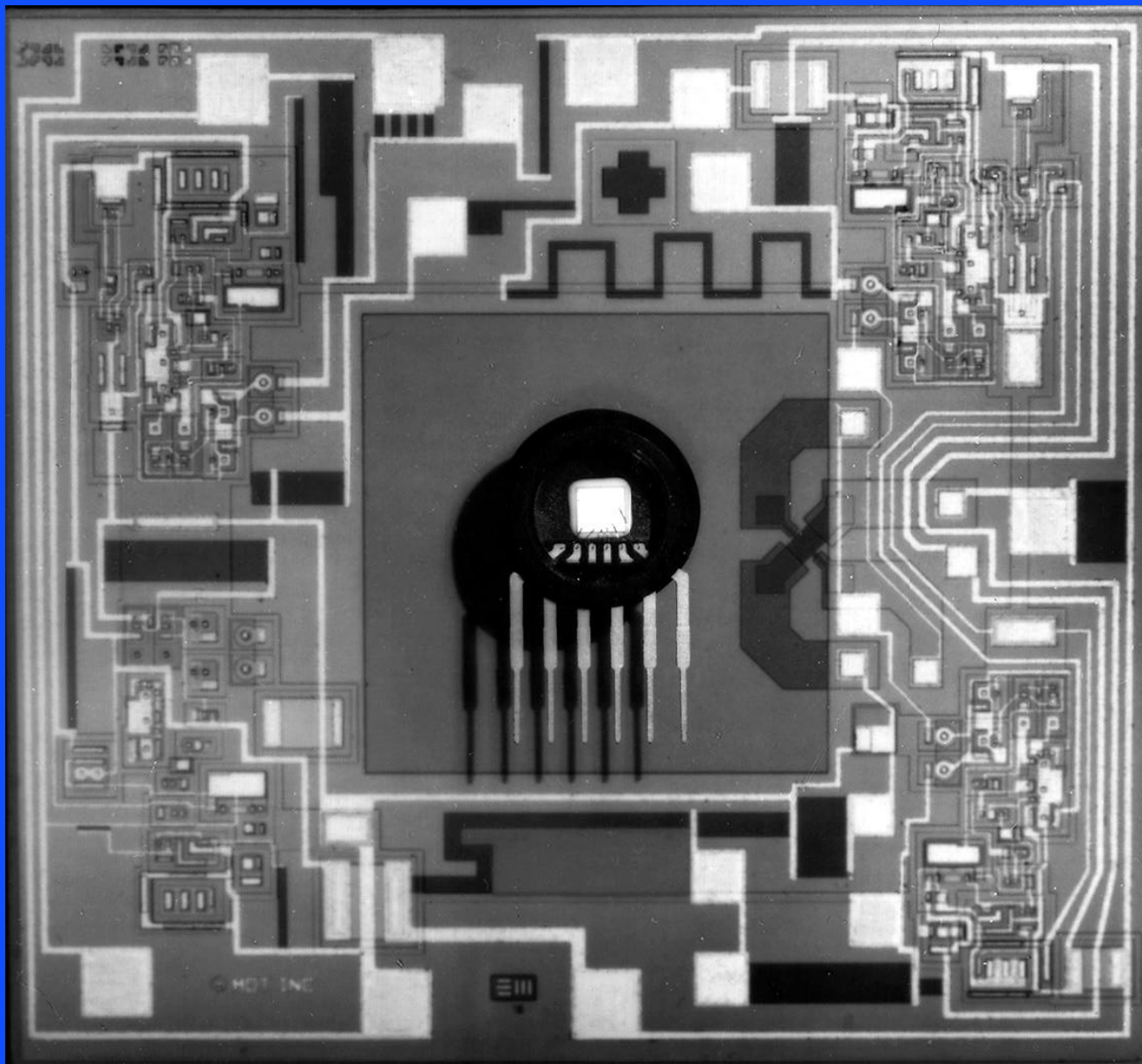
Figure 5. Cross-Sectional Diagrams

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# MOTOROLA PRESSURE SENSOR PACKAGING



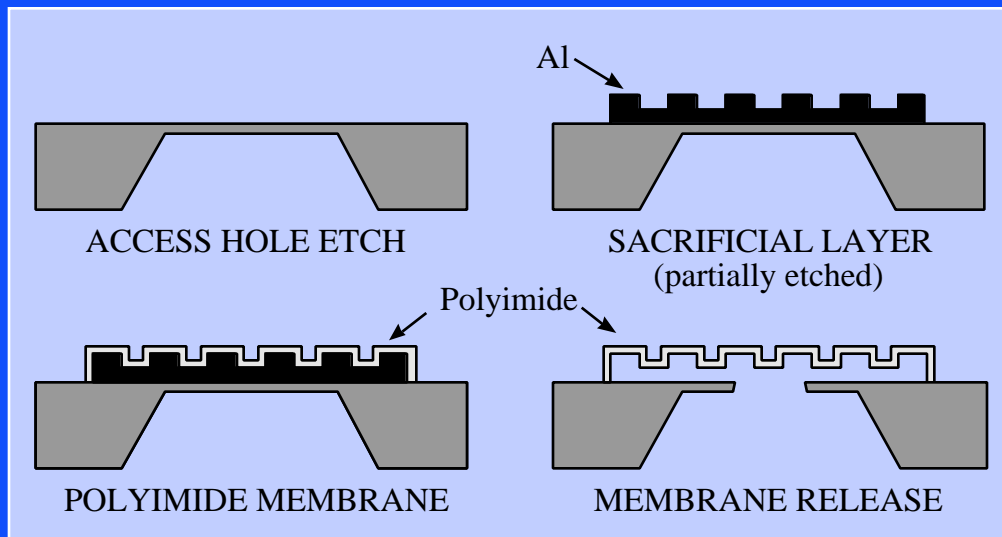




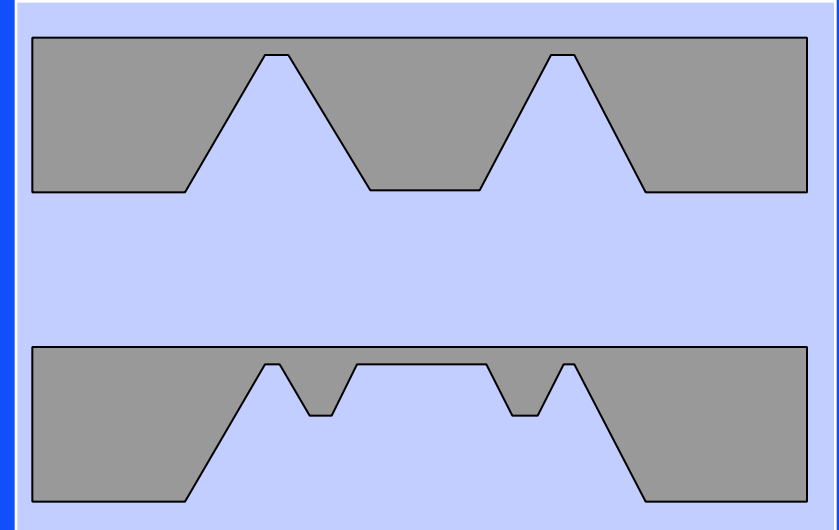
Courtesy Dr. Lj. Ristic, Motorola, Inc.

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# CORRUGATIONS AND BOSSES

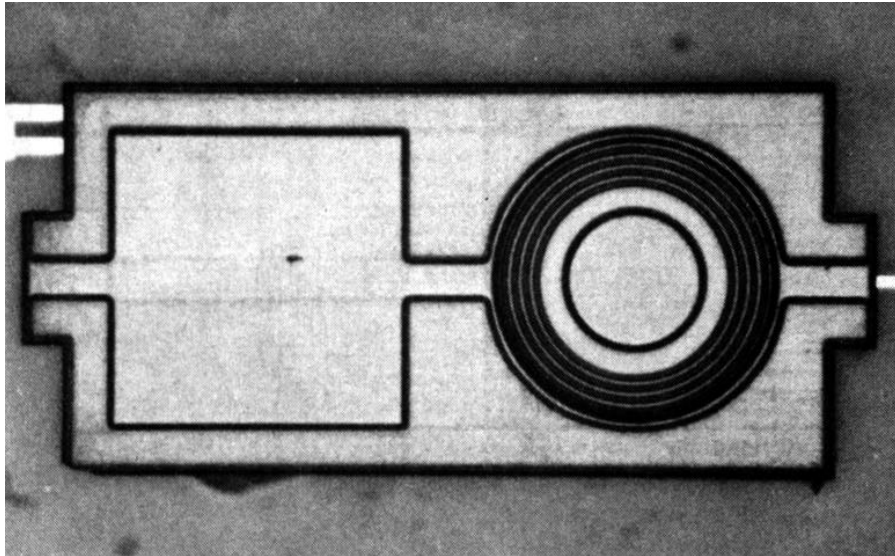


Reference: van Mullem, C. J., Gabriel, K. J., and Fujita, H., "Large Deflection Performance of Surface Micromachined Corrugated Diaphragms," Proceedings of the International Conference on Solid-State Sensors and Actuators, Transducers '91, San Francisco, CA, June 24 - 27, 1991, pp. 1014 - 1017.

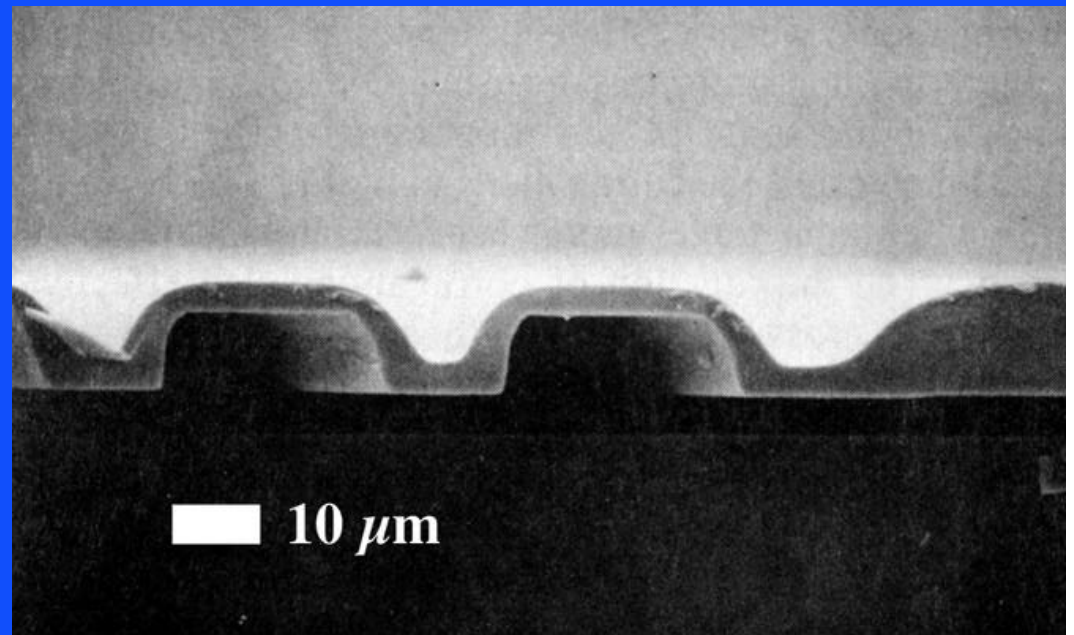


Reference: Bryzek, J., Petersen, K., Mallon, J. R., Christel, L., and Pourahmadi, F., "Silicon Sensors and Microstructures," Lucas NovaSensor, 1055 Mission Court, Fremont, CA, 1991.

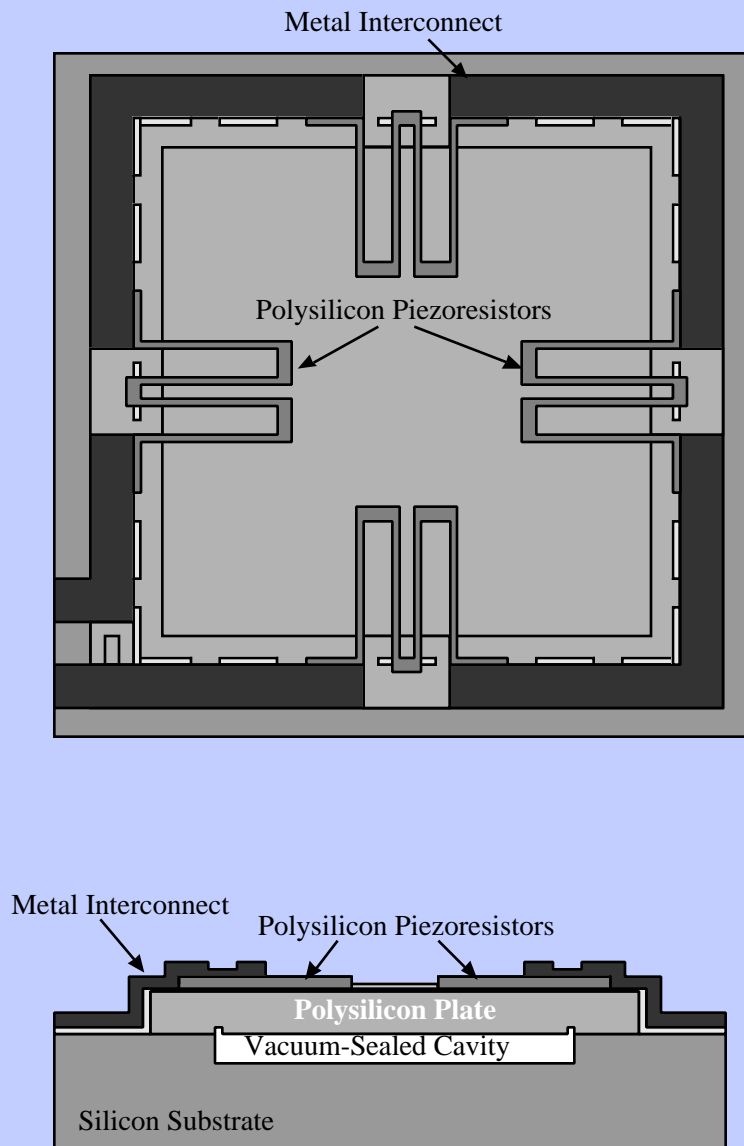




Source: Wise Laboratory, University of Michigan.

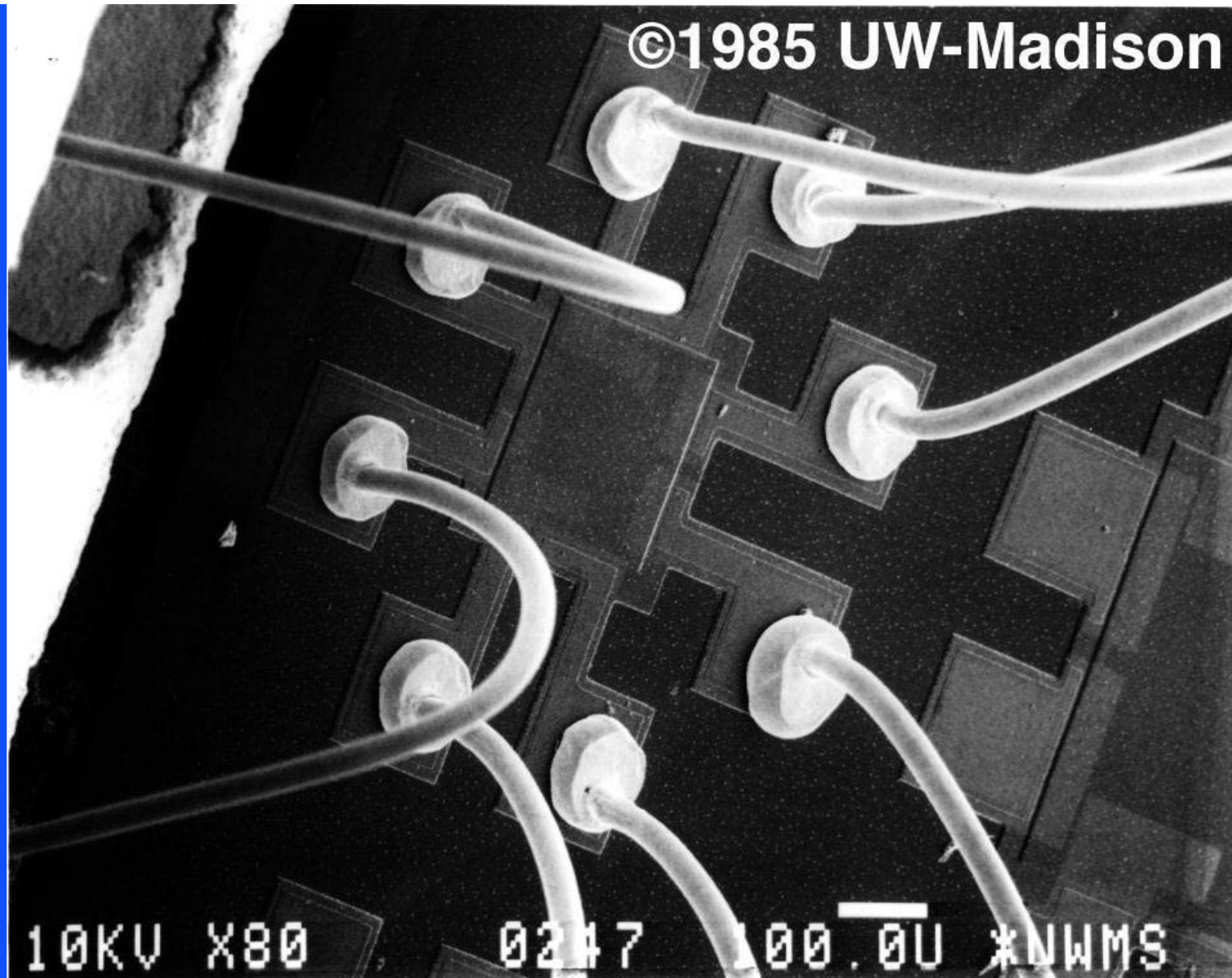


# SURFACE MICROMACHINED PRESSURE SENSORS



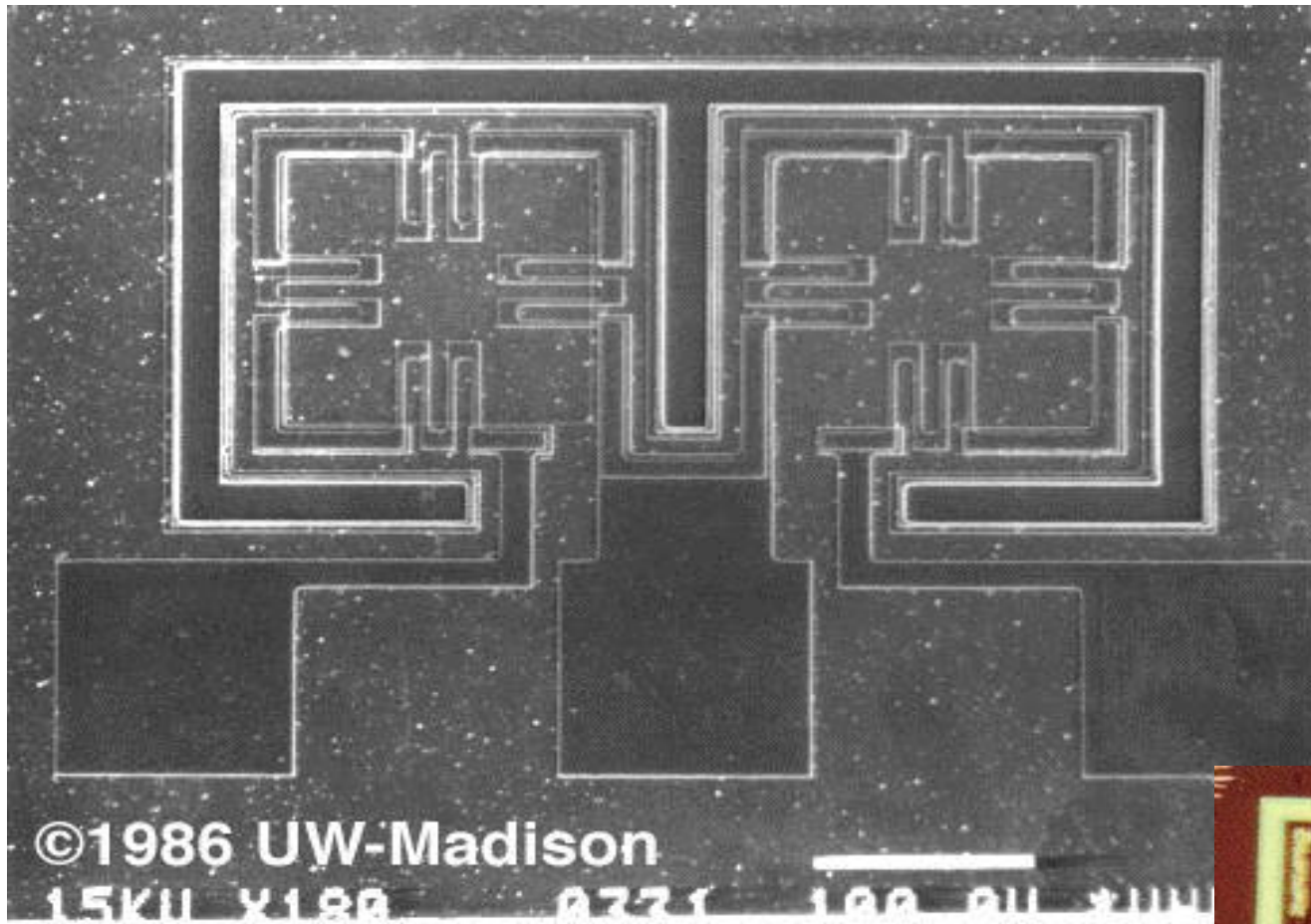
- To obtain “flush” pressure sensors, oxide was thermally grown in cavity regions ( $\approx 2.3$  X less dense than silicon), stripped, and grown again.
- The re-grown oxide was flush with the surface, providing the sacrificial layer.
- Silicon nitride films were used above a polysilicon plate to sandwich implanted polysilicon strain gauges.

Reference: Guckel, H., “Surface Micromachined Pressure Transducers,” *Sensors and Actuators A*, vol. 28, 1991, pp. 133 - 146.



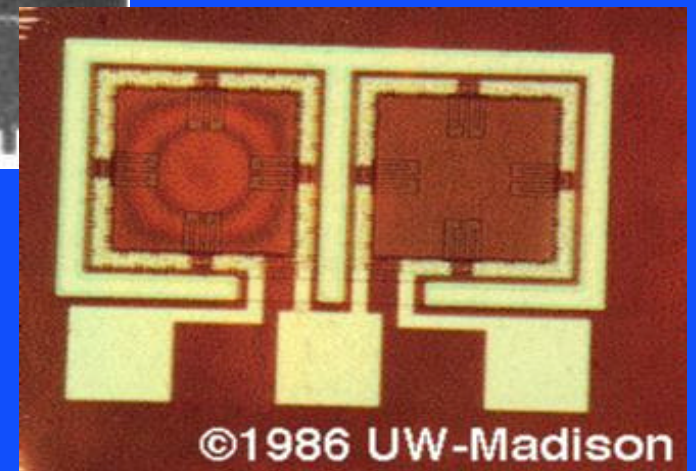
Courtesy of Prof. Henry Guckel <http://mems.engr.wisc.edu/images/>

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Courtesy of Prof. Henry Guckel

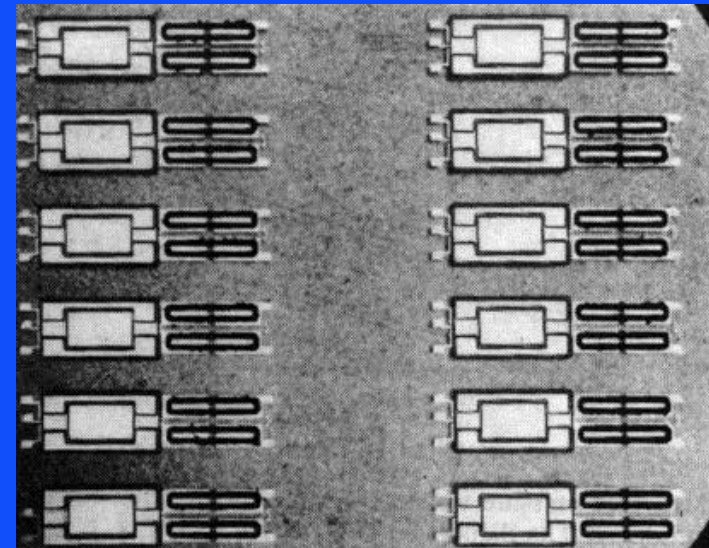
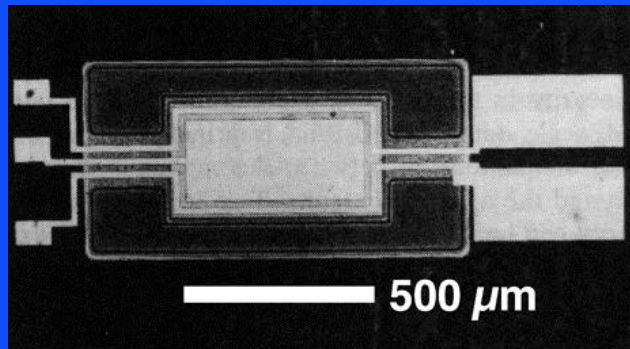
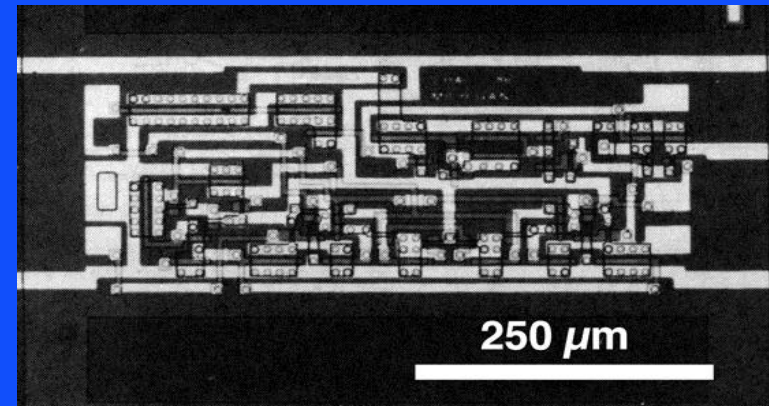
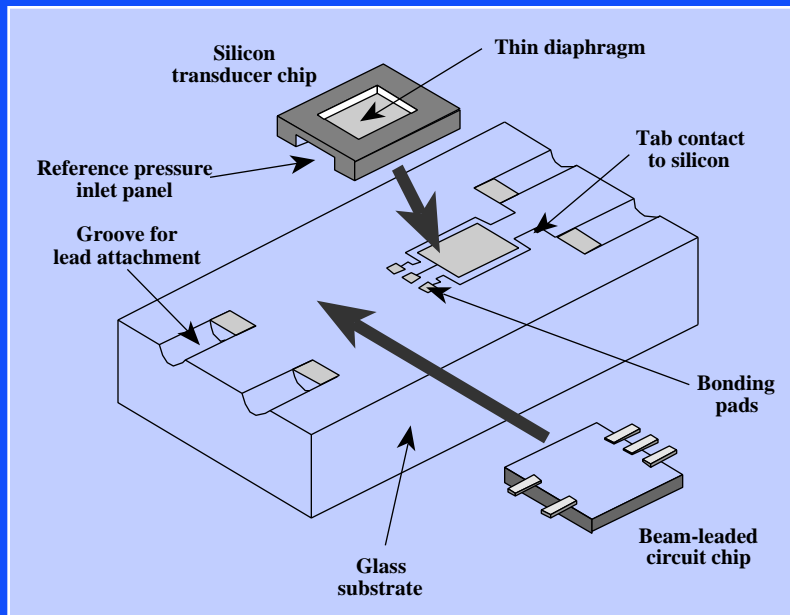
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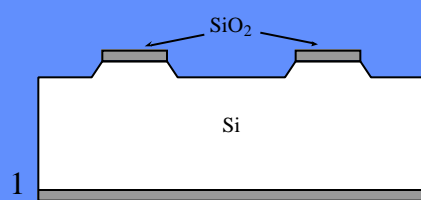
G. Kovacs © 2000



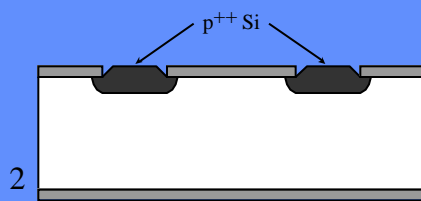
# CATHETER-TIP PRESSURE SENSOR



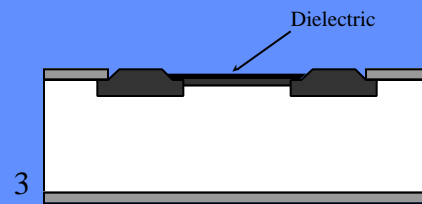
Source: Chau, H.-L. and Wise, K. D., "An Ultraminiature Solid-State Pressure Sensor for a Cardiovascular Catheter," IEEE Transactions on Electron Devices, vol. 35, no. 12, Dec. 1988, pp. 2355 - 2362.



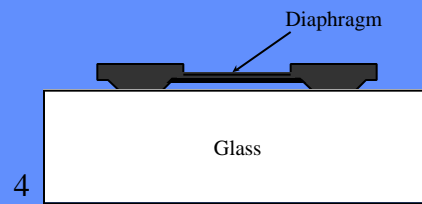
KOH etch.



Long boron diffusion.

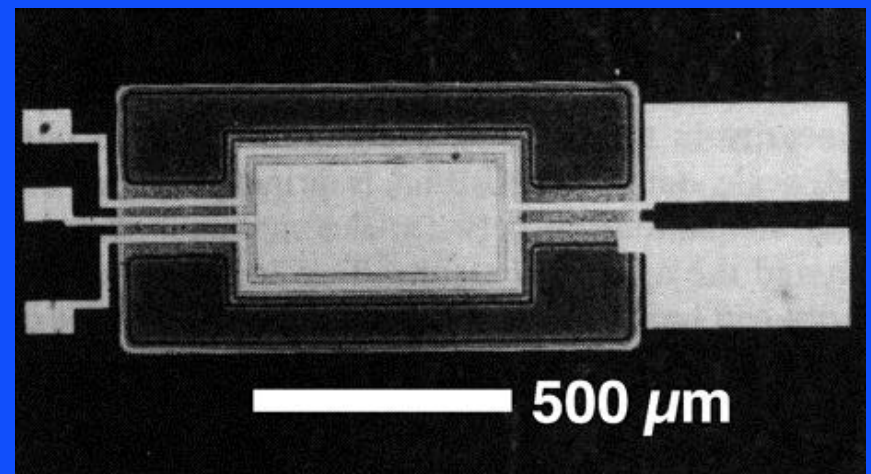


Short boron diffusion and dielectric layer deposition.

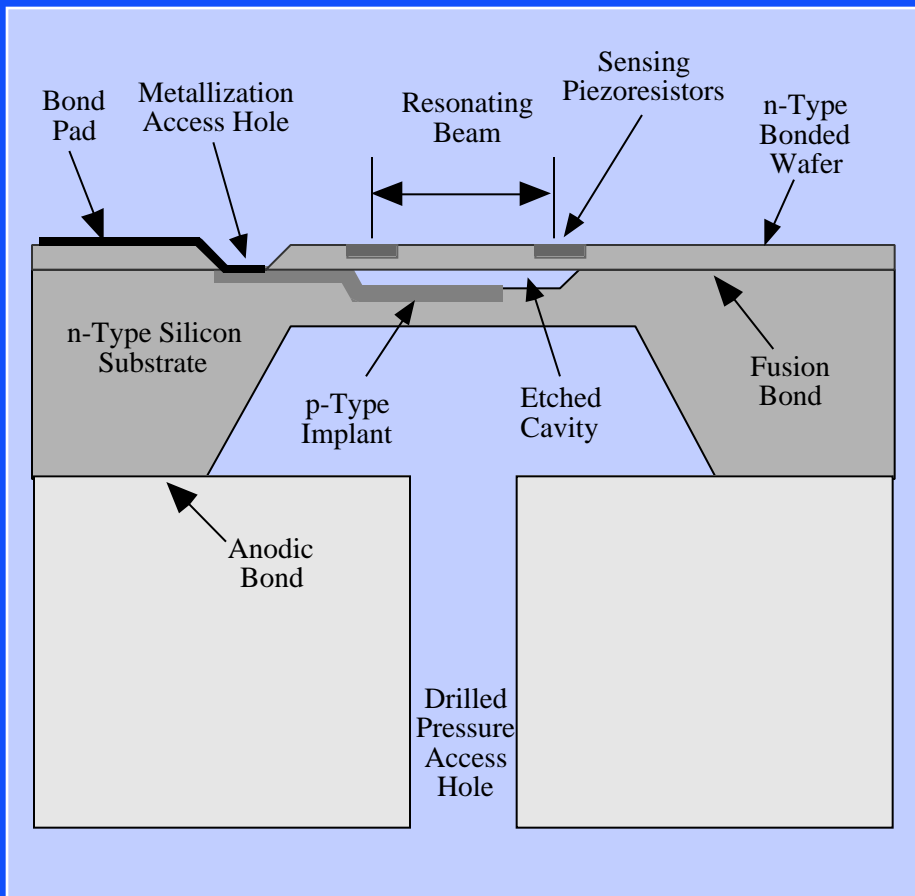


Oxide removal, anodic bonding to glass and EDP etch.

Chau, H.-L. and Wise, K. D., "An Ultraminiature Solid-State Pressure Sensor for a Cardiovascular Catheter," IEEE Transactions on Electron Devices, vol. 35, no. 12, Dec. 1988, pp. 2355 - 2362.



# RESONANT PRESSURE SENSORS



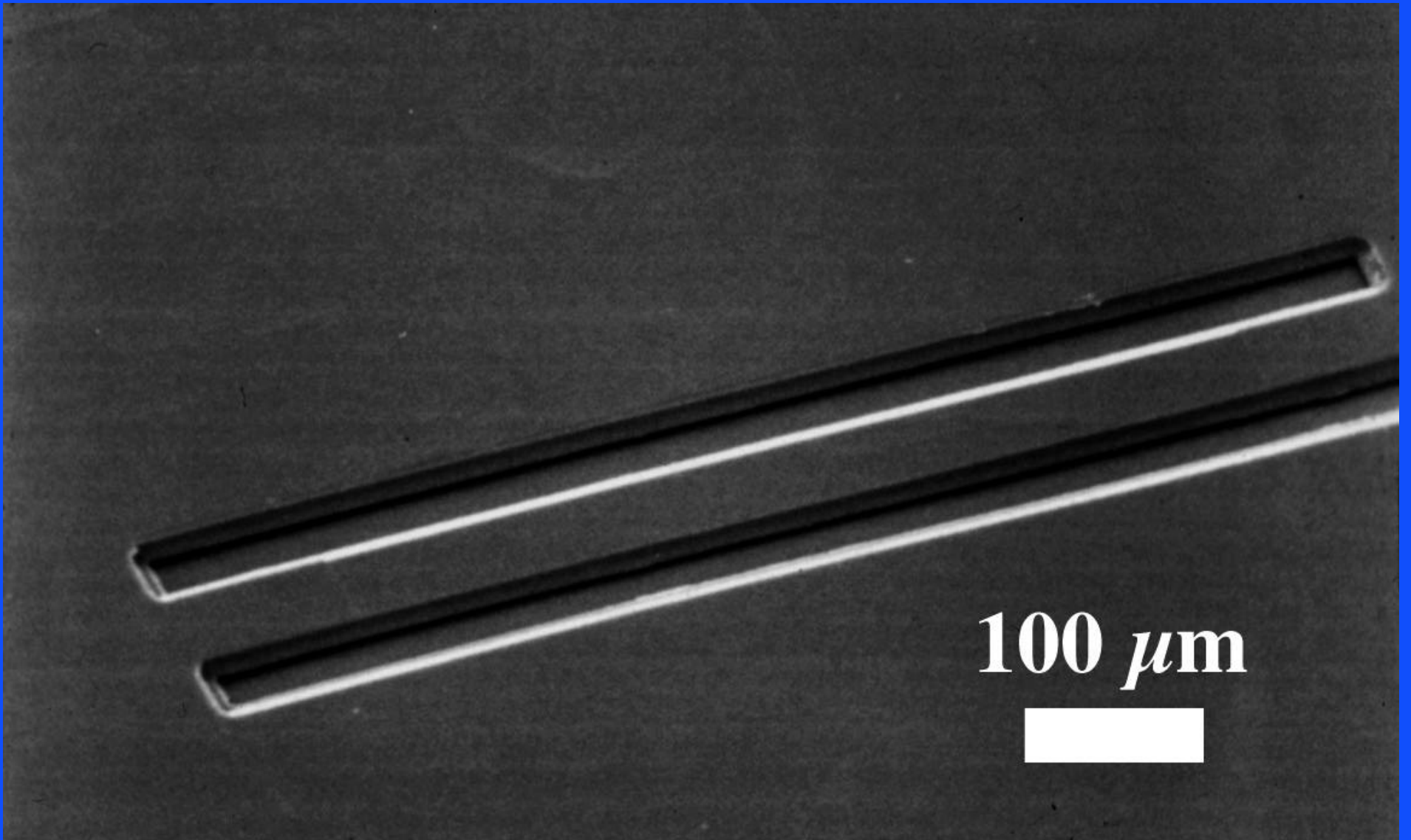
- **Beam excited electrostatically and sensed piezoresistively.**

## Process:

- 1) etch shallow pit in an n-type substrate
- 2) diffuse p-type deflection electrode
- 3) fusion bond second n-type wafer over the surface
- 4) grind and polish top wafer down to 6  $\mu\text{m}$
- 5) form a passivation layer on the top wafer
- 6) implant sensing piezoresistors
- 7) etch contact holes (to allow metallization in step 8 to contact the underlying deflection electrode)
- 8) deposit and pattern interconnect and bond-pad metal
- 9) etch diaphragm into the underlying wafer
- 10) etch two slots next to the beam to release it over the buried cavity

Reference: Petersen, K., et al. "Resonant Beam Pressure Sensor Fabricated With Silicon Fusion Bonding," Proceedings of Transducers '91, June 24 - 27, 1991, San Francisco, CA, pp. 177 - 180.



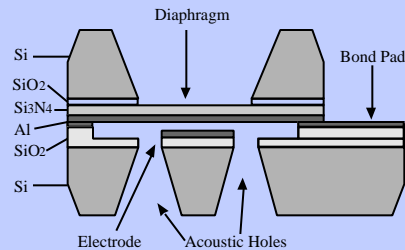


Courtesy Lucas NovaSensor.

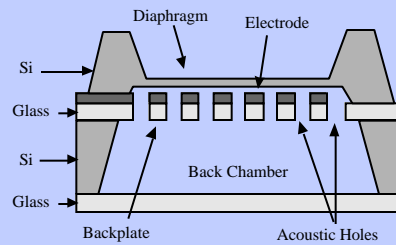
# MICROMACHINED MICROPHONES

- There are many applications where miniaturized microphones (essentially sensitive AC pressure sensors) can be useful (hearing aids, surveillance, etc.).
- Excellent quality conventional devices exist and are very inexpensive, so competition is difficult.
- Most available transduction mechanisms have been utilized.
- Piezoresistive designs offer very low sensitivities (tens of  $\mu\text{V}/\text{Pa}$ ), but low output impedance.
- Capacitive designs offer large sensitivities but low output impedances (need buffers).
- Piezoelectric designs to date have shown moderate sensitivities and high noise levels.

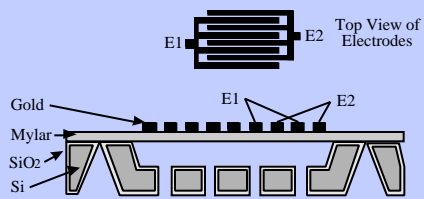
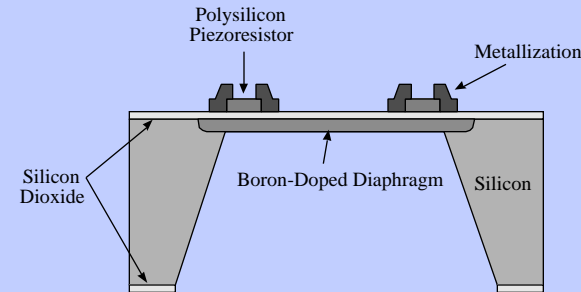
# MICROMACHINED MICROPHONES



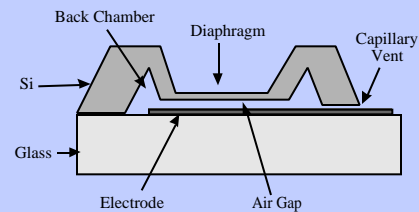
After Hohm, (1986)



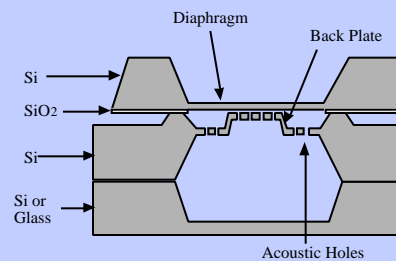
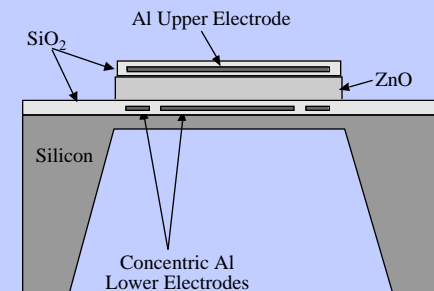
After Berquist and Rudolf, (1990)



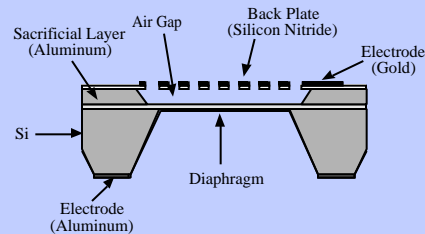
After van der Donk, (1992)



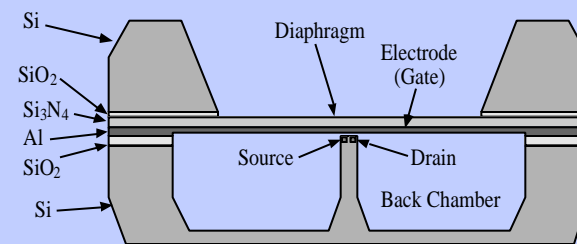
After Bourouina, et al., (1992)



After Berqvist, et al., (1991)



After Scheeper, et al., (1992)



Reference: Scheeper, P., van der Donk, A., Olthuis, W., and Bergveld, P., "A Review of Silicon Microphones," Sensors and Actuators A, vol. 44, 1994, pp. 1 - 11.

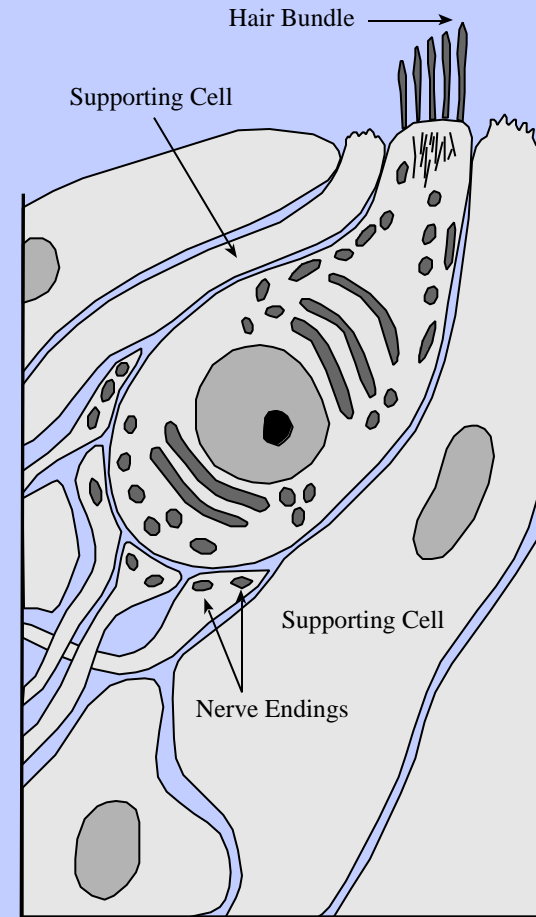
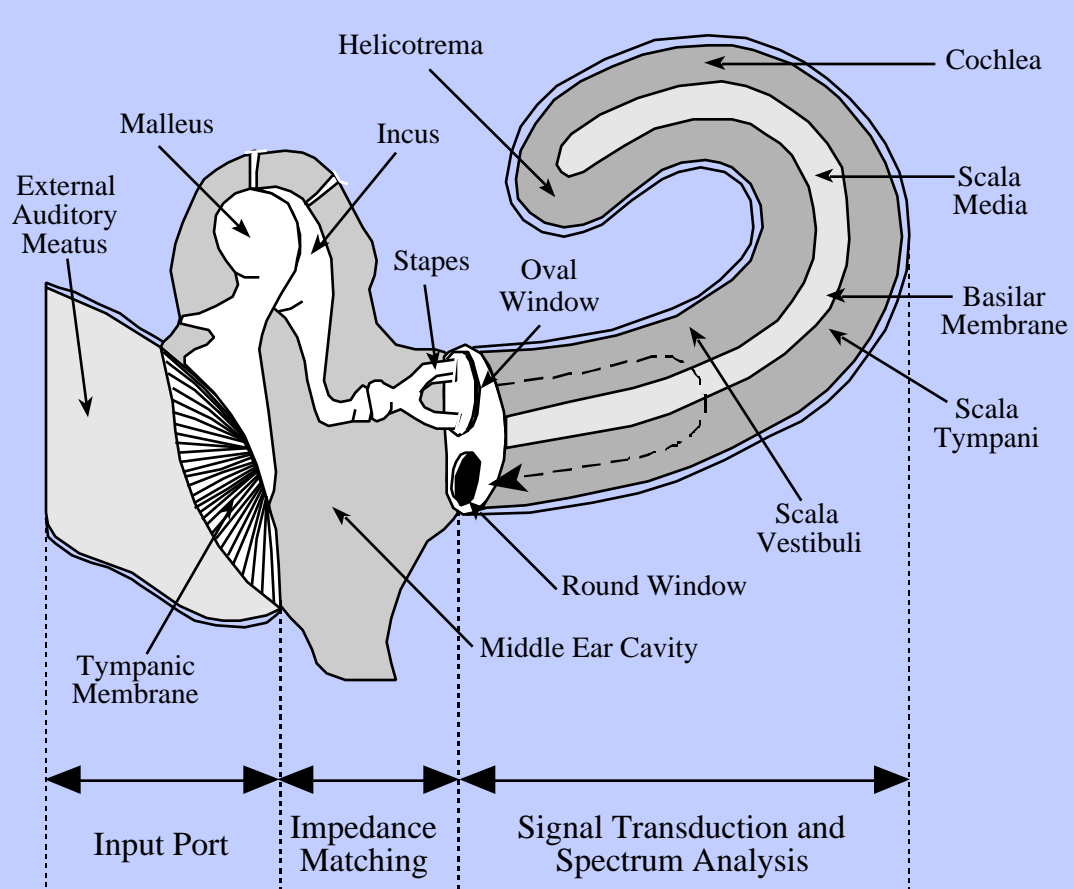


# BIOLOGICAL MECHANICAL TRANSDUCERS

- The cochlea (inner ear) is a mechanical spectrum analyzer.
- Sound is coupled through the eardrum through the inner ear bones (malleus, incus and stapes) and to the oval window of the cochlea.
- High frequencies are sensed at the narrow, stiff end of the cochlea near the oval window, with the wider, more compliant distal regions sensing lower frequencies.
- Tactile sensors in the skin are capable of providing information about discriminative touch (shape, size, texture), proprioception (position), nociception (pain) and temperature.
- Several types of specialized receptors contribute to this.

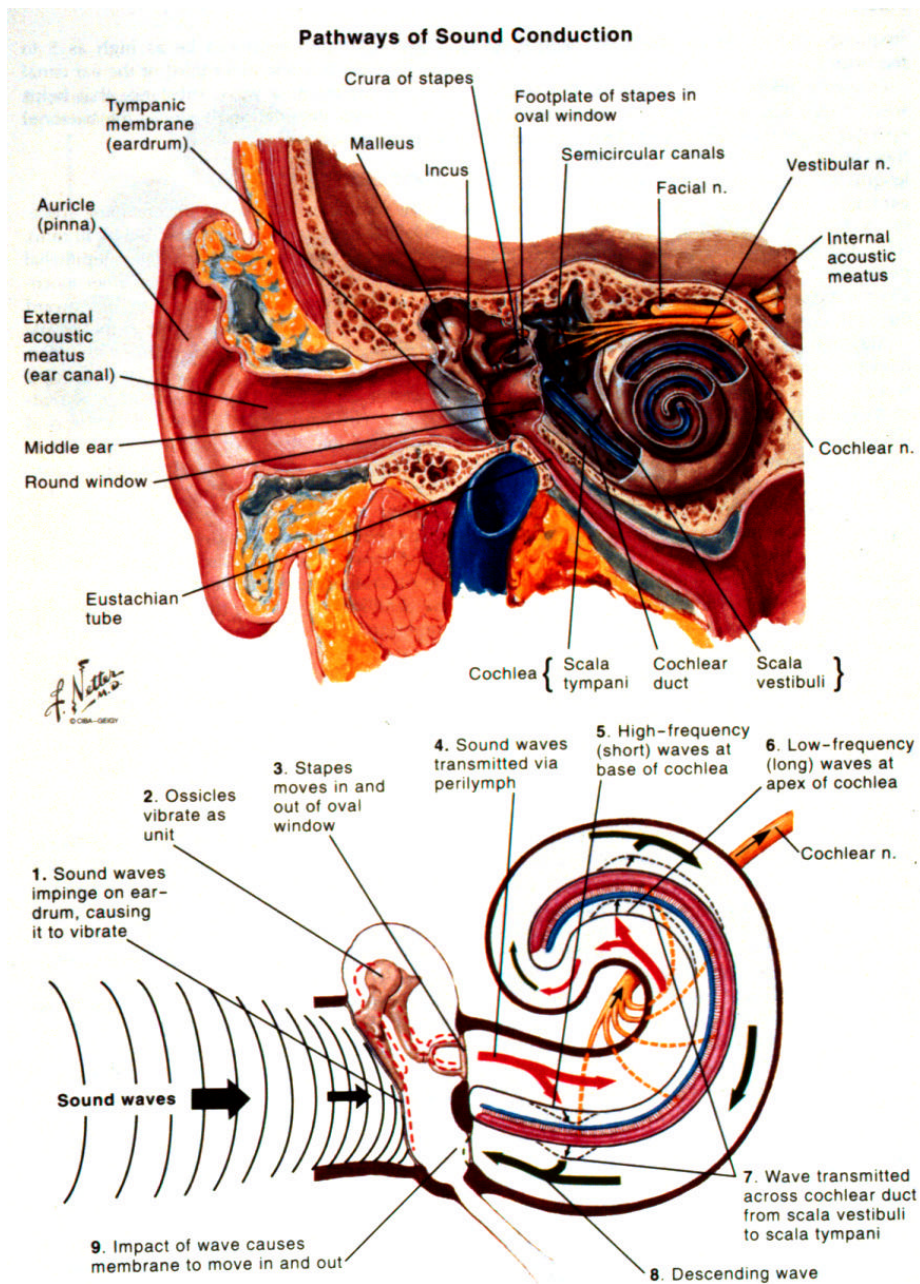


# BIOLOGICAL ACOUSTIC SENSORS



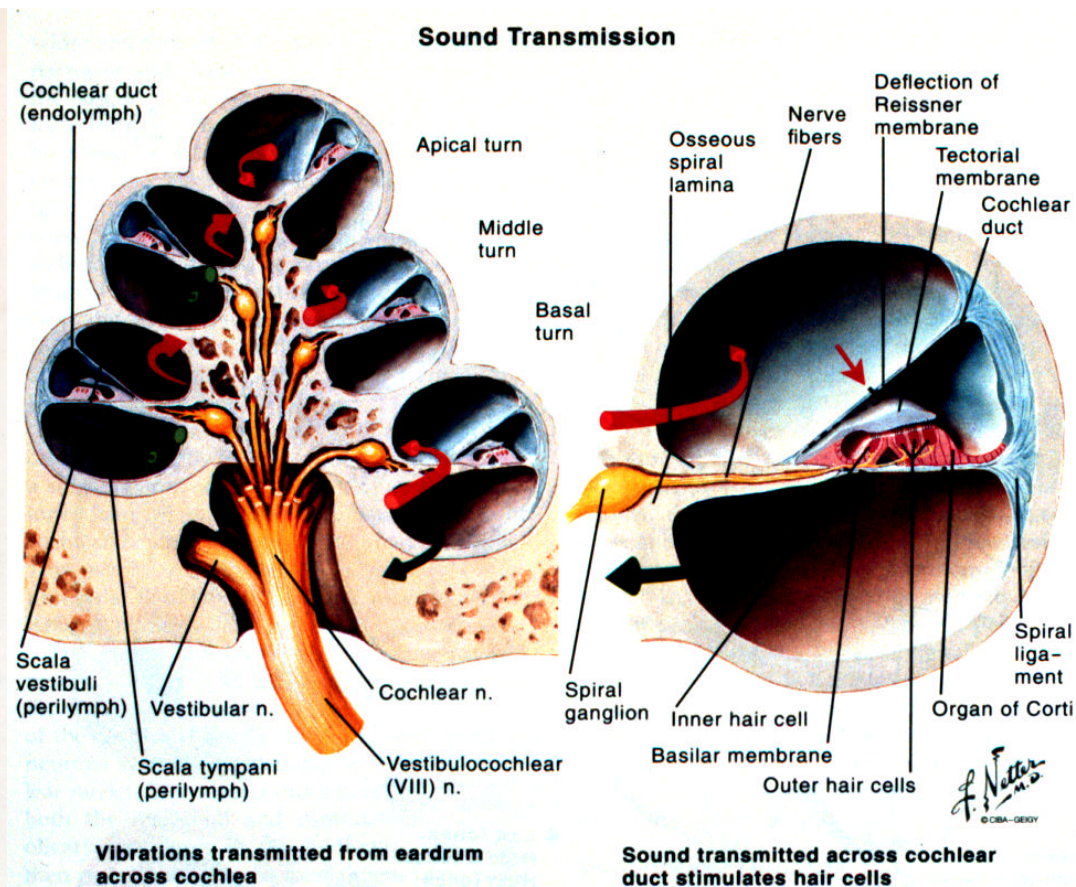
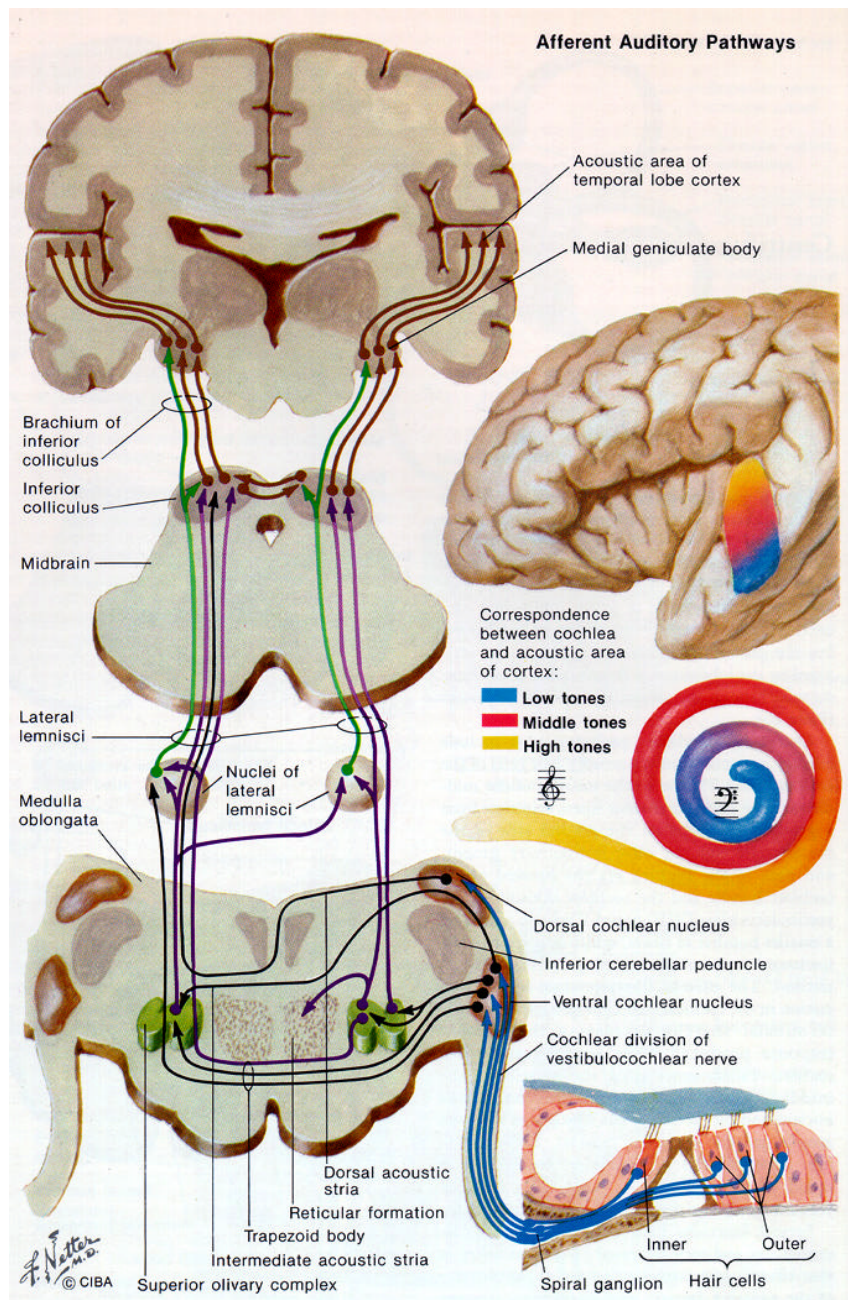
Reference: Kelly, J. P., "Hearing," Chapter 32 in "Principles of Neural Science," Third Edition, Kandel, E. R., Schwartz, J. H., and Jessell, T. M., [eds.], Elsevier, New York, NY, 1991, pp. 481 - 499.





Source: Netter, F., "The CIBA Collection of Medical Illustrations: Volume 1, Nervous System, Part 1, Anatomy and Physiology," CIBA-GEIGY Corp., 1983.





Source: Netter, F., "The CIBA Collection of Medical Illustrations: Volume 1, Nervous System, Part 1, Anatomy and Physiology," CIBA-GEIGY Corp., 1983.

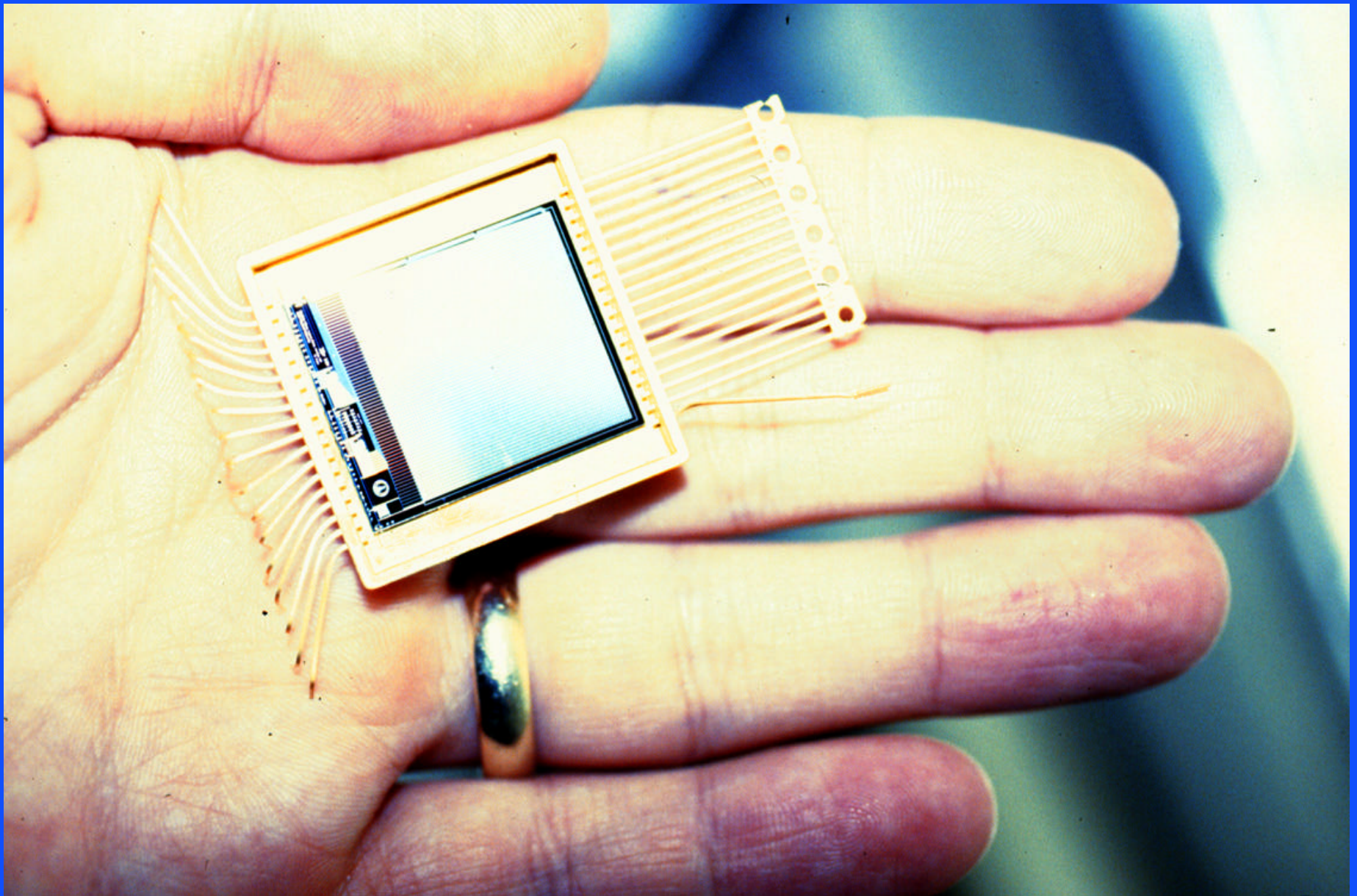
# TACTILE SENSORS

- Tactile sensors can be applied in robotics (end effectors) and research into dextrous manipulation.
- Many different transduction mechanisms have been utilized.
- Few devices have sensed shear forces (very important in object manipulation).

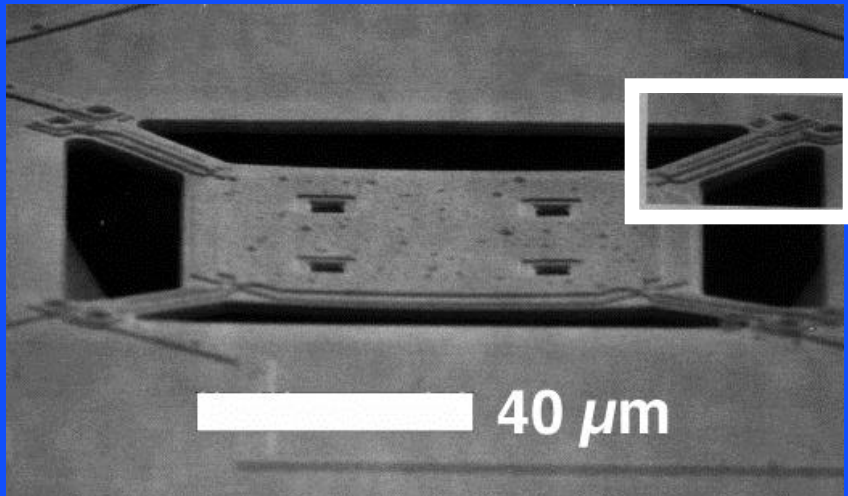






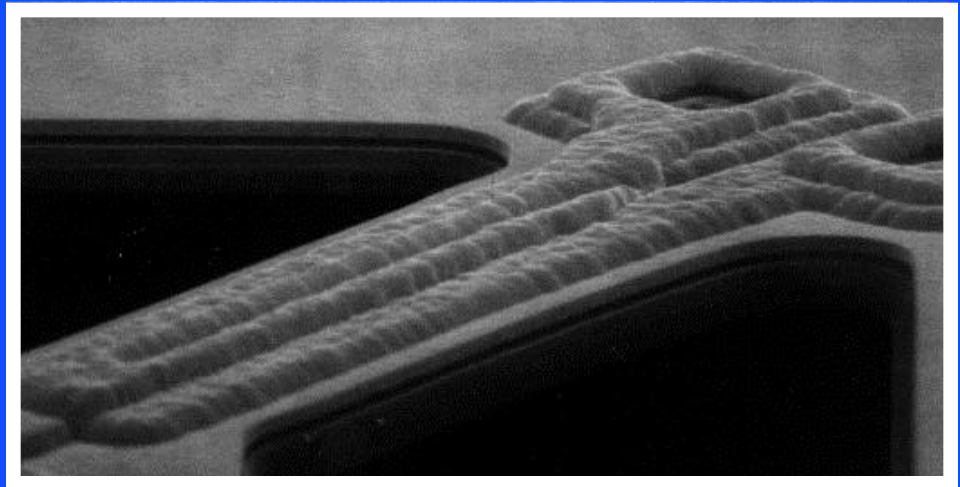


# SHUTTLE PLATE TACTILE SENSOR

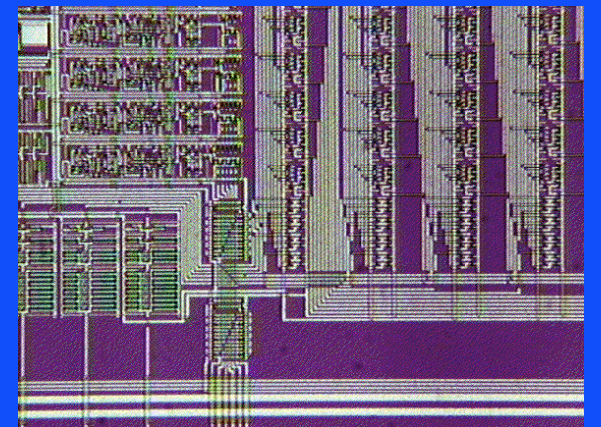
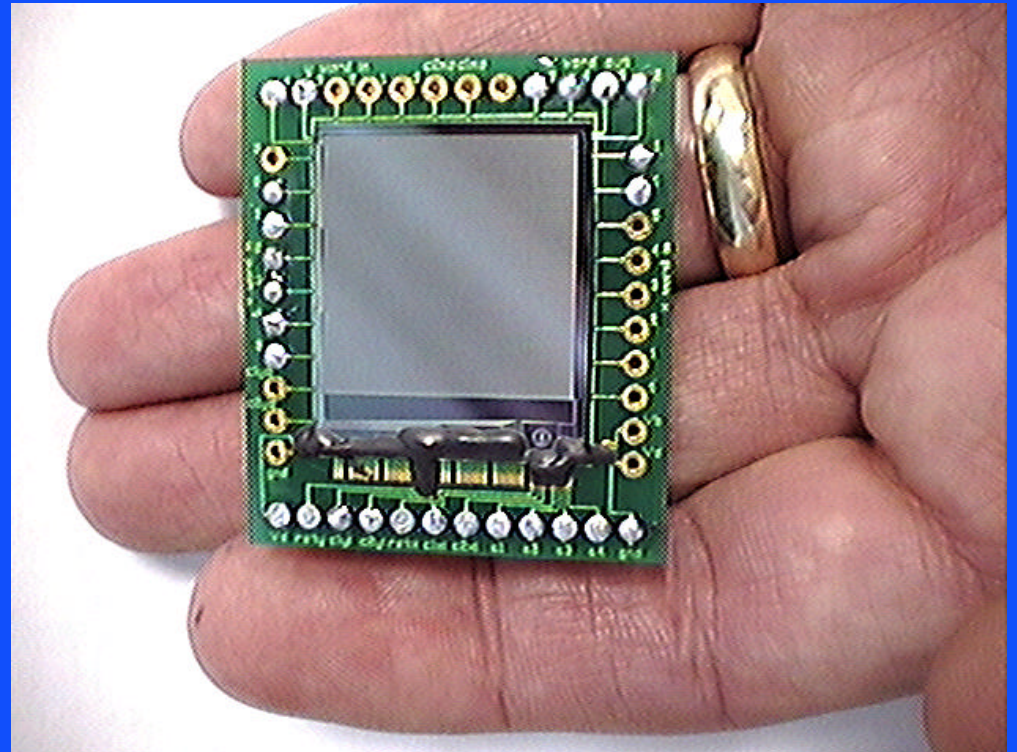
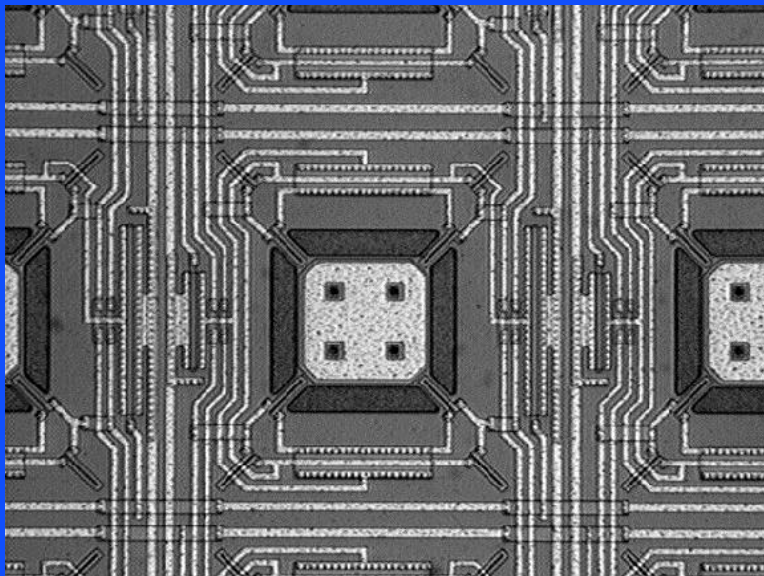
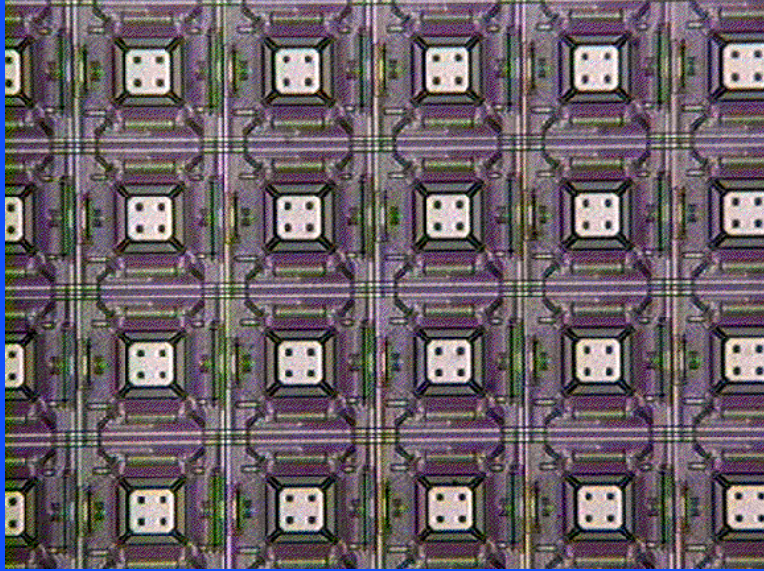


- Shuttle plate with four piezoresistive strain gauges can sense shear and normal forces.
- TMAH undercut of oxide membranes is CMOS compatible.

Reference: Kane, B. J., Cutkosky, M. R., and Kovacs, G. T. A., "CMOS-Compatible Traction Stress Sensor for Use in High-Resolution Tactile Imaging," *Sensors and Actuators A*, vol. A54, 1996, pp. 511 - 516.



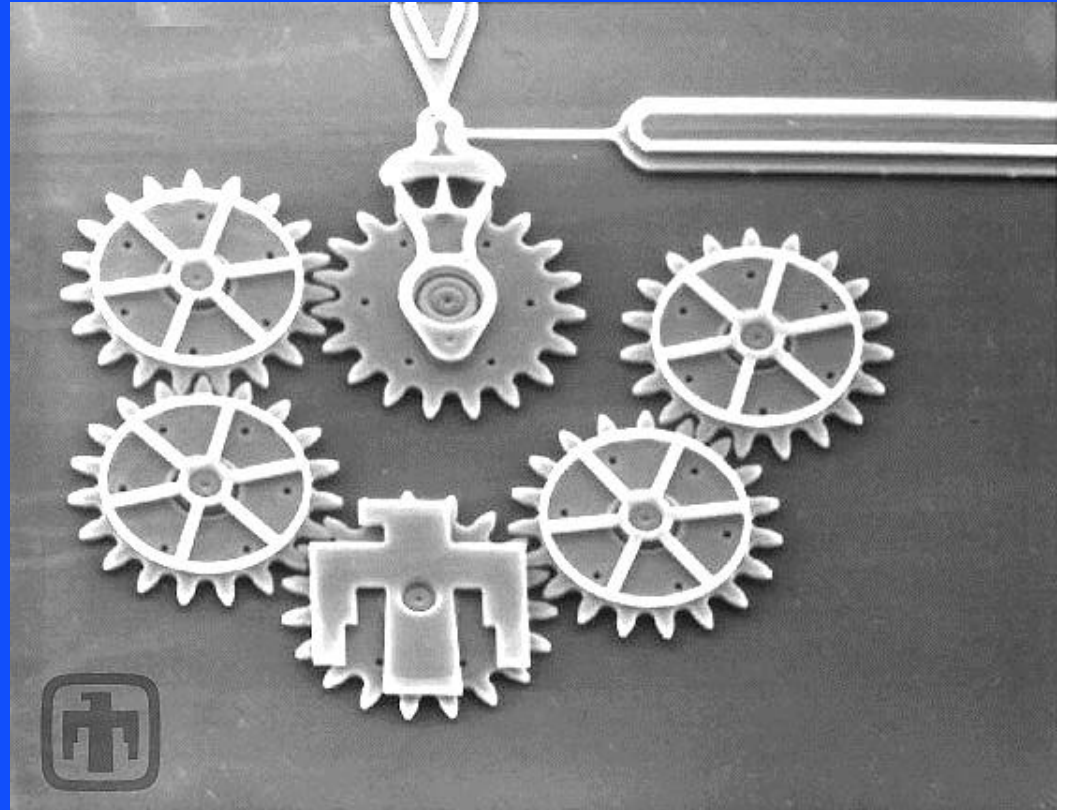






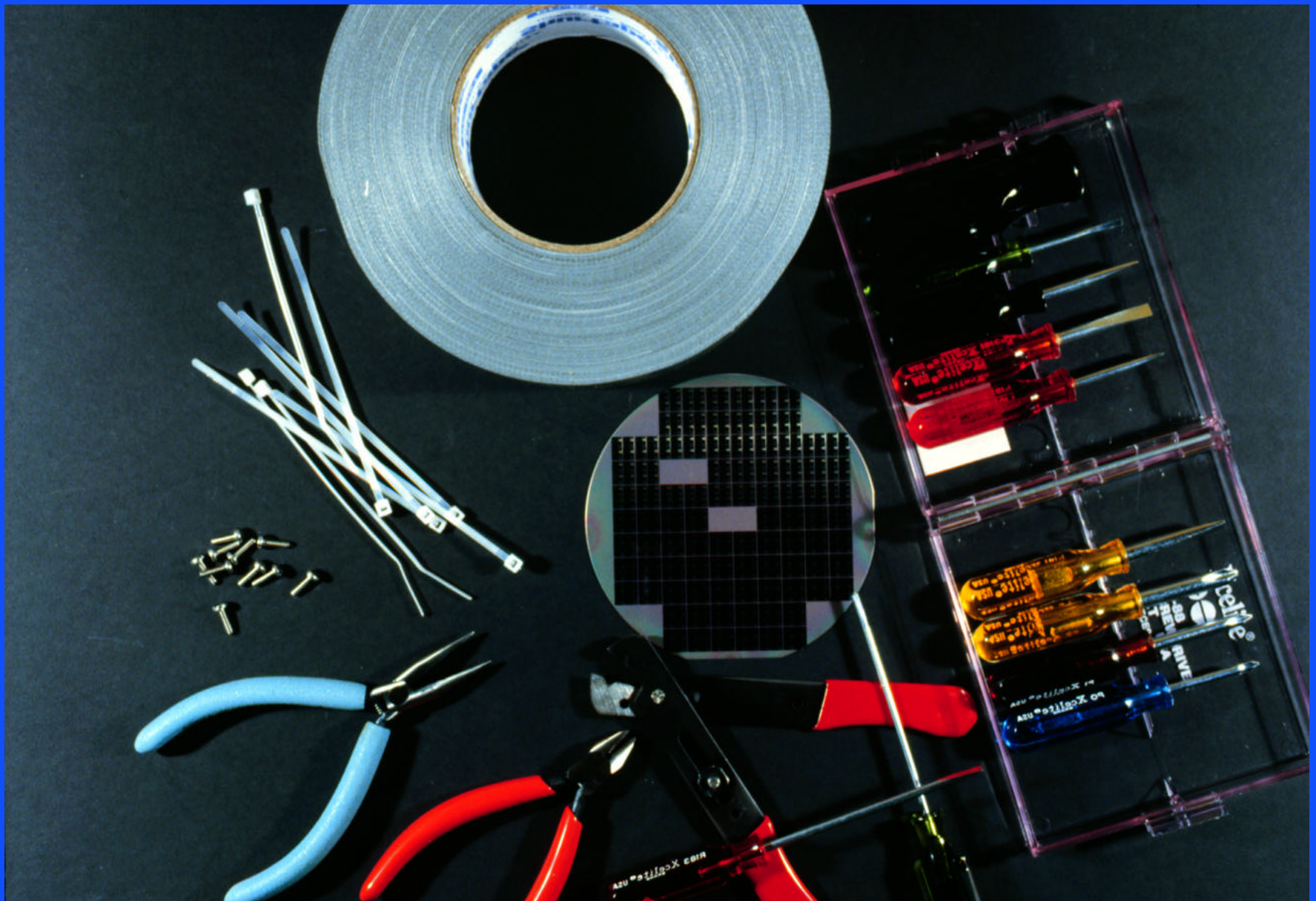


# Micromechanisms

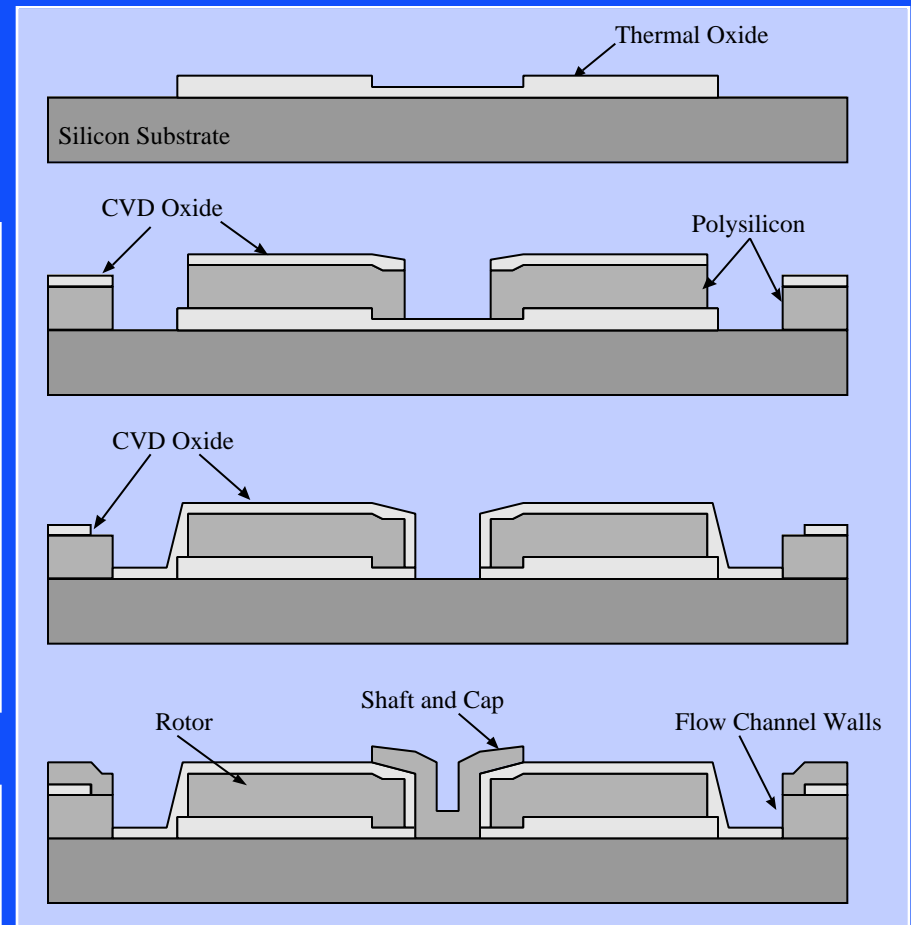
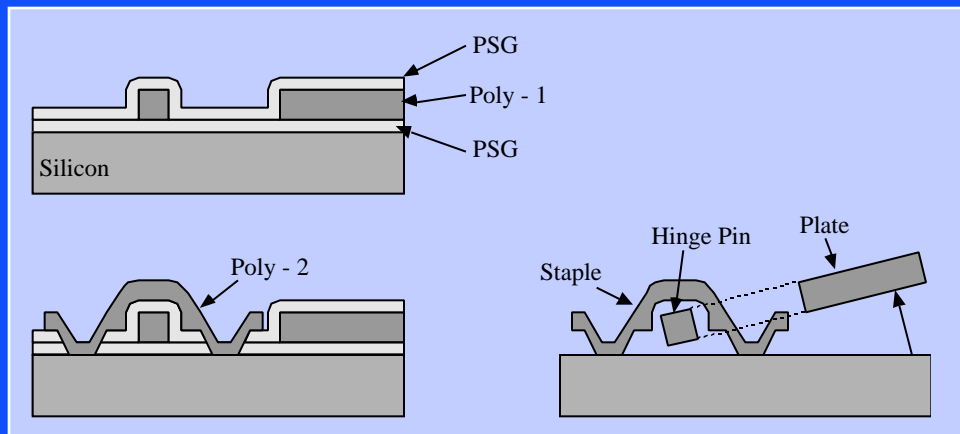
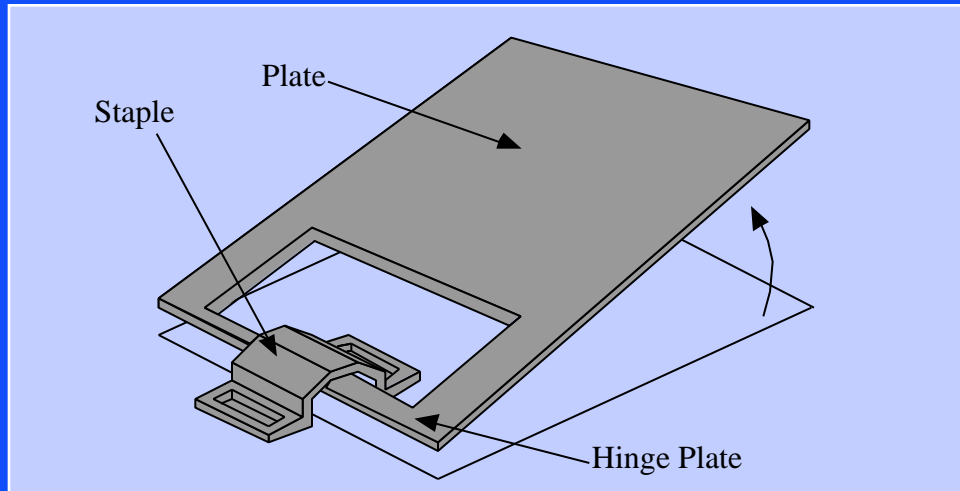


<http://www.mdl.sandia.gov/Micromachine/images.html>





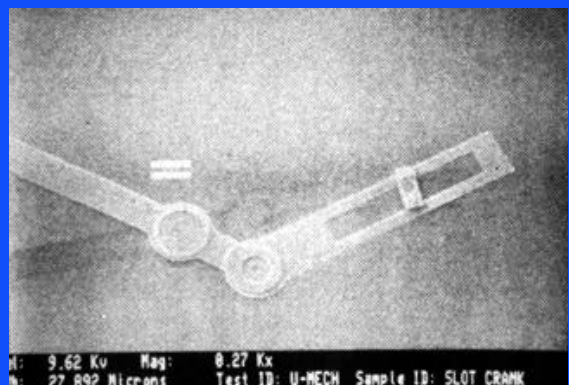
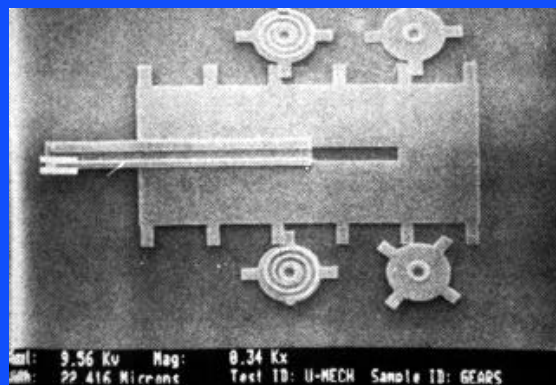
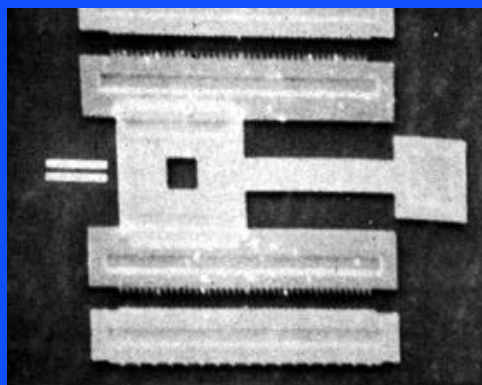
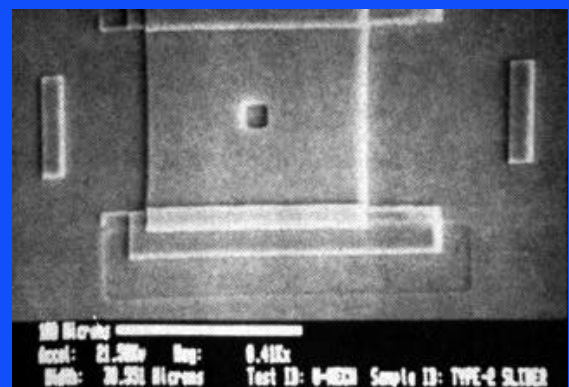
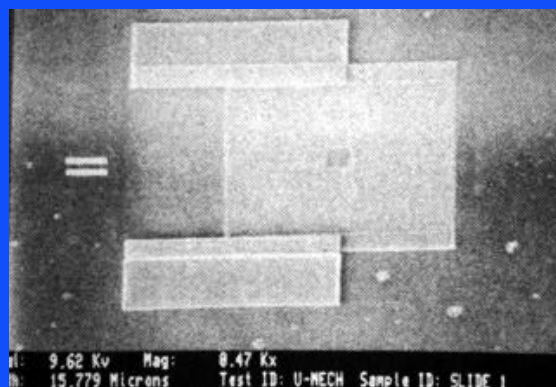
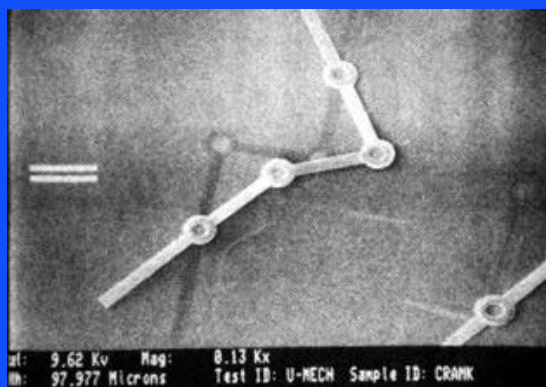
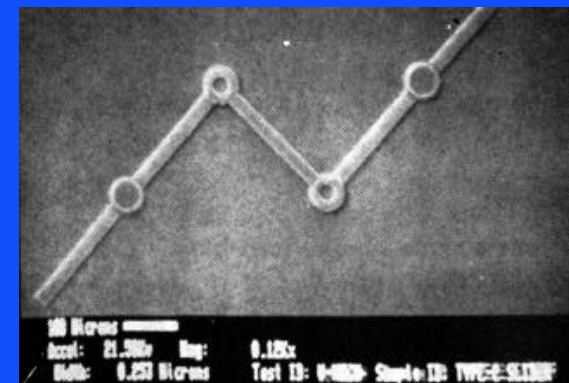
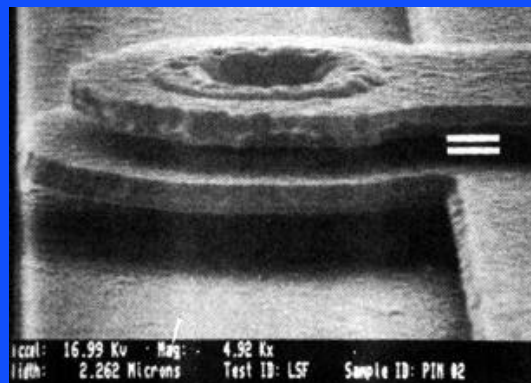
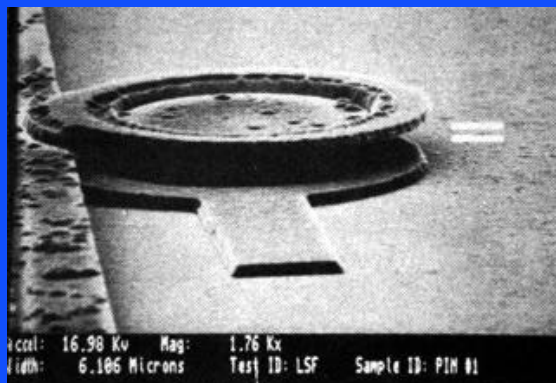
# POLYSILICON MECHANISMS



Reference: Mehregany, M., Gabriel, K. J., and Trimmer, W. S. N., "Integrated Fabrication of Polysilicon Mechanisms," IEEE Transactions on Electron Devices, vol. 35, no. 6, June 1988, pp. 719 - 723.

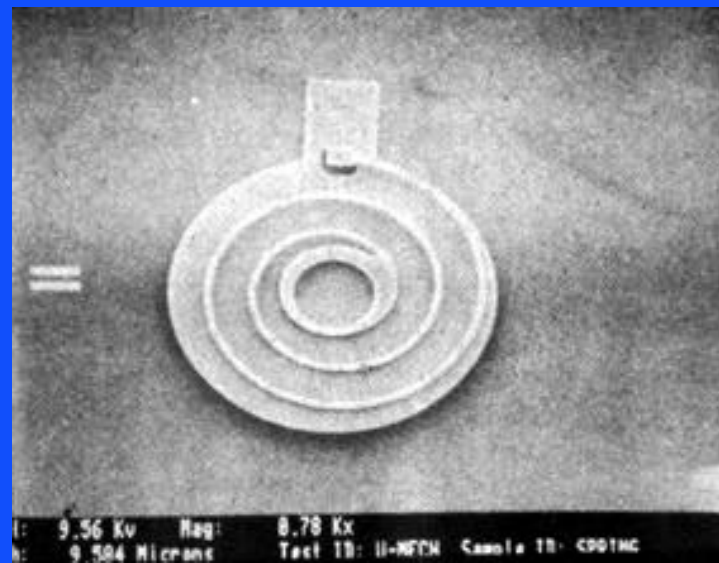
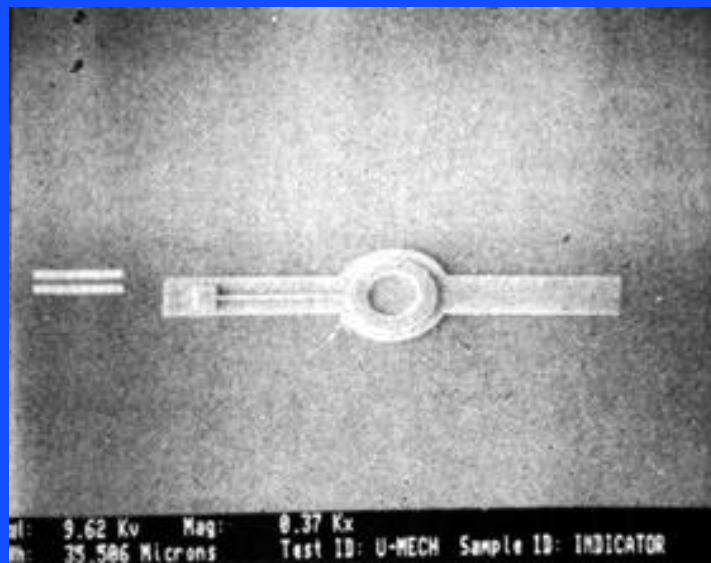
Reference: Pister, K. S. J., Judy, M. W., Burgett, S. R., and Fearing, R. S., "Microfabricated Hinges." Sensors and Actuators A, vol. A33, no. 3, June 1992, pp. 249 - 256.





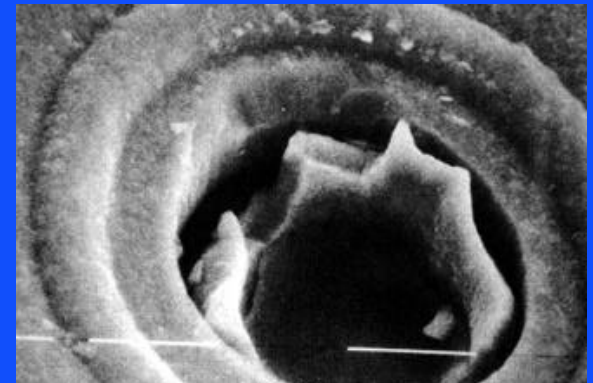
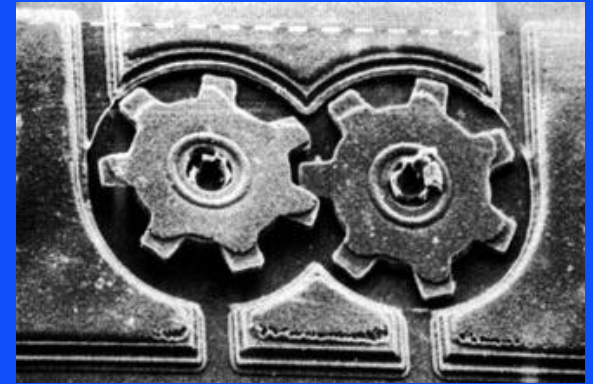
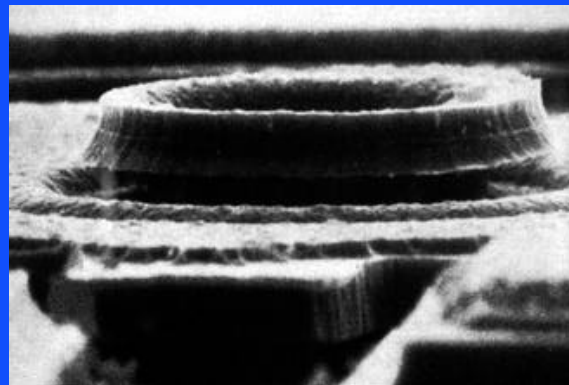
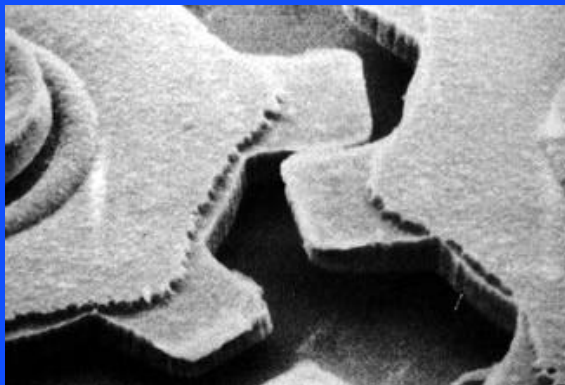
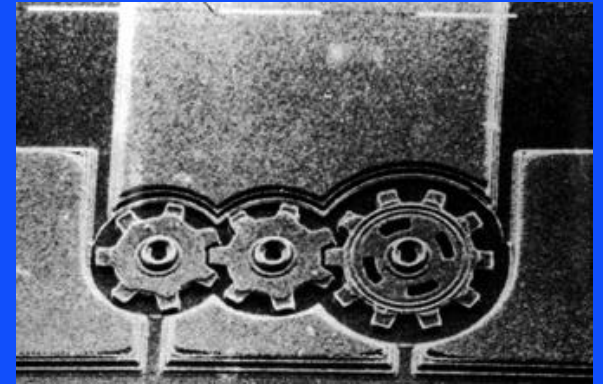
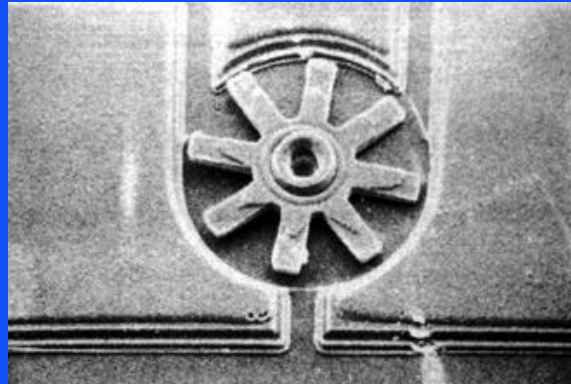
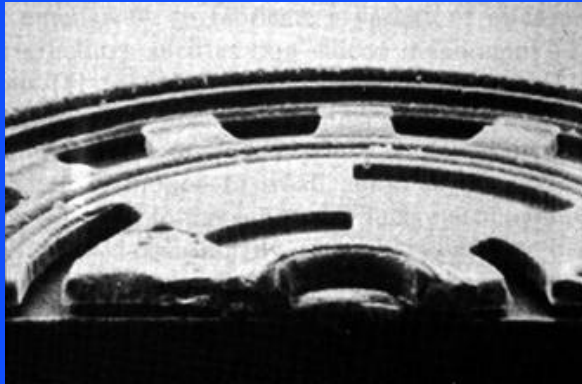
Source: Fan, L.-S., Tai, Y.-C., and Muller, R. S., "Integrated Movable Micromechanical Structures for Sensors and Actuators," IEEE Transactions on Electron Devices, vol. 35, no. 6, June 1988, pp. 724 - 730.

G. Kovacs © 2000



Source: Fan, L.-S., Tai, Y.-C., and Muller, R. S., "Integrated Movable Micromechanical Structures for Sensors and Actuators," IEEE Transactions on Electron Devices, vol. 35, no. 6, June 1988, pp. 724 - 730.

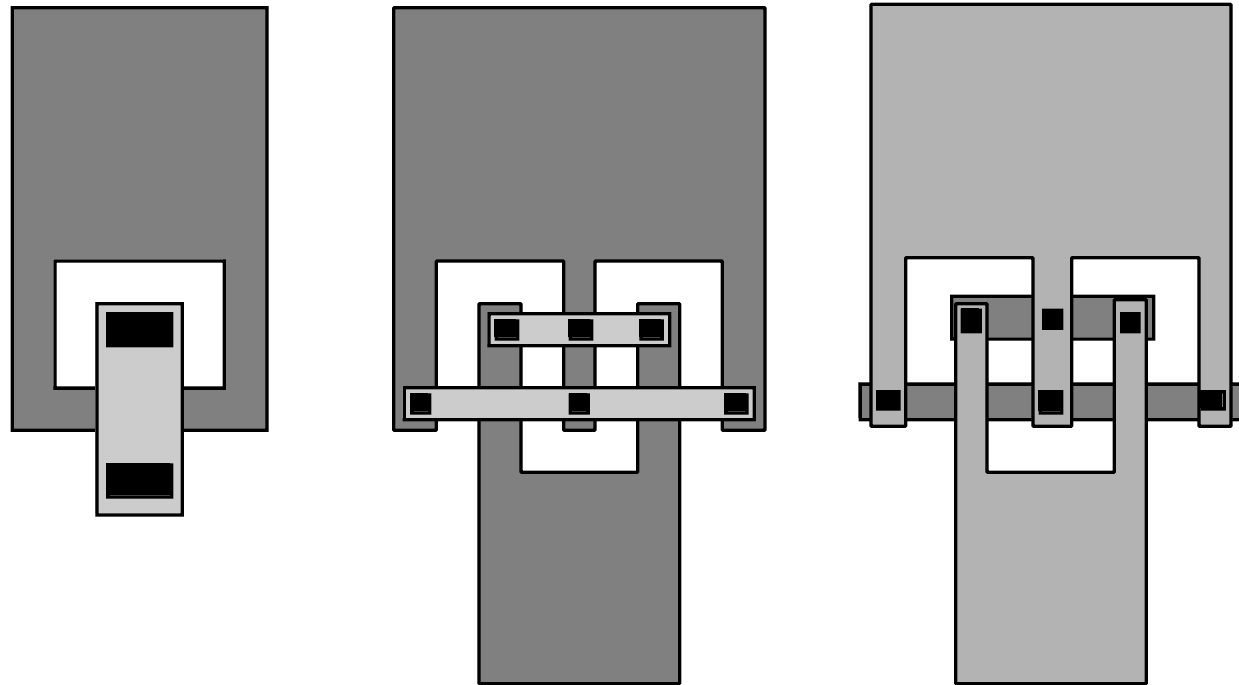




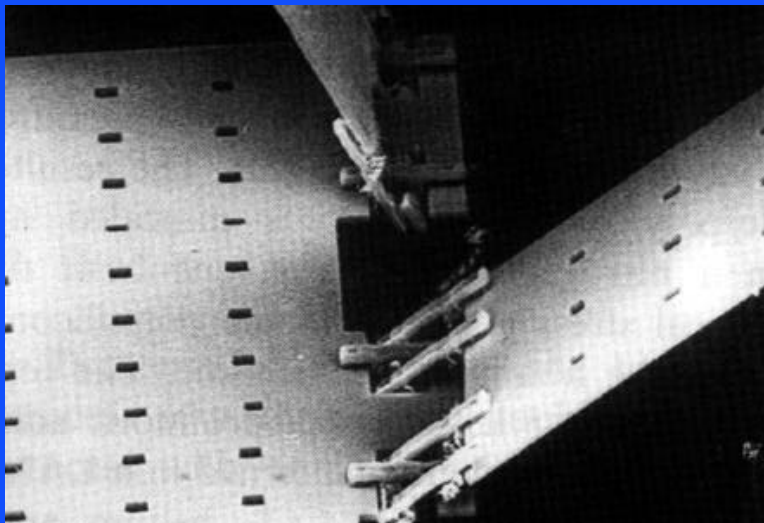
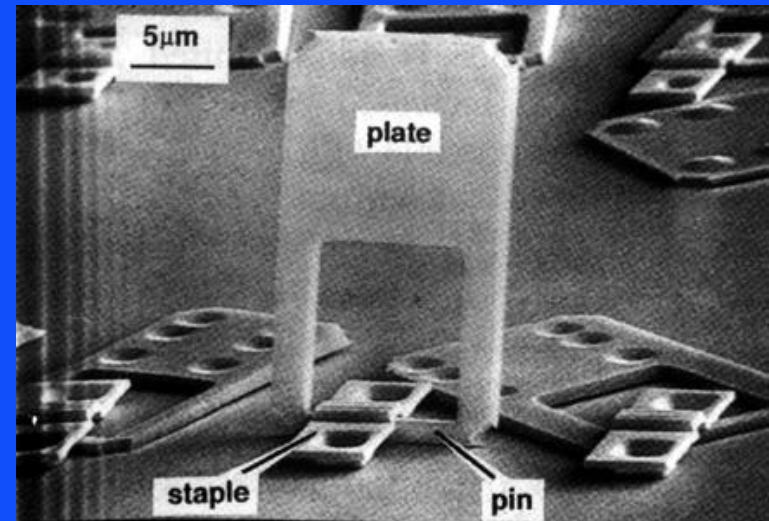
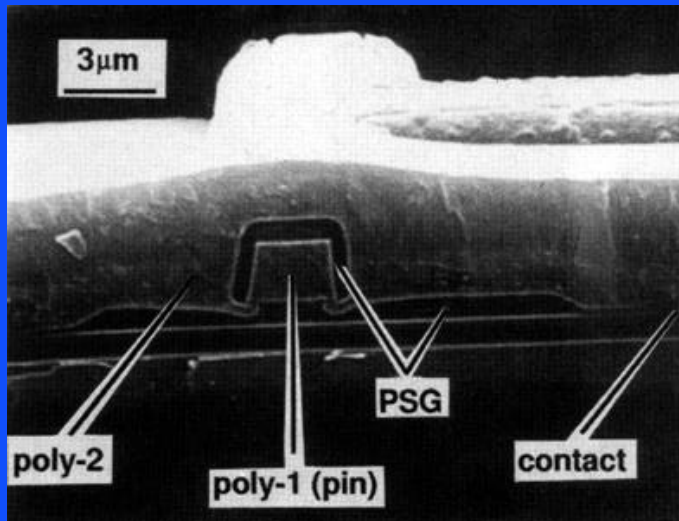
Source: Mehregany, M., Gabriel, K. J., and Trimmer, W. S. N., "Integrated Fabrication of Polysilicon Mechanisms," IEEE Transactions on Electron Devices, vol. 35, no. 6, June 1988, pp. 719 - 723.



■ Poly - 1  
■ Poly - 2  
■ Contact

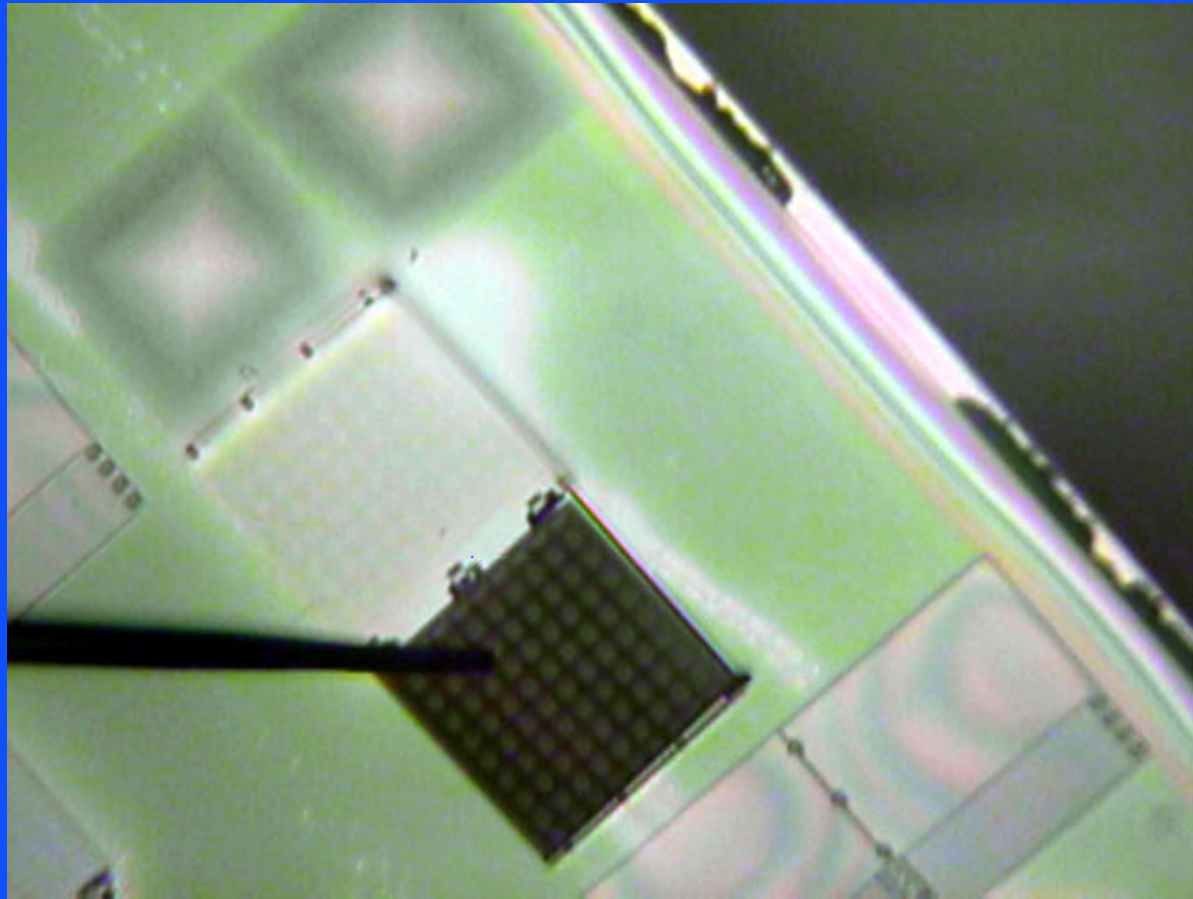


Reference: Pister, K. S. J., Judy, M. W., Burgett, S. R., and Fearing, R. S., "Microfabricated Hinges." *Sensors and Actuators A*, vol. A33, no. 3, June 1992, pp. 249 - 256.



Source: Pister, K. S. J., Judy, M. W., Burgett, S. R., and Fearing, R. S., "Microfabricated Hinges." Sensors and Actuators, vol. A33, no. 3, June 1992, pp. 249 - 256.

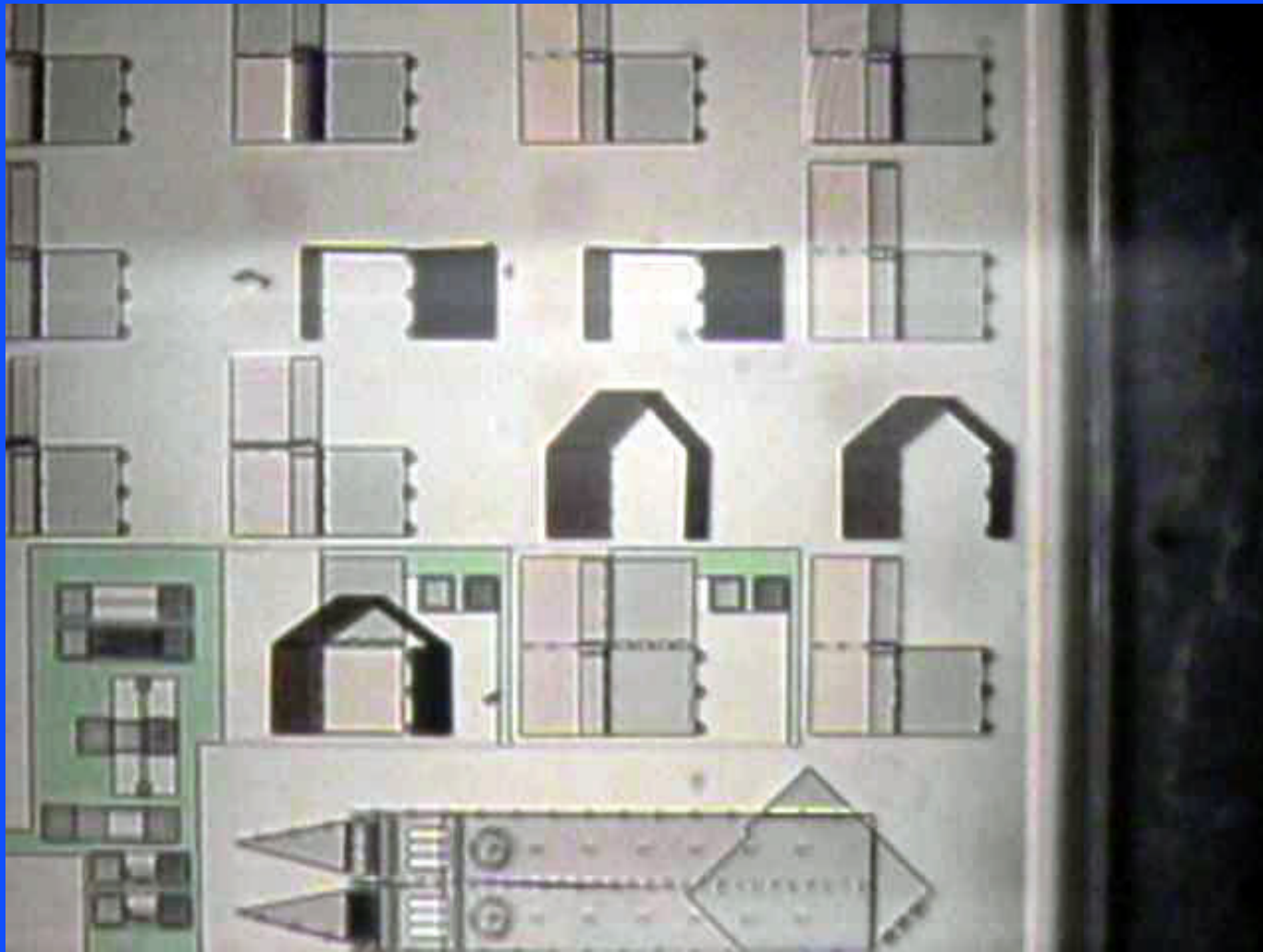
# HINGED STRUCTURE ASSEMBLY



Courtesy E. Hui, U. C. Berkeley.

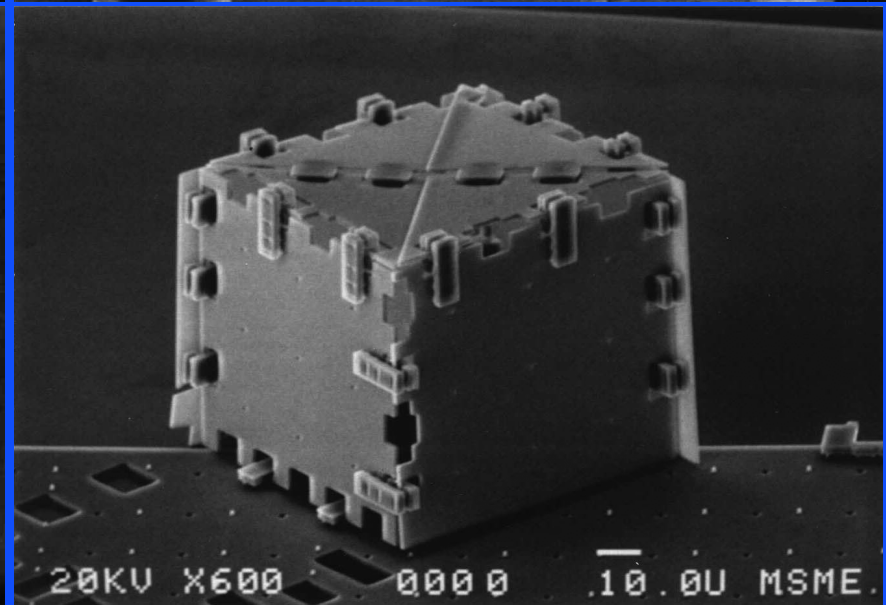
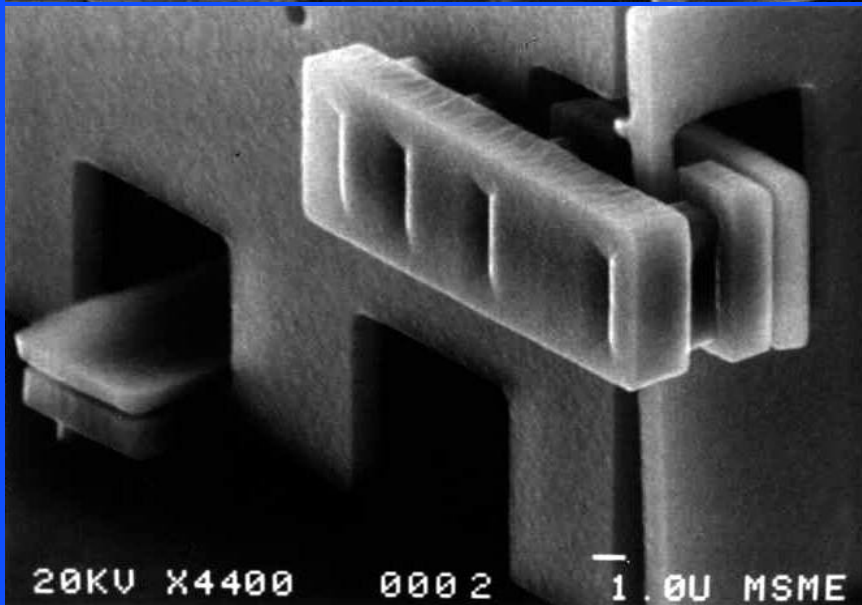
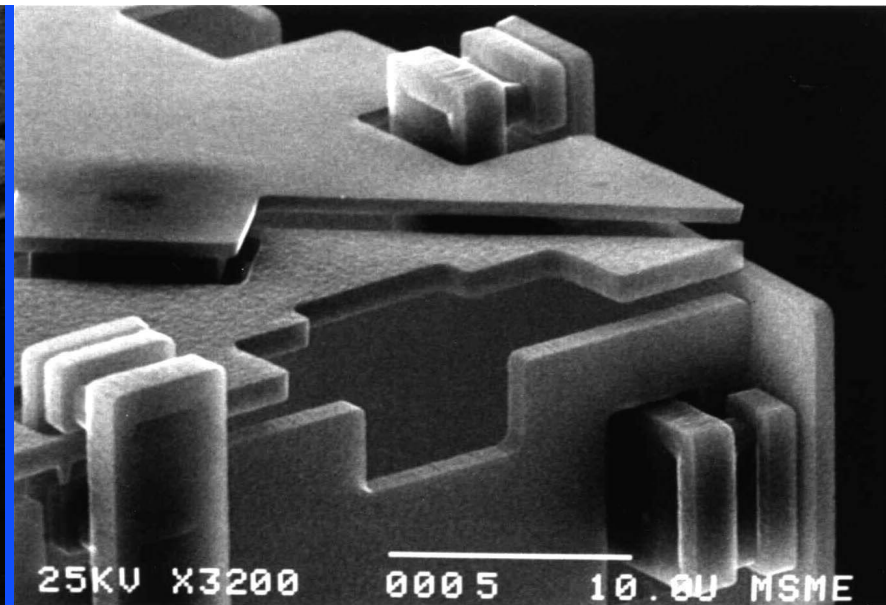
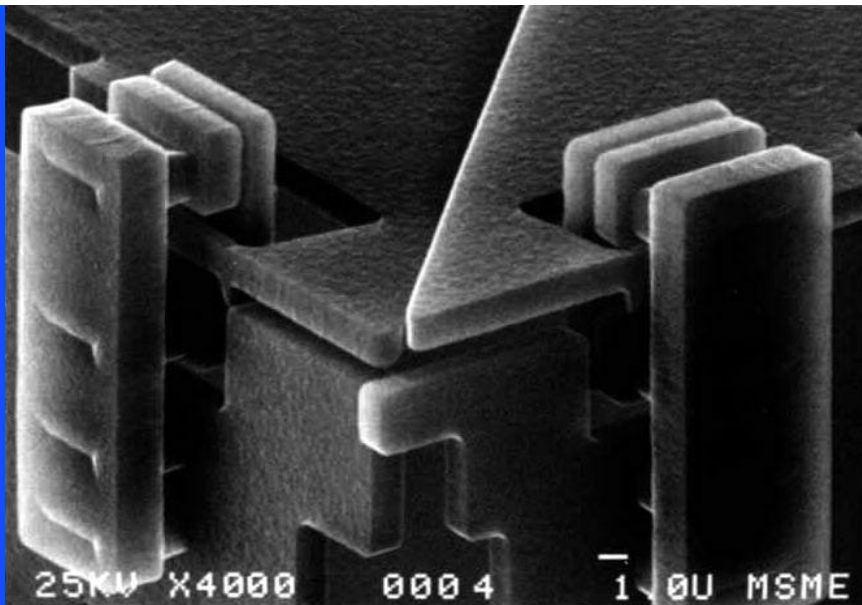


# FLUIDIC ASSEMBLY

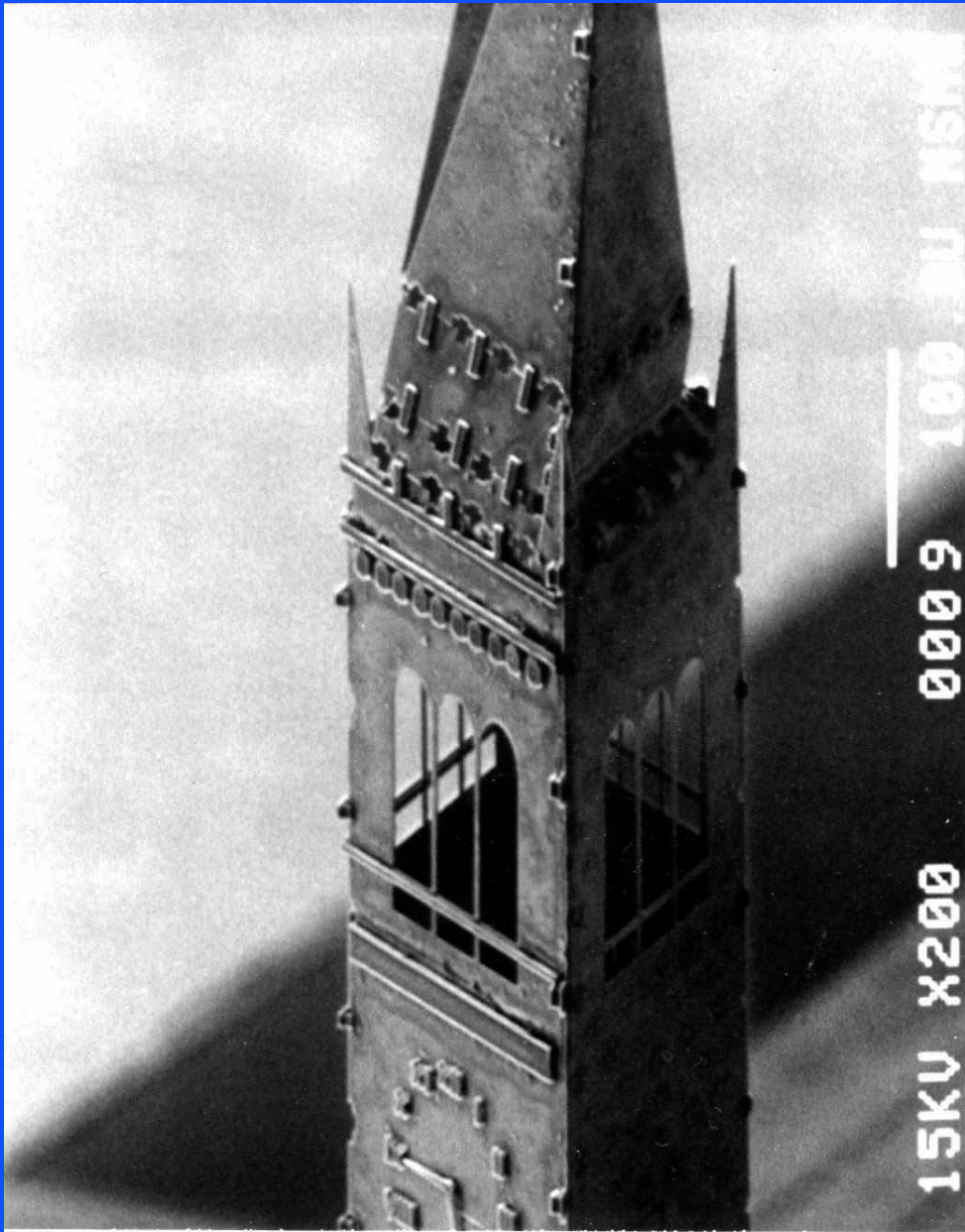


Courtesy E. Hui, U. C. Berkeley.

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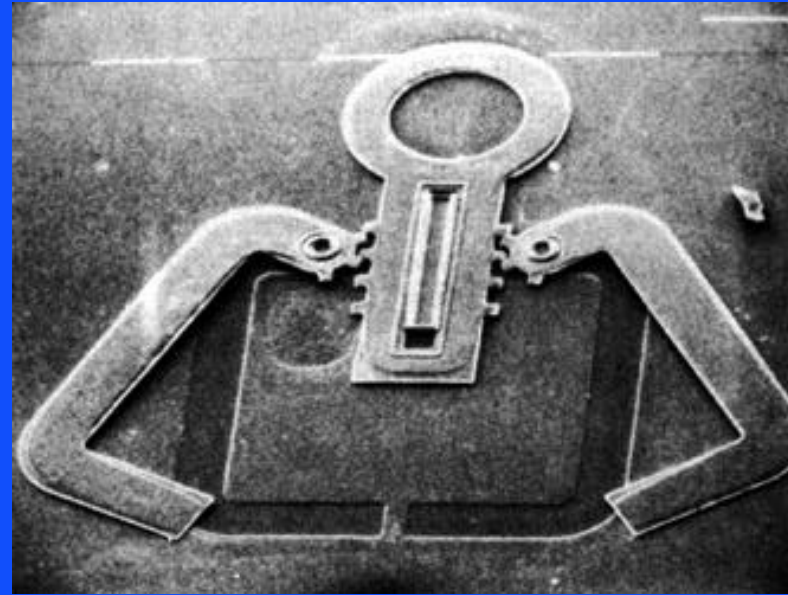
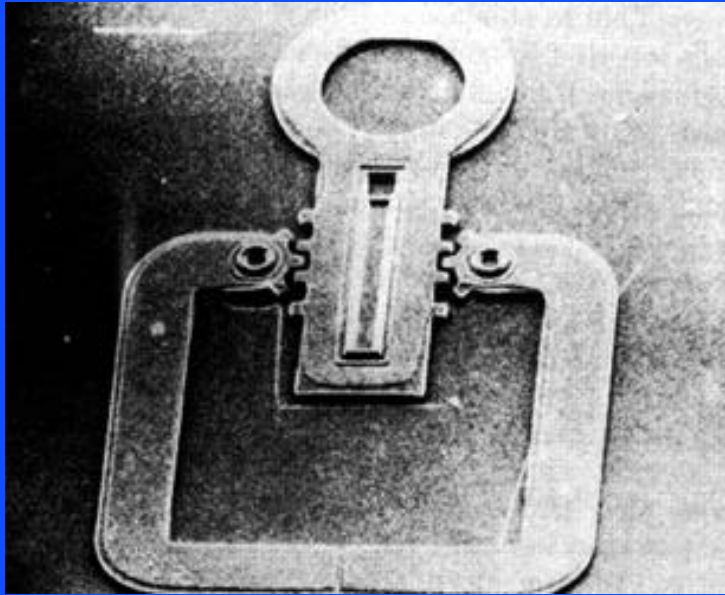


This “pop-up” closed box was assembled in a single flipping step, using tweezers provided by MEMS Precision Instruments. Designed by Elliot Hui in the Sandia SUMMiT 4-level process. 7/22/99 Courtesy E. Hui, U. C. Berkeley.

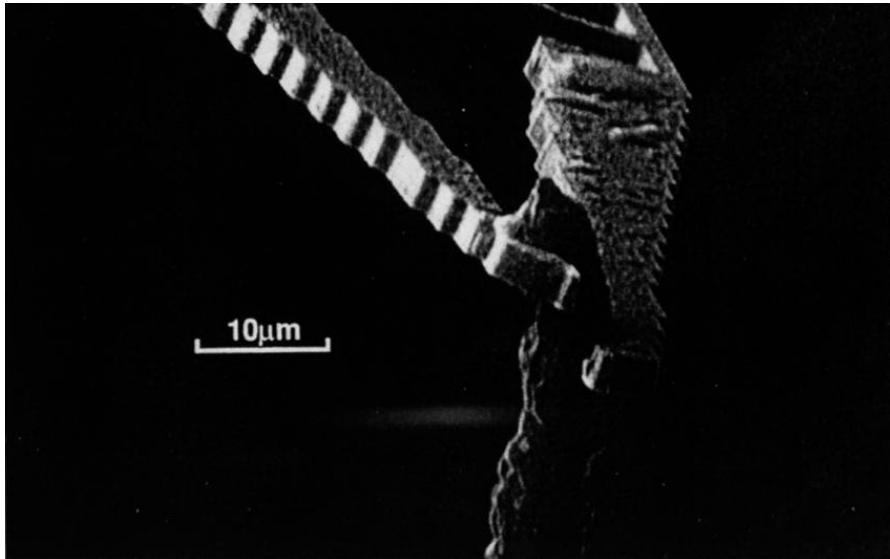


Courtesy E. Hui, U. C. Berkeley.

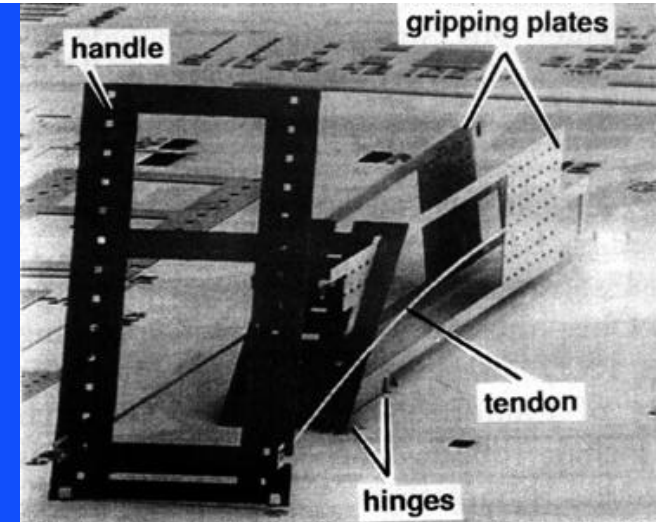
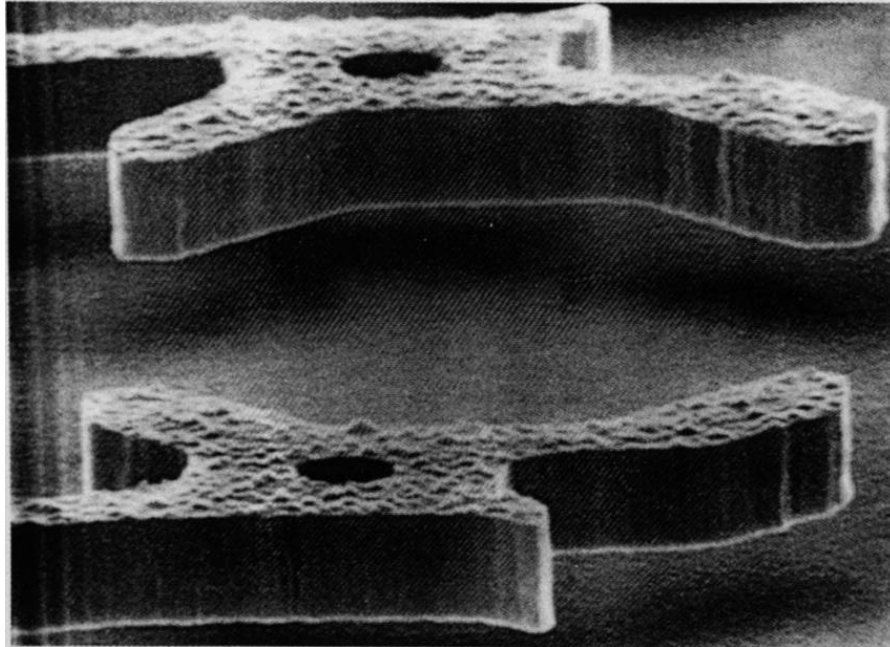




Source: Mehregany, M., Gabriel, K. J., and Trimmer, W. S. N., "Integrated Fabrication of Polysilicon Mechanisms," IEEE Transactions on Electron Devices, vol. 35, no. 6, June 1988, pp. 719 - 723.



**Microgripper.** This scanning electron micrograph shows a microgripper made by Chang-Jin Kim, Albert Pisano, and Richard Muller of the Berkeley Sensor & Actuator Center. The gripper is holding a euglena, a 7- by 40-micron single-cell protozoa.



Source: Pister, K. S. J., Judy, M. W., Burgett, S. R., and Fearing, R. S., "Microfabricated Hinges." *Sensors and Actuators*, vol. A33, no. 3, June 1992, pp. 249 - 256.

Source: Kim, C.-J., Pisano, A. P., and Muller, R. S., "Silicon-Processed Overhanging Microgripper." *Journal Of Microelectromechanical Systems*, vol. 1, no. 1, Mar. 1992, pp. 31 - 36.

# LIGA HOSE CLAMP & SPRING



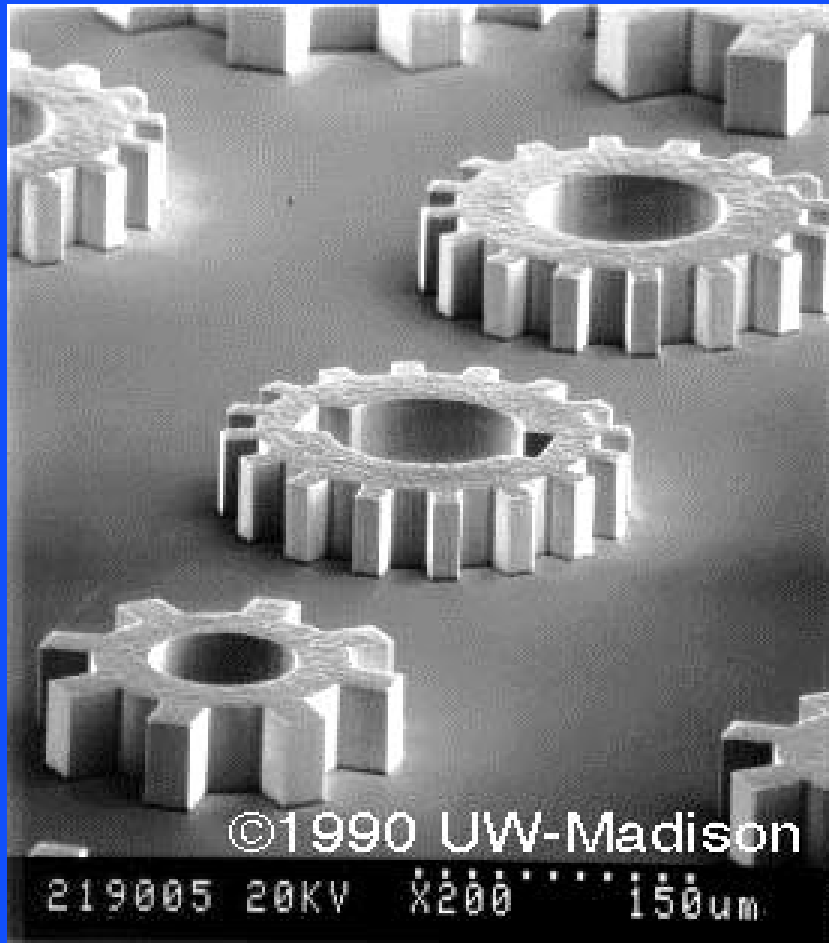
Courtesy of Prof. Henry Guckel

<http://mems.engr.wisc.edu/images/>

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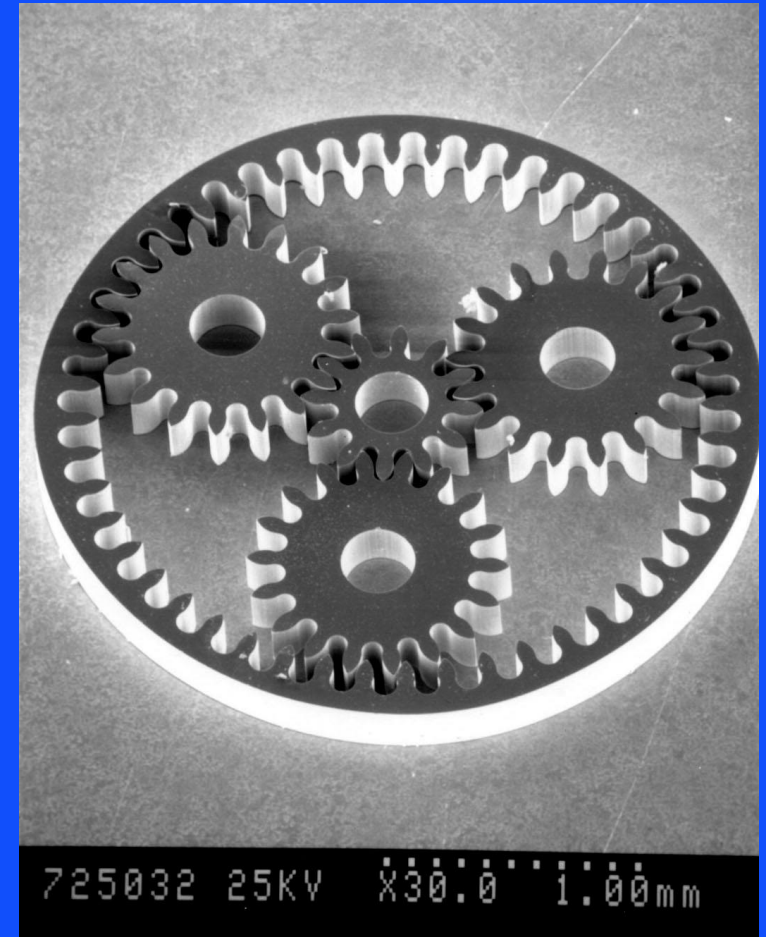


# LIGA GEARS



Courtesy of Prof. Henry Guckel

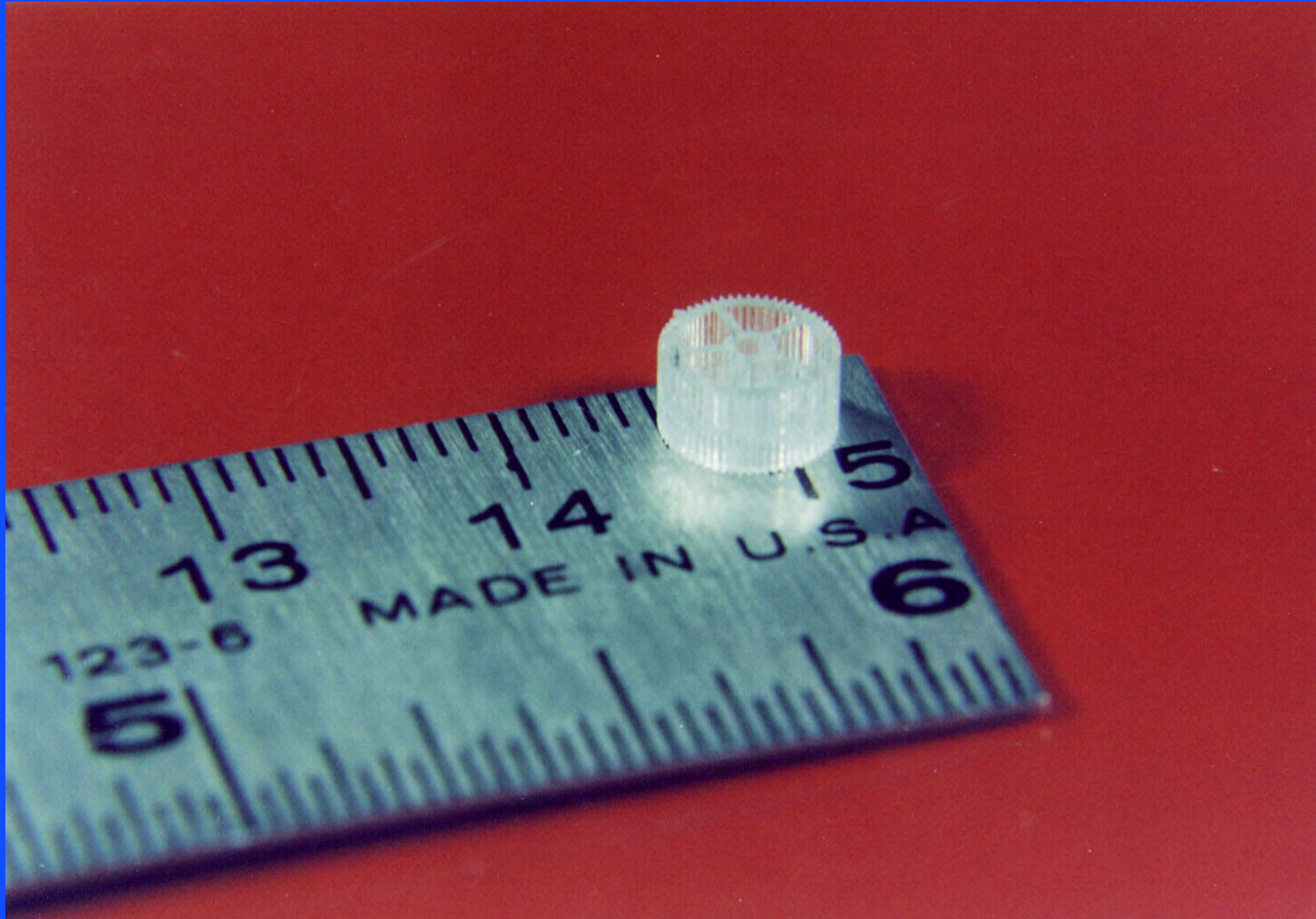
<http://mems.engr.wisc.edu/images/>



Reference: H. Guckel, "Micromechanics for Actuator and Precision Engineering Applications", Meeting Abstracts, 194th Meeting of the Electrochemical Society, Inc., Vol. (98-2), Abstract No. (1154), Boston, MA, November 1998

G. Kovacs © 2000

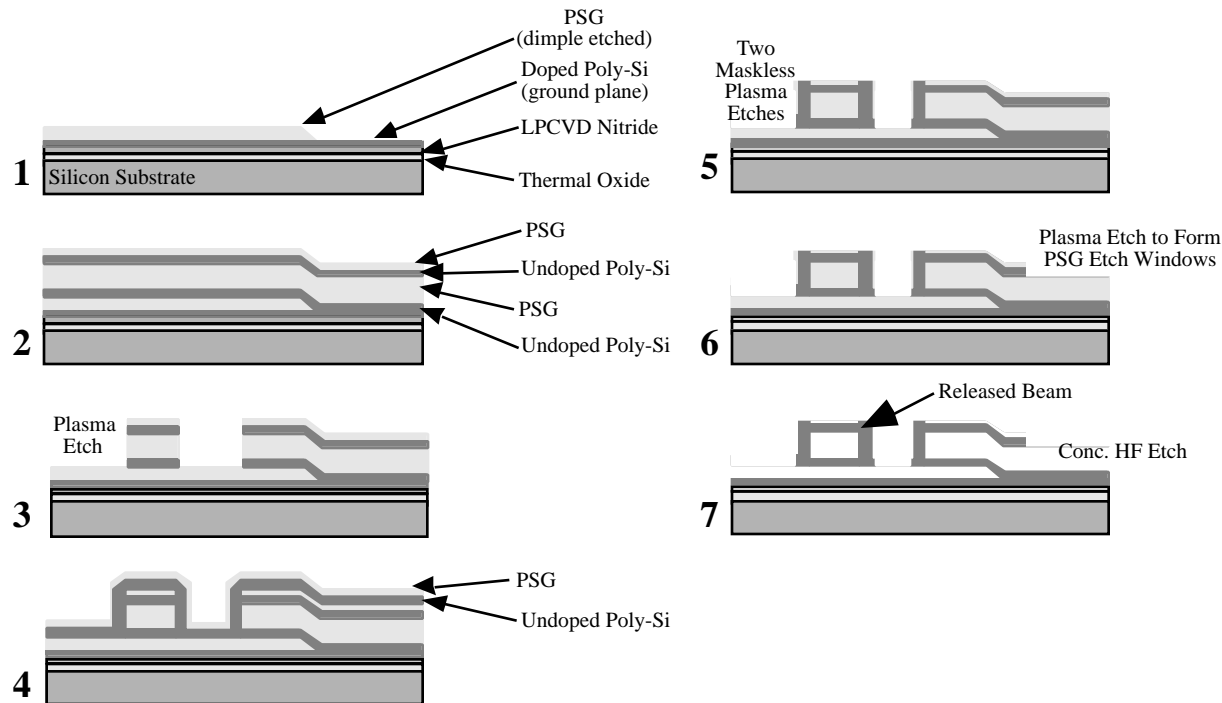
# PMMA GEAR



Courtesy of Prof. H. Guckel, University of Wisconsin.

Reference: D.P. Siddons, E.D. Johnson and H. Guckel, "Precision Machining Using Hard X-rays," Synchrotron Radiation News, (7), No. 2, (1994) pp. 16-18.  
G. Kovacs © 2000

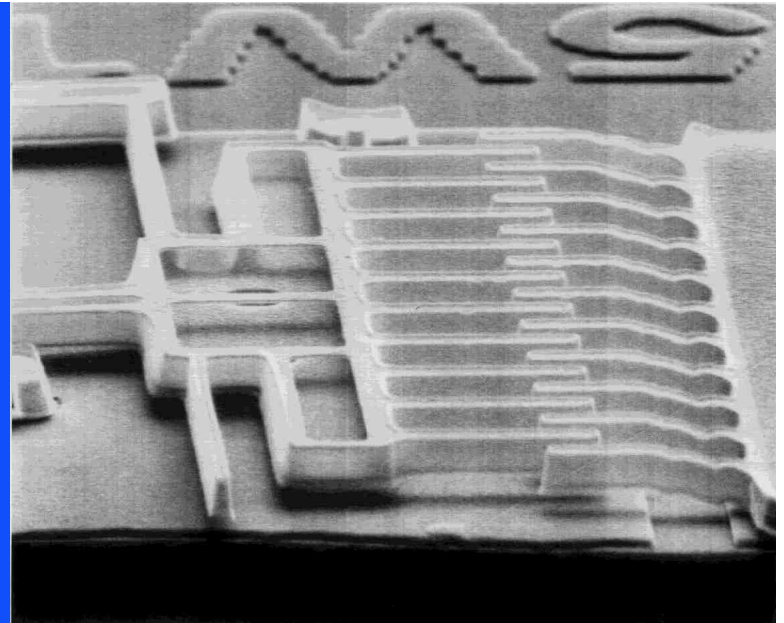
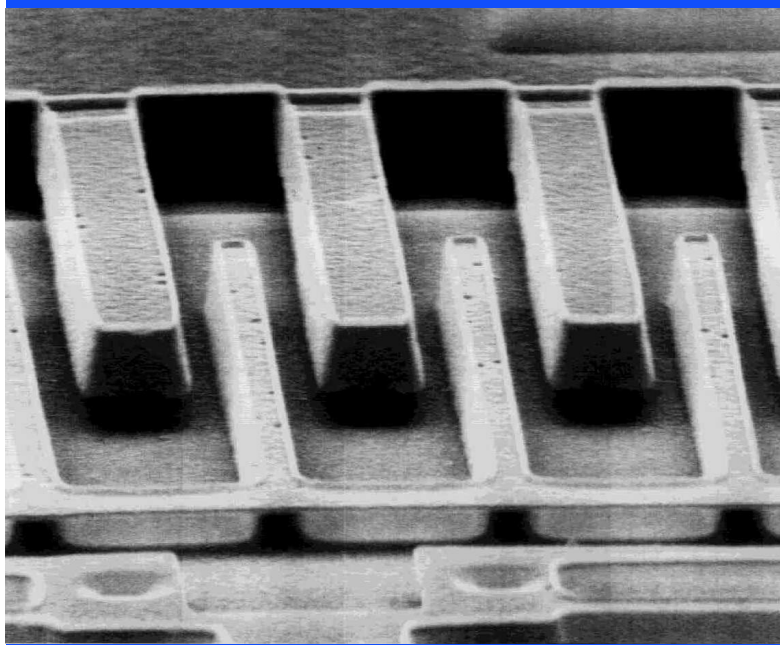
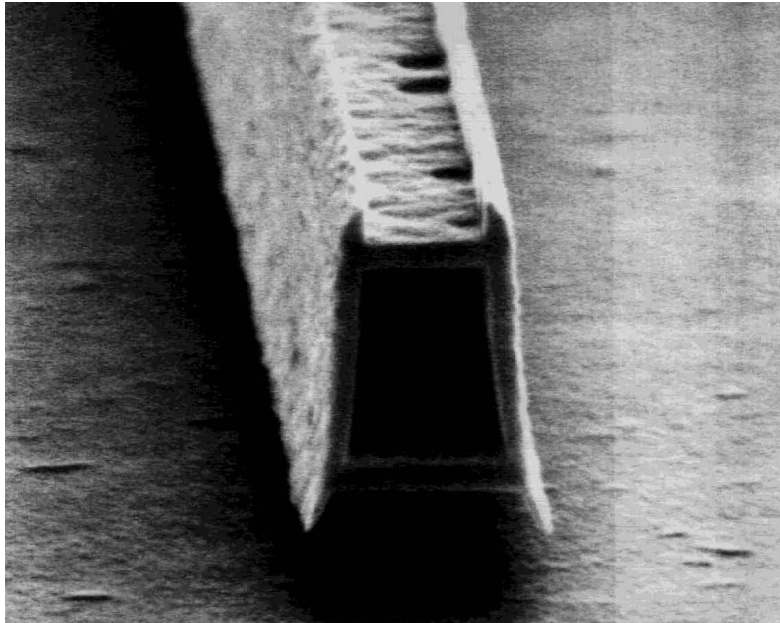
# HOLLOW BEAMS IN POLYSILICON



- Hollow beams of polysilicon can be formed with higher stiffness to mass ratios than solid beams.
- A poly-Si sandwich is formed, followed by sidewall deposition using a blanket poly-Si layer.
- Access holes for HF etching are created and the structures are released.

Reference: Judy, M. W., and Howe, R. T., "Polysilicon Hollow Beam Lateral Resonators," Proceedings of the IEEE Microelectromechanical Systems Conference, Fort Lauderdale, FL, Feb. 1993, pp. 265 - 271.



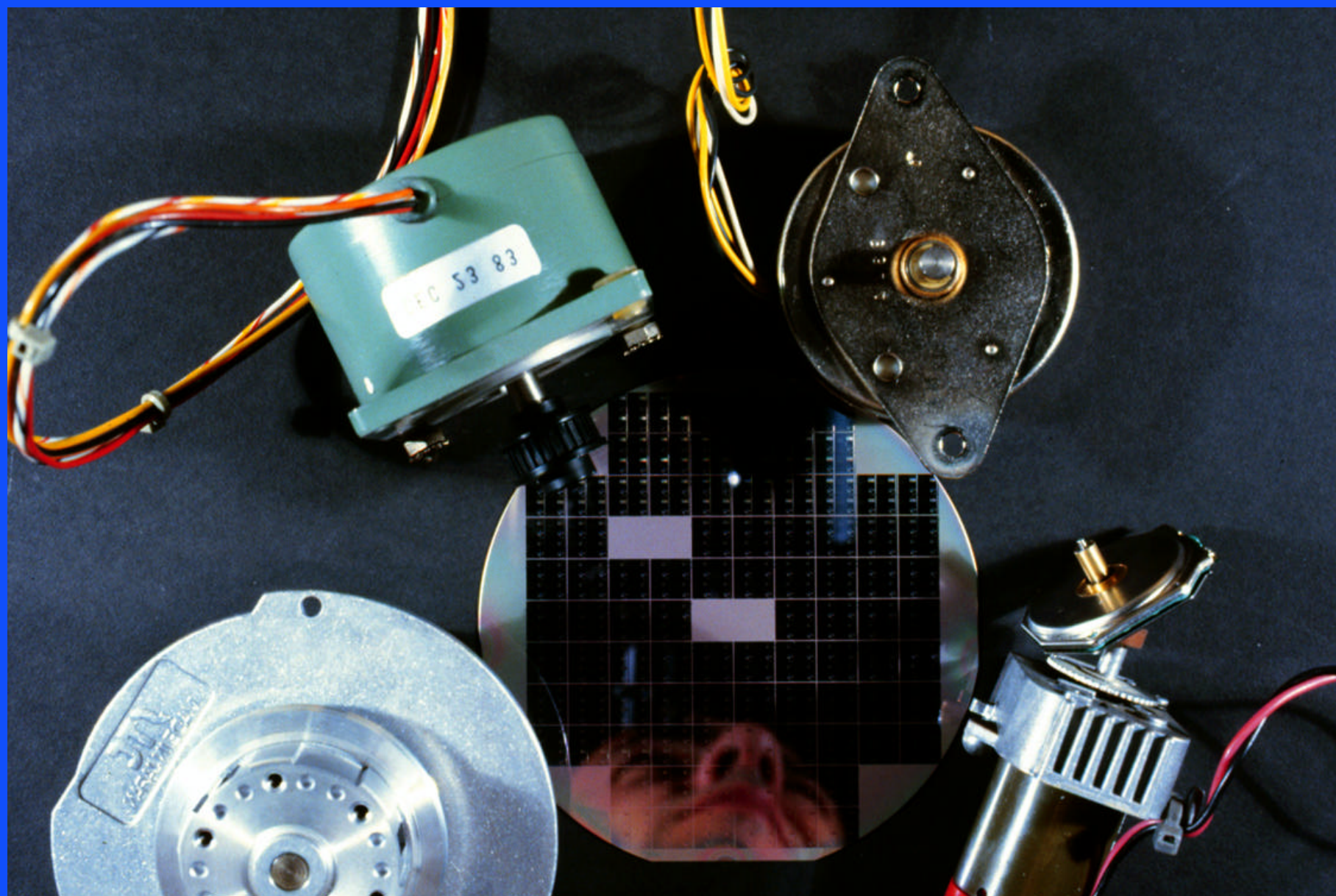


Courtesy Dr. M.  
Judy, Analog  
Devices, Inc.

# ACTUATION IN MECHANICAL TRANSDUCERS

- There is no “perfect” actuation method.
- Electrostatic actuation can generate large forces using low power but is very nonlinear.
- Piezoelectric actuation provides quite linear (although small) displacements at high forces, but may require high voltages (but low power).
- Thermal expansion/bimorph actuators rely on differential thermal expansion of coupled materials and provides linear, moderate forces at high power levels.
- Thermopneumatic, shape memory alloy, vapor bubble, chemical and other actuation schemes are also possible on a micro scale.







<b>Type of Actuator</b>	<b>Stress (MPa)</b>	<b>Strain (%)</b>	<b>Strain Rate (Hz)</b>	<b>Power Density (W/kg)</b>	<b>Efficiency</b>
Electrostatic (Macroscopic Composite)	0.04	> 10	> 1	> 10	> 20
Cardiac Muscle (Human)	0.1	> 40	4	> 100	> 35
Polymer (Polyacrylic Acid/Polyvinyl Alcohol)	0.3	> 40	0.1	> 5	30
Skeletal Muscle (Human)	0.35	> 40	5	> 100	> 35
Polymer (Polyaniline)	180	> 2	> 1	> 1000	> 30
Piezoelectric Polymer (PVDF)	3	0.1	> 1	> 100	< 1
Piezoelectric Ceramic	35	0.09	> 10	> 1000	> 30
Magnetostrictive (Terfenol-D)	70	0.2	1	> 1000	< 30
Shape Memory Alloy (NiTi Bulk Fiber)	> 200	> 5	3	> 1000	> 3

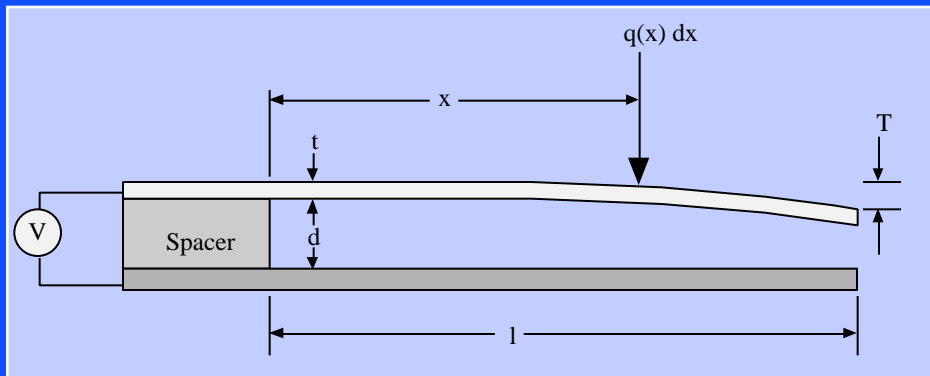
Reference: Hunter, I. W., and Lafontaine, S., "A Comparison of Muscle with Artificial Actuators," Proceedings of the 1992 Solid-State Sensor and Actuator Workshop, Hilton Head Island, South Carolina, June 22 - 25, 1992, pp. 178 - 185.

# ACTUATOR PROPERTIES TO COMPARE

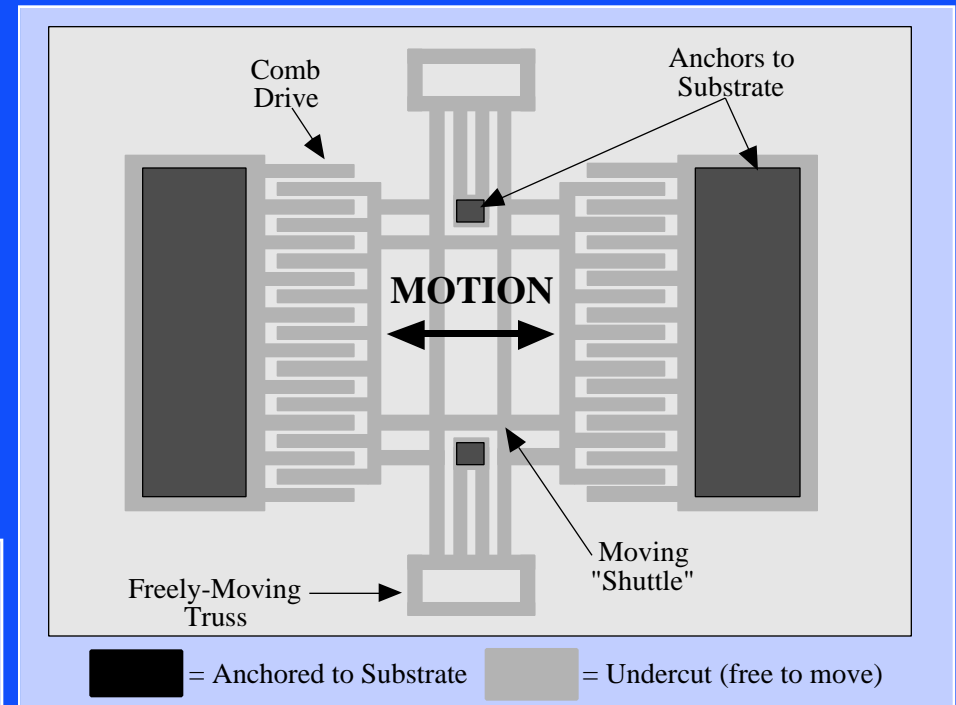
- 1) Power.
- 2) Mechanical efficiency.
- 3) Stress/Strain.
- 4) Robustness (i.e. resistance to mechanical and environmental insults).
- 5) Speed.
- 6) Power-to-mass ratio.
- 7) Linearity.
- 8) Other?

# ELECTROSTATIC ACTUATORS

- Electrostatic actuators are very common in micromachined systems due to their simplicity.
- They are highly nonlinear and may require high voltages.



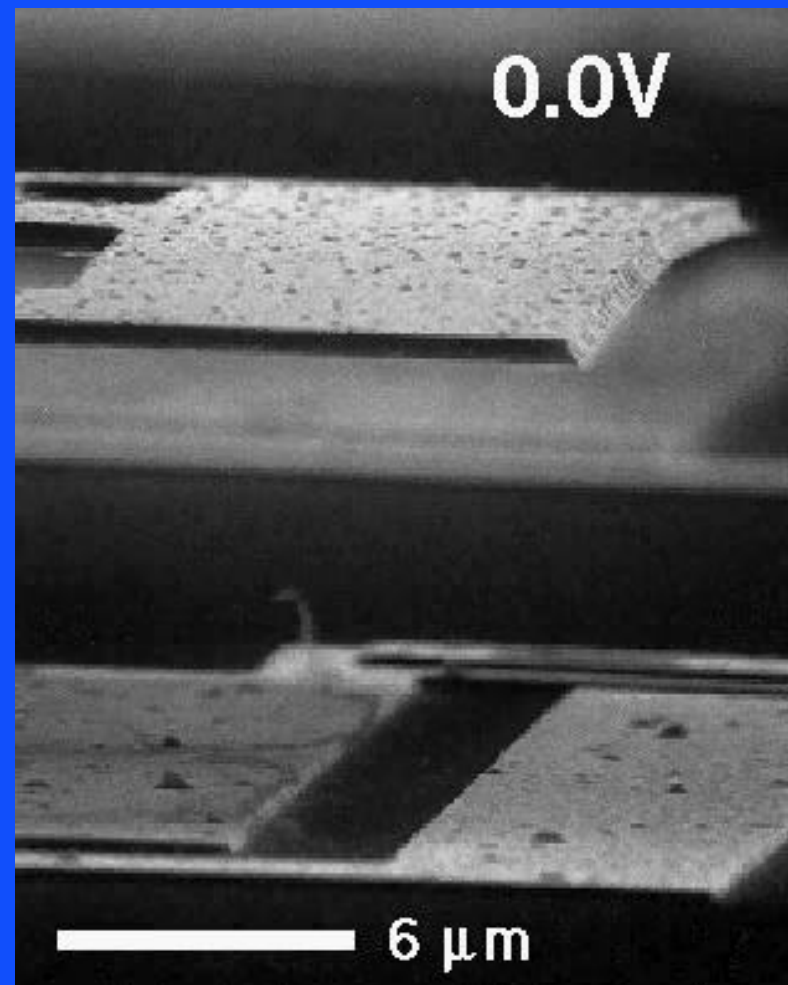
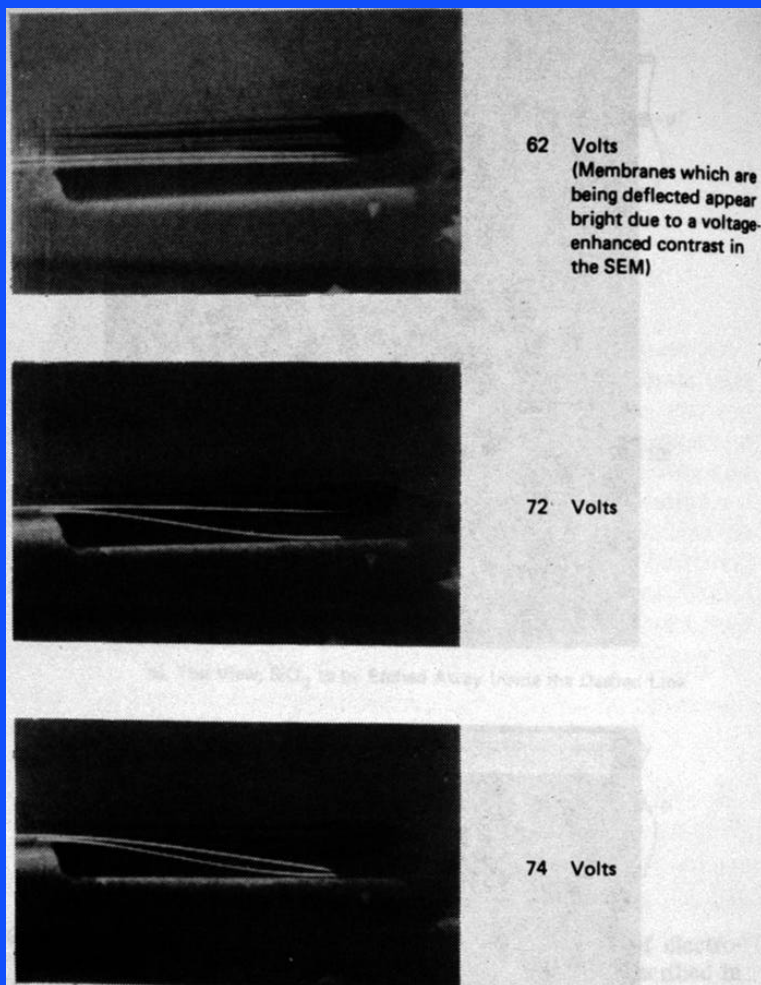
Reference: Petersen, K. E., "Dynamic Micromechanics on Silicon: Techniques and Devices," IEEE Transactions on Electron Devices, vol. ED-25, no. 10, Oct. 1978, pp. 1241 - 1250.



Reference: Judy, M. W., and Howe, R. T., "Polysilicon Hollow Beam Lateral Resonators," Proceedings of the IEEE Microelectromechanical Systems Conference, Fort Lauderdale, FL, Feb. 1993, pp. 265 - 271.

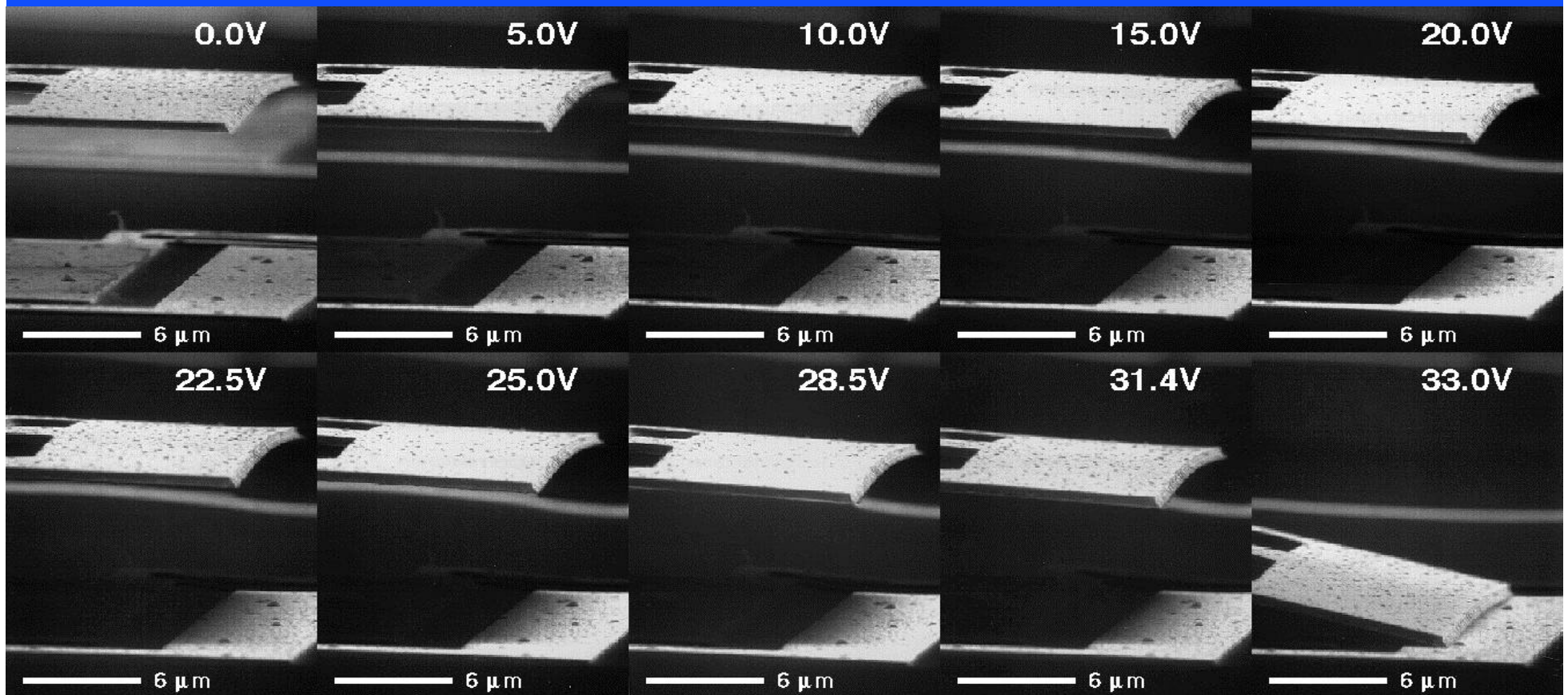


# ELECTROSTATIC NONLINEARITY

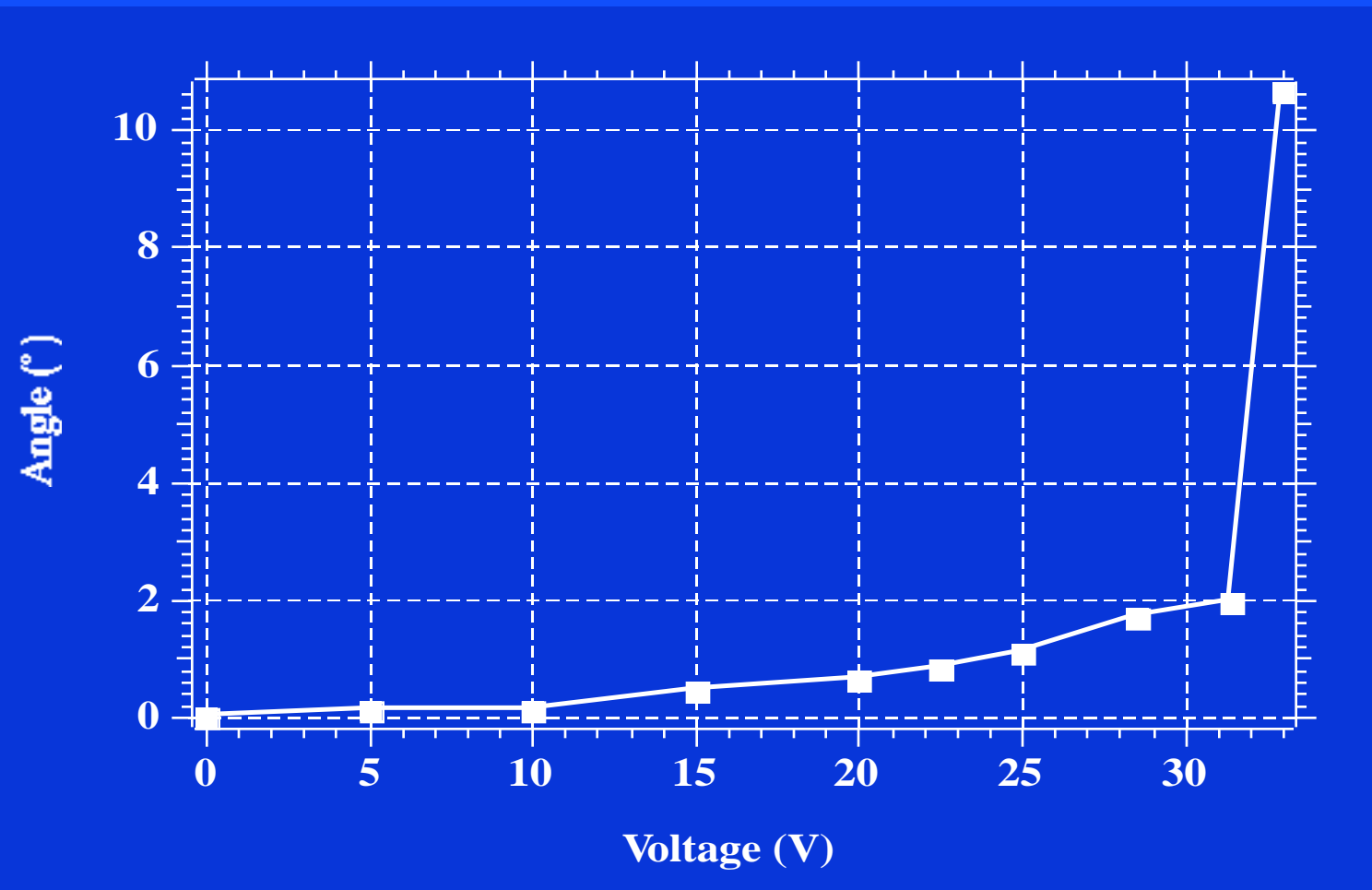


Source (left): Petersen, K. E, "Dynamic Micromechanics on Silicon: Techniques and Devices," IEEE Transactions on Electron Devices, vol. ED-25, no. 10, Oct. 1978, pp. 1241 - 1250.

# SEM ACTUATION STUDIES

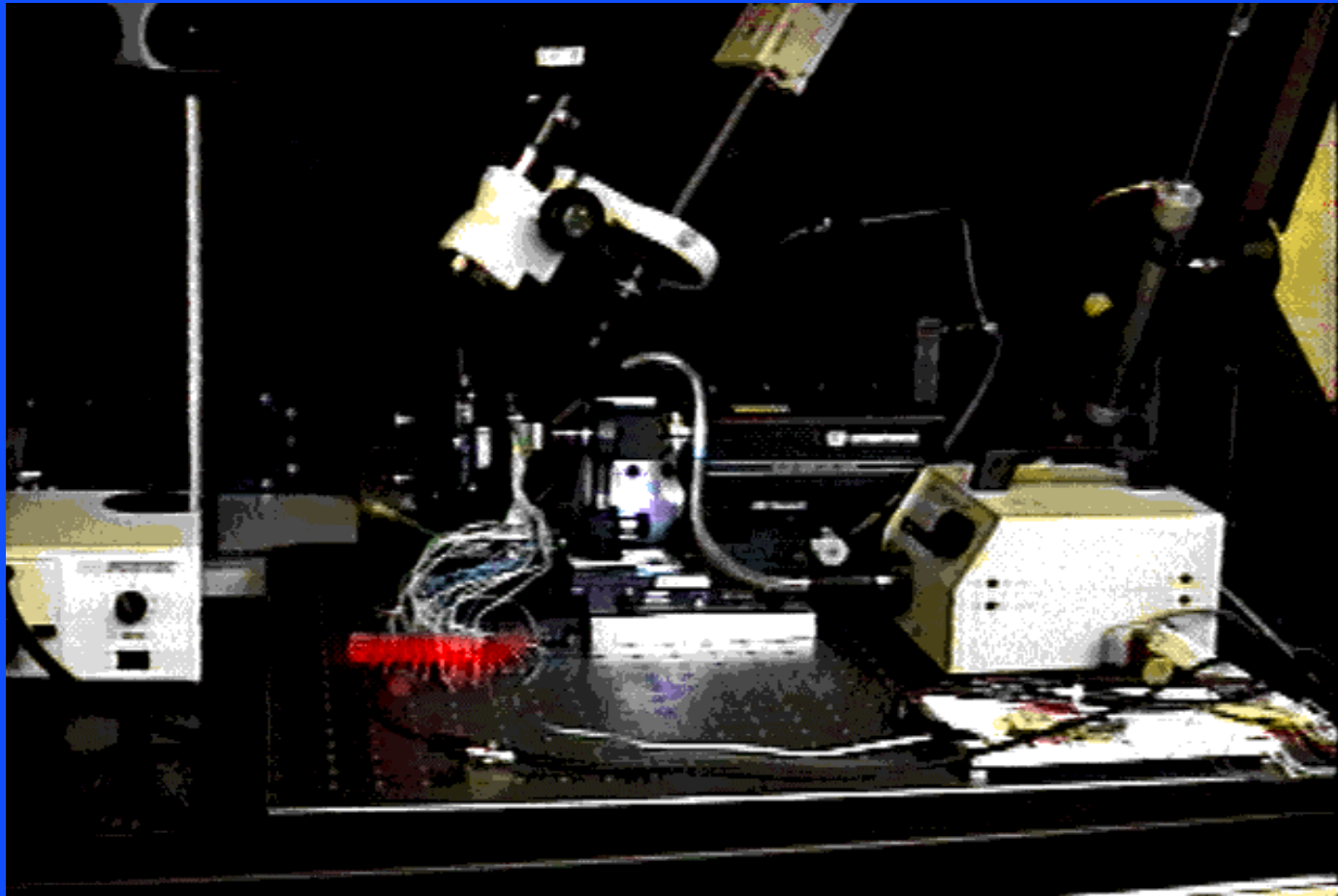


# ANGLE VS. VOLTAGE - SEM





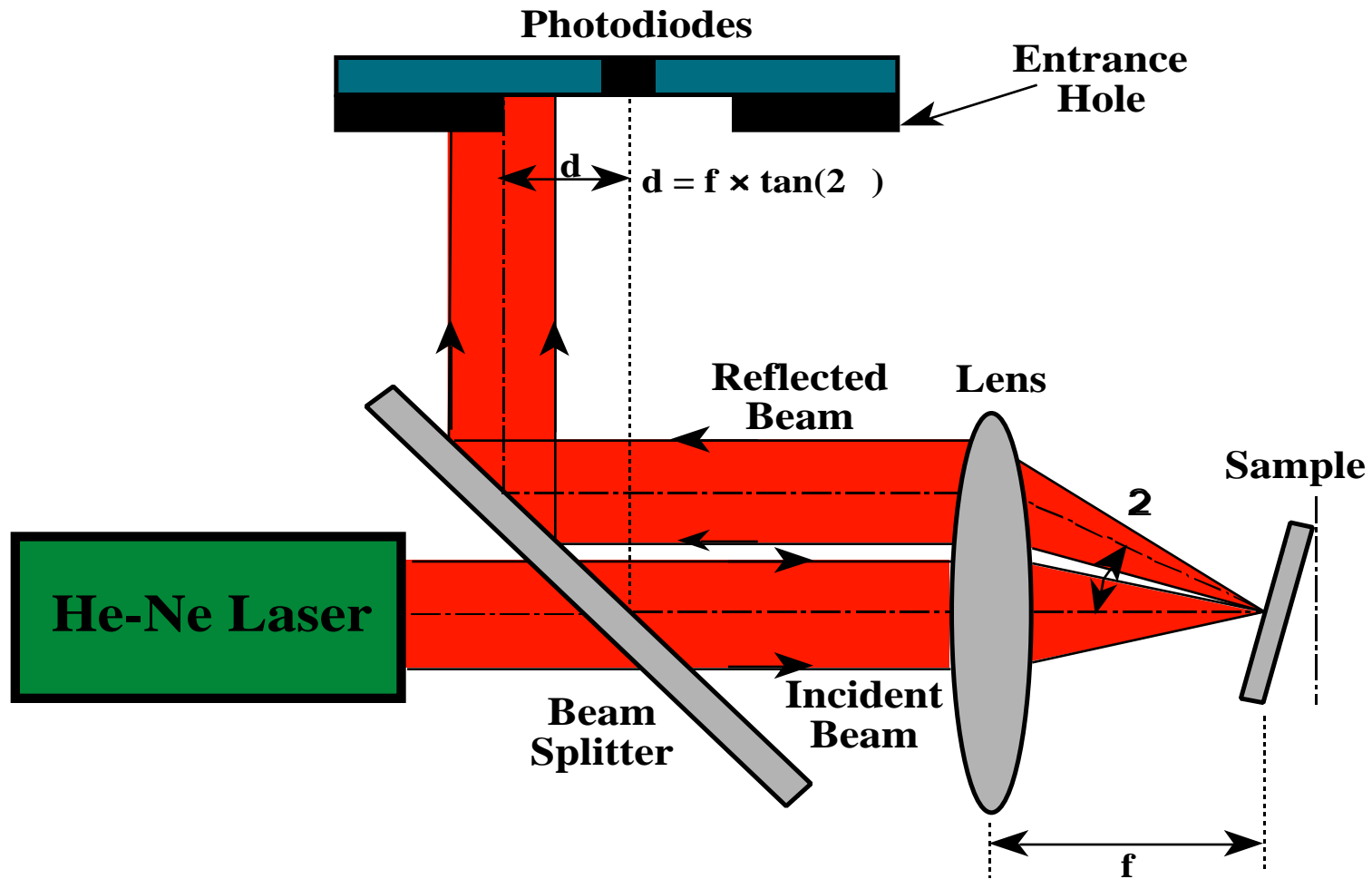
# REAL-TIME OPTICAL DEFLECTION MEASUREMENT SYSTEM



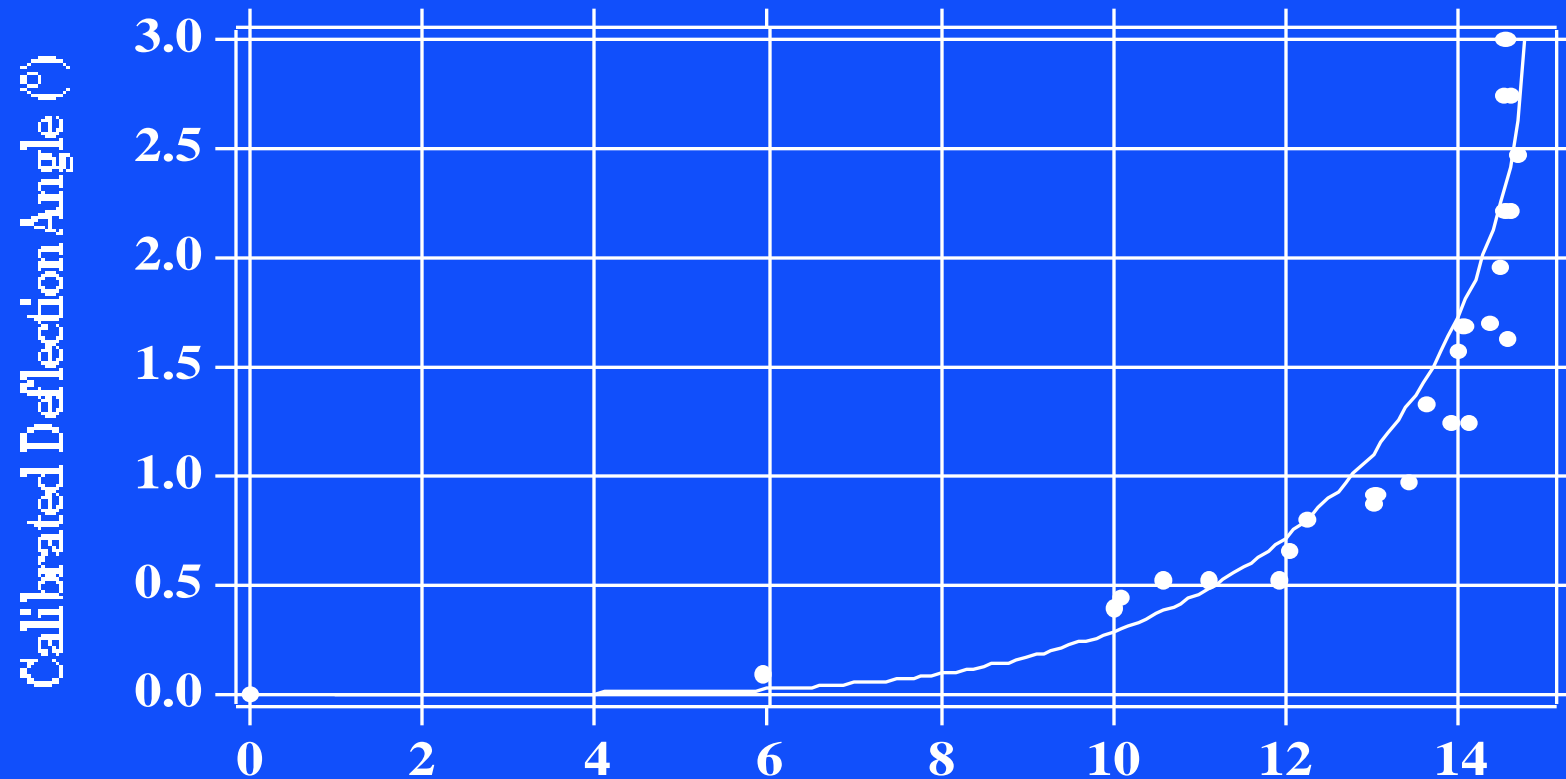
Reference: Honer, K. A., Maluf, N. I., Martinez, E., and Kovacs, G. T. A., "A High-Resolution Laser-Based Deflection Measurement System for Characterizing Aluminum Electrostatic Actuators," Digest of Technical Papers from Transducers '95/Eurosensors IX, Vol. 1, June 25 - 29, 1995, Stockholm, Sweden, pp. 308 - 311.

G. Kovacs © 2000

# OPTICAL DEFLECTION MEASUREMENT



# MEASURED $\theta$ - V CURVE



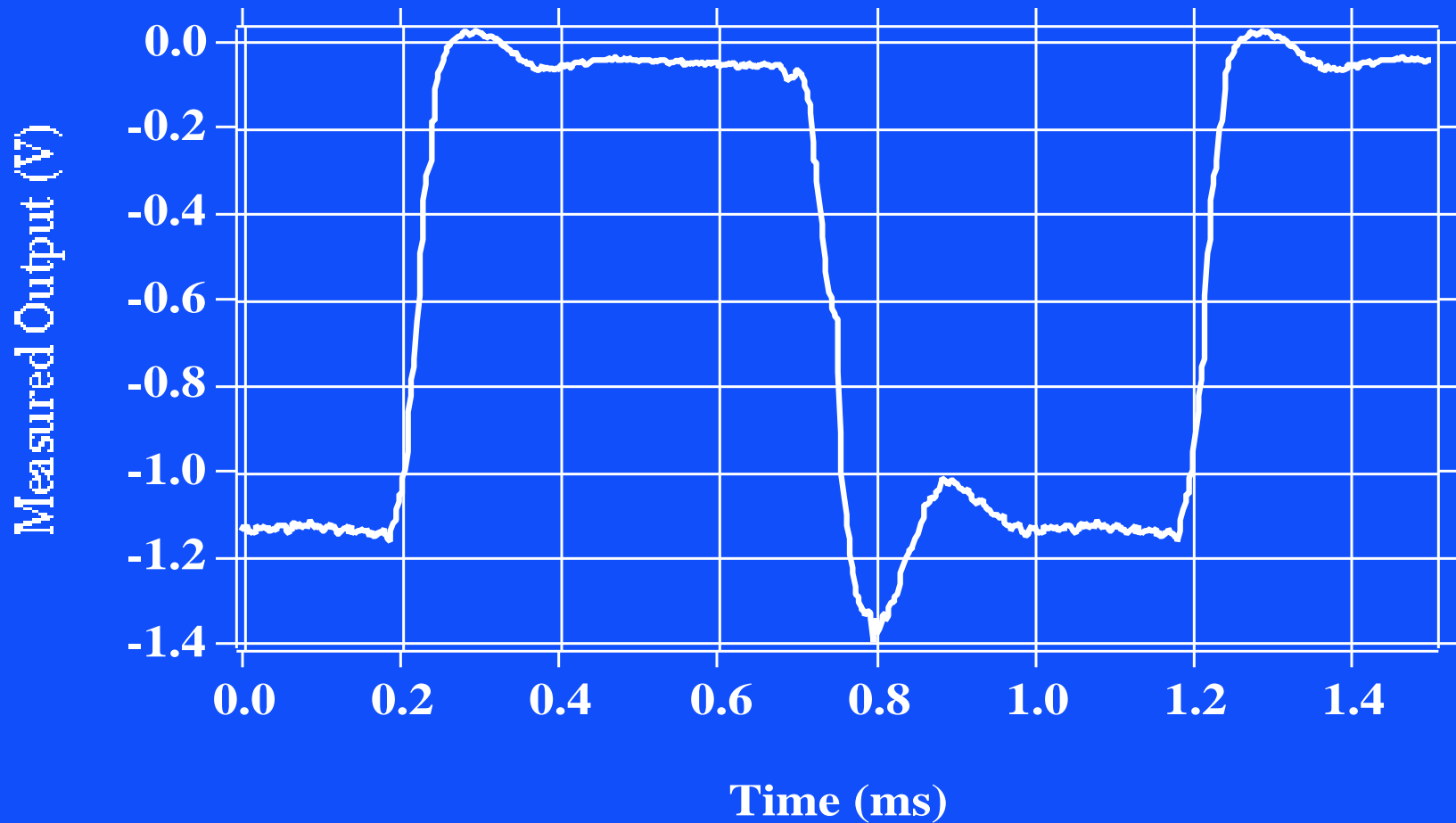
• Measured  
— Best fit

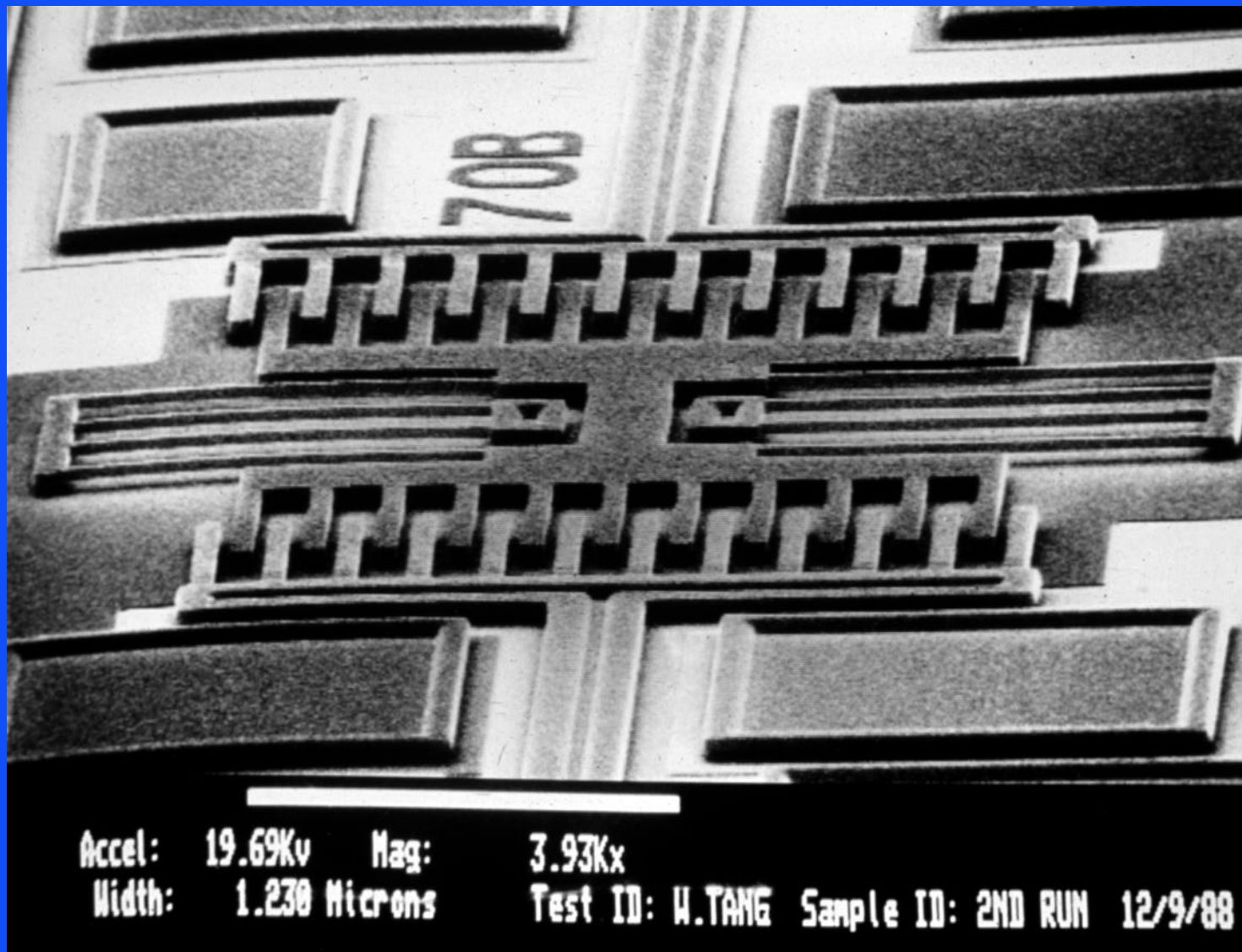
Applied Voltage (V)

$$= 0.035 \arcsin \left( \left[ \frac{V}{15} \right]^4 \right)$$



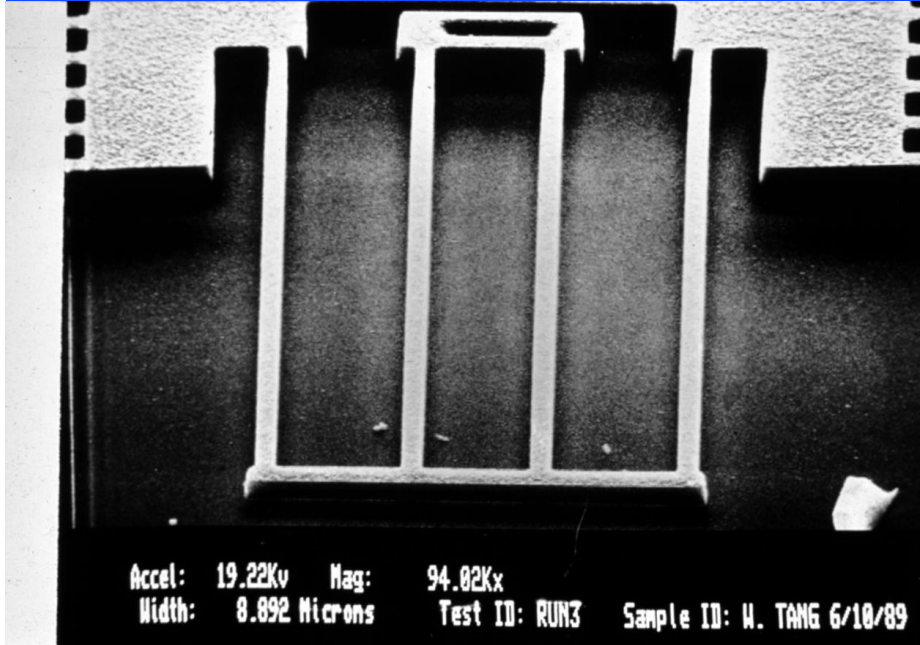
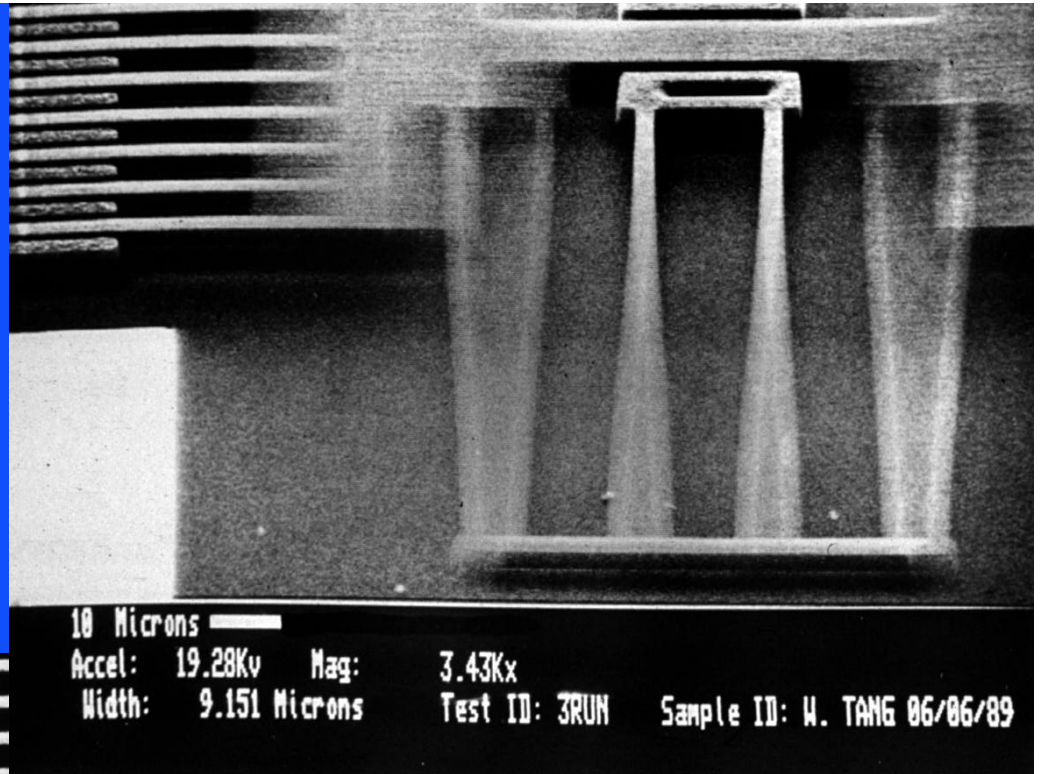
# MEASURED TIME-DOMAIN RESPONSE





Source: Tang, W. C., Nguyen, H., Judy, M. W., and Howe, R. T., "Electrostatic-Comb Drive of Lateral Polysilicon Resonators," Sensors and Actuators, vol. A21, nos. 1 - 3, Feb. 1990, pp. 328 - 331. Courtesy Prof. R. Howe, U.C. Berkeley.

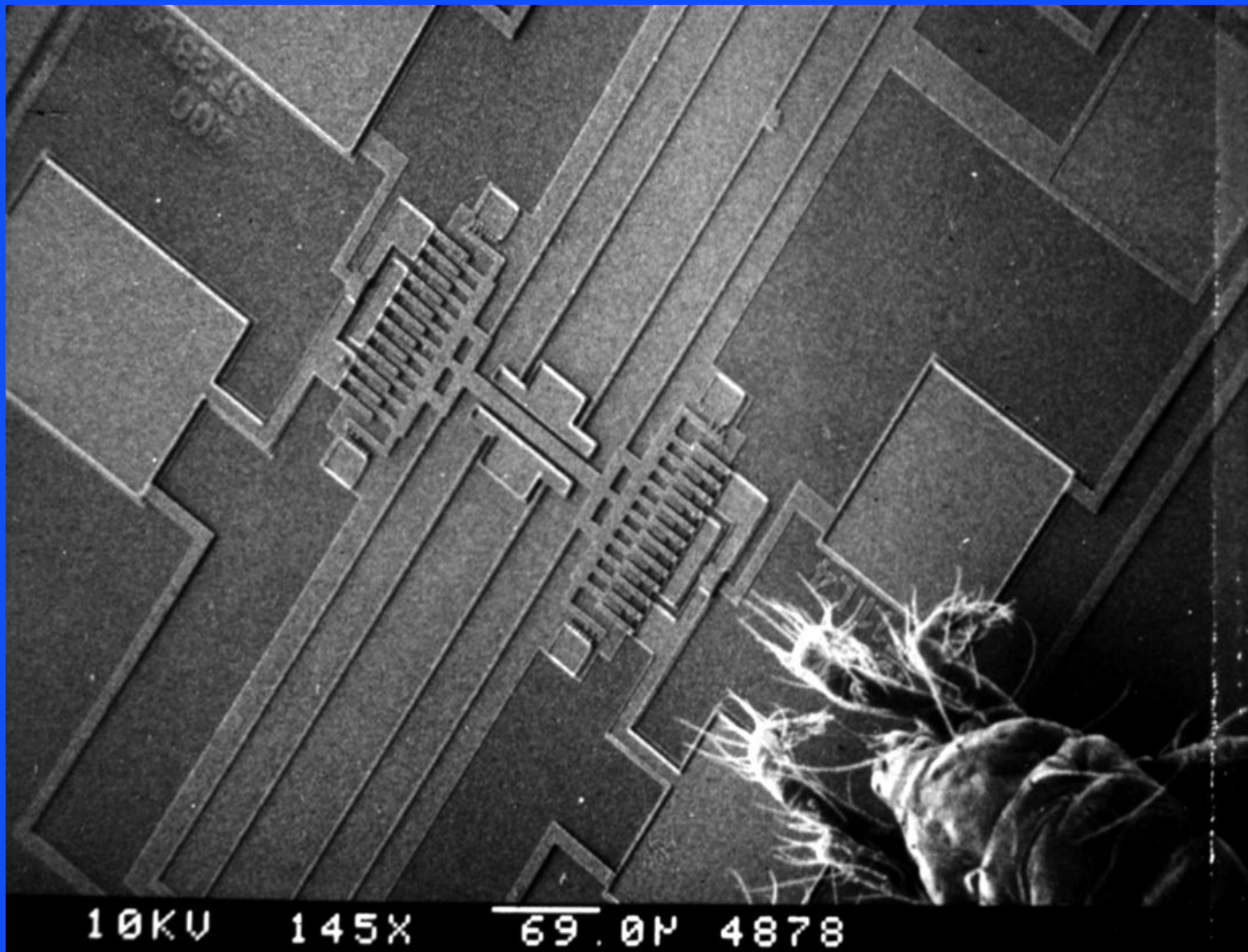
G. Kovacs © 2000



Source: Tang, W. C., Nguyen, H., Judy, M. W., and Howe, R. T.,  
“Electrostatic-Comb Drive of Lateral Polysilicon Resonators,”  
Sensors and Actuators, vol. A21, nos. 1 - 3, Feb. 1990, pp. 328 - 331.

Courtesy Prof. R. Howe, U.C. Berkeley.





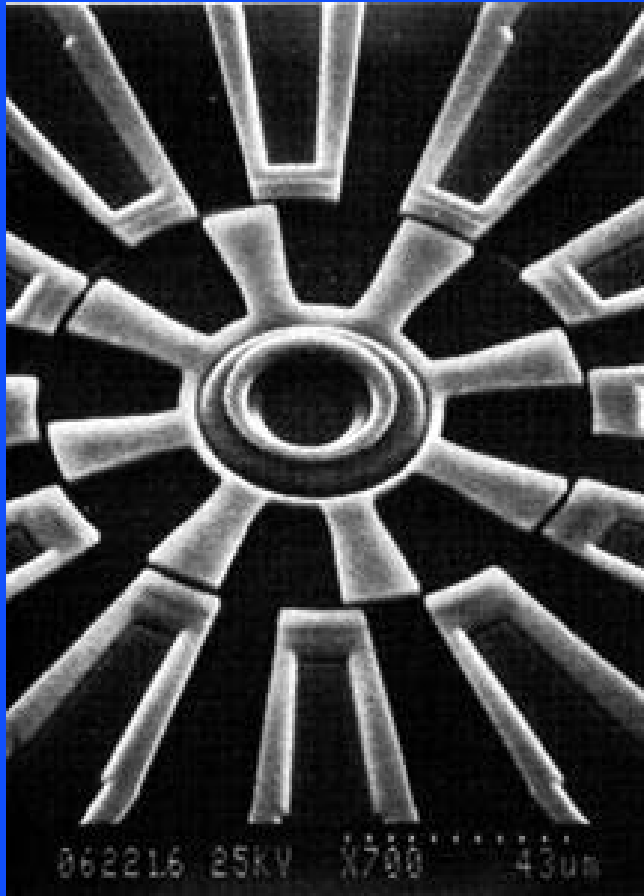
Courtesy Prof. R. Howe, U.C. Berkeley.

G. Kovacs © 2000

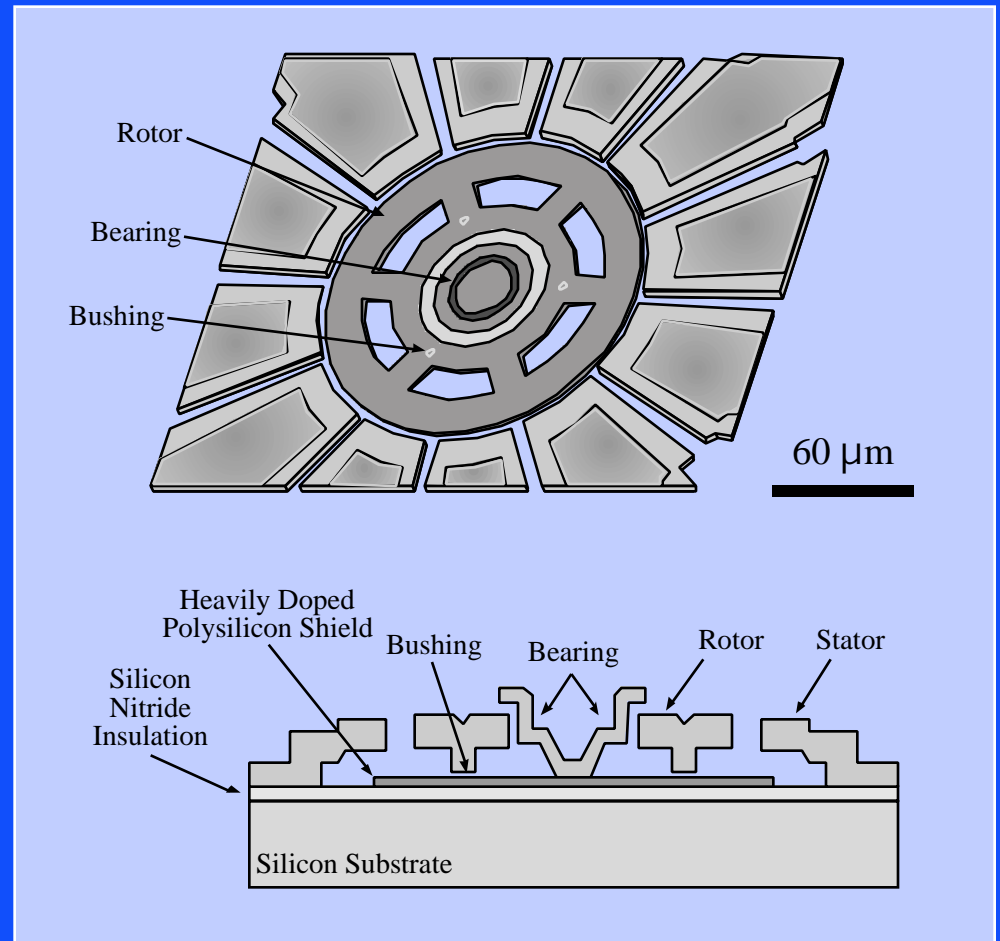
# ELECTROSTATIC MICROMOTORS

- Despite initial enthusiasm, these devices have not emerged in any products after more than a decade.
- Rotary motors have thus far had limited lifetimes, very high speeds, and limited torques.
- Mehregany, et al., (Case Western) have applied them to optical scanning, and optical applications may be the most practical since the motors only have to move themselves.
- Several groups have also applied linear micromotors (“steppers”) to positioning optical components.

# ELECTROSTATIC MICROMOTORS

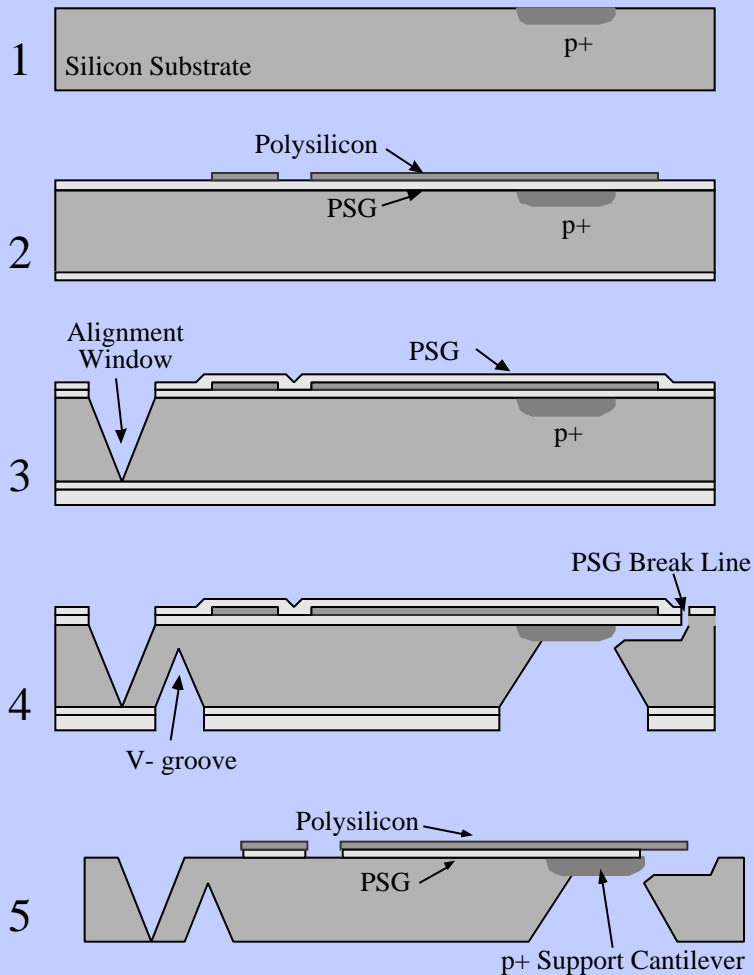


Source (SEM): Mehregany, M., Bart, S. F., Tavrow, L. S., Lang, J. H., Senturia, S. D., and Schlecht, M. F., "A Study of Three Microfabricated Variable-Capacitance Micromotors," *Sensors and Actuators*, vol. A21, nos. 1 - 3, Feb. 1990, pp. 173 - 179.

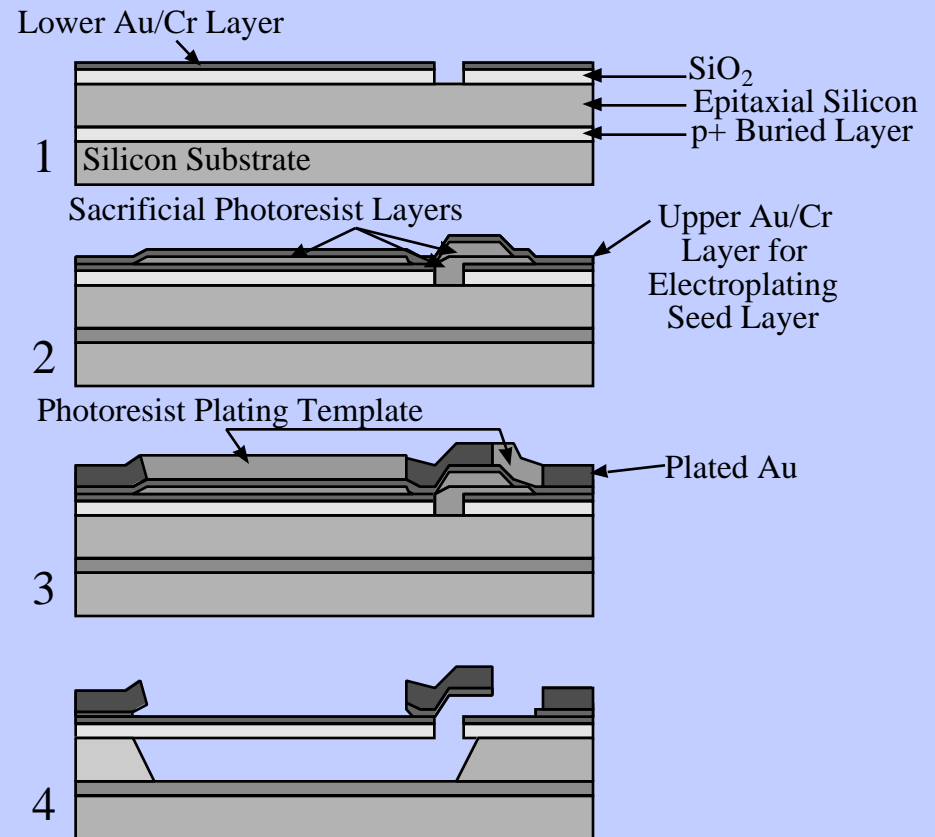




# OTHER ELECTROSTATIC ACTUATORS



Reference: Kim, C.-J., Pisano, A. P., and Muller, R. S., "Silicon-Processed Overhanging Microgripper." *Journal Of Microelectromechanical Systems*, vol. 1, no. 1, Mar. 1992, pp. 31 - 36.

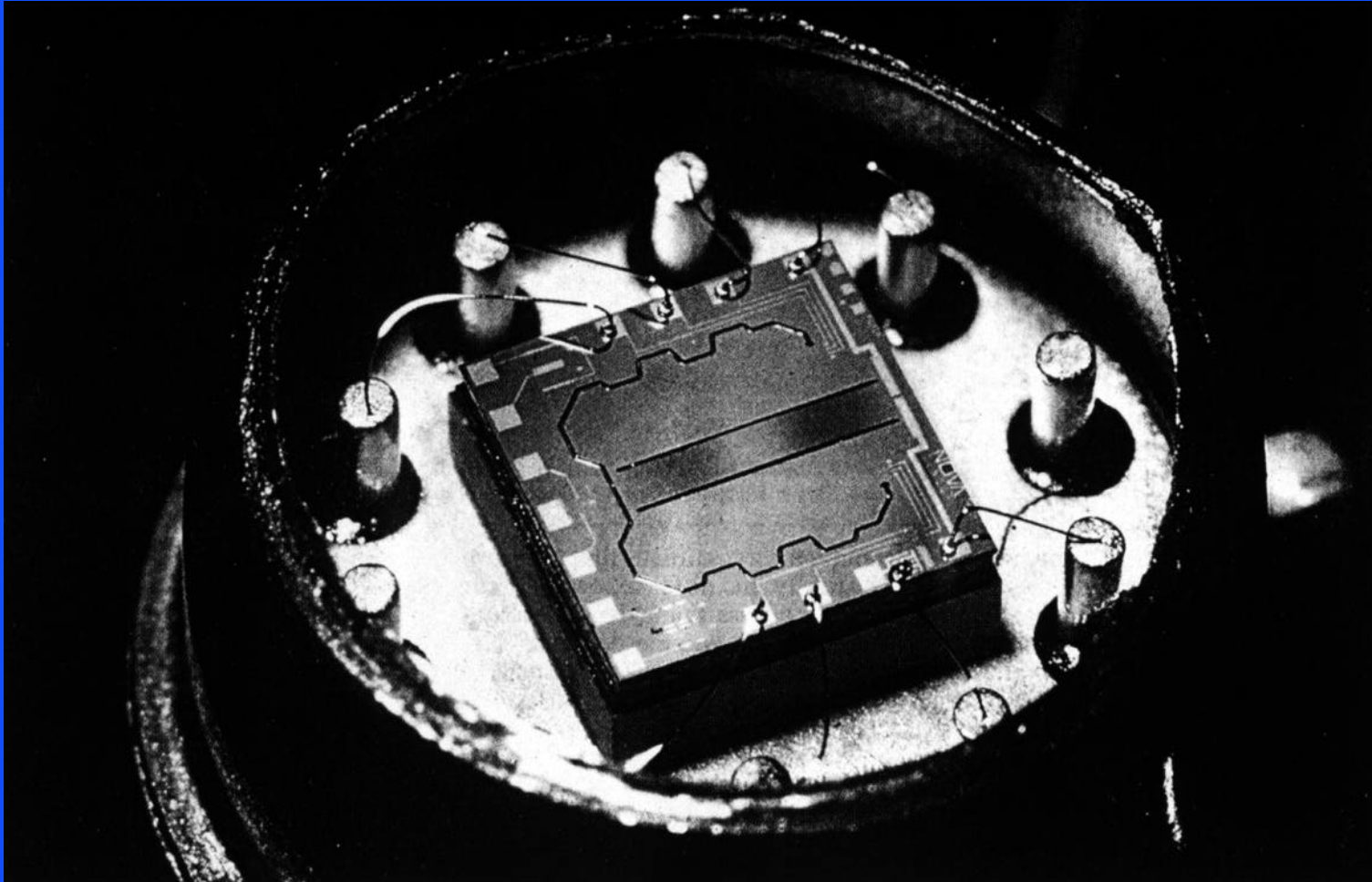


Reference: Petersen, K. E., "Silicon as a Mechanical Material," *Proceedings of the IEEE*, vol. 70, no. 5, May, 1982, pp. 420 - 457.

# THERMAL ACTUATORS

- They require high power, but can generate large forces in a linear fashion (proportional to dissipated power).
- They can be driven using embedded thin film heaters, optically, or using dielectric loss heating.
- Simple “monomorph” devices make use of linear expansion of beams.
- Bimorph devices make use of differential thermal expansion of two bonded layers.
- Phase-change devices make use of bubble formation.

# THERMAL SELF-TEST IN ACCELEROMETER

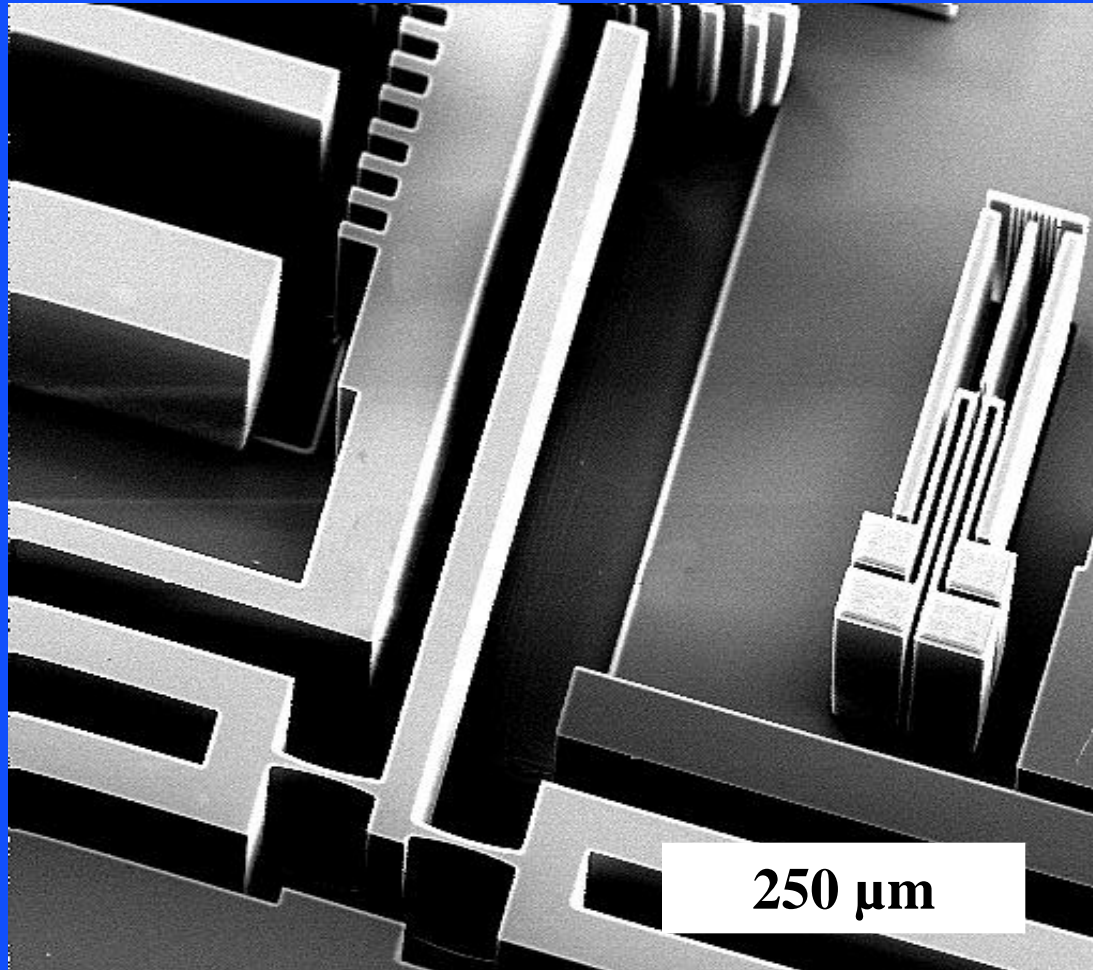


Courtesy Lucas NovaSensor.

G. Kovacs © 2000

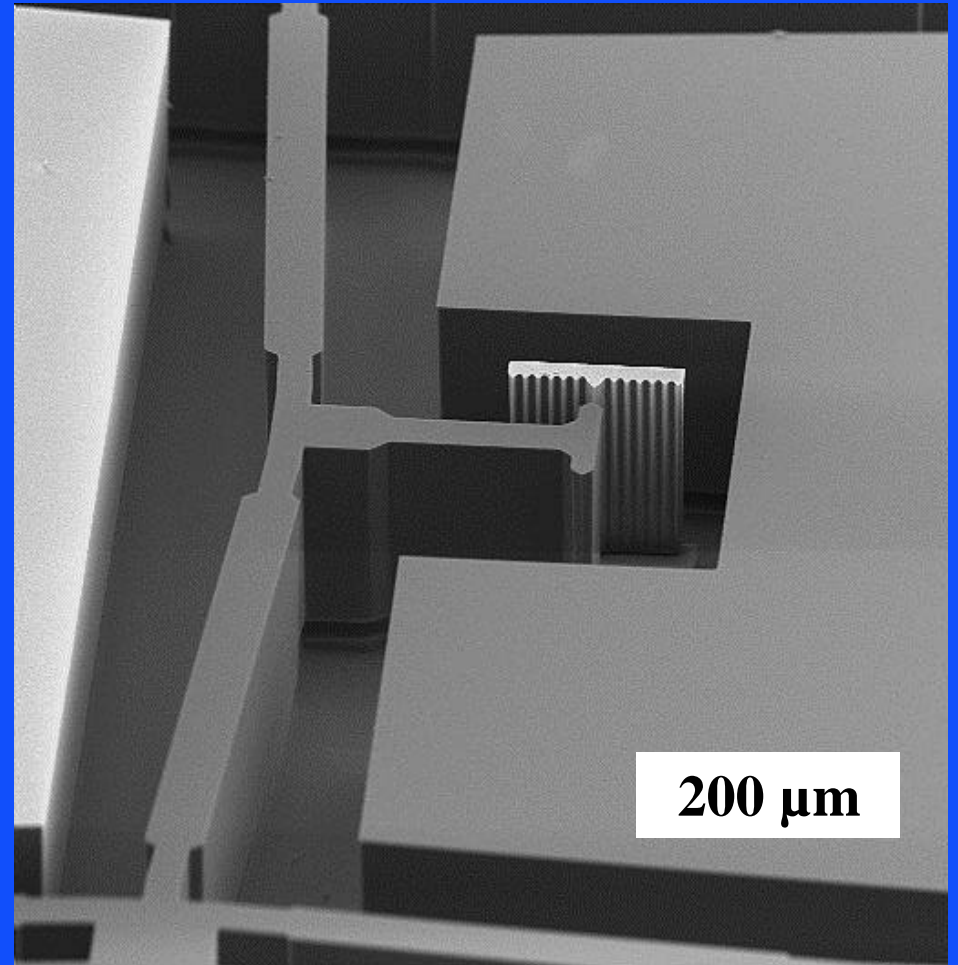
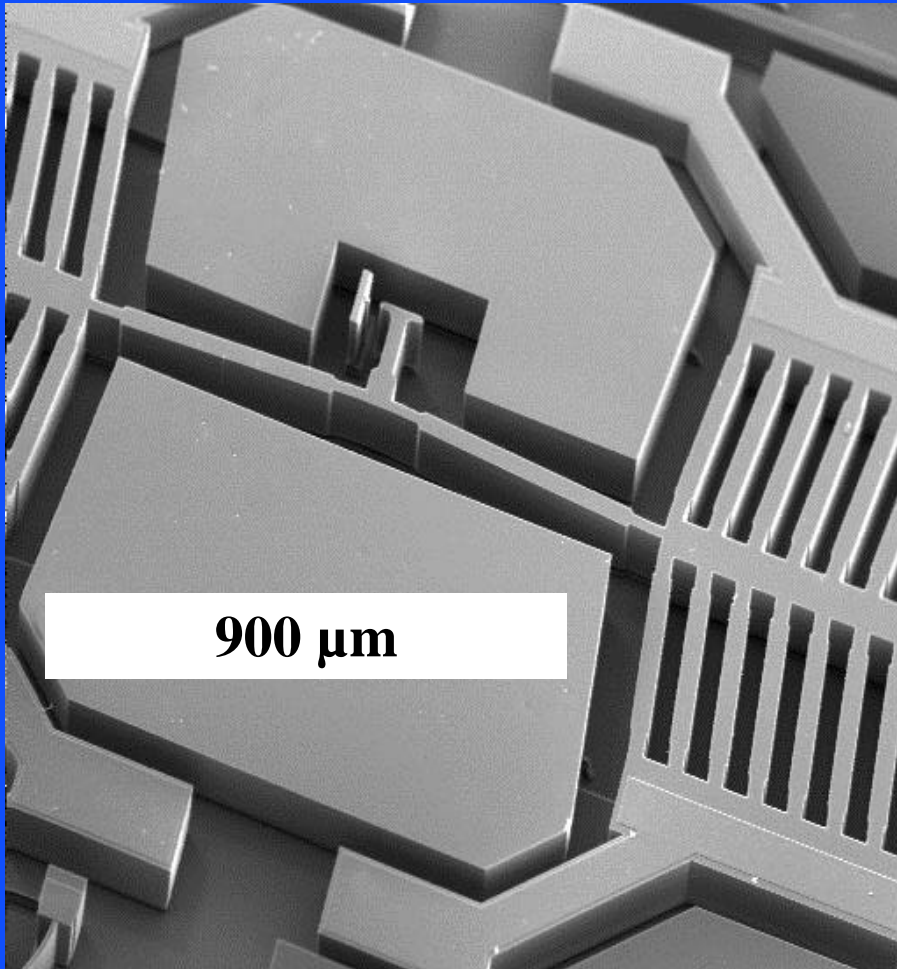


# SFB/DRIE THERMAL ACTUATORS

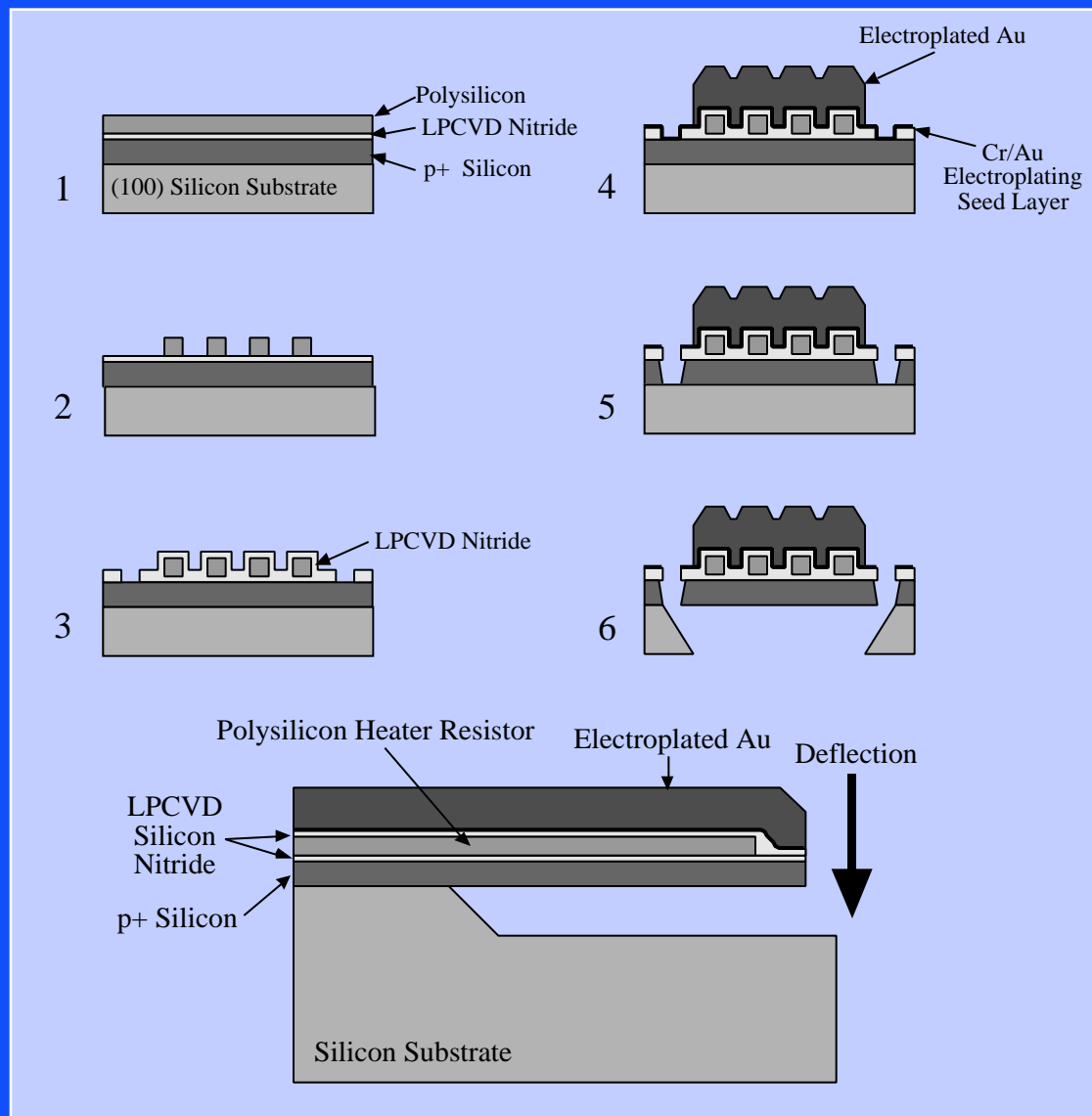


- 100  $\mu\text{m}$  tall
- 10  $\mu\text{m}$  wide tethers
- 100  $\mu\text{m}$  motion

Courtesy Lucas NovaSensor.



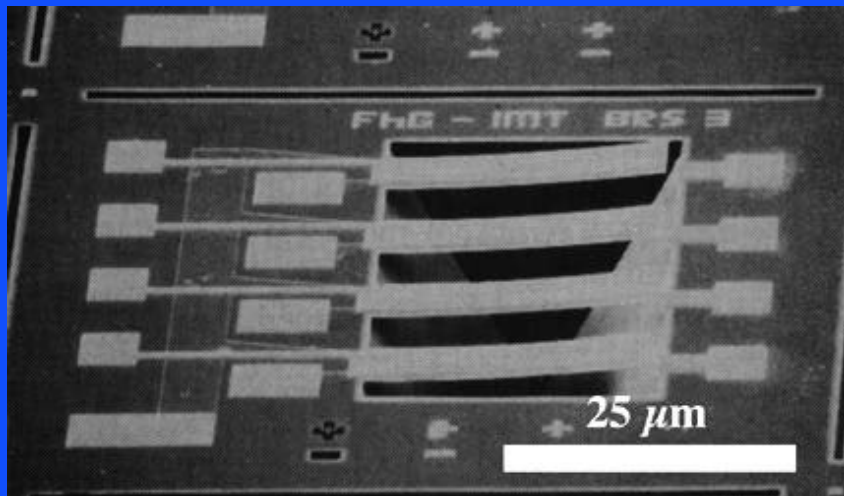
Courtesy Lucas NovaSensor.



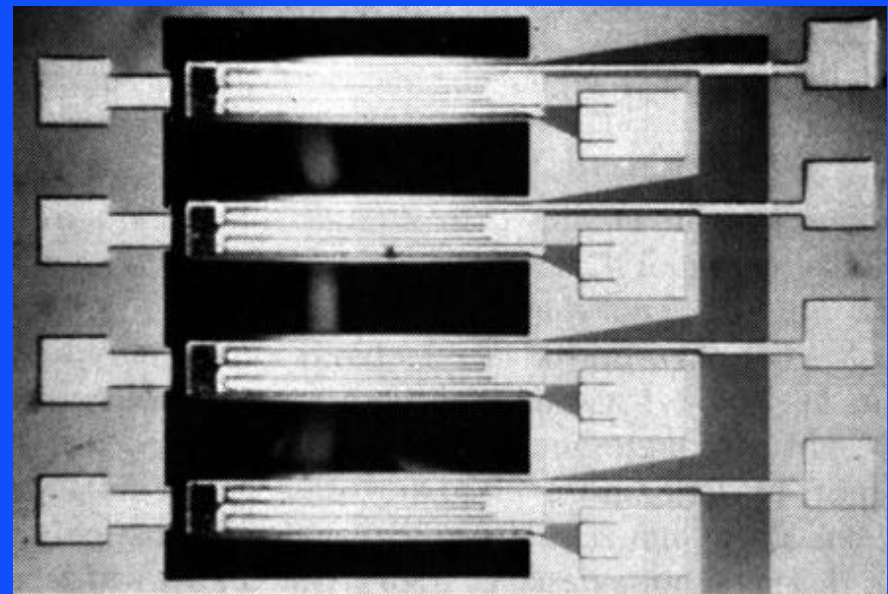
Reference: Riethmüller, W. and Benecke, W., "Thermally Excited Silicon Microactuators," IEEE Transactions on Electron Devices, vol. 35, no. 6, June 1988, pp. 758 - 763.



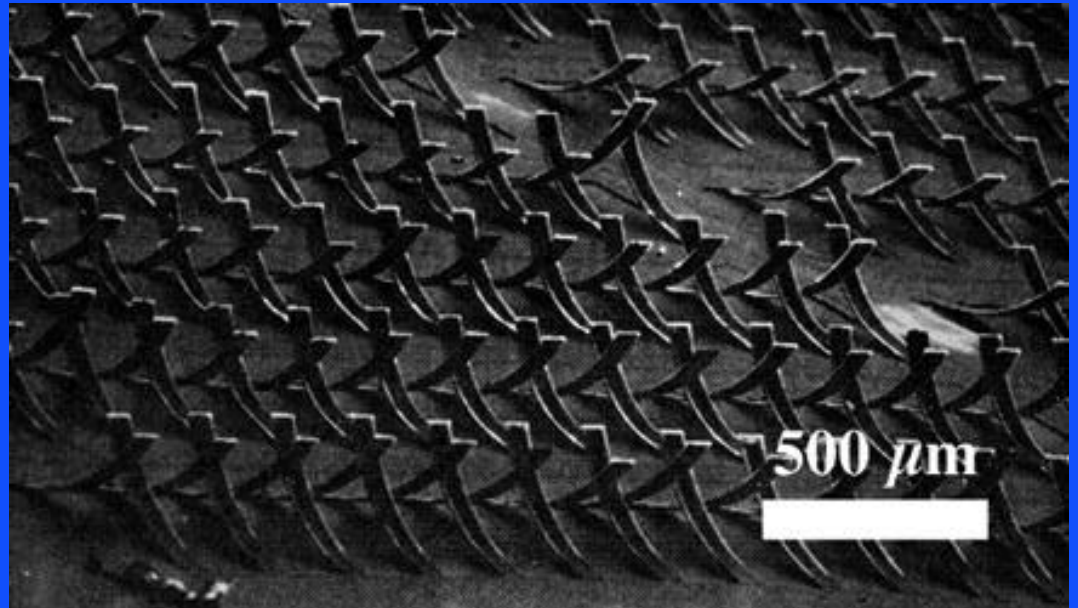
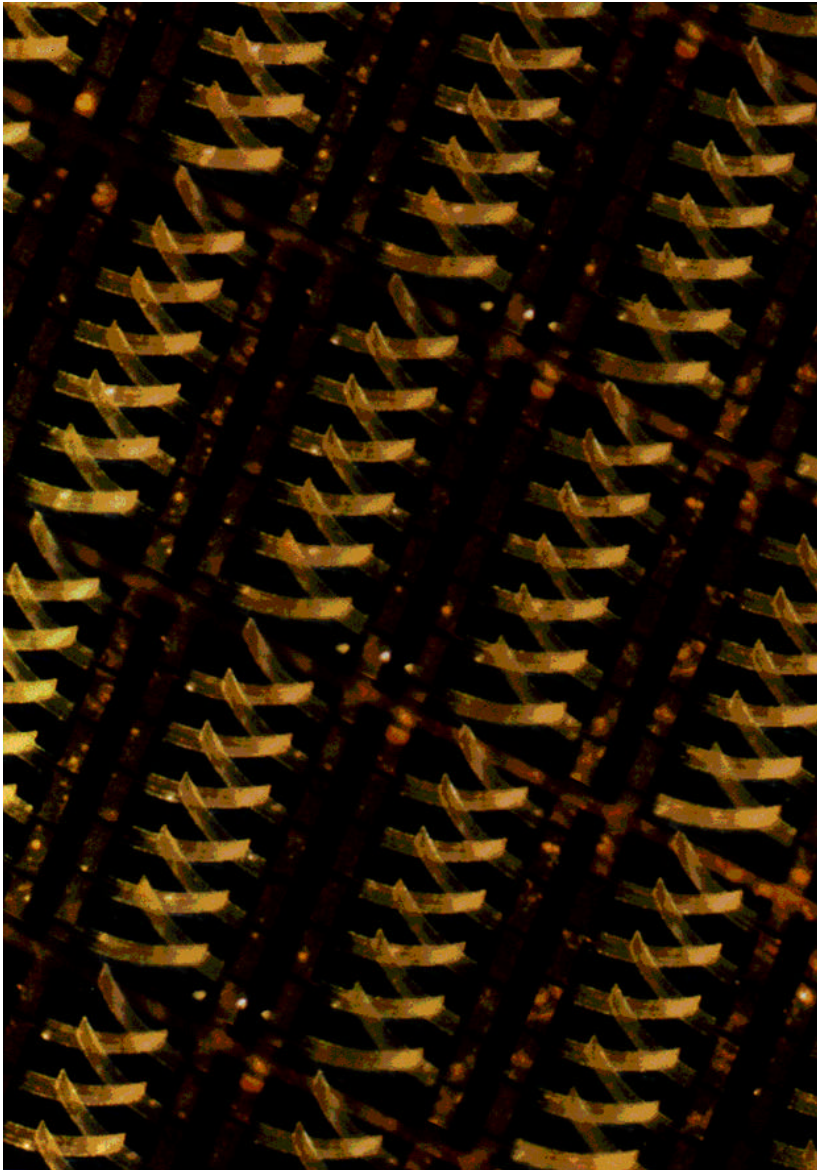
# THERMAL BIMORPHS



Source: Riethmüller, W. and Benecke, W., "Thermally Excited Silicon Microactuators," IEEE Transactions on Electron Devices, vol. 35, no. 6, June 1988, pp. 758 - 763.

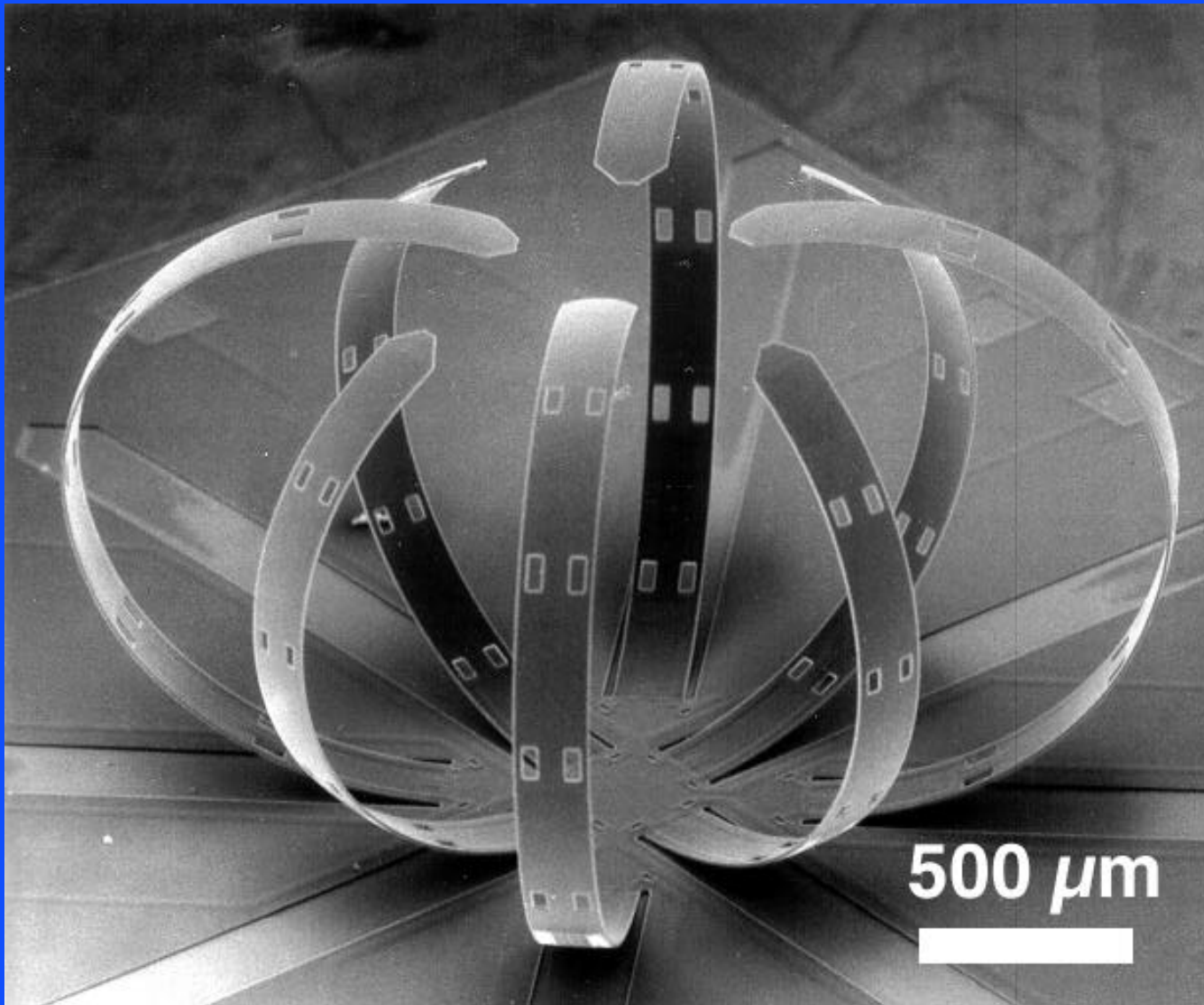


# BIMORPH CILIARY ACTUATORS

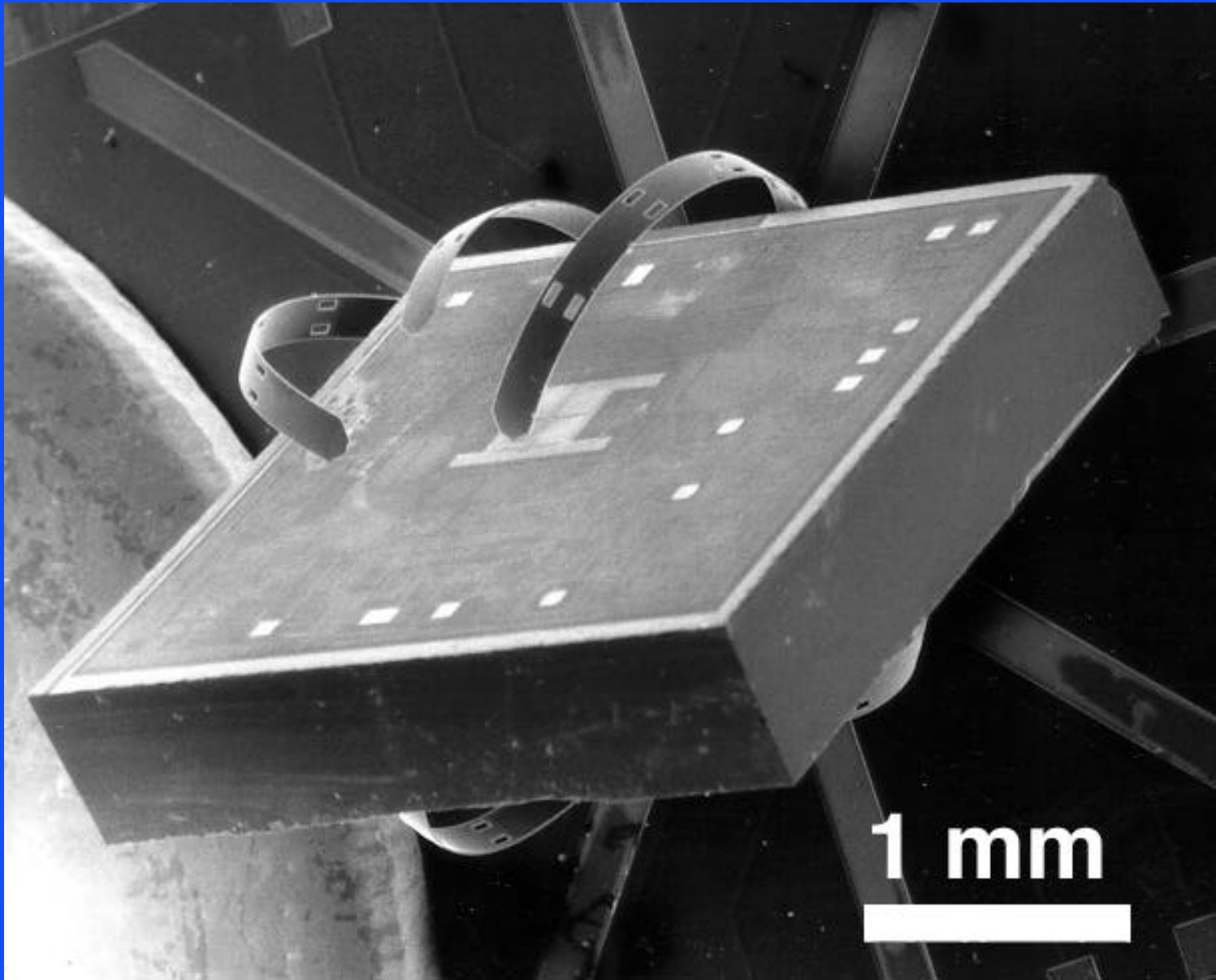


Courtesy Prof. H. Fujita, University of Tokyo.

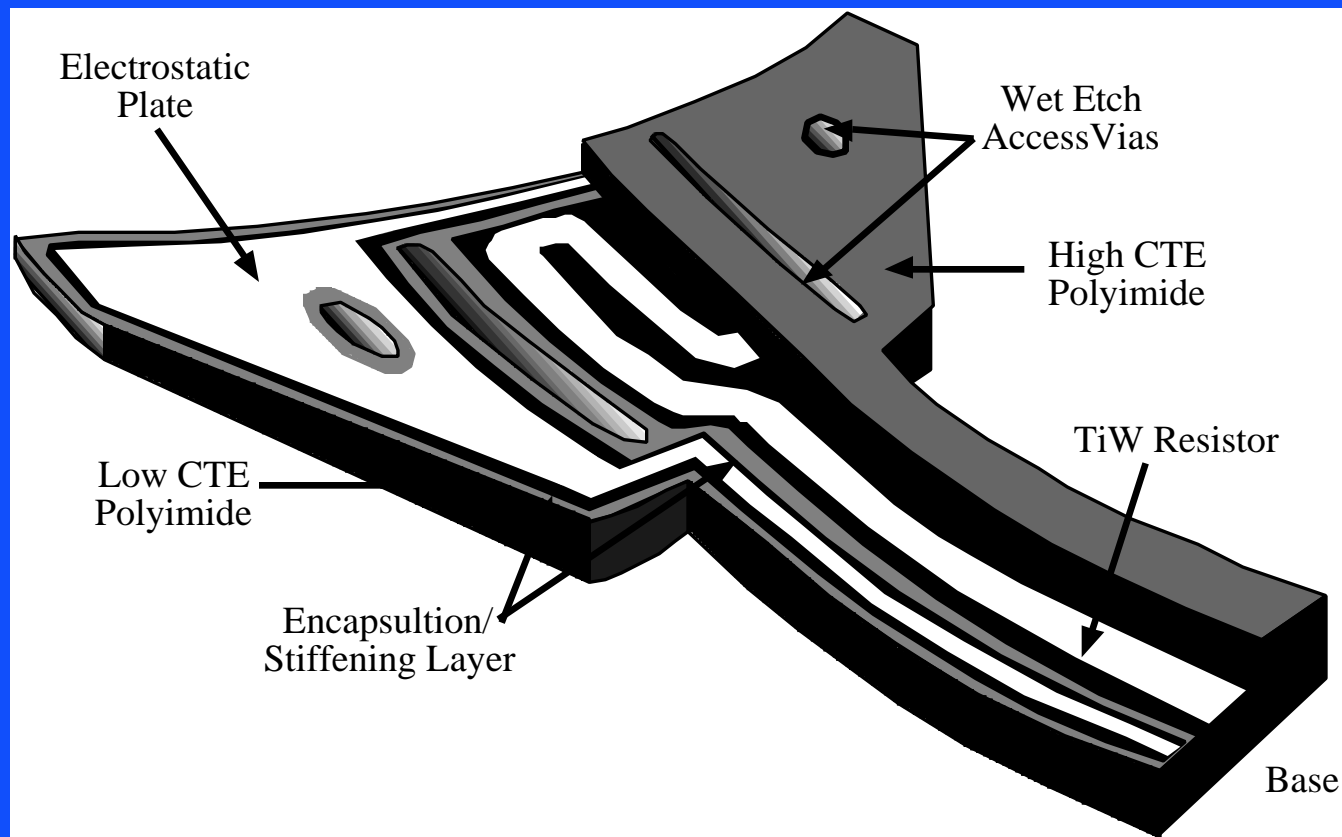
G. Kovacs © 2000





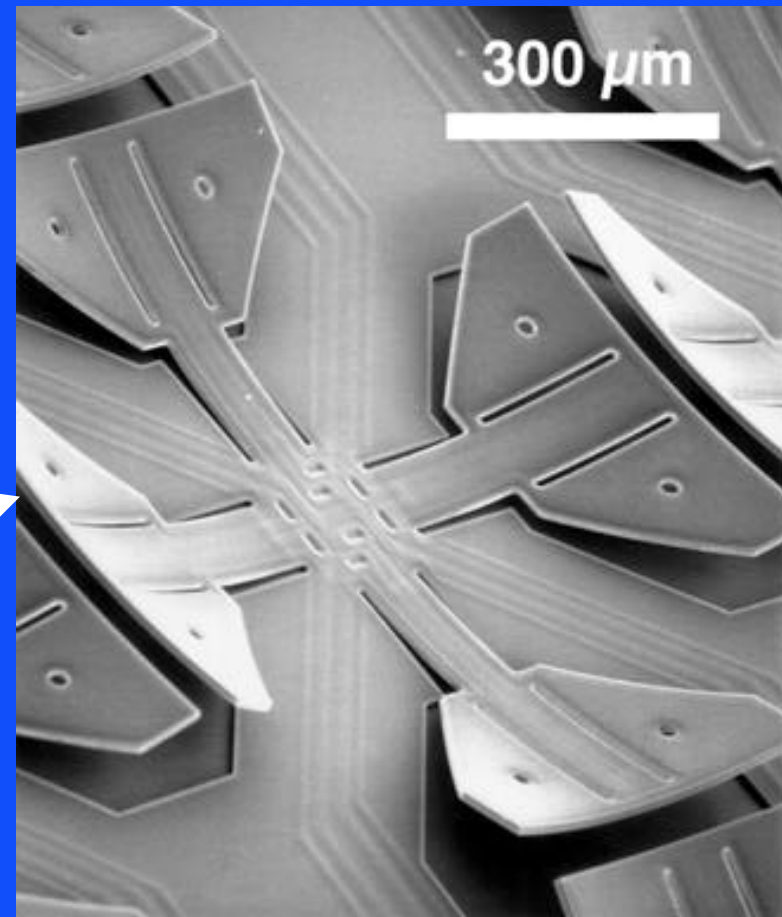
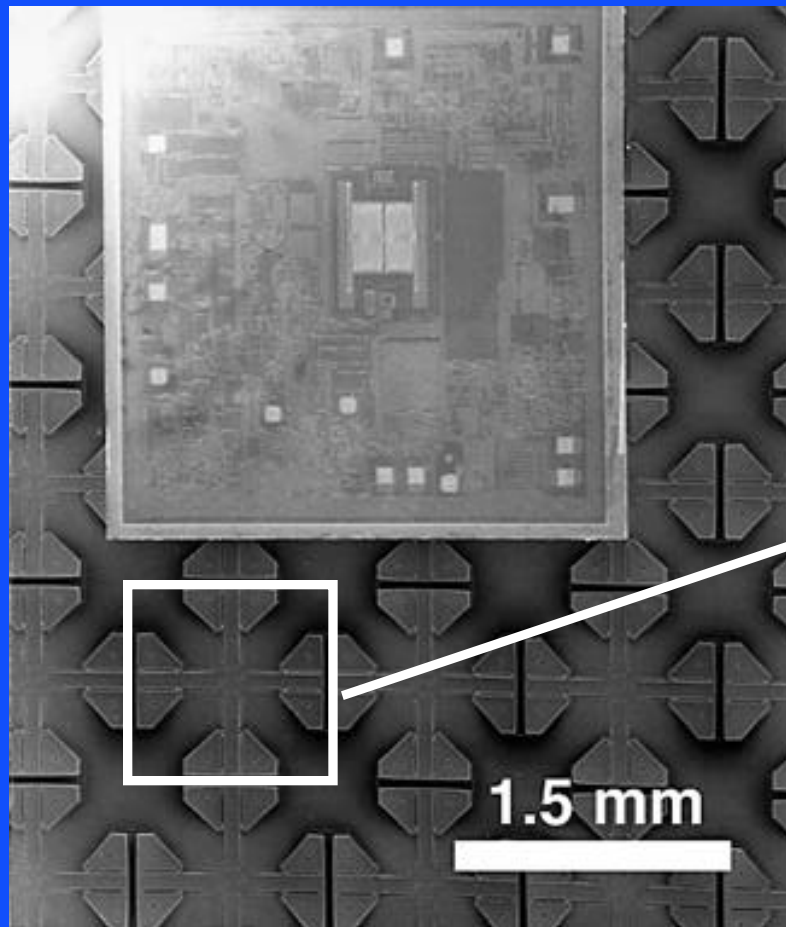


# CILIARY ACTUATOR ARRAYS



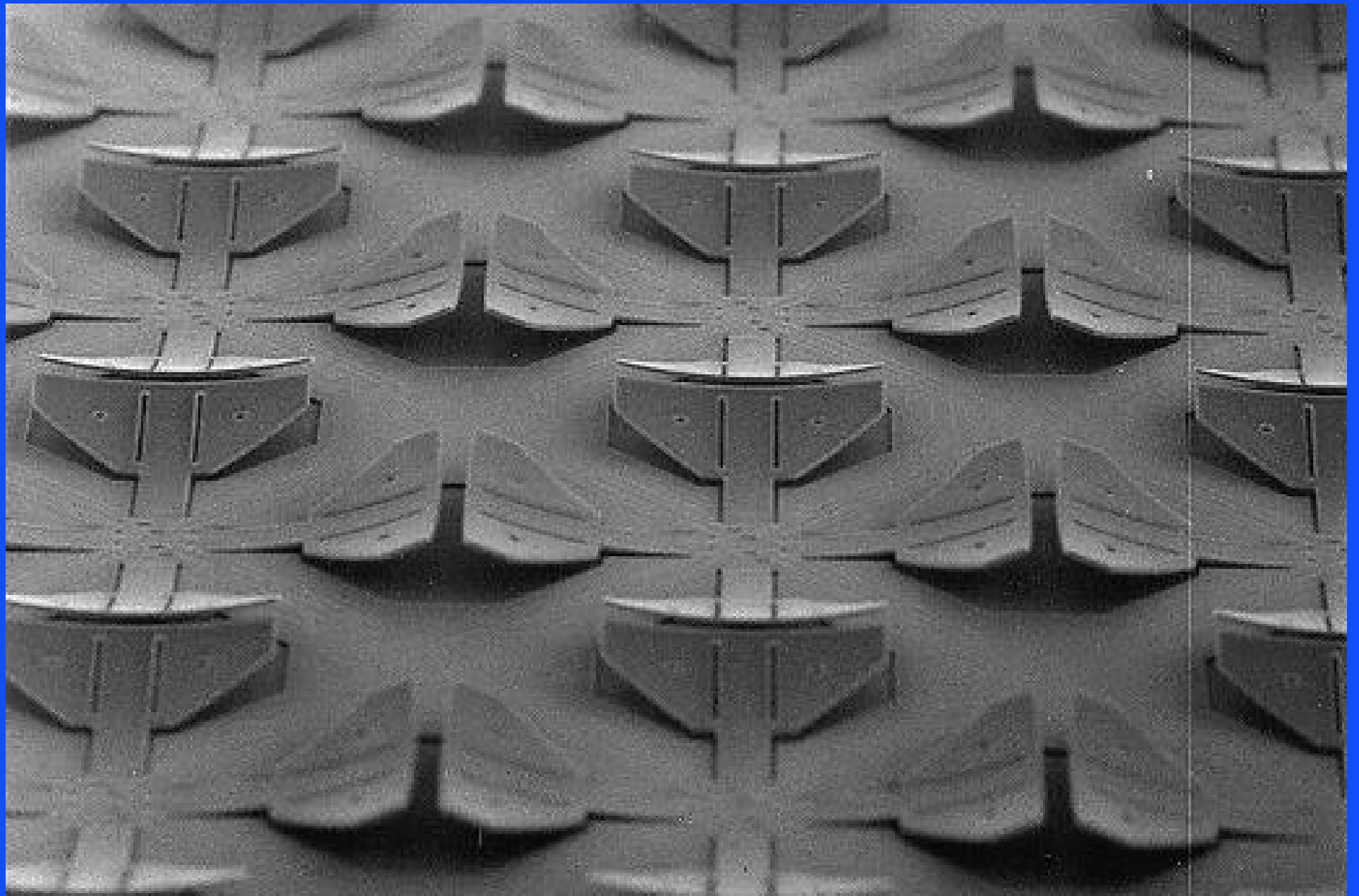
Reference: Suh, J. W., Glander, S. F., Darling, R. B., Storment, C. W., and Kovacs, G. T. A., "Combined Organic Thermal and Electrostatic Omnidirectional Ciliary Microactuator Array for Object Positioning and Inspection," Proceedings of the 1996 Solid-State Sensor and Actuator Workshop, Hilton Head, South Carolina, June 3 - 6, 1996, pp. 168 - 173.

# CILIARY MICROACTUATOR ARRAY

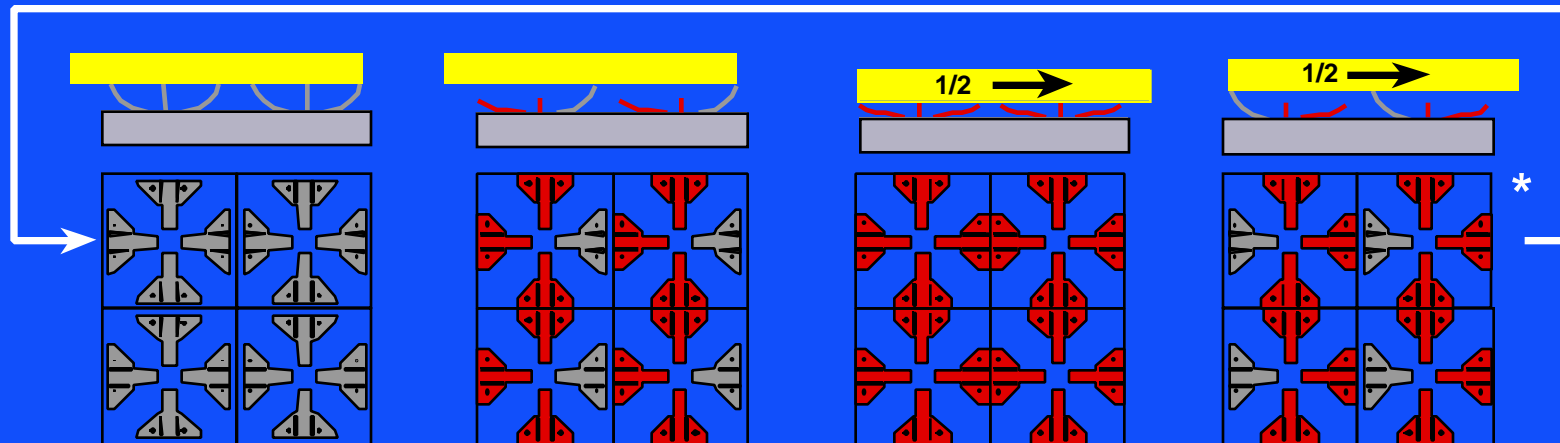


Reference: Suh, J. W., Glander, S. F., Darling, R. B., Storment, C. W., and Kovacs, G. T. A., "Combined Organic Thermal and Electrostatic Omnidirectional Ciliary Microactuator Array for Object Positioning and Inspection," Proceedings of the 1996 Solid-State Sensor and Actuator Workshop, Hilton Head, South Carolina, June 3 - 6, 1996, pp. 168 - 173.

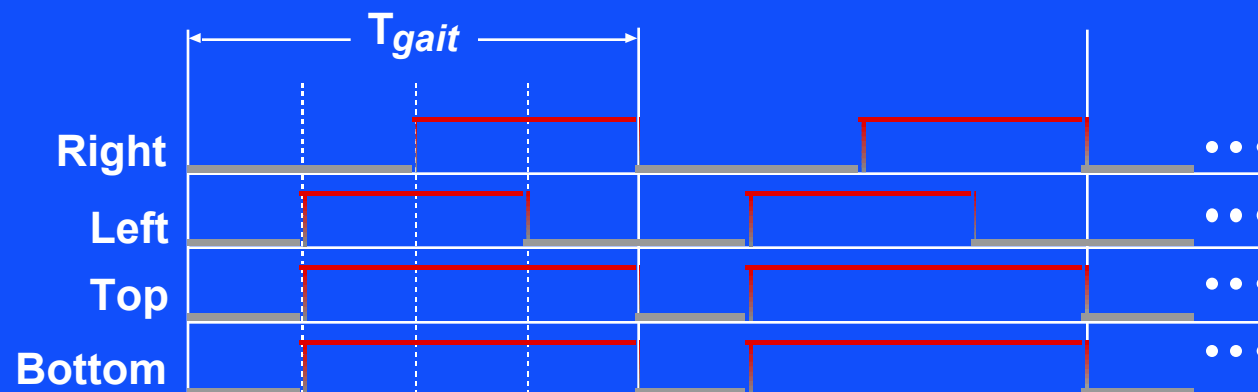
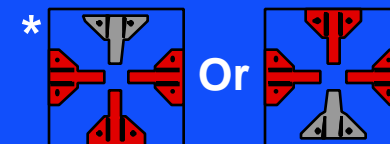




# FOUR PHASE GAIT



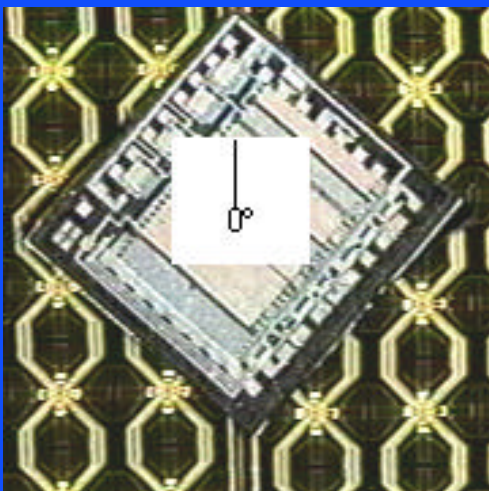
 = Up or Off
  = Down or On



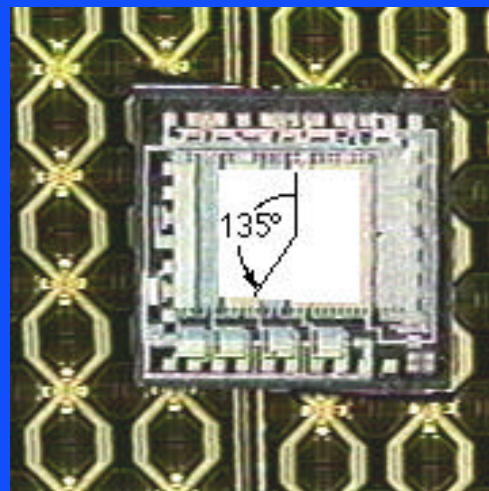
Courtesy J. Suh, Stanford University.

G. Kovacs © 2000

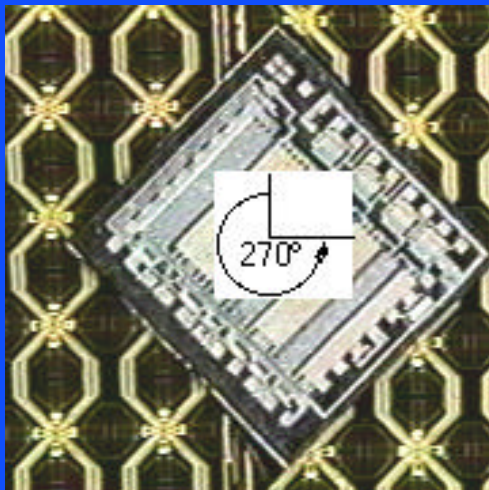
(A)



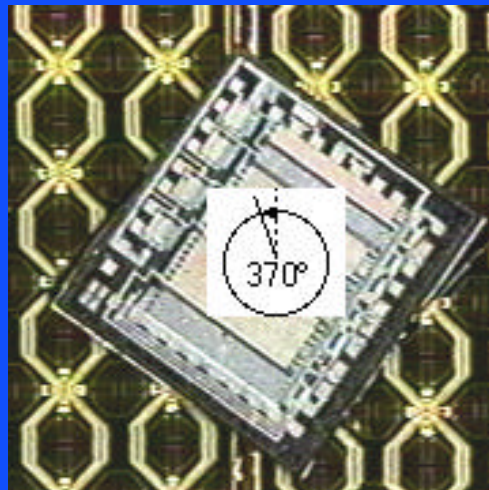
(B)



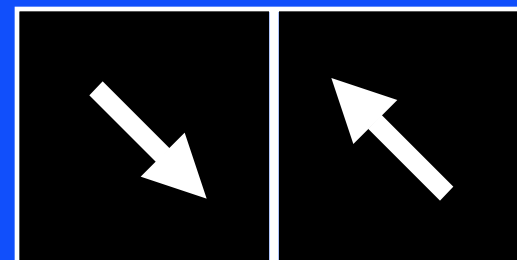
(C)



(D)



## OBJECT ROTATION

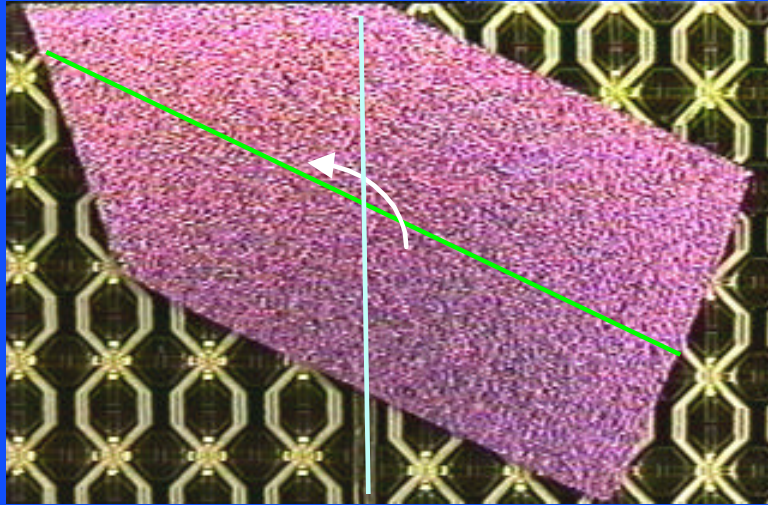


- Two ciliary arrays producing diagonal gaits, rotate object.

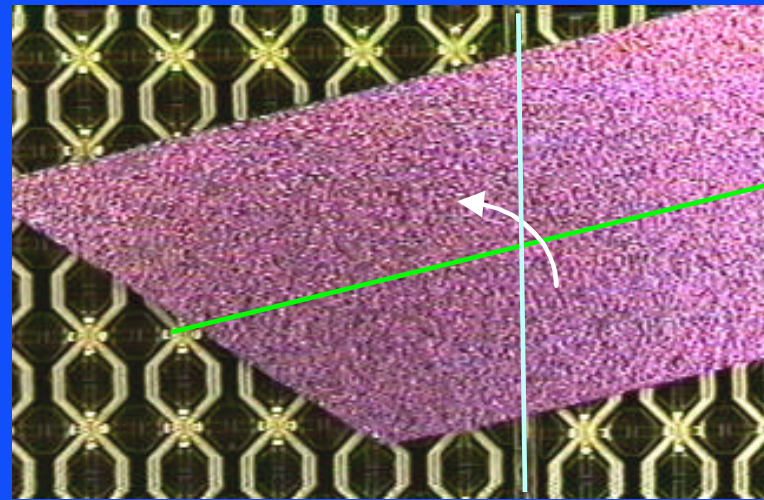


# OBJECT ALIGNMENT

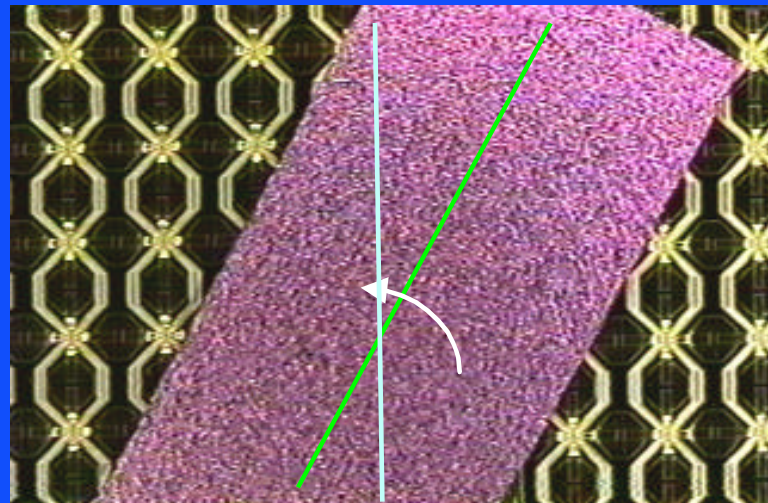
(A)



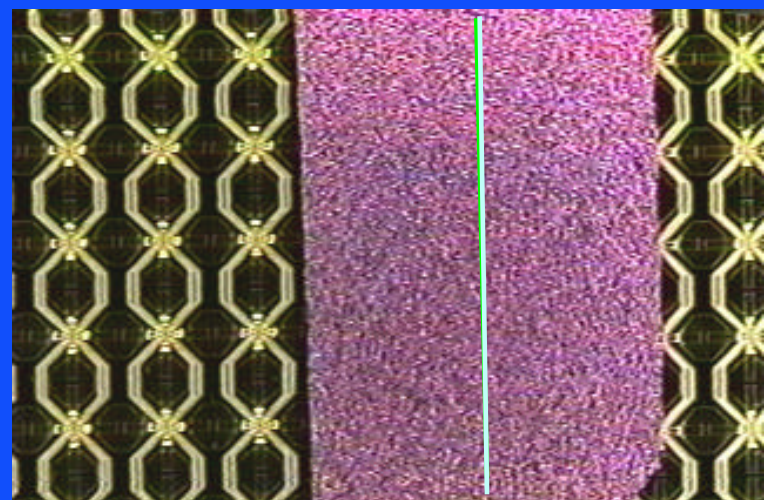
(B)



(C)



(D)

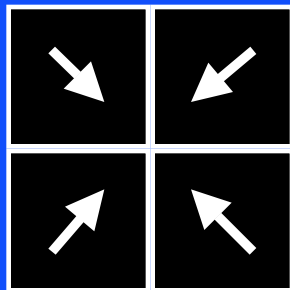
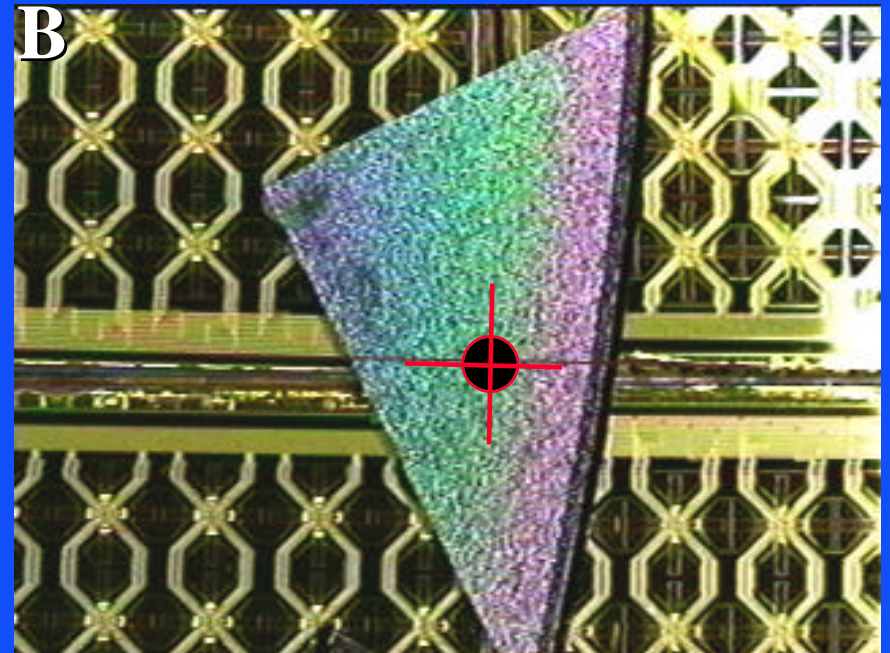
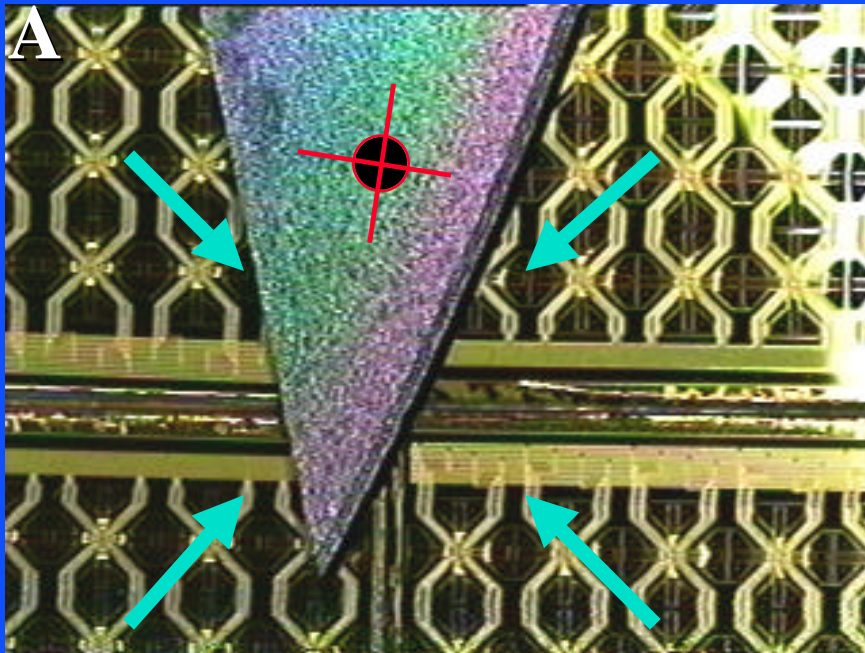


Courtesy J. Suh, Stanford University.

G. Kovacs © 2000

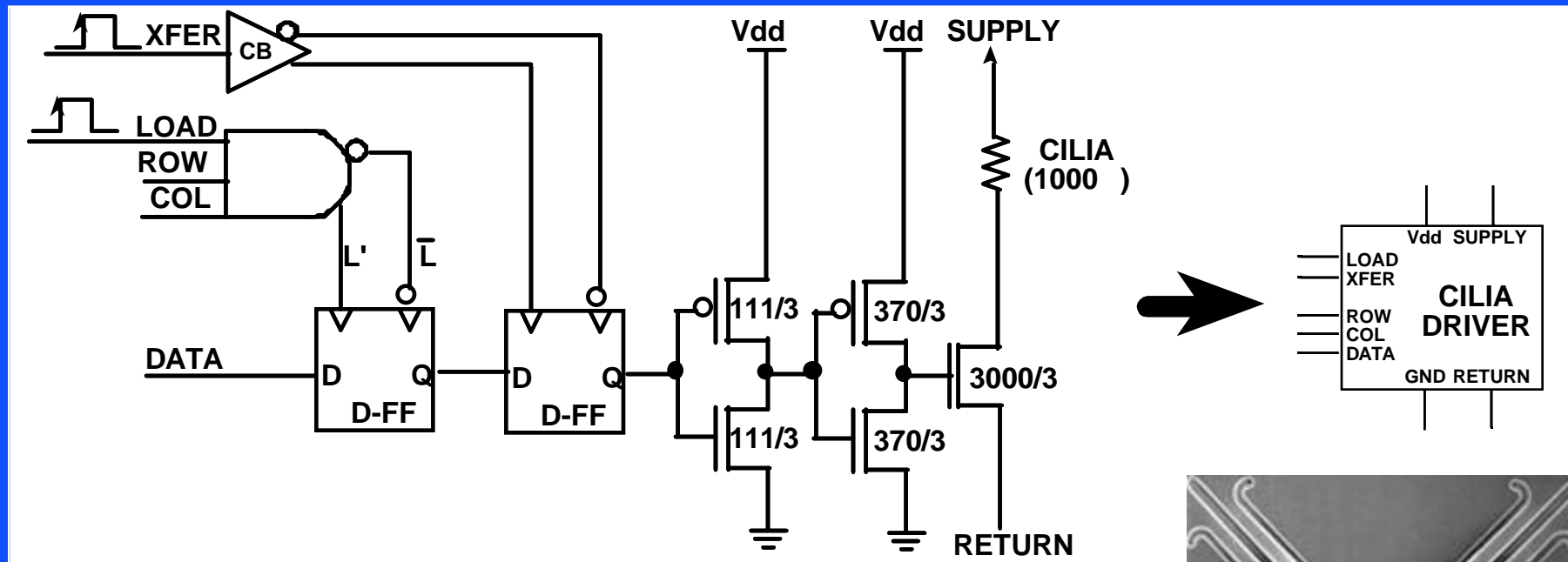


# OBJECT CENTERING

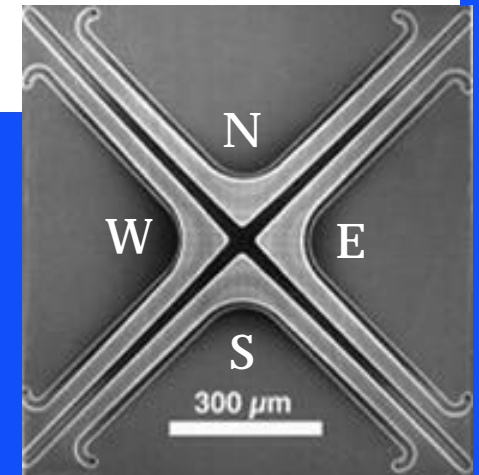


- Four ciliary arrays each producing diagonal gait, centers object.

# CMOS INTEGRATED CILIA



- To turn on actuator in a given cell, ROW and COL go HIGH.
- The desired orientation is chosen with DATA (N, E, W, or S).
- First FF is clocked by a LOAD pulse.
- Second FF continuously drives the CILIA until there is a change in state of first FF and the 2nd FF is clocked with XFER signal.



Courtesy J. Suh, Stanford University.

# TECHNOLOGY INTEGRATION

## Quick CMOS

- 9 Masks

Active  
P-Well  
Poly Si  
N-Plus  
Poly Vias  
Metal1  
Metal Vias  
Metal2  
Scratch LTO



## CMOS Integrated MEMS

- 17 Masks: 9 CMOS + 8 MEMS

Active  
P-Well  
Poly Si  
N-Plus  
Poly Vias  
Metal1  
Metal Vias  
Metal2  
Scratch LTO  
Nitride  
Metal3  
Polyimide1  
Nitride2  
Metal4  
Metal5  
Nitride3  
Polyimide2  
Nitride4



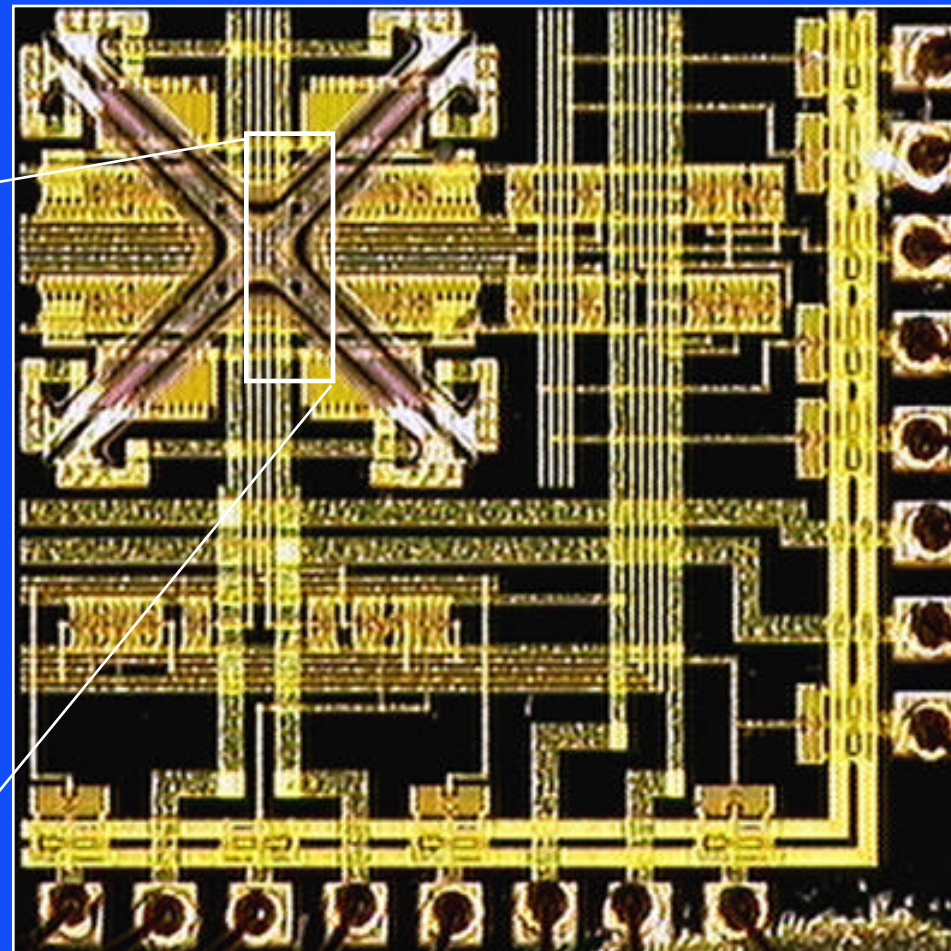
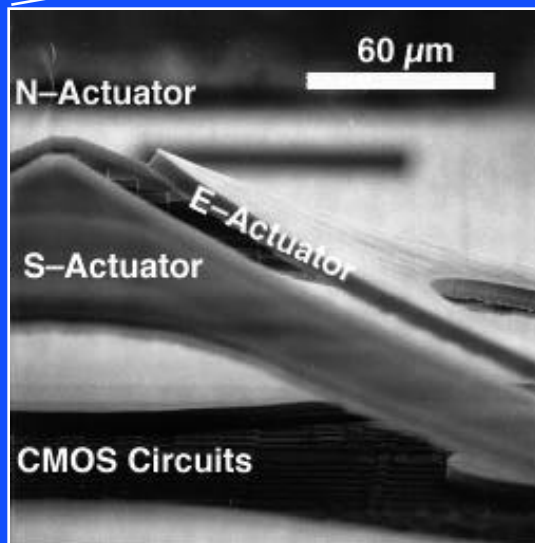
Metal1  
LTO  
-----  
Metal2  
Nitride1  
Polyimide1  
Nitride2  
Metal2  
Metal3  
Nitride3  
Polyimide2  
Nitride4

## Bimorph MEMS

- 9 Masks



# INTEGRATED CILIAM



West  
South  
Row  
North  
East  
Supply  
Return  
S/P  
Select

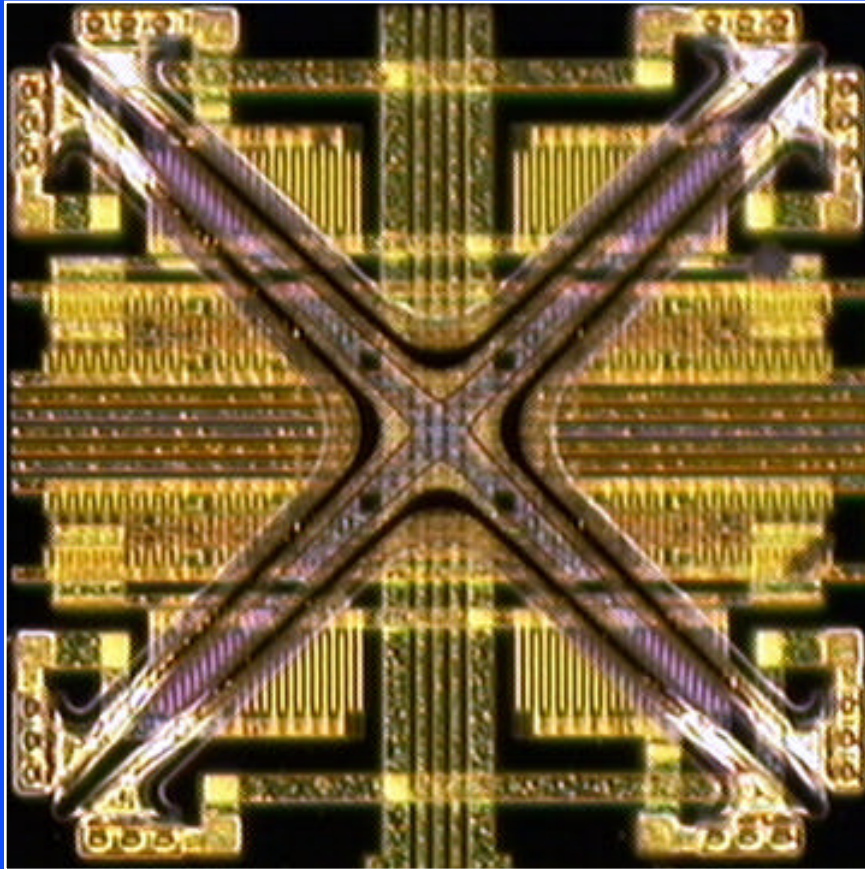
Transfer  
Supply  
Col  
Return  
Load  
Vdd  
Gnd  
S/P  
Select  
Out

Reference: Suh, J. W., Darling, R. B., Böhringer, K.-F., Donald, B. R., Baltes, H., and Kovacs, G. T. A., "CMOS Integrated Ciliary Actuator Array as a General-Purpose Micromanipulation Tool for Small Objects," IEEE/ASME Journal of Microelectromechanical Systems, Dec. 1999, vol. 8, no. 4, pp. 483 - 496.

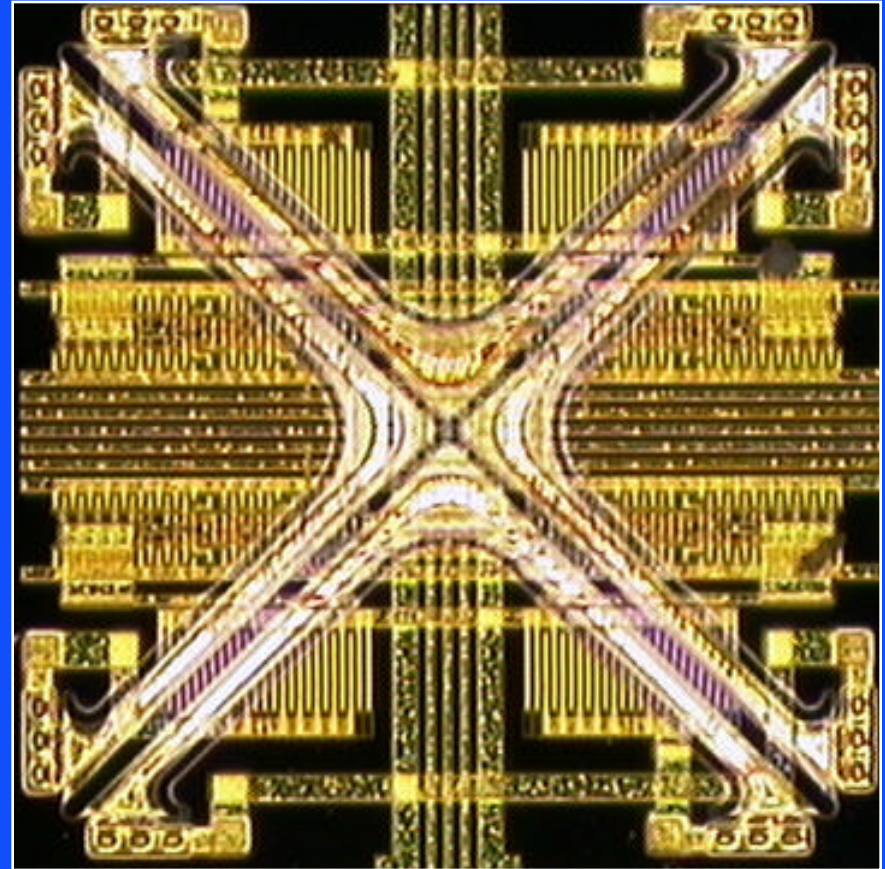
Courtesy J. Suh, Stanford University.

G. Kovacs © 2000





Off



On

Test conditions per device to make “flat”:

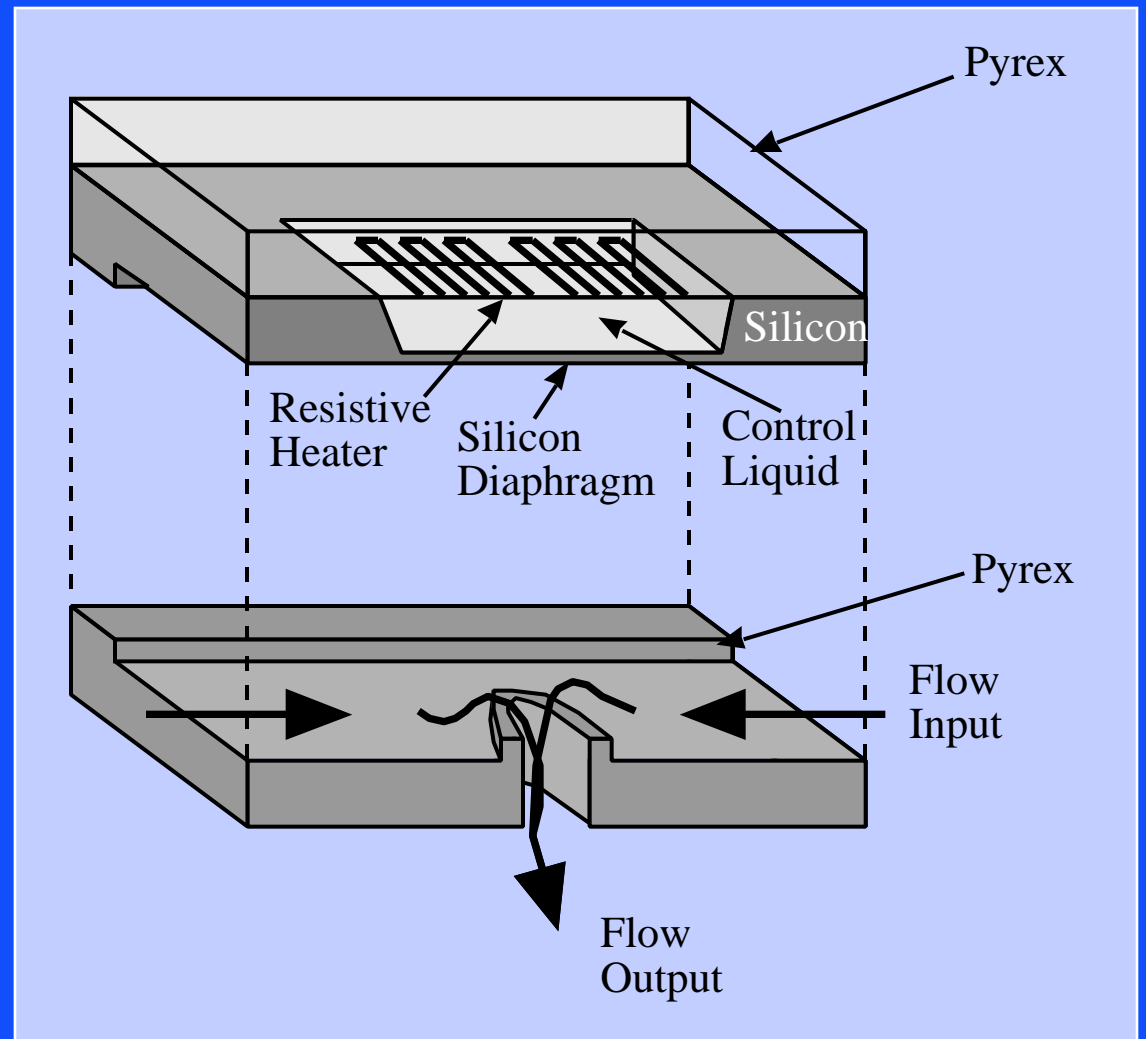
- Supply voltage = 6.25 V
- Actuator current = 6 mA

Courtesy J. Suh, Stanford University.

G. Kovacs © 2000

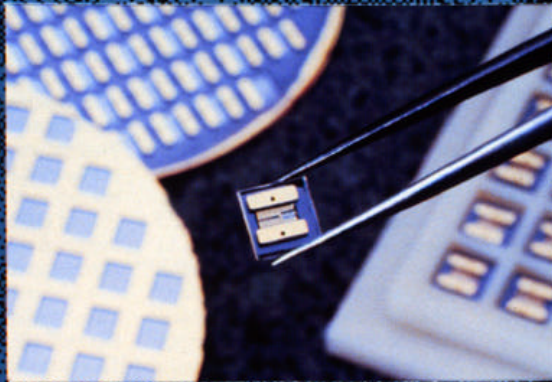
# THERMAL EXPANSION ACTUATORS

- Electrically-controlled heaters are used to expand liquid or gas to generate pressure/force.
- The pressure in turn deforms a membrane, doing mechanical work.
- Valves (Redwood Microsystems) have been fabricated using this approach, require power on the order of 1 W and have responses in the millisecond range.

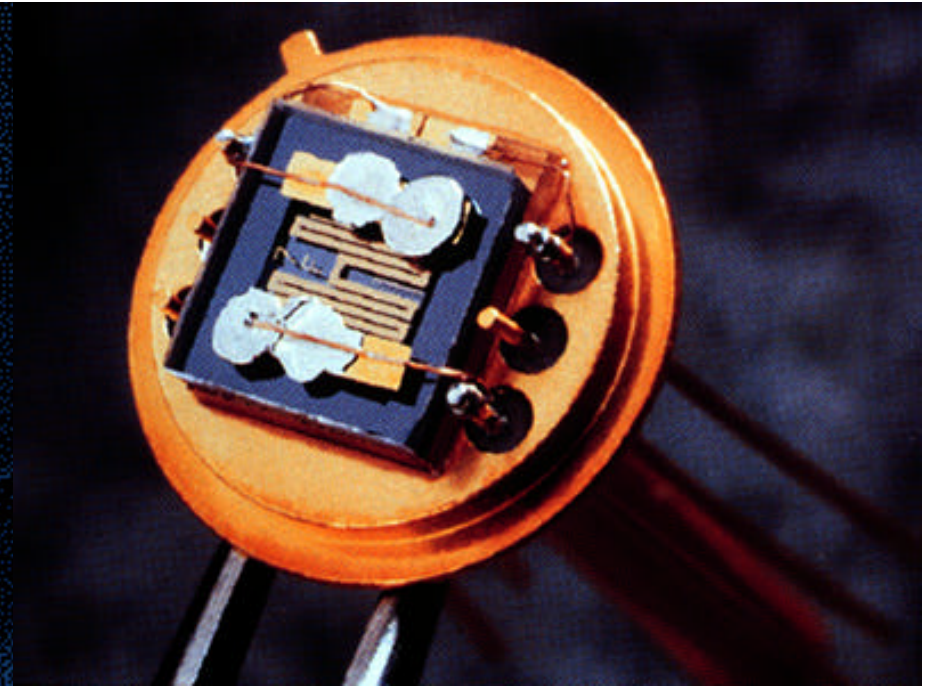




MIGHTY SILICON MACHINES



**REDWOOD**  
MICROSYSTEMS

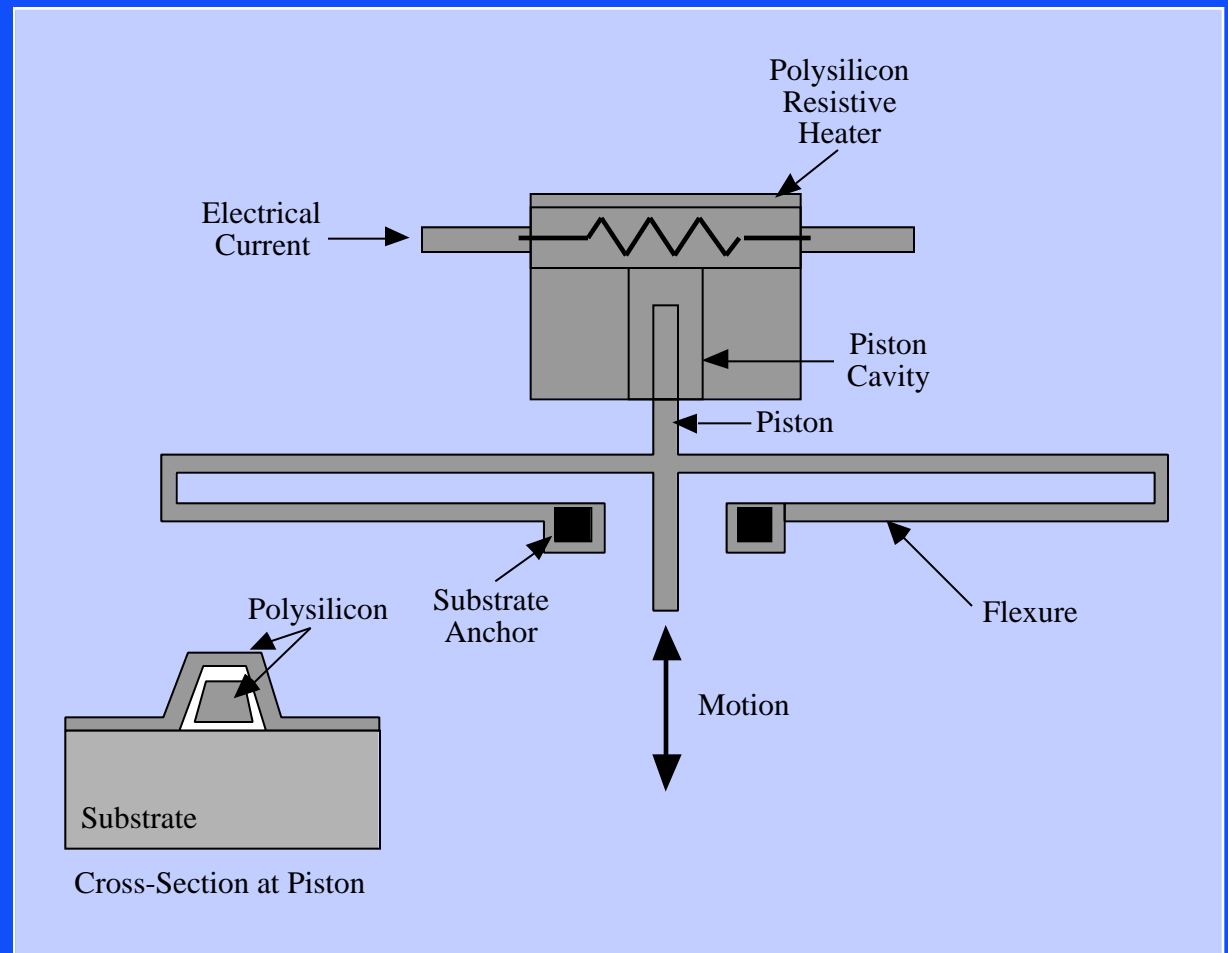


Courtesy Dr. M. Zdeblick, Redwood  
Microsystems.

G. Kovacs © 2000

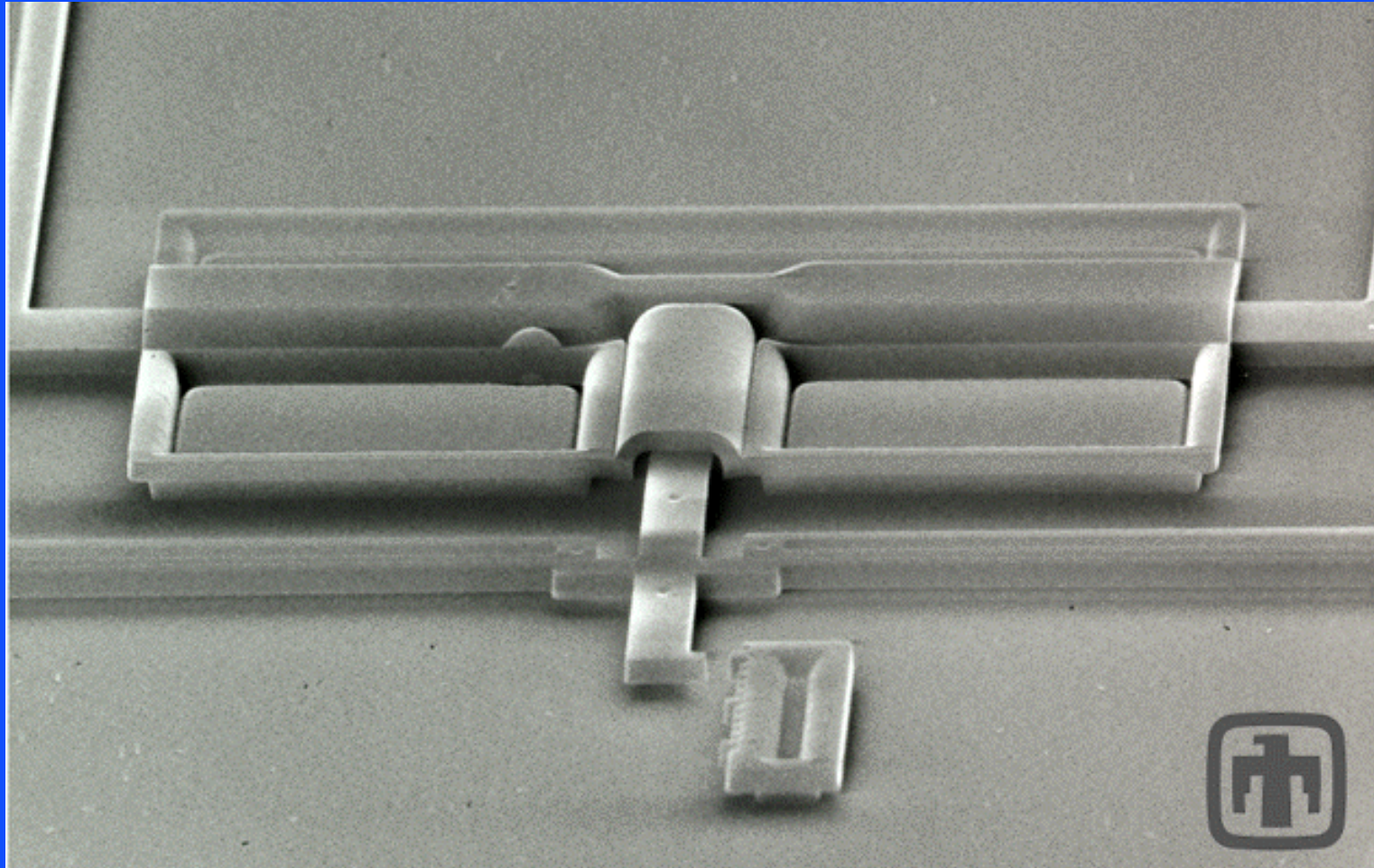
# PHASE-CHANGE ACTUATORS

- Using a heater to form vapor bubbles in a liquid can be used to actuate mechanisms.
- Liquid media must be used, and their thermal conductivity may limit efficiency.



Reference: Sniegowski, J. J., "A Microactuation Mechanism Based on Liquid-Vapor Surface Tension," Abstracts of Late News Papers from Transducers '93, the 7th International Conference on Solid-State Sensors and Actuators, Yokohama, Japan, June 7 - 10, 1993, Institute of Electrical Engineers, Japan, pp. 12 - 13.





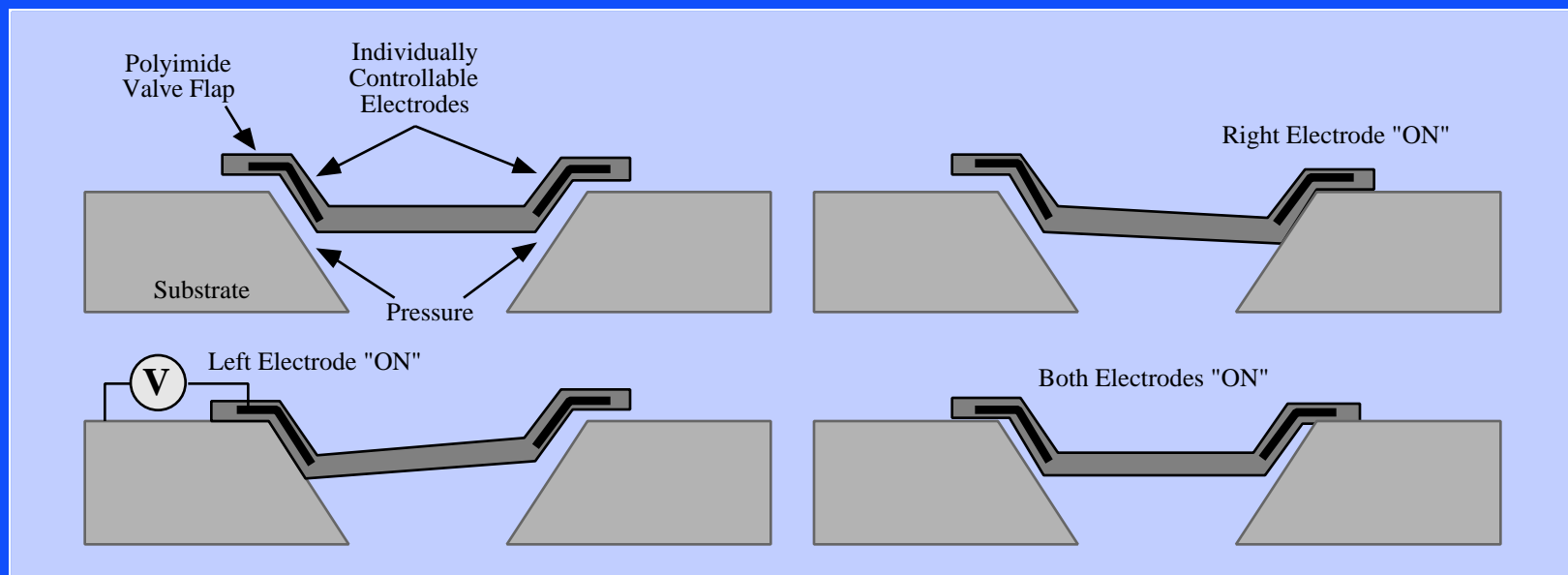
<http://www.mdl.sandia.gov/Micromachine/images.html>

# SHAPE MEMORY ALLOY ACTUATORS

- Since the 1950's, it has been known that certain alloys, such as AuCu, InTi and TiNi, could be deformed but would return to their original shape once heated.
- TiNi exhibits the SMA effect due to a temperature-dependent phase transition between the *martensite* and *austenite* forms. Heating causes contraction via transition to the austenite phase.
- TiNi thin films have been used in microactuators, and can generate stresses greater than 200 MPa with strains > 5% and with rather low efficiencies ( $\approx 3\%$ ).

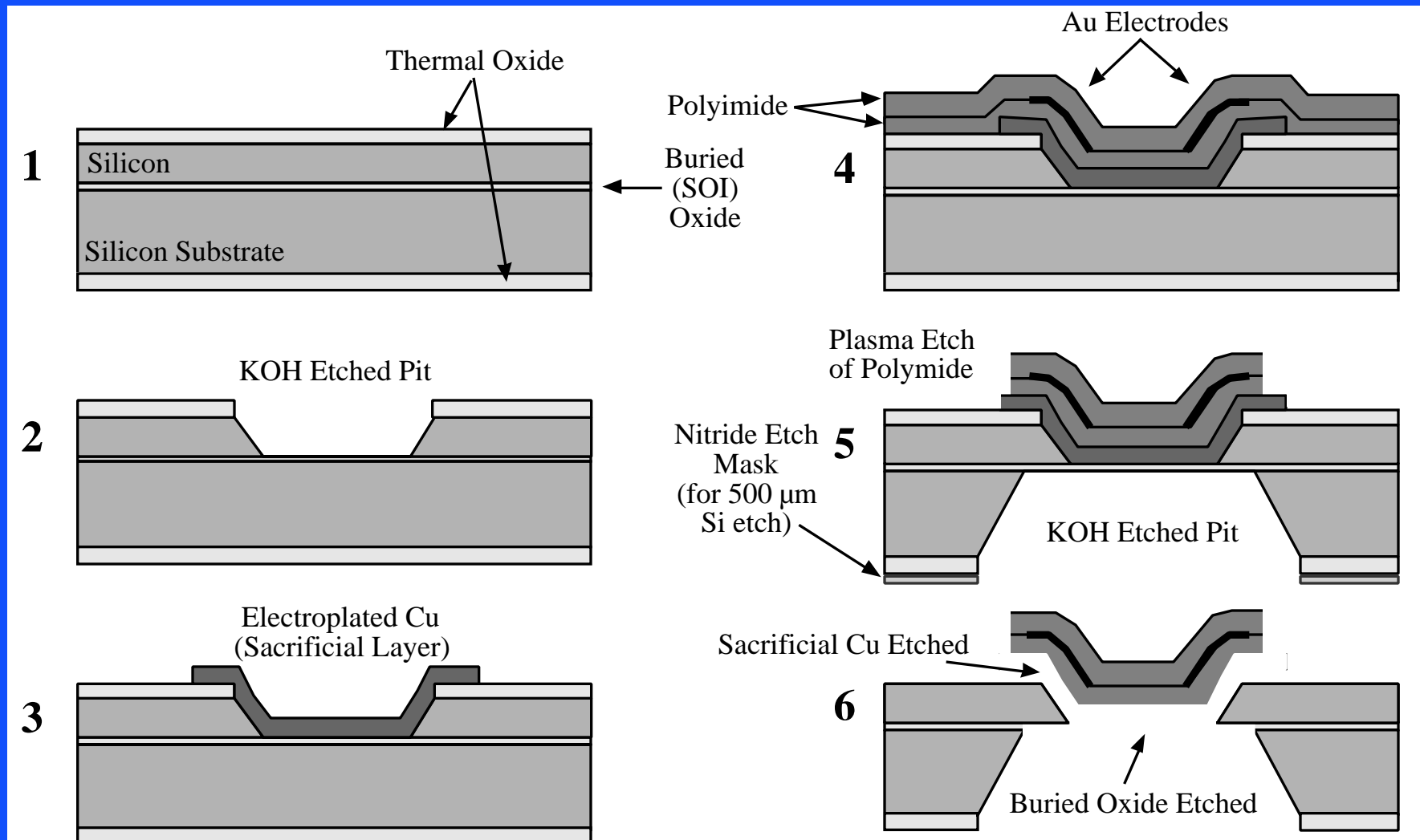
# PNEUMATIC ACTUATION

- Such actuators generally rely on a low power mechanism to gate gas pressure on and off (liquid gating would be referred to as hydraulic).
- The added complications of fluidics are brought into play with these actuators, but large forces are possible.

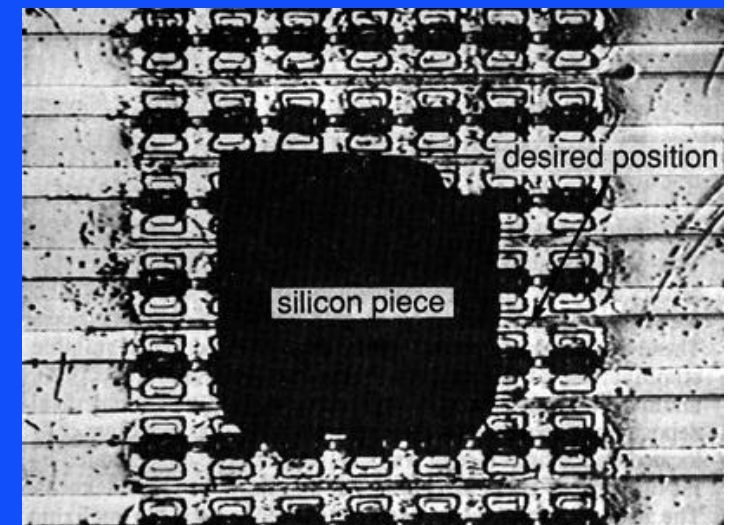
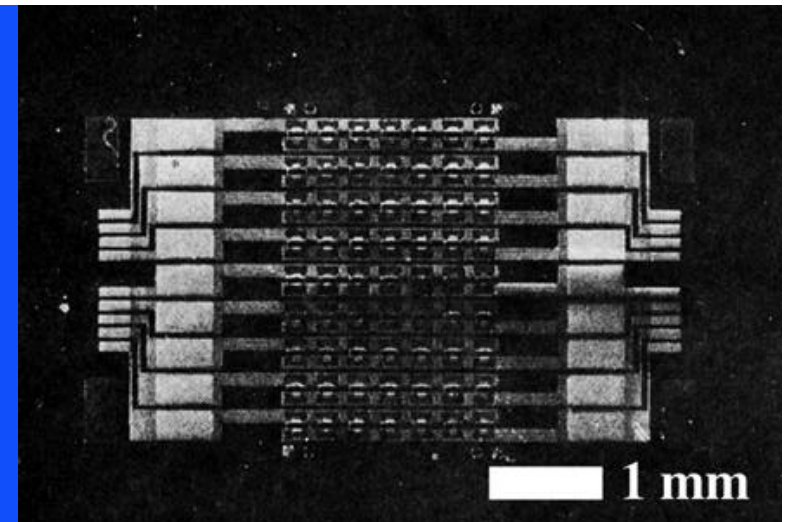
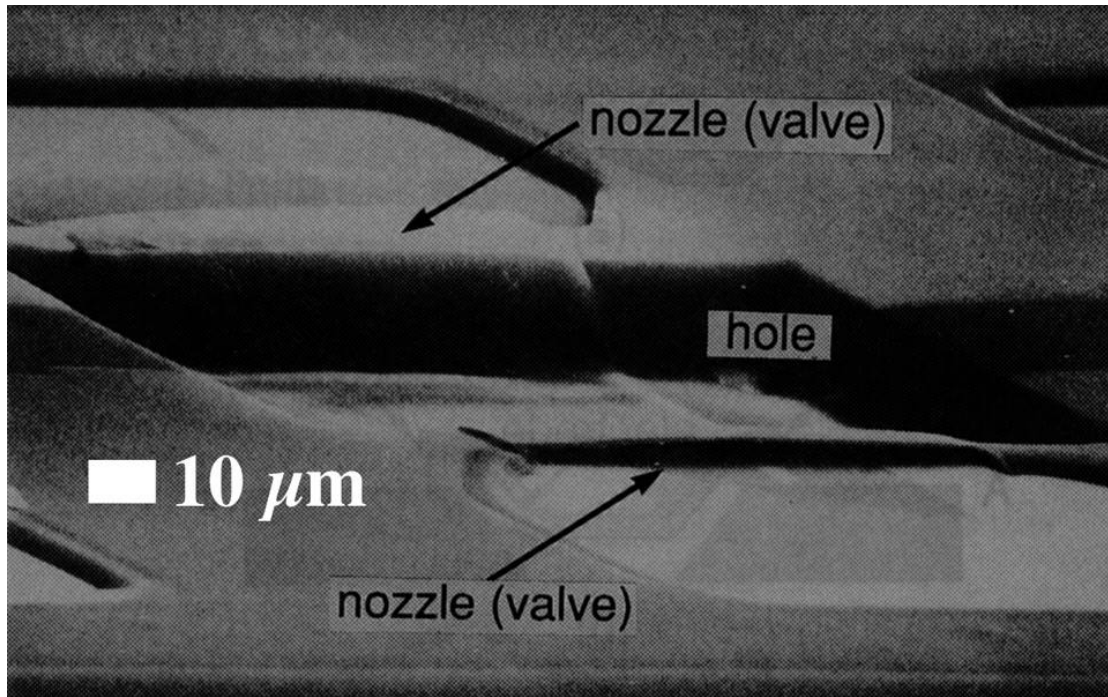


Reference: Konishi, S., and Fujita, H., "A Conveyance System Using Air Flow Based on the Concept of Distributed Micro Motion Systems," Proceedings of Transducers '93, the 7th International Conference on Solid-State Sensors and Actuators, Yokohama, Japan, June 7 - 10, 1993, Institute of Electrical Engineers, Japan, pp. 28 - 31.





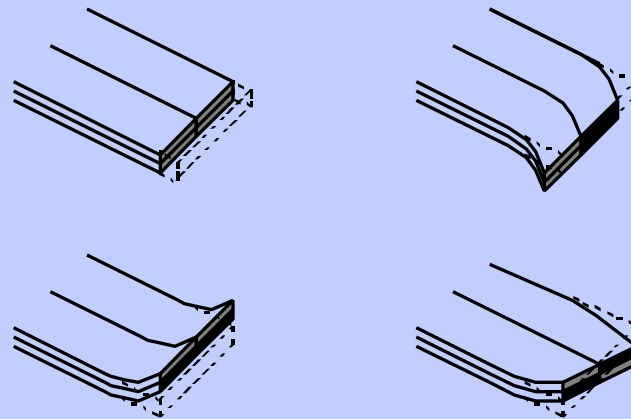
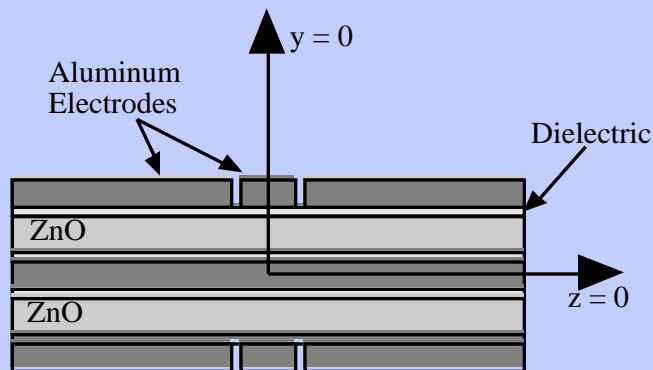
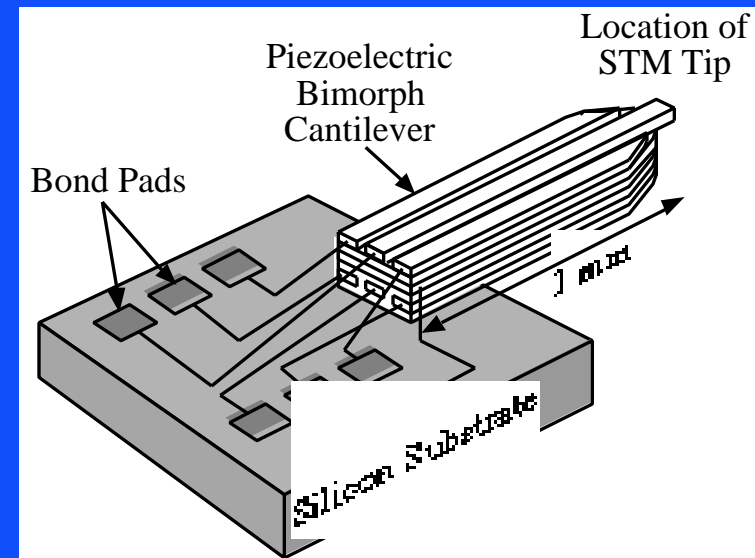
Reference: Konishi, S., and Fujita, H., "A Conveyance System Using Air Flow Based on the Concept of Distributed Micro Motion Systems," Proceedings of Transducers '93, the 7th International Conference on Solid-State Sensors and Actuators, Yokohama, Japan, June 7 - 10, 1993, Institute of Electrical Engineers, Japan, pp. 28 - 31.



Source: Konishi, S., and Fujita, H., "A Conveyance System Using Air Flow Based on the Concept of Distributed Micro Motion Systems," Proceedings of Transducers '93, the 7th International Conference on Solid-State Sensors and Actuators, Yokohama, Japan, June 7 - 10, 1993, Institute of Electrical Engineers, Japan, pp. 28 - 31.

# PIEZOELECTRIC ACTUATION

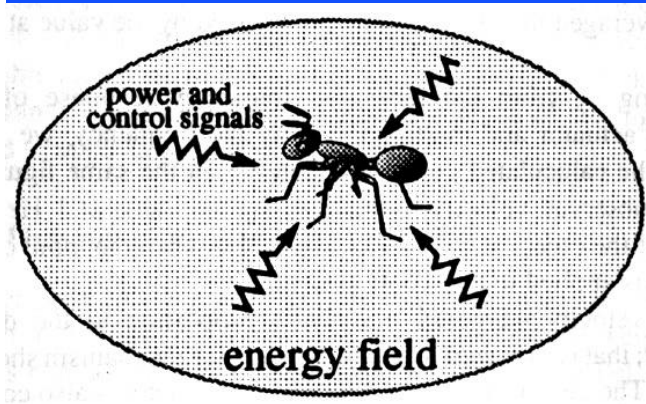
- Small strains ( $< 0.1\%$ ) but high forces ( $\approx 40$  MPa) and speeds are characteristic of piezoelectric actuators.



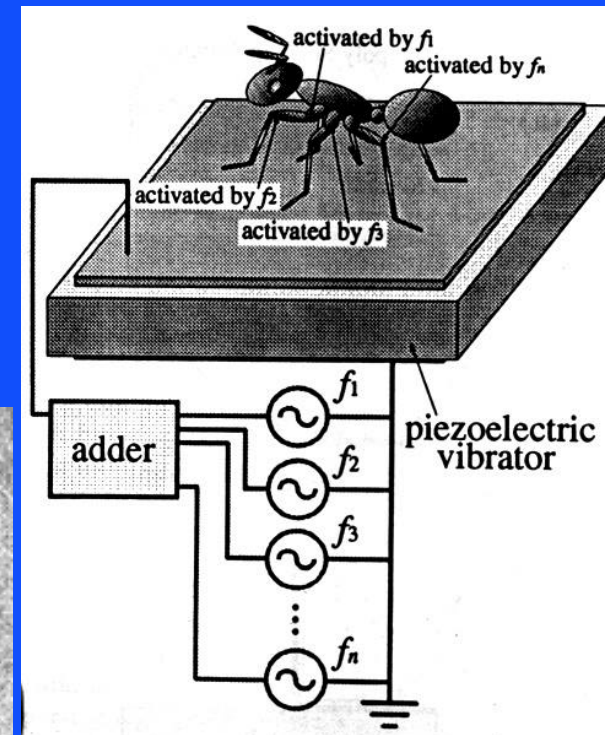
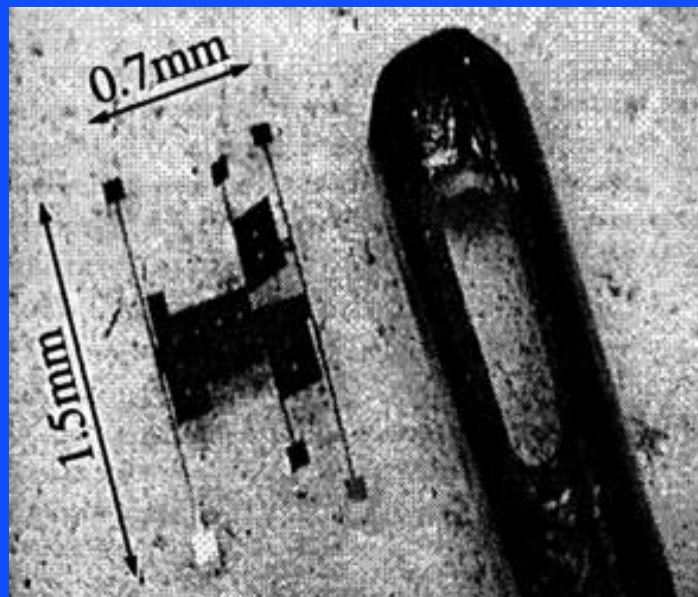
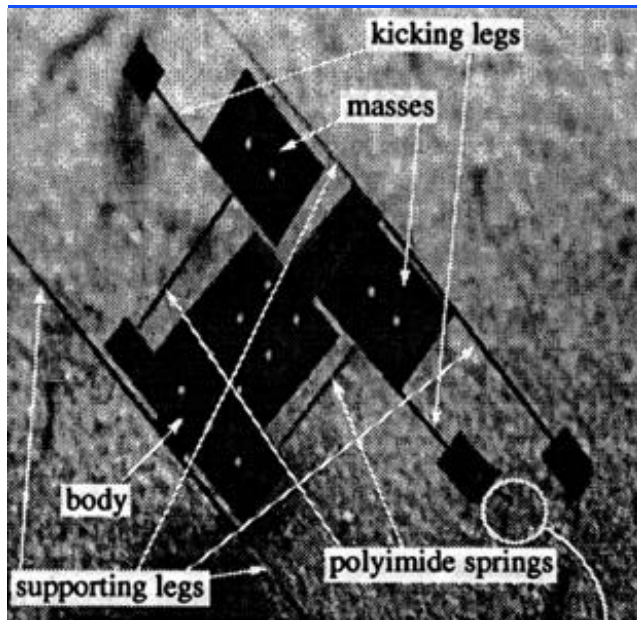
Reference: Akamine, S., Albrecht, T. R., Zdeblick, M. J., and Quate, C. F., "A Planar Process for Microfabrication of a Scanning Tunneling Microscope," *Sensors and Actuators*, A21-A23, 1990, pp. 964 - 970.



# VIBRATORY ACTUATION



Source: Yasuda, T., Shimoyama, I., and Miura, H., "Microrobot Actuated by a Vibration Energy Field," Proceedings of Transducers '93, the 7th International Conference on Solid-State Sensors and Actuators, Yokohama, Japan, June 7 - 10, 1993, pp. 42 - 45.



# MAGNETIC ACTUATION

- **Forces between current carrying wires and/or permanent magnets (e.g. electroplated Permalloy) can be used to generate considerable forces with fast response times.**
- **Magnetic forces can be used to drive rotary motors, galvanometers, etc.**
- **Resistive losses must be carefully taken into account.**
- **This material is covered in the Magnetic Transducers section.**



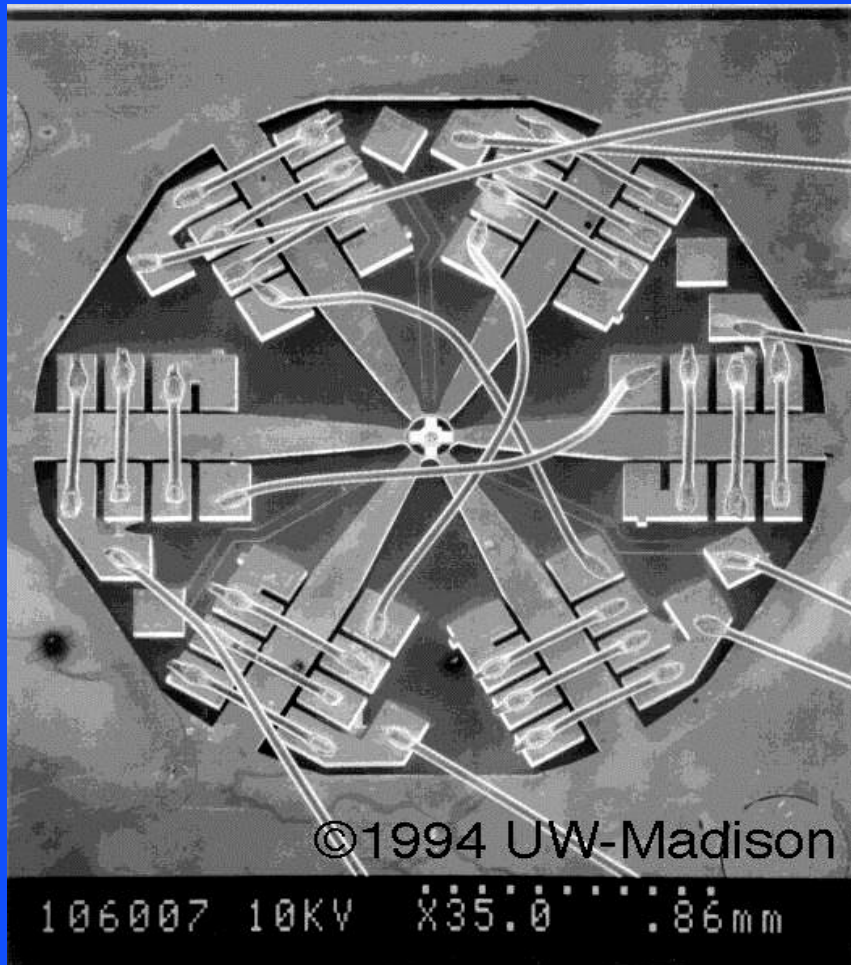
Courtesy of Prof. H. Guckel, University of Wisconsin.

<http://mems.engr.wisc.edu/images/>

G. Kovacs © 2000

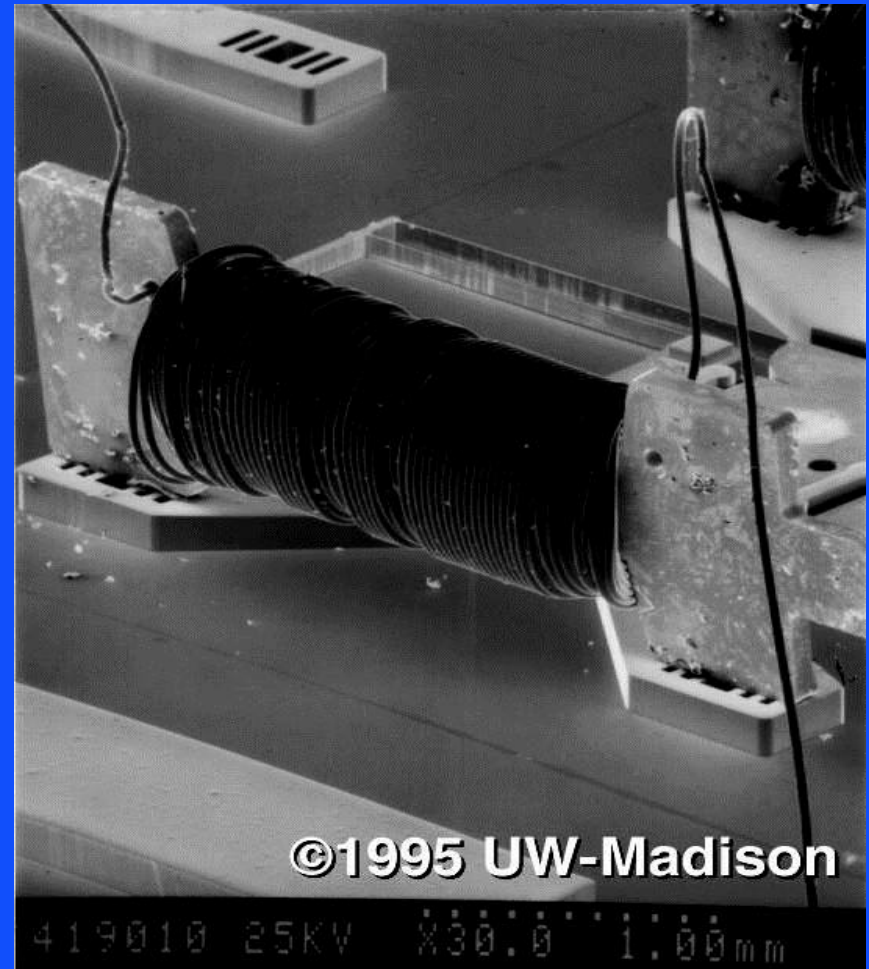


# COILS

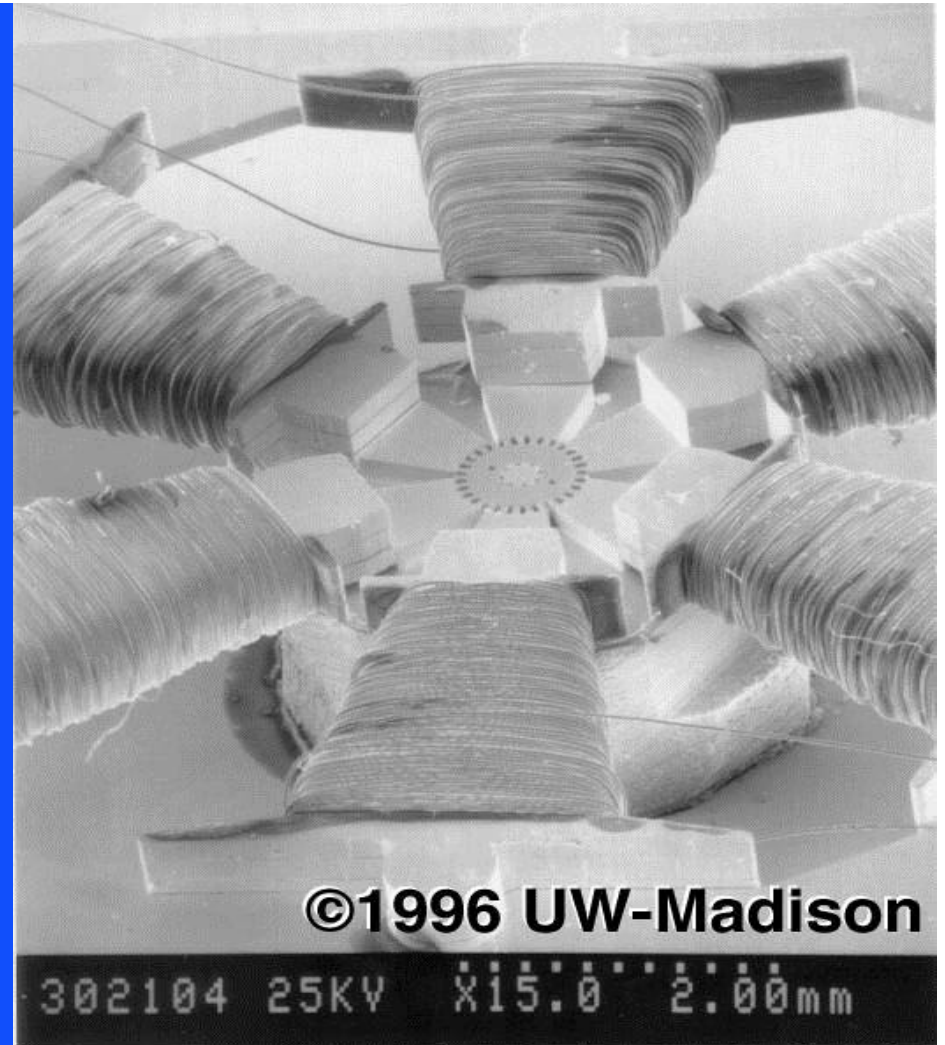
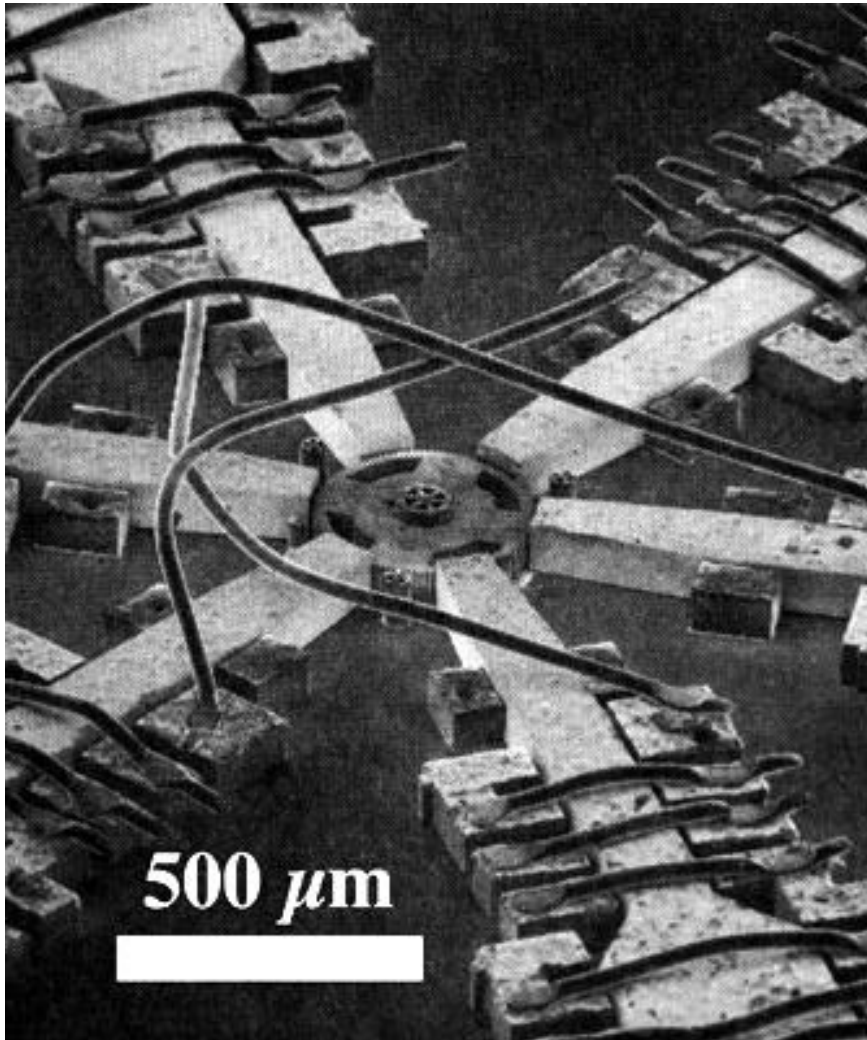


Courtesy of Prof. Henry Guckel

<http://mems.engr.wisc.edu/images/>



G. Kovacs © 2000

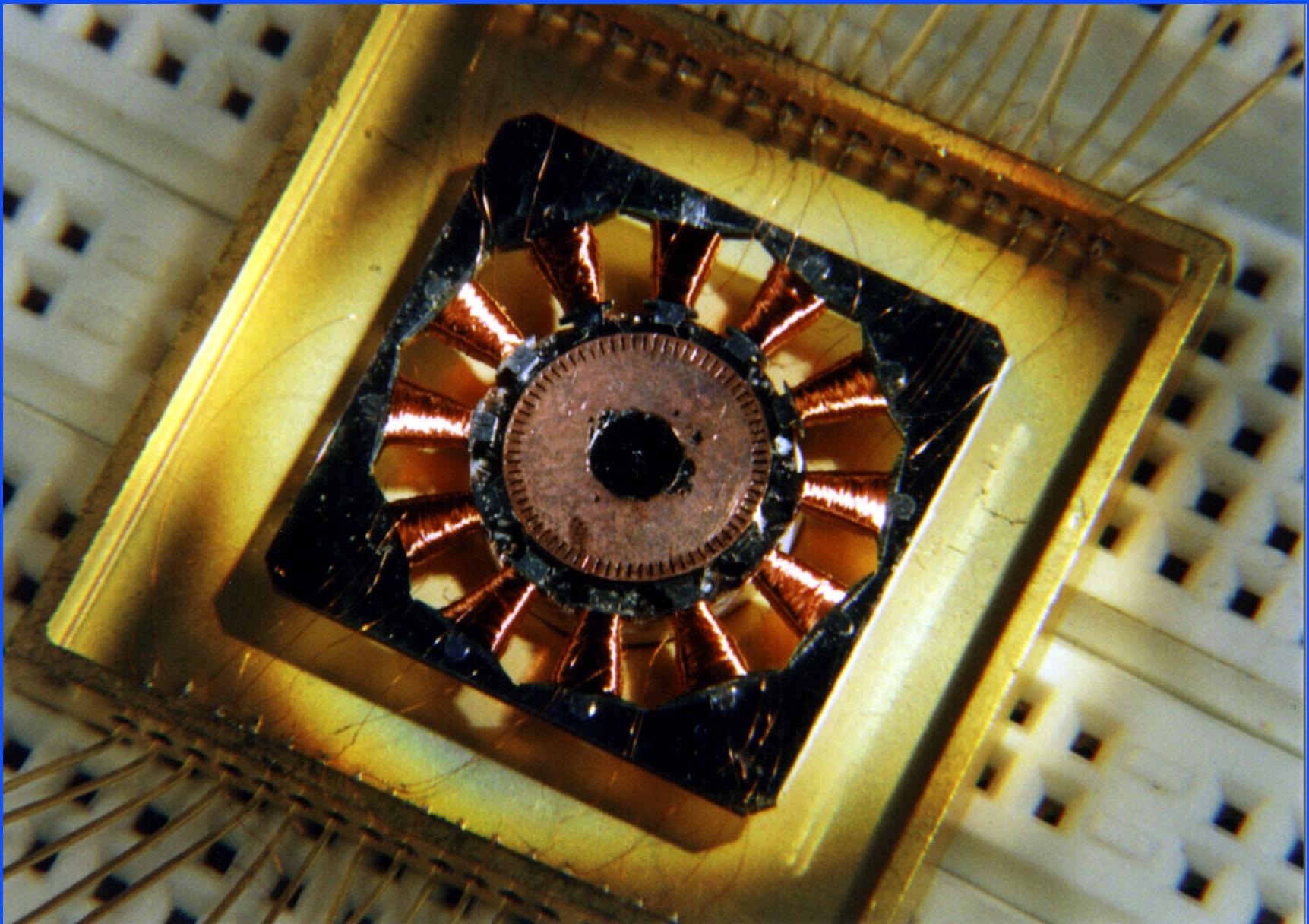


Courtesy of Prof. H. Guckel, University of Wisconsin.

<http://mems.engr.wisc.edu/images/>

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Courtesy of Prof. H. Guckel, University of Wisconsin.

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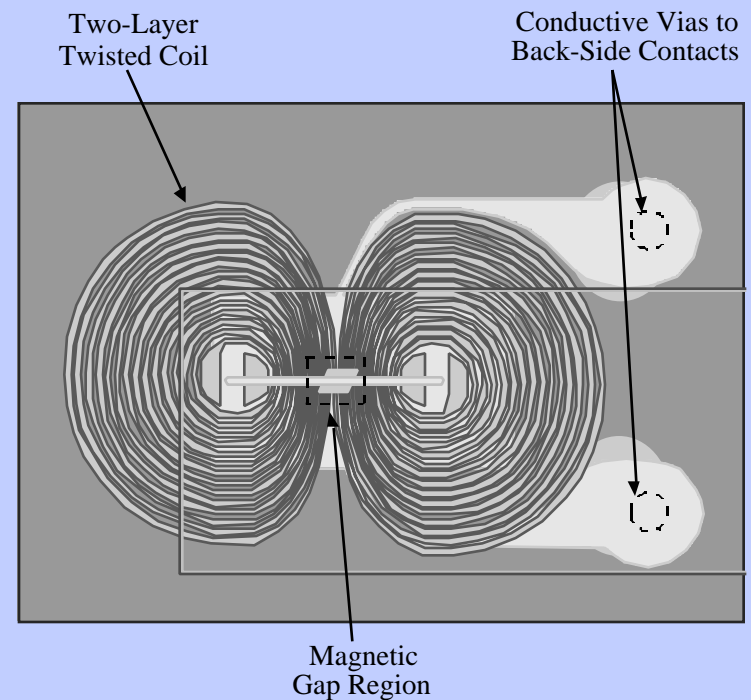
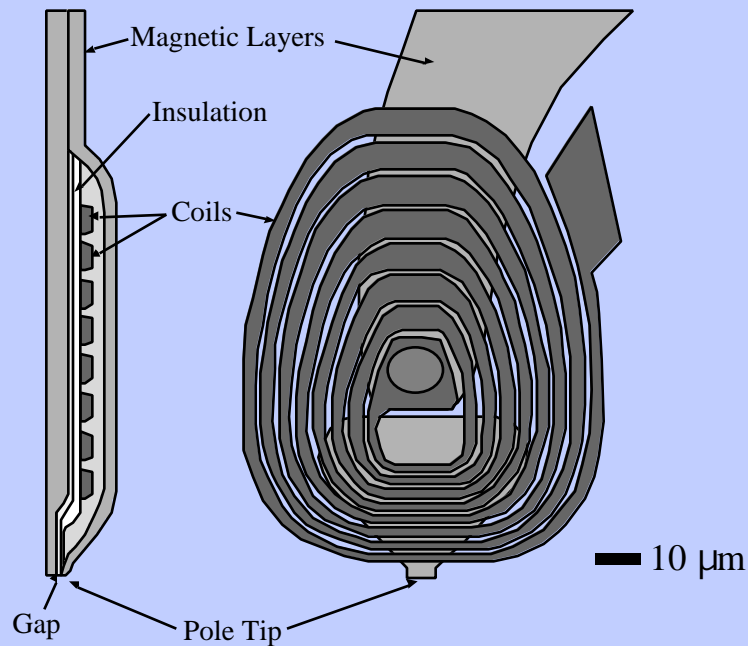
Reference: Klein J,  
Preliminary Results of a micro  
induction motor, Ph.D Thesis,  
University of Wisconsin at  
Madison, 1998.



Courtesy of J. Klein, University of Wisconsin.

G. Kovacs © 2000

# MAGNETIC READ/WRITE HEADS



Reference: Romankiw, L. T., "Evolution of the Plating Through Lithographic Mask Technology," Proceedings of the Fourth International Symposium on Magnetic Materials, Processes and Devices - Applications to Storage and Microelectromechanical Systems (MEMS), Chicago, IL, Oct. 9 - 12, 1995 (published in 1996), pp. 253 - 272.

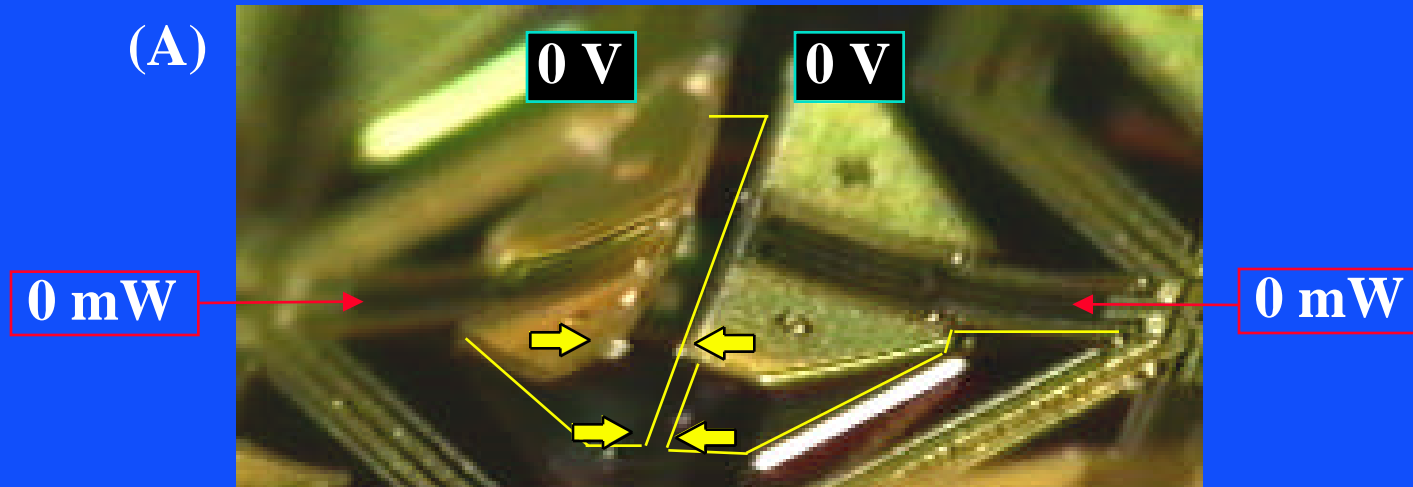
Reference: Lazzari, J. P., "Planar Silicon Heads for Disc Drive Industry," Proceedings of Transducers '97, the 1997 International Conference on Solid-State Sensors and Actuators, Chicago, IL, June 16 - 19, 1997, vol. 2, pp. 1077 - 1080.

# **HYBRID ACTUATORS**

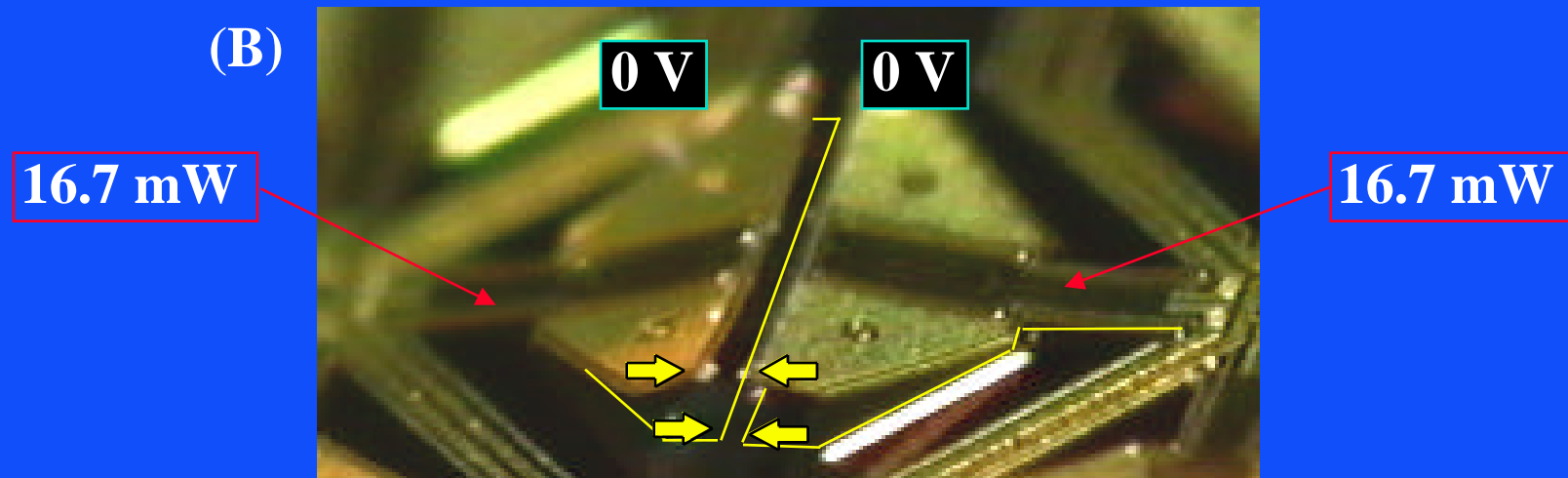
- **It is sometimes possible to combine more than one actuation scheme to help mitigate the drawbacks of each one individually.**
- **Combinations that have been demonstrated in micromachined devices include thermal/electrostatic and magnetic/electrostatic.**



(A)



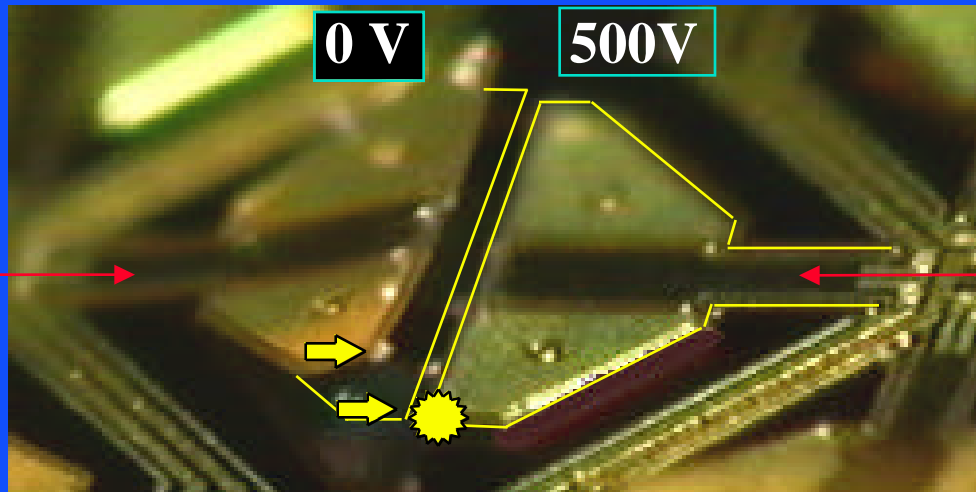
(B)



Reference: Suh, J. W., Glander, S. F., Darling, R. B., Storment, C. W., and Kovacs, G. T. A., "Combined Organic Thermal and Electrostatic Omnidirectional Ciliary Microactuator Array for Object Positioning and Inspection," Proceedings of the 1996 Solid-State Sensor and Actuator Workshop, Hilton Head, South Carolina, June 3 - 6, 1996, pp. 168 - 173.

(C)

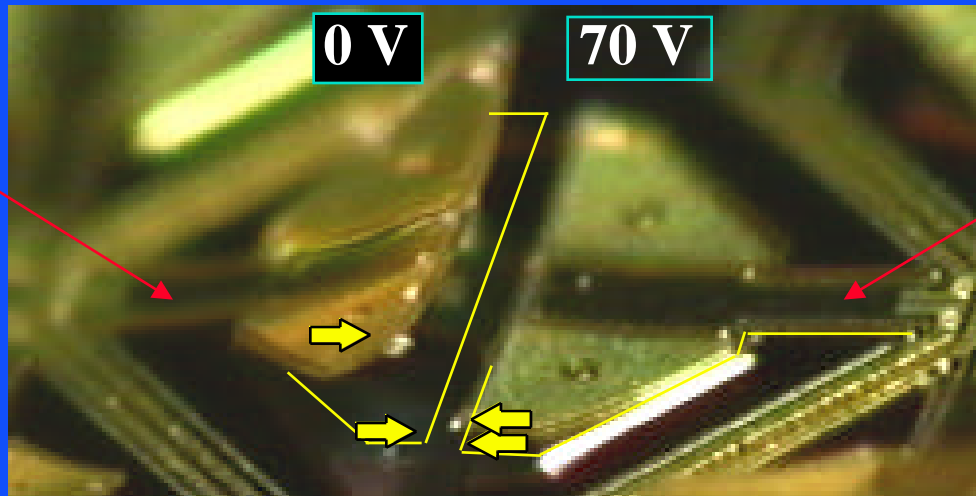
16.7 mW



16.7 mW

(D)

0 mW



0 mW

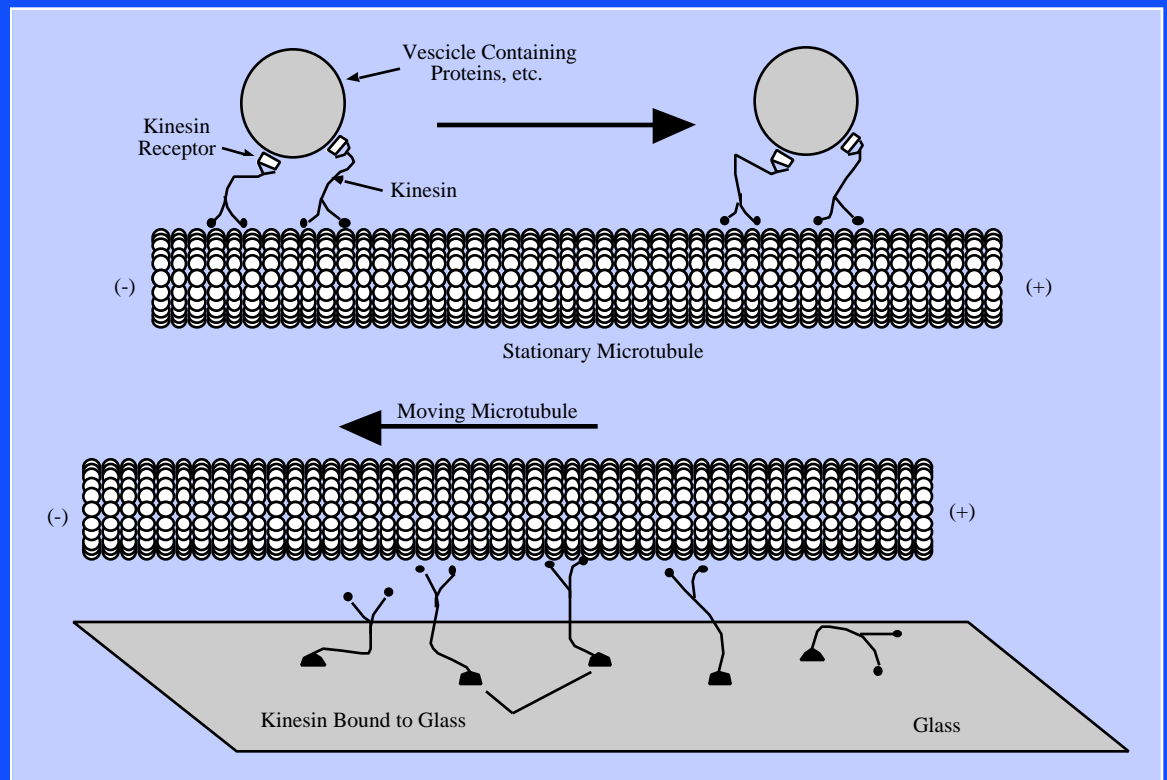
Reference: Suh, J. W., Glander, S. F., Darling, R. B., Storment, C. W., and Kovacs, G. T. A., "Combined Organic Thermal and Electrostatic Omnidirectional Ciliary Microactuator Array for Object Positioning and Inspection," Proceedings of the 1996 Solid-State Sensor and Actuator Workshop, Hilton Head, South Carolina, June 3 - 6, 1996, pp. 168 - 173.

# BIOLOGICAL ACTUATORS

- Clearly, a wide variety of efficient actuation mechanisms have evolved in order to allow organisms to move.
- These are chemical to mechanical transducers.
- Microtubules are cellular scaffolding, along which kinesin molecules can move (powered by ATP) themselves and bound vesicles containing cellular products.

Microtubule dimensions: 24 nm diameter, length varies.

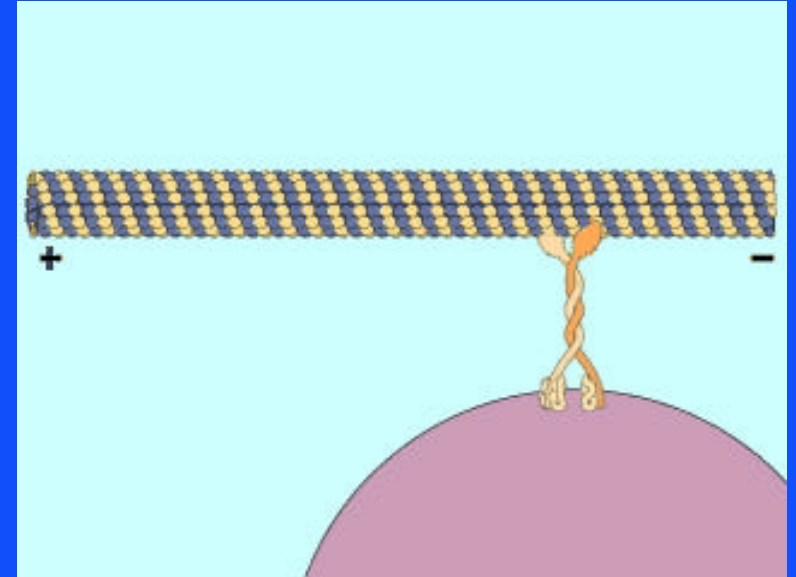
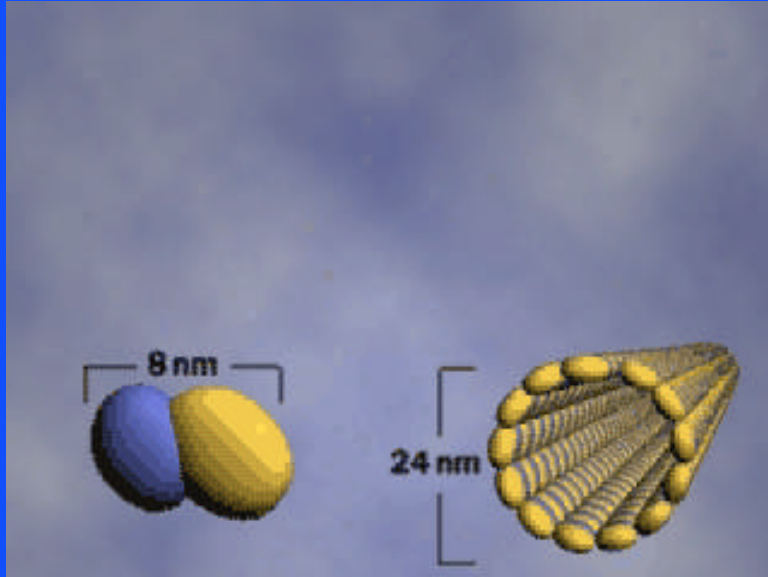
Kinesin dimensions:  $\approx 70$  nm length.



Reference: Darnell, J., Lodish, H., and Baltimore, D., "Molecular Cell Biology," Second Edition, Scientific American Books, W. H. Freeman and Co., New York, NY, 1991.

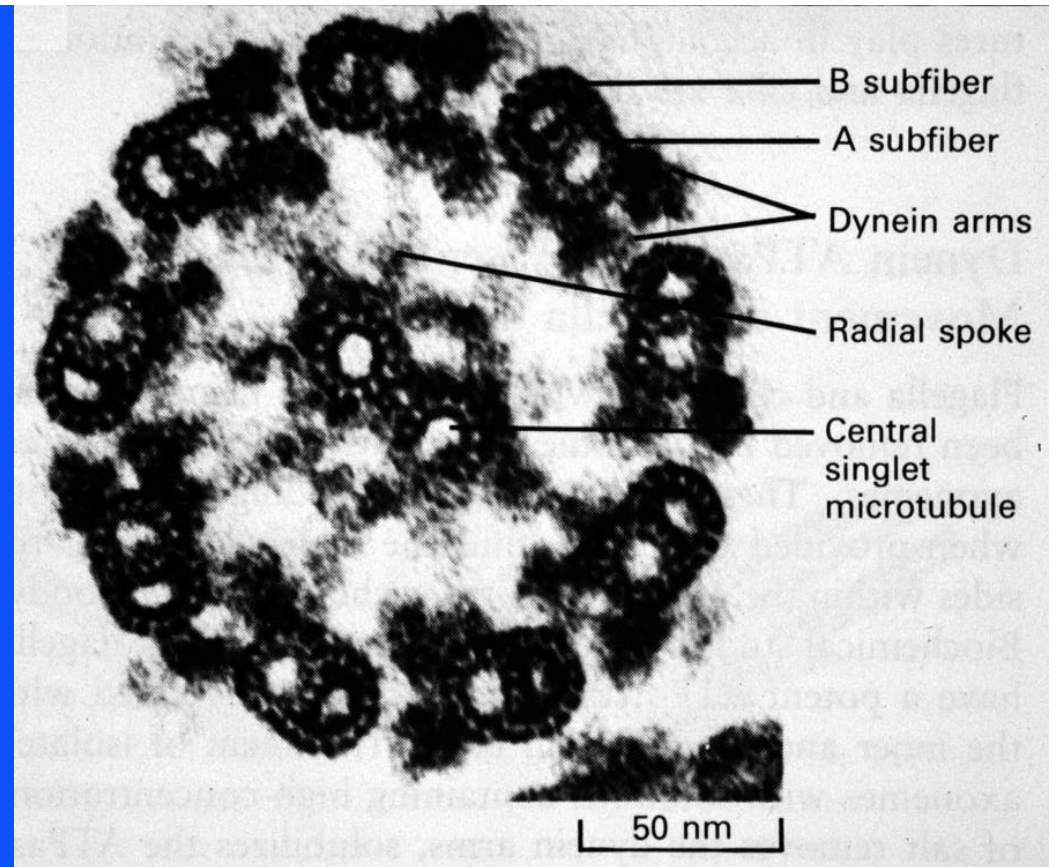
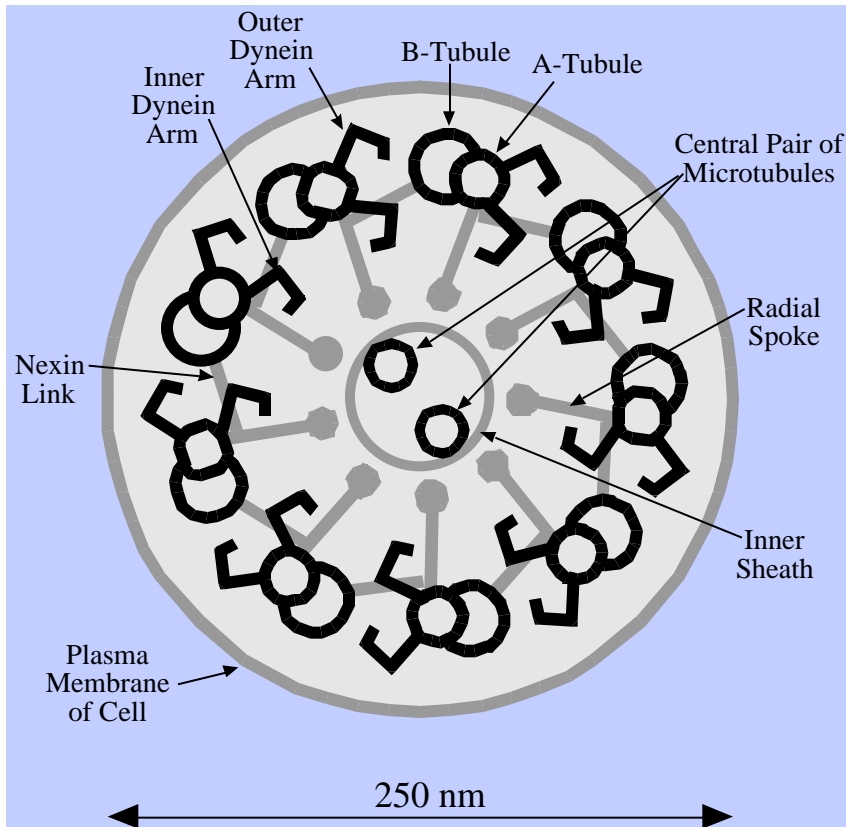


# MICROTUBULES & KINESIN



Movies courtesy Prof. H. C. Heller,  
Stanford University.

Source: Purves, Orians, Heller, and  
Sadava, "Life: The Science of Biology,"  
Sinauer Associates/W.H. Freeman & Co.,  
New York, 1999.



Source: Darnell, J., Lodish, H., and Baltimore, D., "Molecular Cell Biology," Second Edition, Scientific American Books, W. H. Freeman and Co., New York, NY, 1991.

G. Kovacs © 2000



Movie courtesy Prof. H. C. Heller, Stanford University.

Source: Purves, Orians, Heller, and Sadava, "Life: The Science of Biology," Sinauer Associates/W.H. Freeman & Co., New York, 1999.

Mitosis and  
cell plate formation in a  
flattened endosperm cell  
of the African blood lily,  
*Haemanthus katherinae*,  
observed with  
phase contrast microscopy

Video Enhanced DIC Microscopy  
of Mitosis in Newt Lung Cells  
(*Taricha granulosa*)

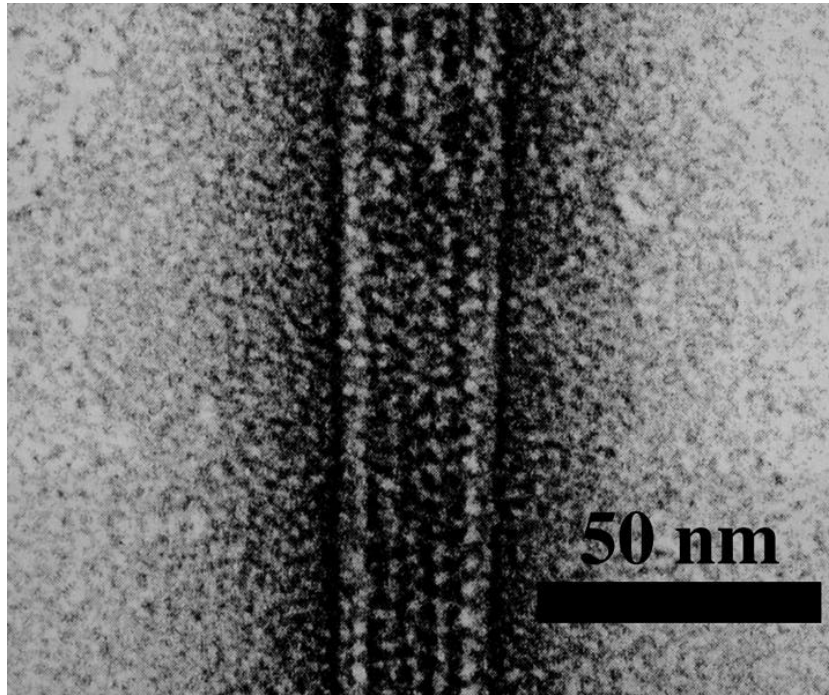
Victoria Skeen,  
Robert Skibbens, and  
E. D. Salmon

University of North Carolina at Chapel Hill  
(see Skibbens et al., 1993, J. Cell Biol.  
122:859-875)

Frame Time = HR:MIN:SEC

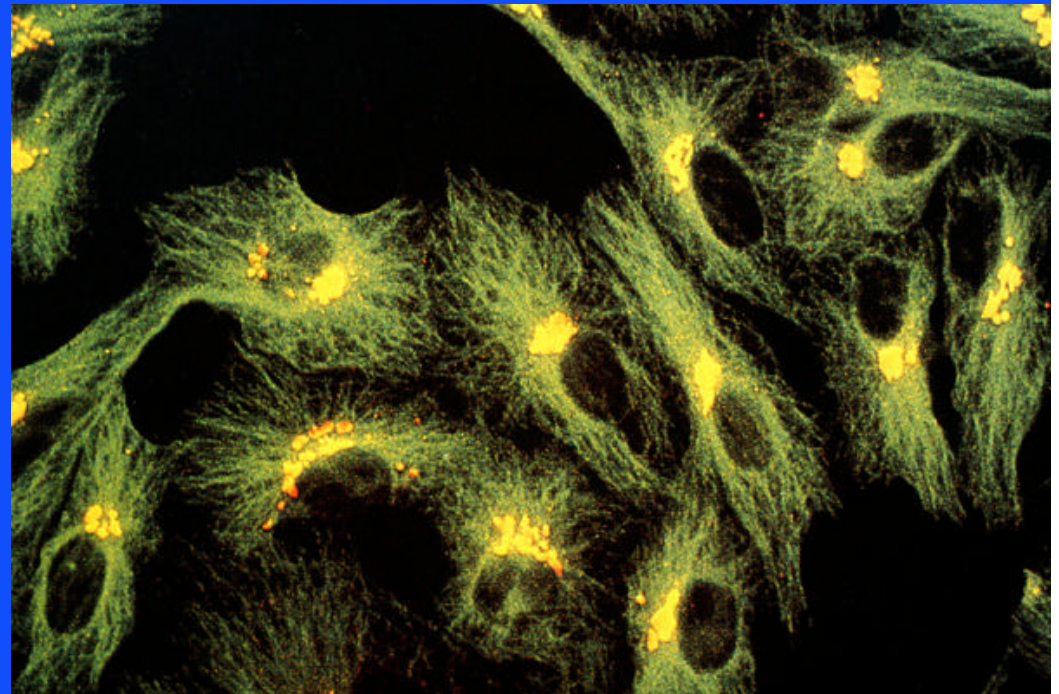
Mitosis in tissue-cultured  
lung cell of a newt,  
*Taricha granulosa*, recorded  
with the new Pol-Scope.





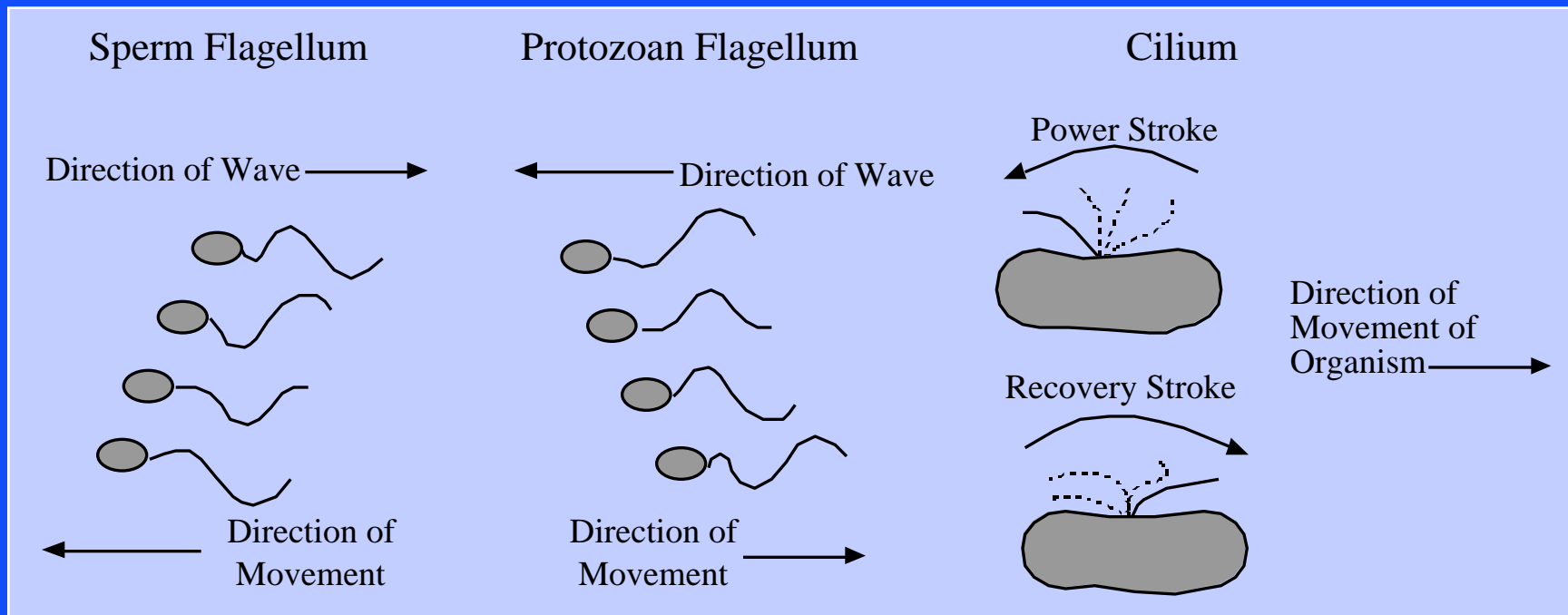
**Fluorescent Speckle Imaging:  
Microtubules in the Mitotic  
Spindle of a Living Epithelial Cell**

C.M. Waterman-Storer  
A. Desai  
J. C. Bulinski  
E.D. Salmon



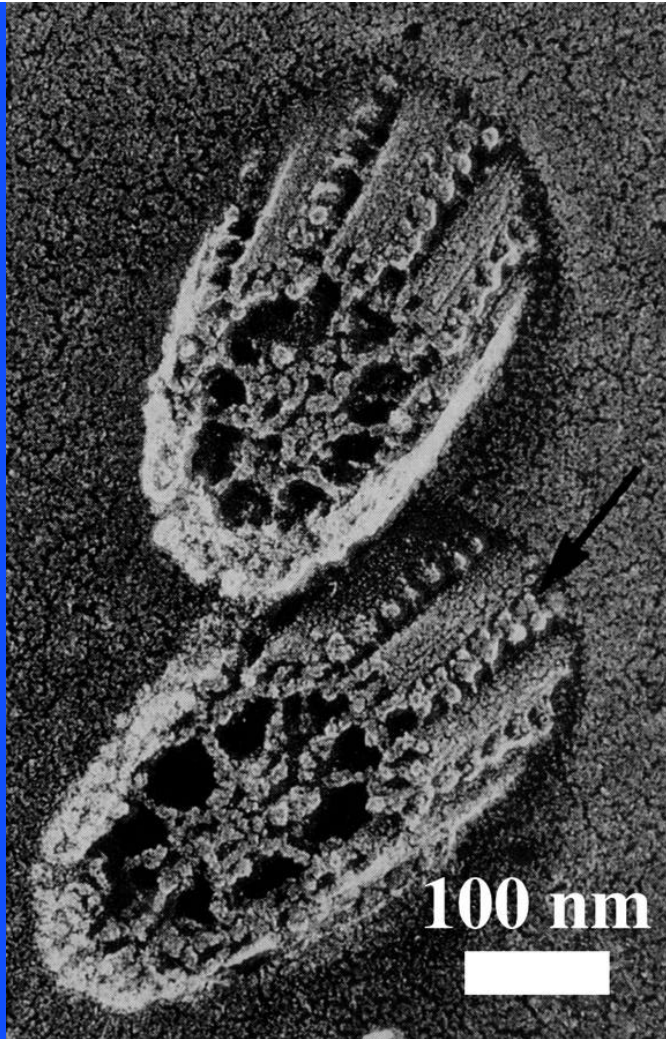
# CILIA AND FLAGELLA

- A bundle of microtubules surrounded by an extension of the cell's membrane forms these actuators.
- Nine pairs of A and B subunits surround a pair of single microtubules.
- Dynein “arms” on A subunits push B subunits and radial “spokes” convert the pushing into bending motion.

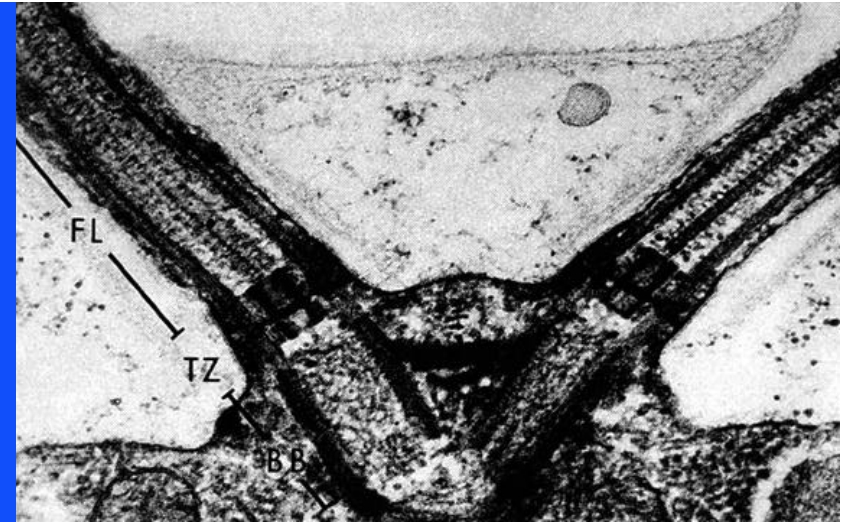


Reference: Darnell, J., Lodish, H., and Baltimore, D., "Molecular Cell Biology," Second Edition, Scientific American Books, W. H. Freeman and Co., New York, NY, 1991.

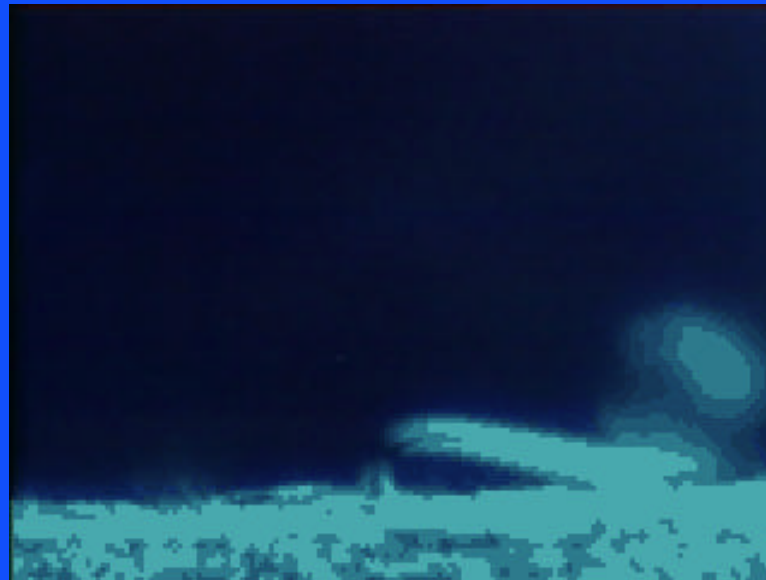




Source (images): Darnell, J., Lodish, H., and Baltimore, D., "Molecular Cell Biology," Second Edition, Scientific American Books, W. H. Freeman and Co., New York, NY, 1991.



**Flagellar basal region.**

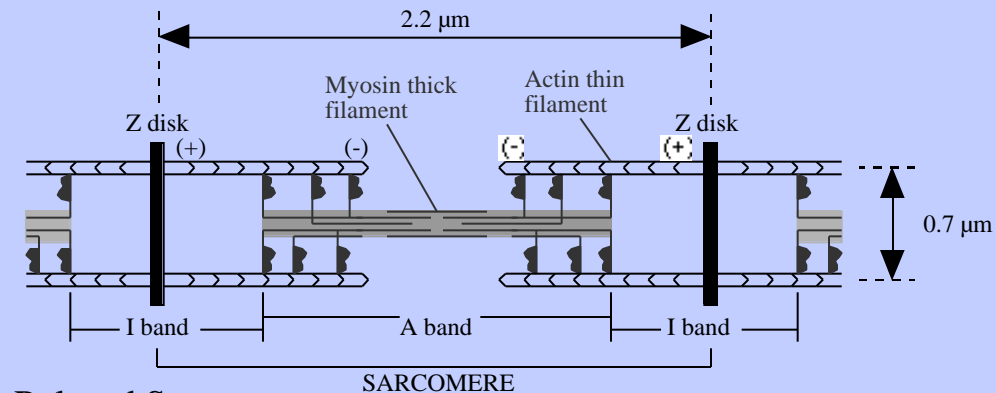


Movie courtesy Prof. H. C. Heller, Stanford University.

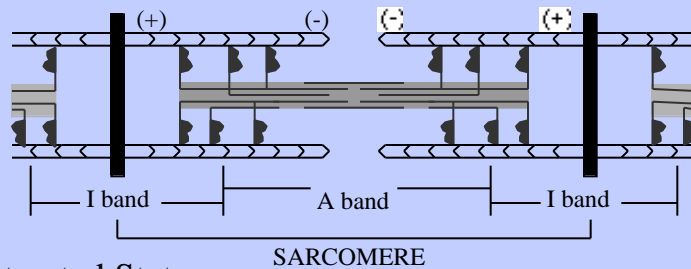
Source: Purves, Orians, Heller, and Sadava, "Life: The Science of Biology," Sinauer Associates/W.H. Freeman & Co., New York, 1999.



# MUSCLES

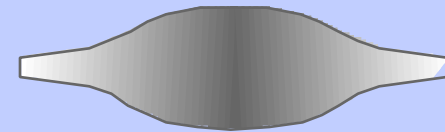


Relaxed State



Contracted State

Muscle



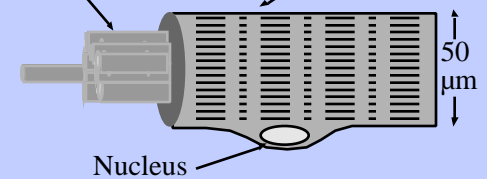
Bundle of Myofibers



Myofibril

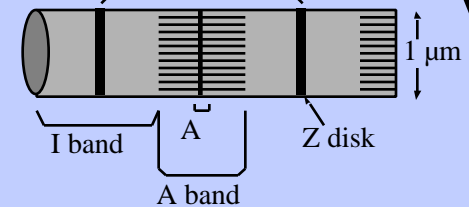
Plasma Membrane

One Myofiber



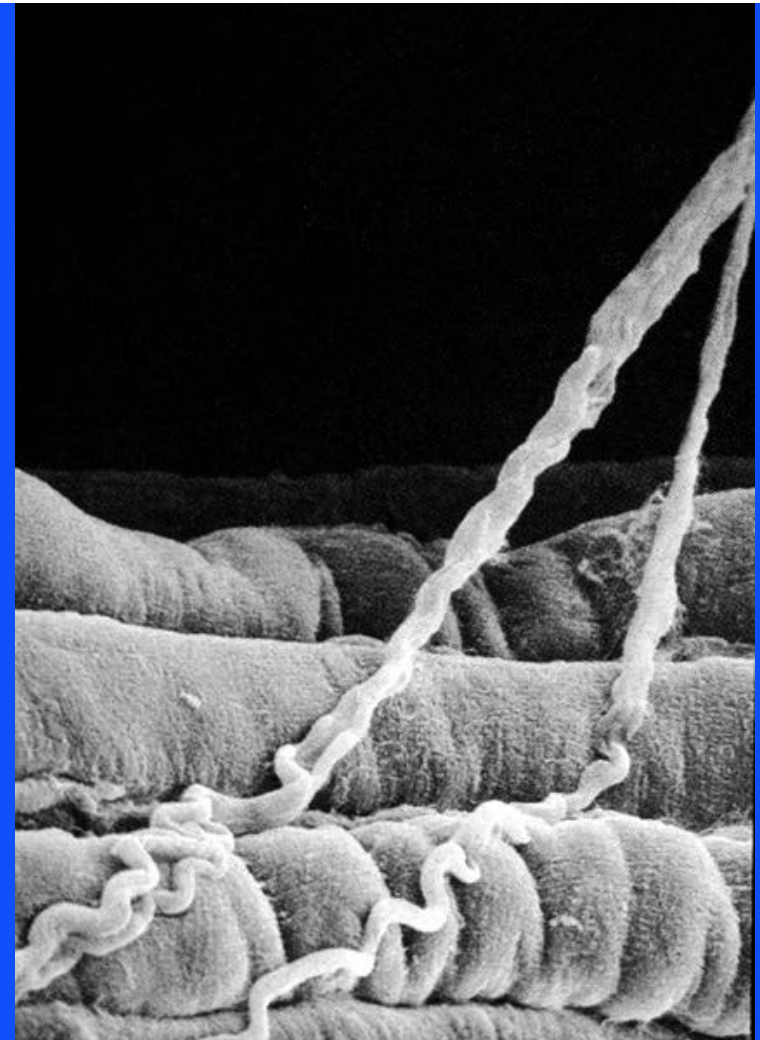
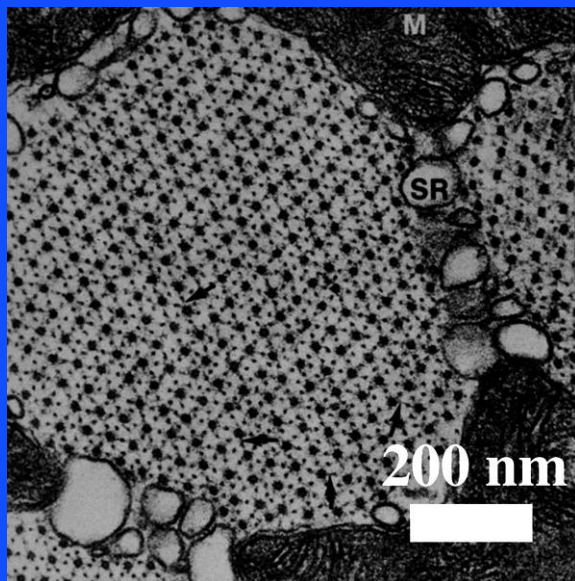
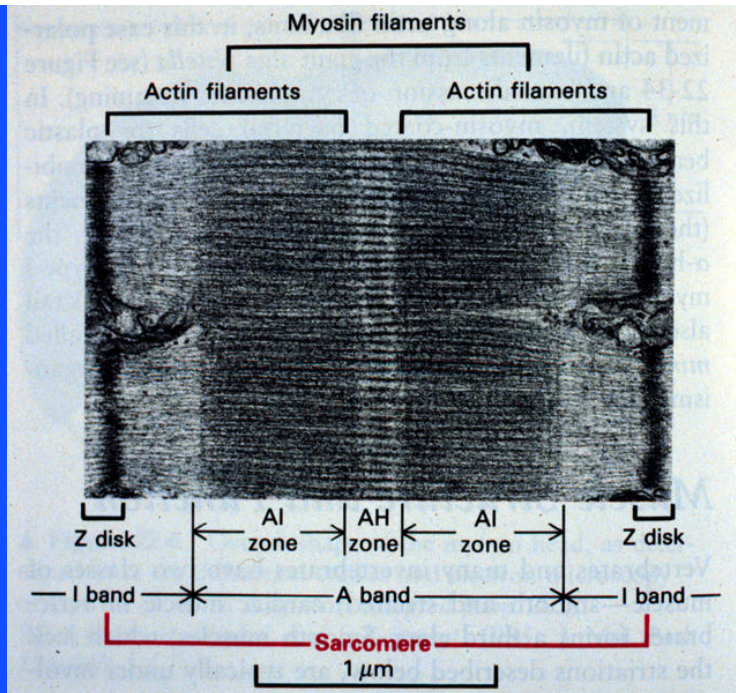
Sarcomere

Enlarged Myofibril Showing Sarcomere and Adjacent Bands



Decreasing Size

Reference: Darnell, J., Lodish, H., and Baltimore, D., "Molecular Cell Biology," Second Edition, Scientific American Books, W. H. Freeman and Co., New York, NY, 1991.



Source: Darnell, J., Lodish, H., and Baltimore, D., "Molecular Cell Biology," Second Edition, Scientific American Books, W. H. Freeman and Co., New York, NY, 1991.